



Nanotechnology

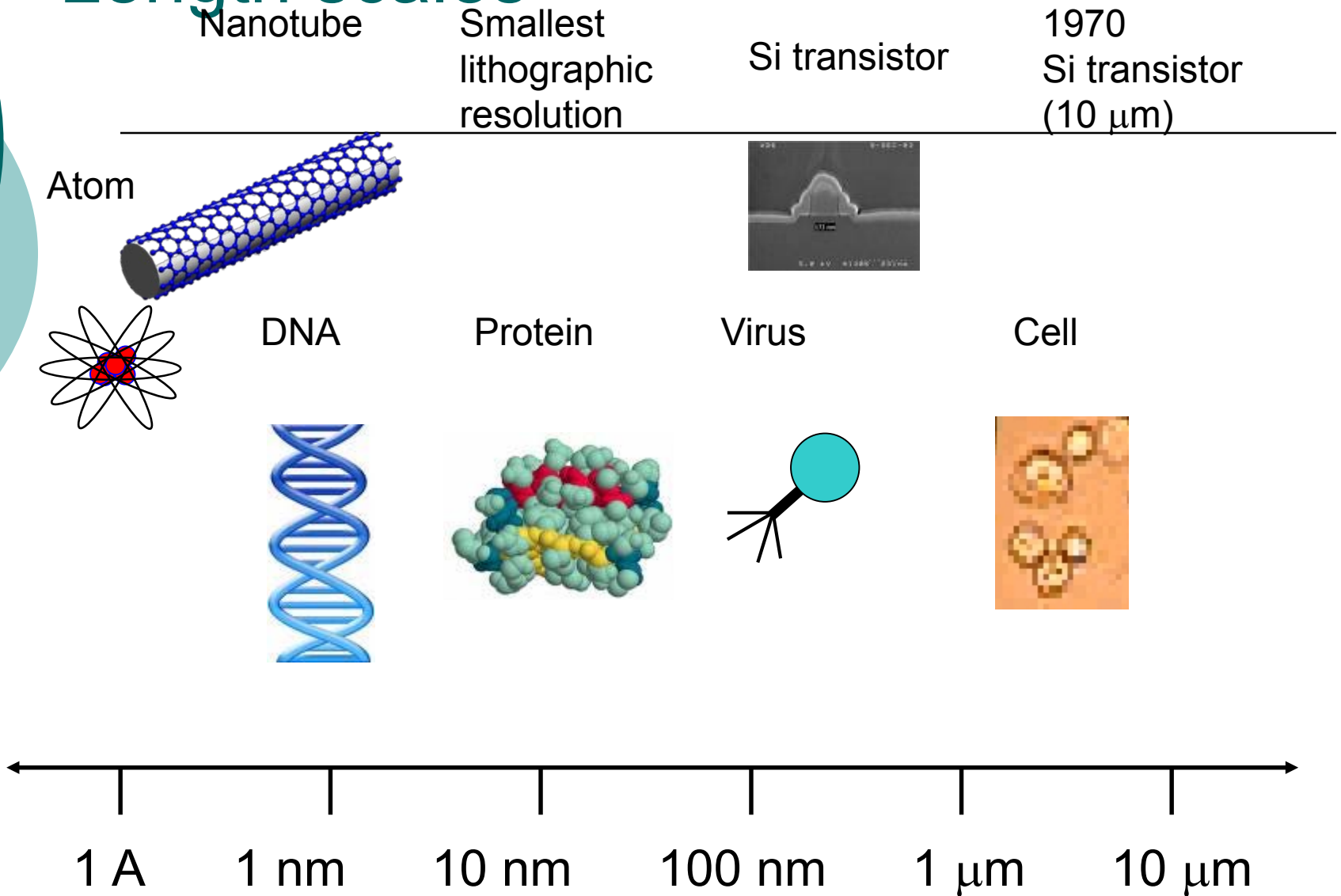
- Nanofabrication techniques
- Characterization techniques
- Single electron transistors
- Quantization of electrical resistance
- Nanotubes, nanowires



Units

- Meter (m)
- Millimeter (mm) = 10^{-3} m
- Micrometer (μm) = 10^{-6} m
- Nanometer (nm) = 10^{-9} m
- Picometer (pm) = 10^{-12} m
- Femtometer (fm) = 10^{-15} m

Length scales



What is nanotechnology?

- “Top down” approach
 - Micron scale lithography
 - optical, ultra-violet
 - Focused Ion Beam
 - 10-100 nm
 - Electron-beam lithography
- “Bottom up” approach
 - Chemical self-assembly
 - Man-made synthesis (e.g. carbon nanotubes)
 - Biological synthesis (DNA, proteins)
 - Manipulation of individual atoms
 - Atomic Force Microscopy
 - Scanning Tunneling microscopy

A brief history of nanotechnology

- Democritus in ancient Greece: concept of atom
- Rutherford, 1900: discovery of atomic nucleus
- Feynman, 1960: speech at Caltech
- Drexler, 1986, 1992: *Engines of Creation, Nanosystems*
- Clinton, speech, Caltech, 2000
- *National Nanotechnology Initiative* since 2000

Feynman challenges



- “There’s Plenty of Room at the Bottom”
- Feynman, Caltech 1960 set two challenges
 - Construct a 1/64 cubic inch motor
 - claimed in 1960
 - On display at Caltech today
- Encyclopedia Britanica on head of a pin
 - Actually on page in 10 microns²
 - Claimed in 1985
 - Used electron-beam lithography

Foresight challenges

- Drexler wrote two books:
 - 1986: *Engines of Creation: The Coming Era of Nanotechnology*
 - 1992: *Nanosystems: Molecular Machinery, Manufacturing, and Computation*
- Foresight/Feynman \$250,000 prize
 - 100 nm arm nano-robot
 - 50 nm³ 8-bit adder

Biosystems

○ DNA

- 2-3 nm per base pair
- Human genome contains $\sim 10^9$ base pairs

○ Proteins

- typically 1-10 nm in size
- $\sim 100,000$ different proteins in human genetic code
- all are synthesized enzymatically (bottom up)

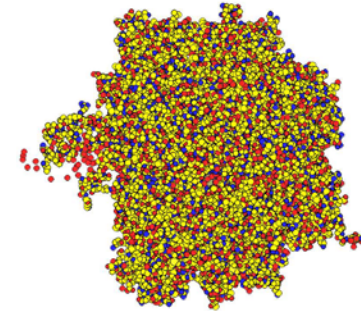
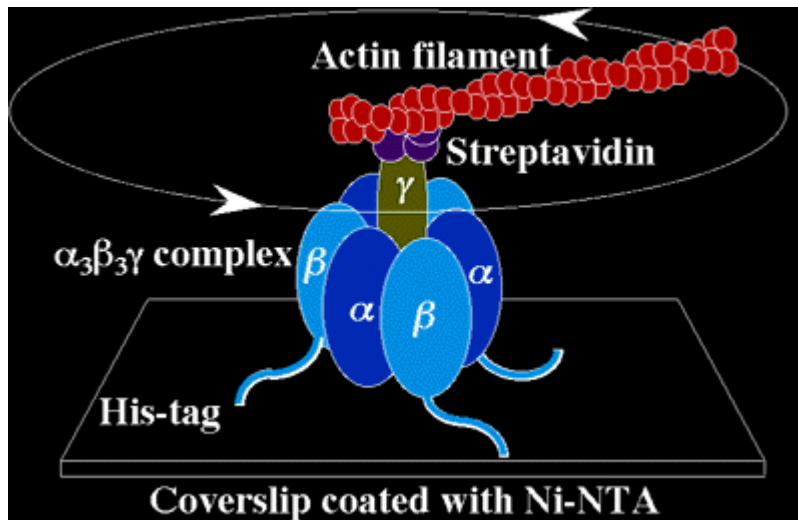
○ Biological Nano-motors

- ATP synthase
- Kinesin, Actin important for muscle movement

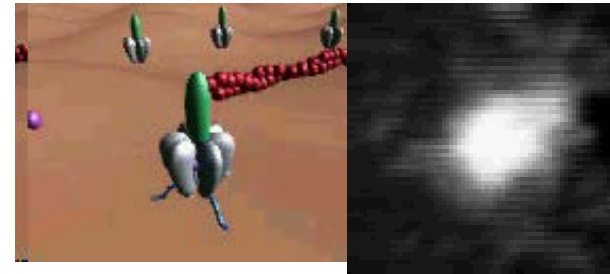
○ *Nanotechnology is important for life itself*

ATP Synthase

- 10 nm nanomachine at the mitochondria membrane
- Uses proton gradient to convert ADP to ATP
- Extremely important for metabolism



10 nm



Movie source: www.res.titech.ac.jp

References: Boyer, Annu. Rev. Biochem. 1997
Yoshida, Nature Rev. Mol. Cell Bio. 1997
Soong, Montemagno, Nature, 2000

Nano-manufacturing

- Lithography can do 10 nm
- Tricks to 2 nm
- Biosystems can add 2 carbon atoms at a time
 - typical in lipid biosynthesis
 - enzymes are nano machines
- We do not know how to design enzymes, only copy them
- As such, nanotechnology does not yet exist according to Drexler's definition

Readings this lecture covers

- Ferry, pp. 1-5
- Feynman,
“There’s plenty of room at the bottom”
- Moore’s law original paper
- Moore’s law slides
- Drexler ch. 2
- Hanson p. 1-14

Course themes

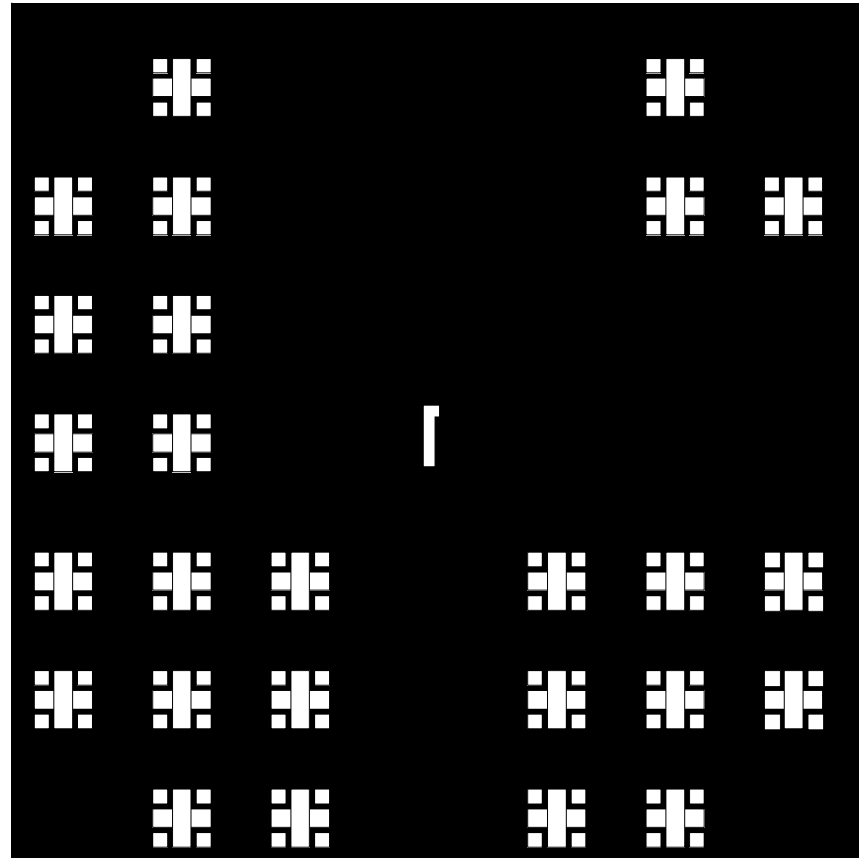
- *Nano-electronics: Wave/particle duality*
- Particle:
 - Charging energy e^2/C
(single electron transistor)
- Wave:
 - Gradually reduced dimensions:
 - 3 (bulk)
 - 2 (2DEG)
 - 1 (nanowire)
 - 0 (quantum dot).
 - Quantization of electrical resistance: e^2/h

Fabrication

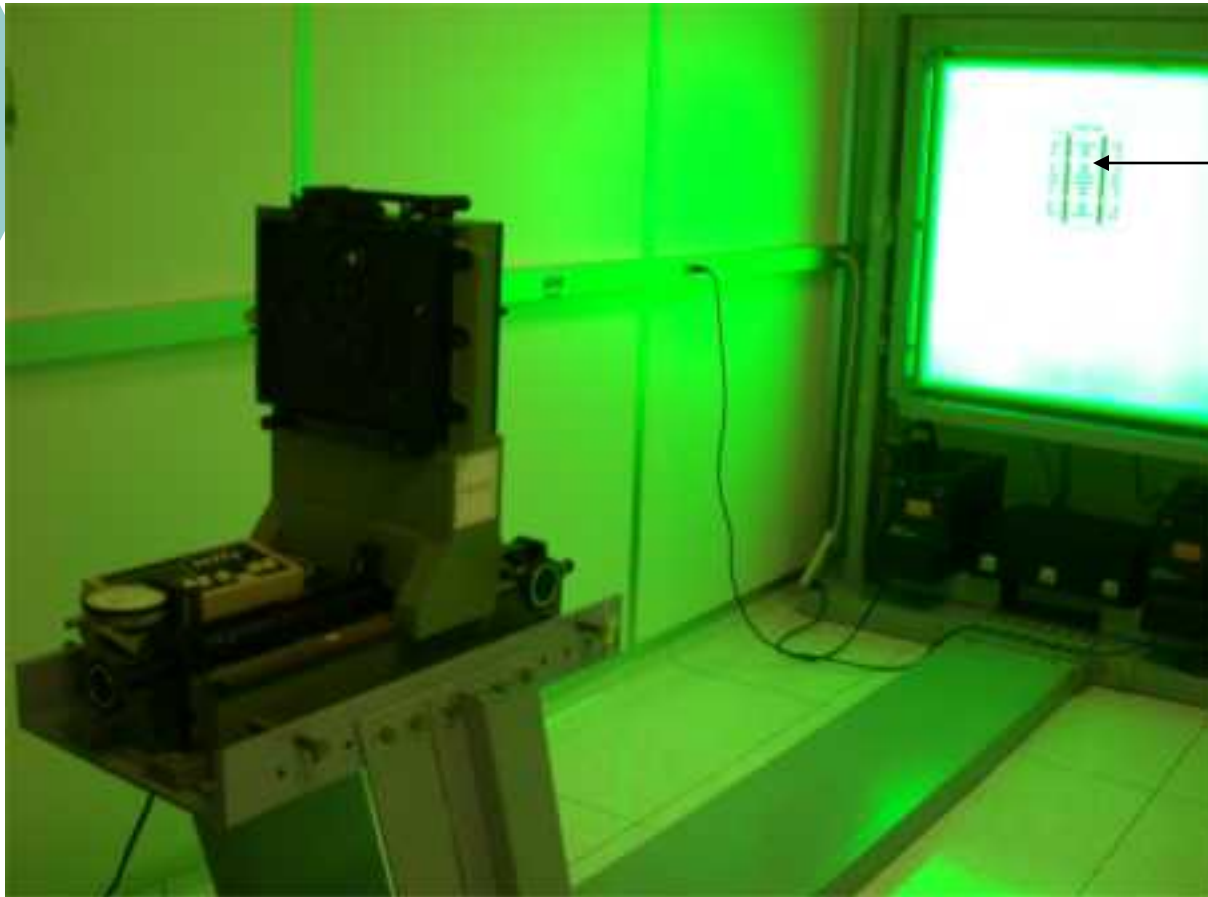
- “Top down” approach to nanotechnology
- This is overview, for more details take MAE courses by Marc Madou, Andre Shkel
- Thanks to Sungmu Kang for INRF images

Photomasks

Design geometry on computer.



Mask fabrication



← transparency

After Exposure
Developer
Stop bath
Fixer

Dark room (1/20 reduction)

Spin on photoresist

wafer

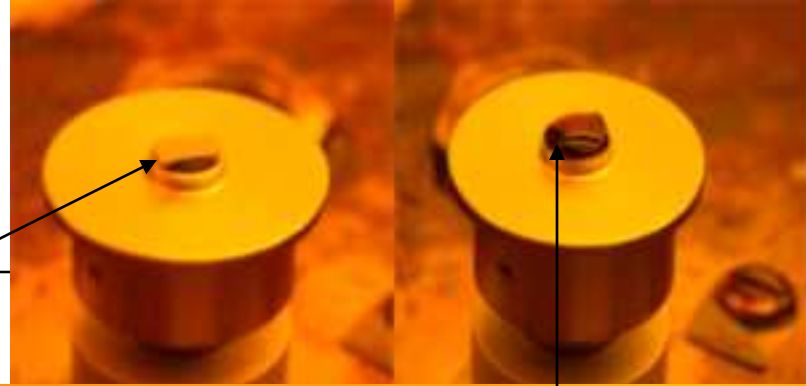


Photo resist

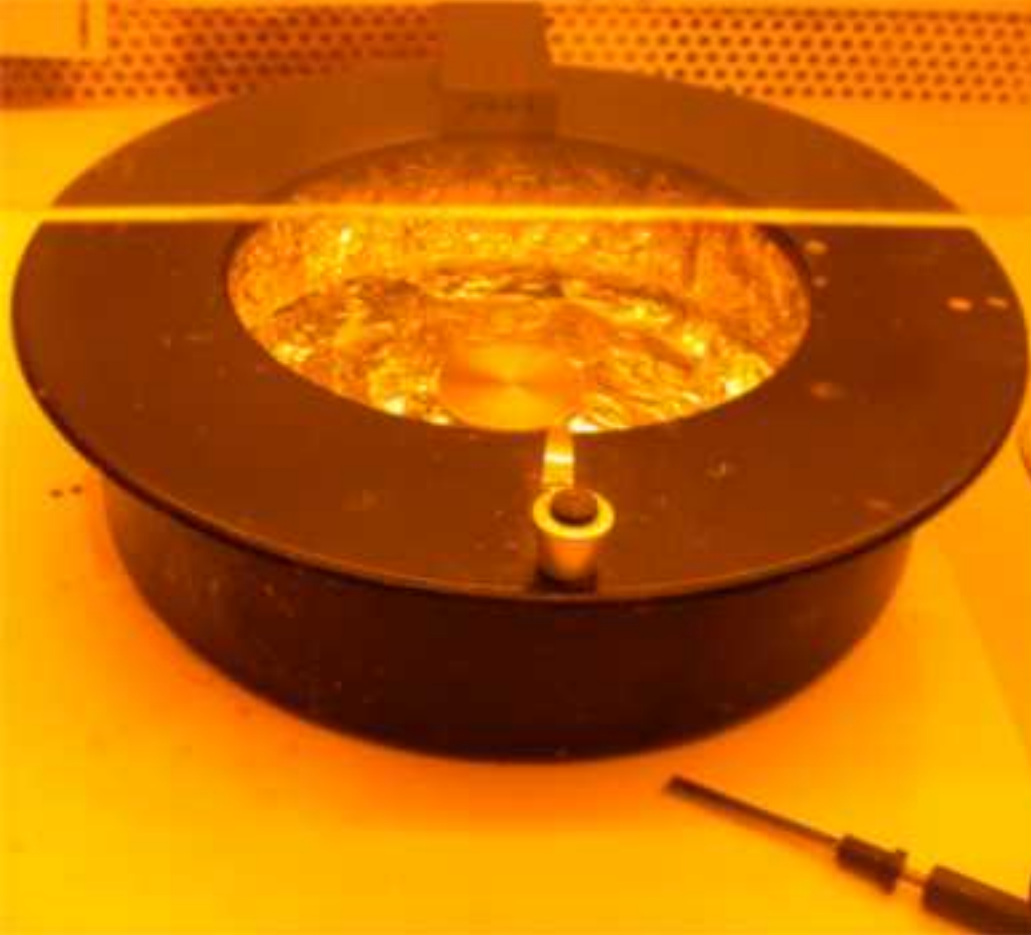


Photo resist spinner

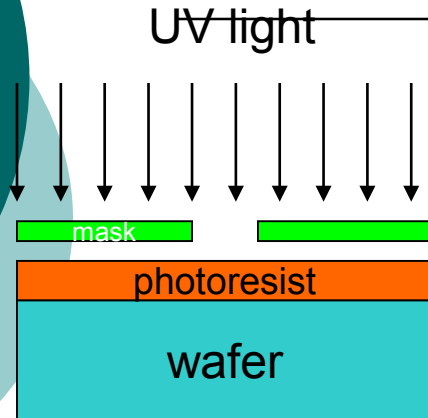
EECS 277C Nanotechnology © 2017 P. Burke

Soft bake

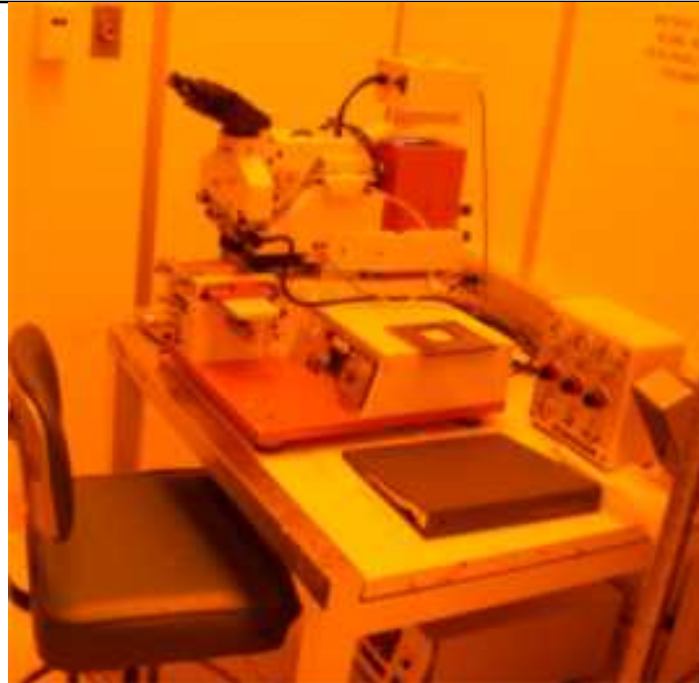


Oven for soft baking of photo resist
(at 90C for 30 min)

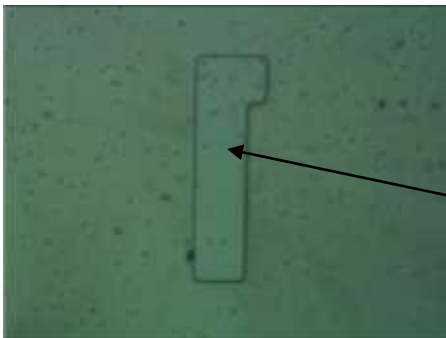
Expose to UV light



Development
For Shipley 1827
Water : MF351 = 5.5 : 1



Mask Aligner



Exposed regions
dissolved in developer
leaving bare wafer

*This is the step which limits
the spatial resolution.*

Thermal evaporation



Thermo evaporator



Alumina coated W boat

Useful for e.g.
Al, Ni, Au, Cr, Ti, NiCr, Pb, Sn

E-beam evaporation

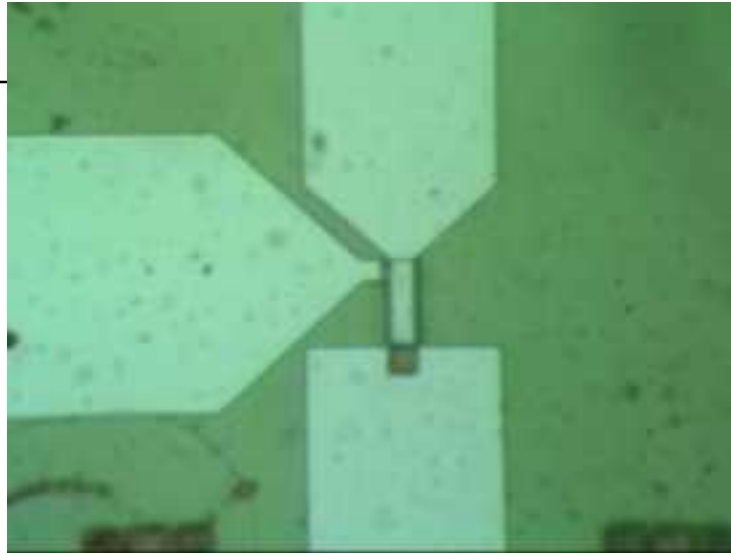


Electron beam evaporator

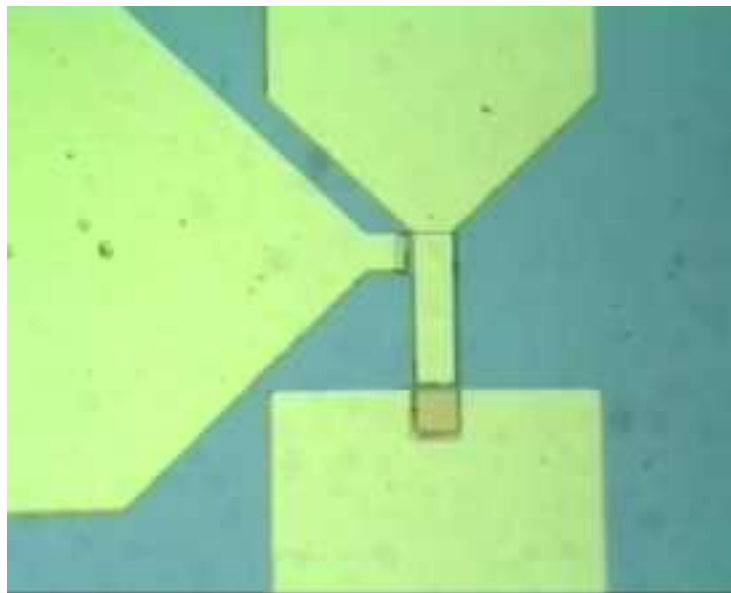
Au



Liftoff



Opening of photo resist
for Ti/Au gate



After deposition of Ti/Au,
then soaking in acetone

Resolution of optical lithography

$$R = \frac{3}{2} \sqrt{\frac{\lambda z}{2}}$$

Contact printing

z is resist thickness
(typically 0.1-1 μm)

$$R = 0.61 \frac{\lambda}{NA}$$

Projection printing

NA is numerical aperture
(typically 0.5)

Light sources

Source	λ	Resolution
○ Hg lamp	(g-line) 436 nm	400 nm
○ Hg lamp	(i-line) 365 nm	350 nm
○ KrF	248 nm	150 nm
○ ArF	193 nm	80 nm
○ F ₂	157 nm	research

↑ increasing cost ↓

Extreme UV, x-ray lithography research topics.
Difficulties lie in sources, and materials for optics and masks.

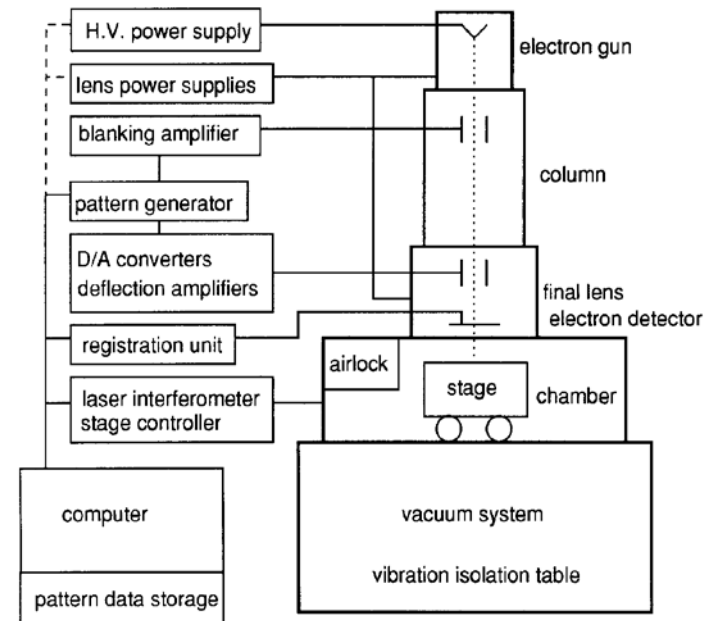
Electron Beam Lithography

Advantages

- Resolution
 - electron wavelength small
 - beamsize 1 nm
 - resolution from scattering typically 10 nm
- Flexibility
 - All patterns under computer control

Disadvantages

- Cost
 - Need high vacuum
 - Need precision electron focusing magnets
- Throughput
 - Only one pixel exposed at a time
 - Not commercially viable except for a few applications





Reference: SPIE Handbook of Microlithography, Micromachining, and Microfabrication available at <http://www.cnf.cornell.edu/spiebook/toc.htm>



In spite of its disadvantages, e-beam lithography is the main tool for nanotechnology research.

 Integrated Nanosystems Research Facility
Engineering the nanoworld at the University of California, Irvine



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 **Acc.V** **Spot** **Magn** **Det** **WD**  **20 µm**
5.00 kV **3.0** **800x** **SE** **7.2** **XL30 SFEG D1591**

Irvinne

Acc.V Spot Magn Det WD Exp |-----| 500 nm
30.0 kV 3.0 64000x SE 7.1 0 XL30 SFEG D1591

34.6 nm

21. nm

24. nm

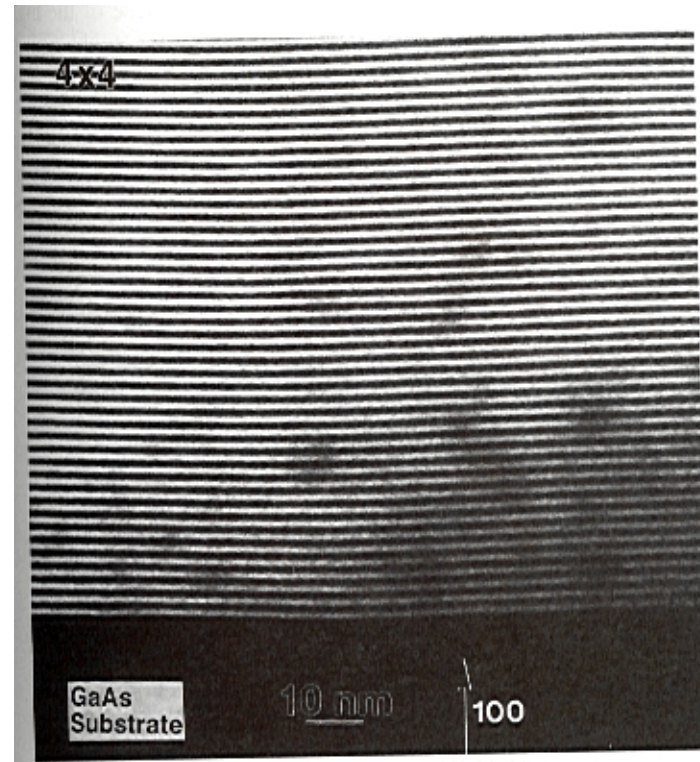
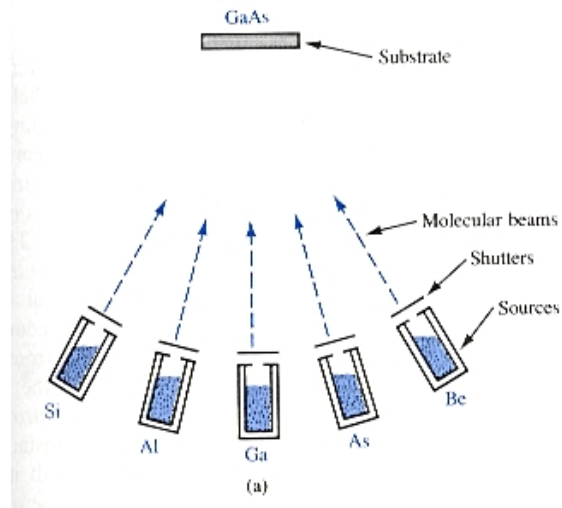
27.1 nm

45.1 nm

25.6 nm

Acc.V	Spot	Magn	Det	WD	200 nm
30.0 kV	3.0	128000x	SE	7.1	XL30 SFEG D1591

Molecular Beam Epitaxy (MBE)

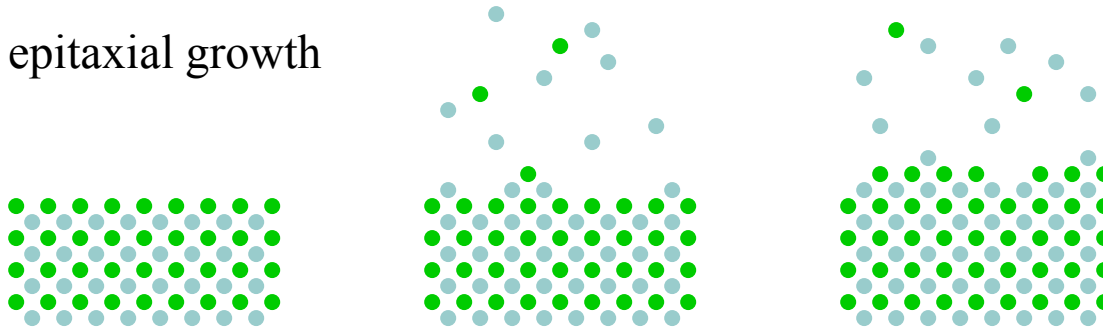


4 atom per layer!

(From Streetman, Solid State Electronic Devices)

MBE

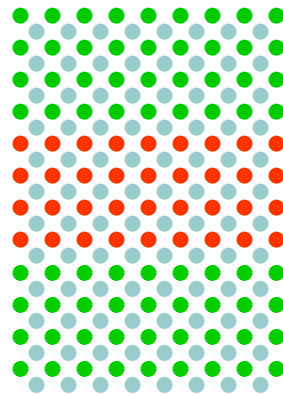
epitaxial growth



AlAs

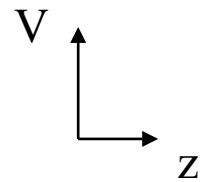
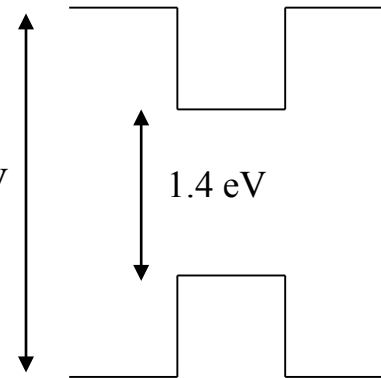
GaAs

AlAs



2.2 eV

1.4 eV

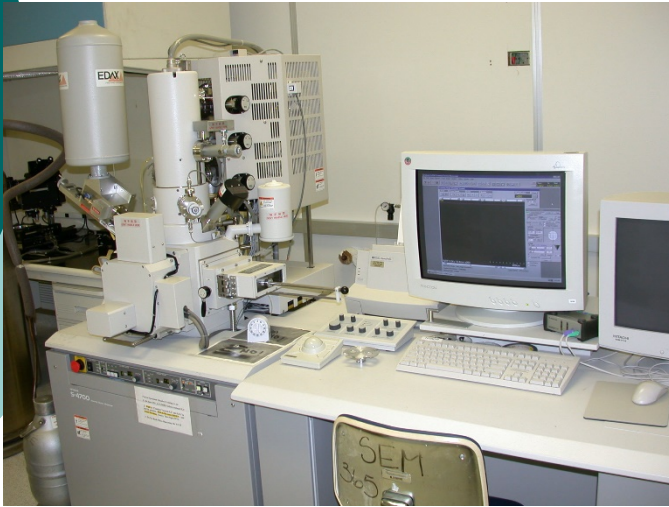


Also InP, InGaAs, InAlAs, InGaAsP ...

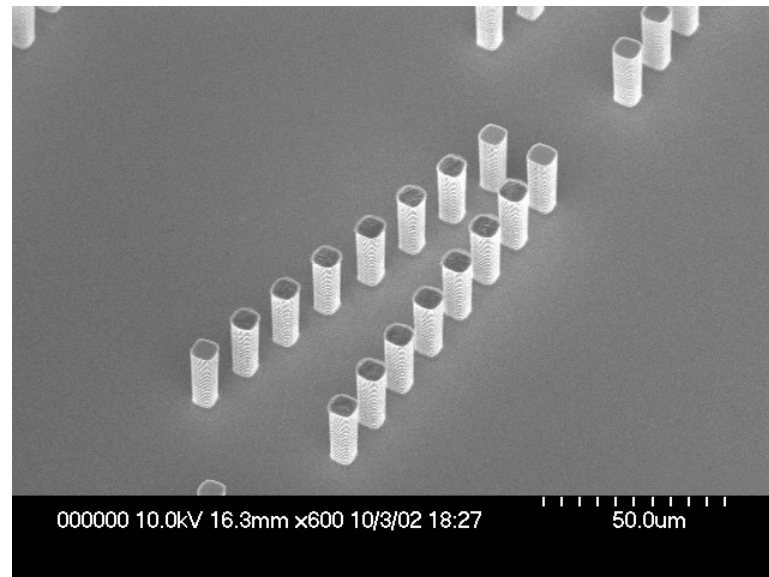
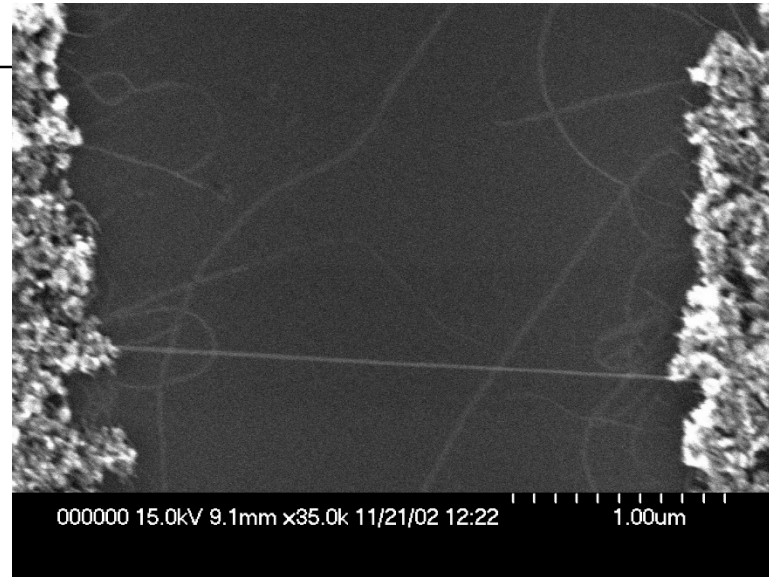
Characterization

- Optical microscopy cannot see better than wavelength of light, $\sim 1 \mu\text{m}$
- Scanning electron microscope (SEM)
- Transmission electron microscope (TEM)
- Scanning probe microscopy (SPM)
- Atomic force microscope (AFM)

SEM

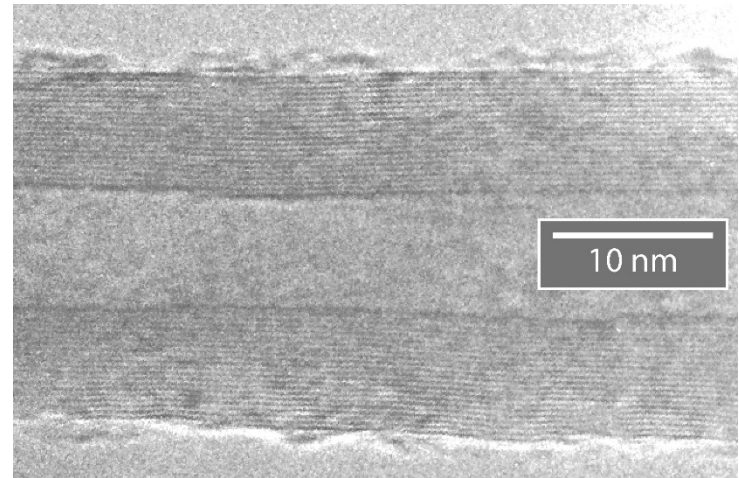


- Advantages:
 - resolution to 1 nm
 - fast
 - 3d structures visible
 - back-scattered x-ray spectrum gives compositional information
- Disadvantage
 - must be in vacuum environment (not good for bio)
 - expensive
 - samples must be conductive





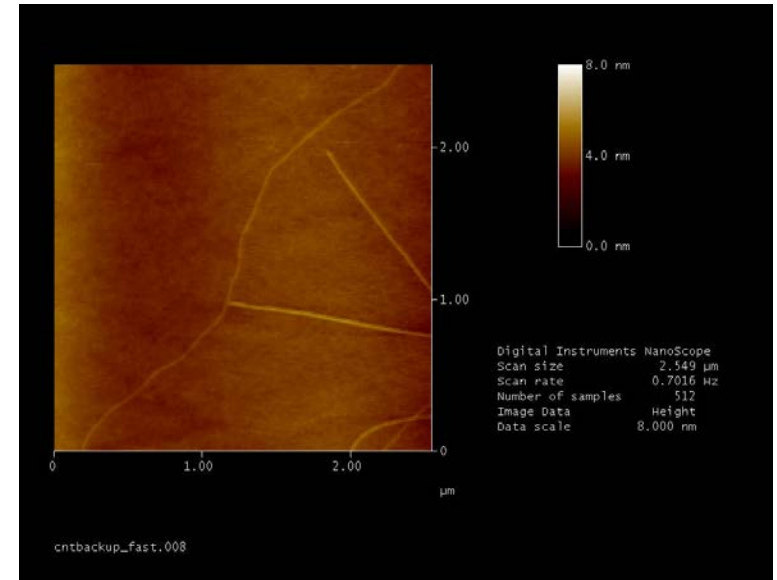
Multiwalled carbon nanotube



Shengdong Li, submitted

- Advantages
 - resolution < 1 nm
 - fast
 - diffraction pattern gives crystallographic info
- Disadvantages
 - expensive
 - high vacuum
 - sample must be thinned

SPM/AFM



- Mode of operation
 - non-contact
 - tunneling
- Advantages
 - works in air or liquid
 - angstrom resolution possible
 - can image individual atoms
 - probes various quantities
 - conductance
 - magnetism
- Disadvantages
 - extremely slow
 - many minutes for one image

Length scales

- Atoms
 - \sim angstrom 10^{-10} m
- Light
 - wavelength $\sim \mu\text{m}$
- Electrons
 - De Broglie wavelength = h/p (quantum mechanics)
= $\text{sqrt}(150/V)$ in angstroms (V is energy in volts)
 $\sim 0.1\text{-}10$ nm
 - If circuit element is about the size of an electron wavelength, wave nature will be *crucial*
 - Conductance quantized at these small scales in units of e^2/h
- Mean free path (MFP)
 - 10^{-10} m in metals at room temperature
 - 10^{-4} m in ultra high quality semiconductors at low temperatures

Energies

- Electronic transition energies
 - $\sim 1\text{-}10\text{ eV}$
- Fermi energy
 - $1\text{-}10\text{ eV}$ in metals
 - $1\text{-}10\text{ meV}$ in semiconductors
- kT
 - 30 meV at room temperature


Quantum mechanics of free electrons

- Important for quantized resistance calculation
- Important for single electron transistors
- Density of states
 - 3 dimensions
 - 2 dimensions
 - 1 dimensions
 - 0 dimensions
- Dimensionality (effective)
 - Set by size of nano-device compared to electron wavelength

Readings for this lecture

- Ferry, *Quantum Mechanics for Electrical Engineering*, ch. 1 (in handout packet)
- Hanson p. 16-44,62-69,85-101,chapter 8
- Good references:
 - Brandsen and Joachian, *Introduction to Quantum Mechanics*, Longman Scientific, 1989
 - Kittel, *Introduction to Solid State Physics*, Wiley, 1996
 - Ashcroft/Mermin, *Solid State Physics*, Saunders College, 1976

Quantum mechanics of free particles


$$|\Psi(\vec{r}, t)|^2$$

is probability of finding an electron at point r at time t .

Ψ is complex, and both real and imaginary parts are physical.

Quantum mechanics of free particles:

$|\Psi(\vec{r}, t)|^2$ is probability of finding an electron at point r at time t .

Ψ is complex, and both real and imaginary parts are physical.

$$\omega = E / \hbar$$

For a free particle:

$$\Psi(\vec{r}, t) \sim e^{i(\vec{k} \cdot \vec{r} - \omega t)}$$

Momentum:

$$\vec{p} = \hbar \vec{k}$$

Energy:

$$E = \frac{p^2}{2m} = \frac{(\hbar k)^2}{2m}$$

Schrodinger equation:

$$i\hbar \frac{\partial}{\partial t} \Psi(x, t) = -\frac{\hbar^2}{2m} \frac{\partial^2}{\partial x^2} \Psi(x, t)$$

(1 dimension)
(Time dependent)

Let

$$\Psi(x, t) = A \cdot e^{i(kx - \omega t)}$$

A is a (complex) constant.

Then

$$\begin{aligned} i\hbar \frac{\partial}{\partial t} \Psi(\vec{r}, t) &= i\hbar \frac{\partial}{\partial t} A \cdot e^{i(kx - \omega t)} = i\hbar(-i\omega) A \cdot e^{i(kx - \omega t)} \\ &= E \cdot A \cdot e^{i(kx - \omega t)} = E \cdot \Psi(x, t) \end{aligned}$$

$$\begin{aligned} -\frac{\hbar^2}{2m} \frac{\partial^2}{\partial x^2} \Psi(x, t) &= -\frac{\hbar^2}{2m} \frac{\partial^2}{\partial x^2} (A \cdot e^{i(kx - \omega t)}) = \left(-\frac{\hbar^2}{2m} \right) (ik)^2 (A \cdot e^{i(kx - \omega t)}) \\ &= \frac{\hbar^2 k^2}{2m} (A \cdot e^{i(kx - \omega t)}) = \frac{p^2}{2m} \Psi(x, t) \end{aligned}$$

Schrodinger equation:

(3 dimensions)

$$i\hbar \frac{\partial}{\partial t} \Psi(\vec{r}, t) = -\frac{\hbar^2}{2m} \vec{\nabla}^2 \Psi(\vec{r}, t) = -\frac{\hbar^2}{2m} \left(\frac{\partial^2}{\partial x^2} + \frac{\partial^2}{\partial y^2} + \frac{\partial^2}{\partial z^2} \right) \Psi(\vec{r}, t)$$

Let $\Psi(\vec{r}, t) = A \cdot e^{i(\vec{k} \cdot \vec{r} - \omega t)} = A \cdot e^{i(k_x \cdot x + k_y \cdot y + k_z \cdot z) - \omega t}$

Then $i\hbar \frac{\partial}{\partial t} \Psi(\vec{r}, t) = i\hbar(-i\omega)\Psi(\vec{r}, t) = E \cdot \Psi(\vec{r}, t)$ as before.

But:

$$\begin{aligned} -\frac{\hbar^2}{2m} \left(\frac{\partial^2}{\partial x^2} + \frac{\partial^2}{\partial y^2} + \frac{\partial^2}{\partial z^2} \right) \Psi(\vec{r}, t) &= -\frac{\hbar^2}{2m} \left(\frac{\partial^2}{\partial x^2} + \frac{\partial^2}{\partial y^2} + \frac{\partial^2}{\partial z^2} \right) \left(A \cdot e^{i(\vec{k} \cdot \vec{r} - \omega t)} \right) \\ &= \left(-\frac{\hbar^2}{2m} \right) \left((ik_x)^2 + (ik_y)^2 + (ik_z)^2 \right) \left(A \cdot e^{i(\vec{k} \cdot \vec{r} - \omega t)} \right) = \left(\frac{\hbar^2(k_x^2 + k_y^2 + k_z^2)}{2m} \right) \Psi(\vec{r}, t) \\ &= \frac{\hbar^2 k^2}{2m} \left(A \cdot e^{i(\vec{k} \cdot \vec{r} - \omega t)} \right) = \frac{p^2}{2m} \Psi(\vec{r}, t) \end{aligned}$$

Quantum mechanics of free particles:

$$\Psi(\vec{r}, t) \sim e^{i(\vec{k} \cdot \vec{r} - \omega t)}$$

Generally,

$$\Psi(\vec{r}, t) = \sum_n A_n e^{i(k_n x - \omega_n t)} \rightarrow \int dk A(k) e^{i(kx - \omega t)}$$

is also a possibility.

Time-independent Schrodinger equation

$$\Psi(\vec{r}, t) = A \cdot e^{i(\vec{k} \cdot \vec{r} - \omega t)}$$

$$= A \cdot e^{i((k_x \cdot x + k_y \cdot y + k_z \cdot z) - \omega t)} = \underbrace{A \cdot e^{i(k_x \cdot x + k_y \cdot y + k_z \cdot z)}}_{\text{Call this } \psi(\vec{r})} \cdot e^{-i\omega t}$$

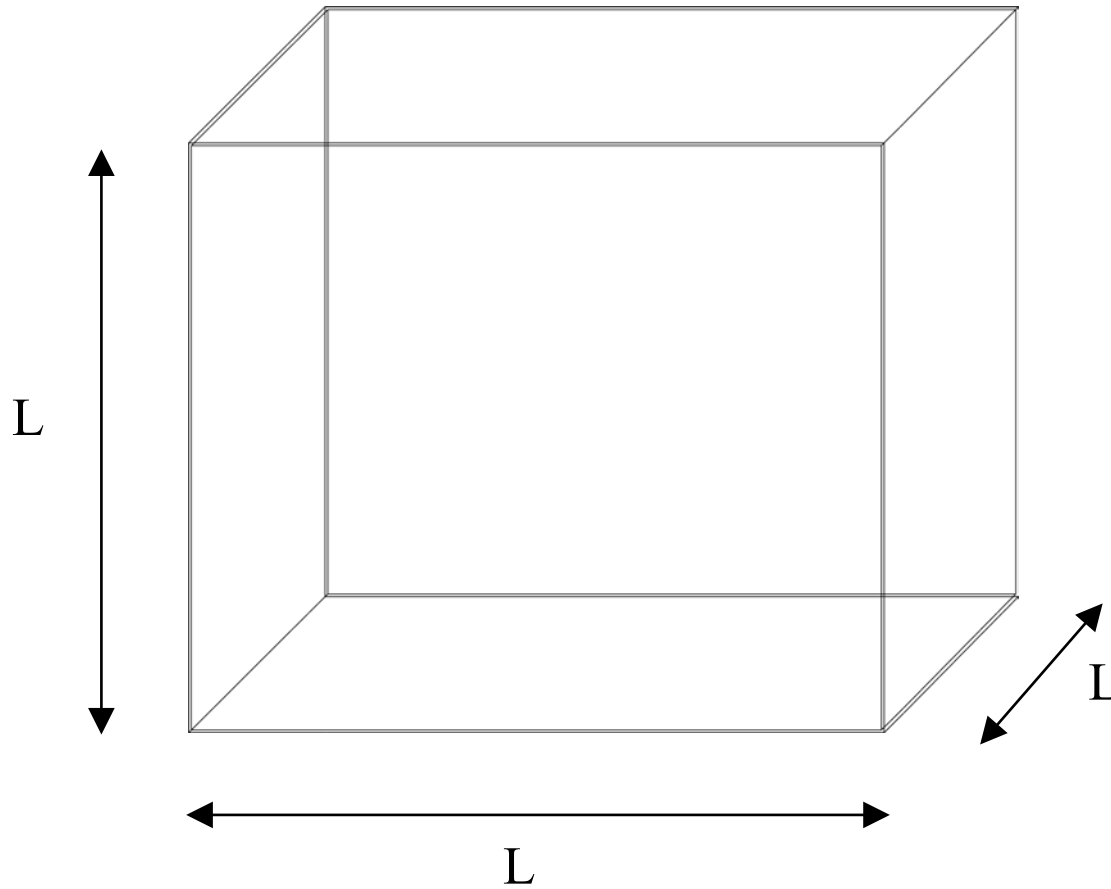
$$\Rightarrow \Psi(\vec{r}, t) = \psi(\vec{r}) \cdot e^{-i\omega t}$$

From:
$$i\hbar \frac{\partial}{\partial t} \Psi(\vec{r}, t) = -\frac{\hbar^2}{2m} \vec{\nabla}^2 \Psi(\vec{r}, t)$$

$$i\hbar \frac{\partial}{\partial t} \Psi(\vec{r}, t) = i\hbar \frac{\partial}{\partial t} \psi(\vec{r}) \cdot e^{-i\omega t} = i\hbar(-i\omega) \psi(\vec{r}) \cdot e^{-i\omega t} = E \cdot \psi(\vec{r}) \cdot e^{-i\omega t} = -\frac{\hbar^2}{2m} \vec{\nabla}^2 \Psi(\vec{r}, t) = -\frac{\hbar^2}{2m} \vec{\nabla}^2 \psi(\vec{r}) \cdot e^{-i\omega t}$$

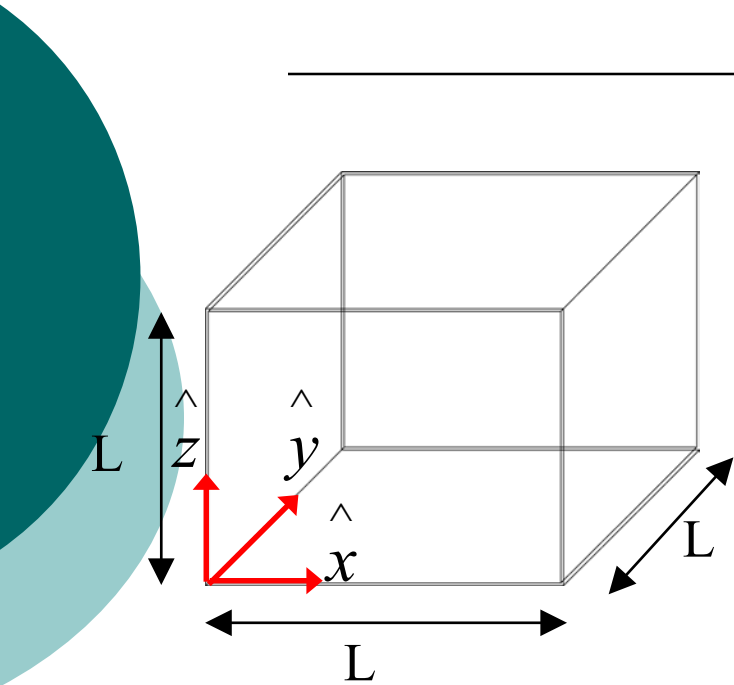
$$\Rightarrow -\frac{\hbar^2}{2m} \vec{\nabla}^2 \psi(\vec{r}) = E \cdot \psi(\vec{r})$$

Confined particles: A box



Goal: find $\psi(\vec{r})$

Similar to electric field inside the box.



Goal: find $\psi(\vec{r})$

Everywhere outside the box

$$|\psi(\vec{r})|^2 = 0$$

In particular,

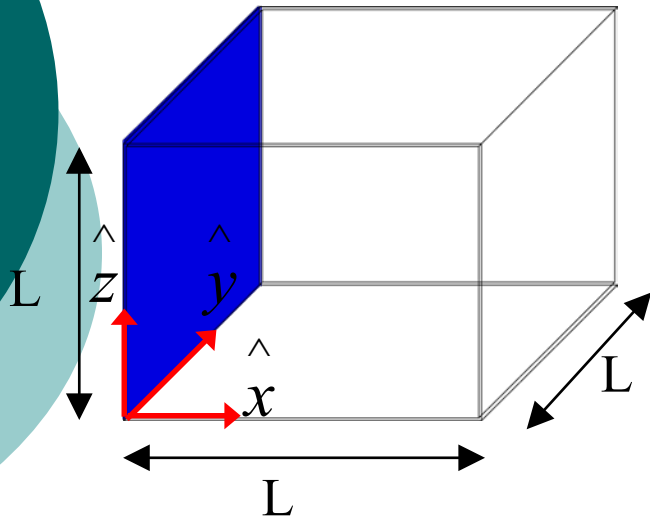
$$|\psi(\vec{r})|^2 = 0$$

on the boundaries.

As before, we will consider all six surfaces:

Boundary conditions:

The plane $x=0$:



Try:

$$\psi(\vec{r}) = A \cdot e^{i(k_x \cdot x + k_y \cdot y + k_z \cdot z)}$$

$$\psi(x=0, y, z) = A \cdot e^{i(k_x \cdot x + k_y \cdot y + k_z \cdot z)} = A \cdot e^{i(k_y \cdot y + k_z \cdot z)}$$

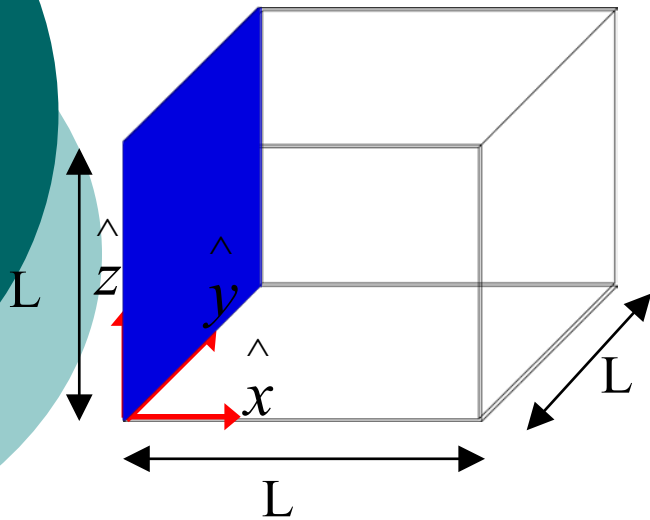
(Note: A red arrow points from the $k_x \cdot x$ term to a red '0' below it, indicating its elimination.)

Does not solve boundary condition!!!

Boundary conditions:

The plane $x=0$:

Let's try something:



$$\psi(\vec{r}) = A \cdot e^{i(k_x \cdot x + k_y \cdot y + k_z \cdot z)}$$

$$-A \cdot e^{i(-k_x \cdot x + k_y \cdot y + k_z \cdot z)}$$

$$\psi(\vec{r}) = A \cdot (e^{ik_x \cdot x} - e^{-ik_x \cdot x}) \cdot e^{i(k_y \cdot y + k_z \cdot z)}$$

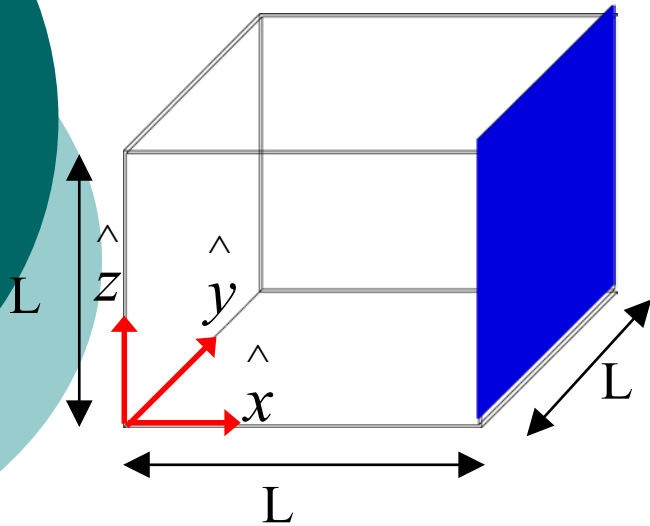
$$e^{a \cdot b} = e^a \cdot e^b$$

$$\begin{aligned} \psi(x=0, y, z) &= A \cdot (e^{i\cancel{k}_x \cdot x} - e^{-i\cancel{k}_x \cdot x}) \cdot e^{i(k_y \cdot y + k_z \cdot z)} \\ &= A \cdot (e^0 - e^0) \cdot e^{i(k_y \cdot y + k_z \cdot z)} = 0 \end{aligned}$$

Does solve boundary condition!!!

Boundary conditions:

The plane $x=L$:



$$\begin{aligned}\psi(\vec{r}) &= A \cdot \left(e^{ik_x \cdot x} - e^{-ik_x \cdot x} \right) \cdot e^{i(k_y \cdot y + k_z \cdot z)} \\ &= 2iA \cdot \sin(k_x x) \cdot e^{i(k_y \cdot y + k_z \cdot z)}\end{aligned}$$

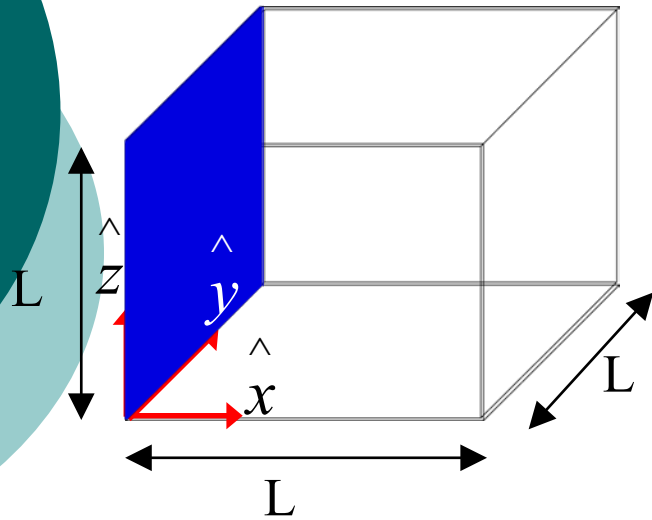
$$\sin(\theta) = \frac{1}{2i} \left(e^{i\theta} - e^{-i\theta} \right)$$

$$\psi(x = L, y, z) = 2iA \cdot \sin(k_x L) \cdot e^{i(k_y \cdot y + k_z \cdot z)} = 0?$$

If and only if:

$$k_n = n\pi / L \quad n = 1, 2, 3 \dots$$

Boundary conditions:



We can do the same for y, z:

$$\psi(\vec{r}) = (2i)^3 A \cdot \sin(k_{n_x} x) \cdot \sin(k_{n_y} y) \cdot \sin(k_{n_z} z)$$

$$k_{n_x} = n_x \pi / L$$

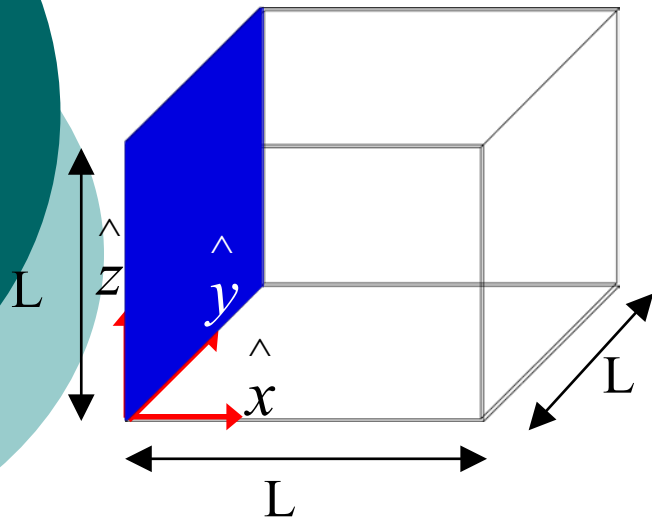
$$k_{n_y} = n_y \pi / L$$

$$k_{n_z} = n_z \pi / L$$

$$E = \frac{\hbar^2 (k_{n_x}^2 + k_{n_y}^2 + k_{n_z}^2)}{2m} = \frac{\hbar^2 (\pi / L)^2}{2m} (n_x^2 + n_y^2 + n_z^2)$$

These are the allowed energy levels, or “quantum states”

Many electrons:

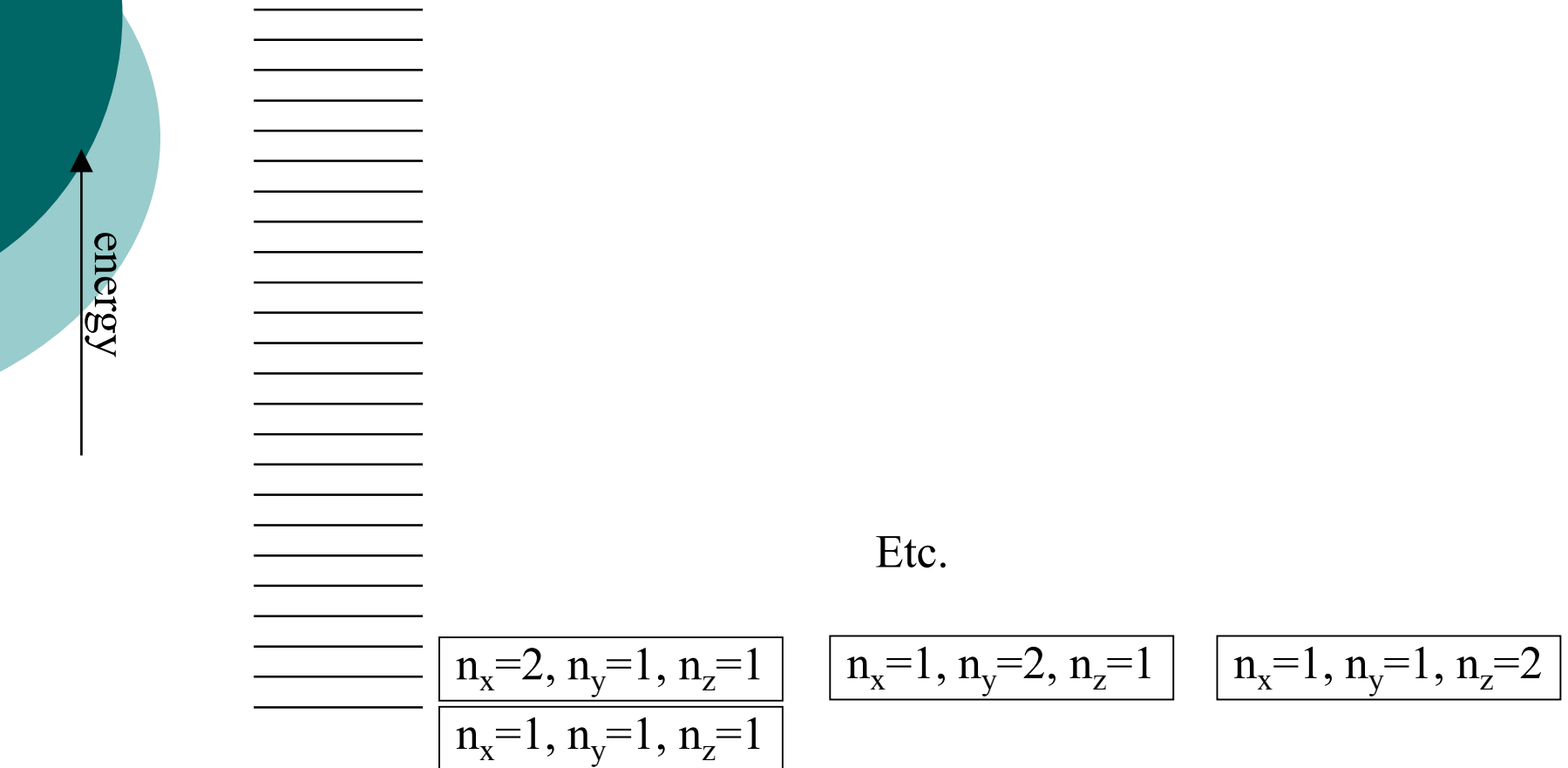


$$E = \frac{\hbar^2 (\pi / L)^2}{2m} (n_x^2 + n_y^2 + n_z^2)$$

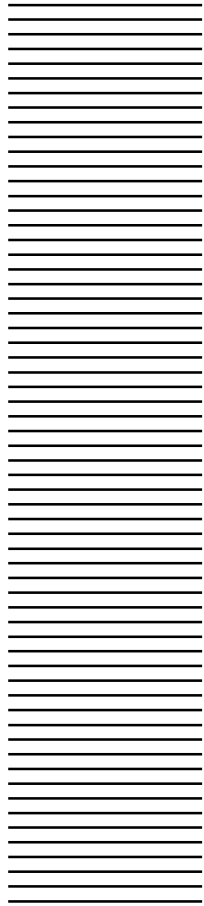
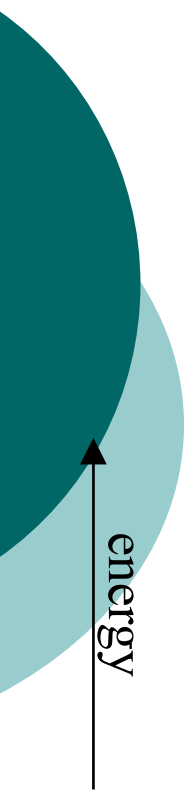
These are the allowed energy levels,
or “quantum states”

Pauli exclusion principle: Each unique combination of n_x , n_y , n_z can only have two electrons (spin up, spin down).

Energy spectrum of free particles



Density of states



If L is large, states are very close together.
Approximate as a continuum.

$E+dE$
 E

How many states?

$$N_E dE = ?$$

Number of states with energy between E and $E + dE$

$$\rho(E) dE = ?$$

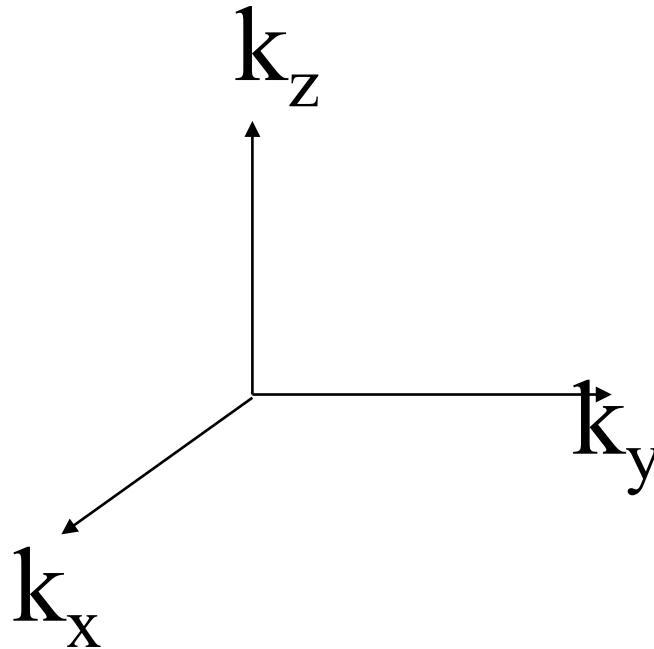
Number of states with energy between E and $E + dE$ *per volume*.

Density of states

Easier first to think of in k -space:

Density of states in k -space is uniform:

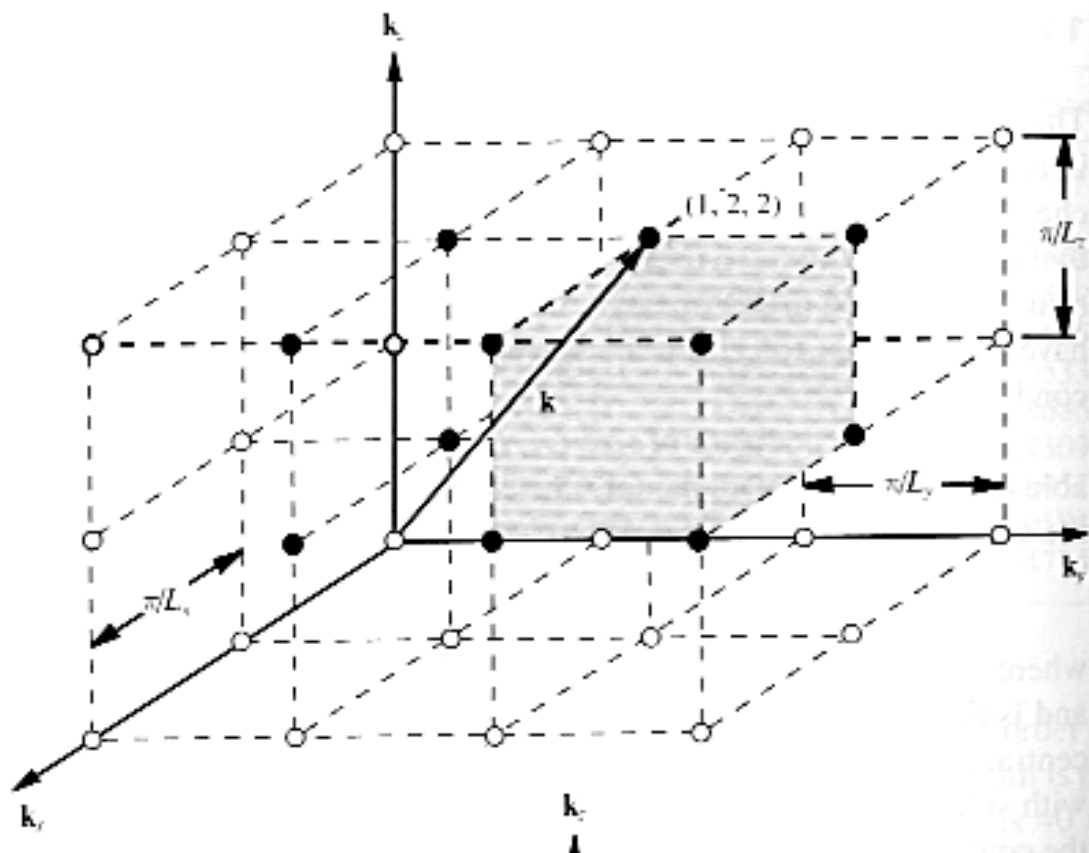
One state per $(\pi/L)^3$:



Density of states

Easier first to think of in k -space:
Density of states in k -space is uniform:

One state per $(\pi/L)^3$:

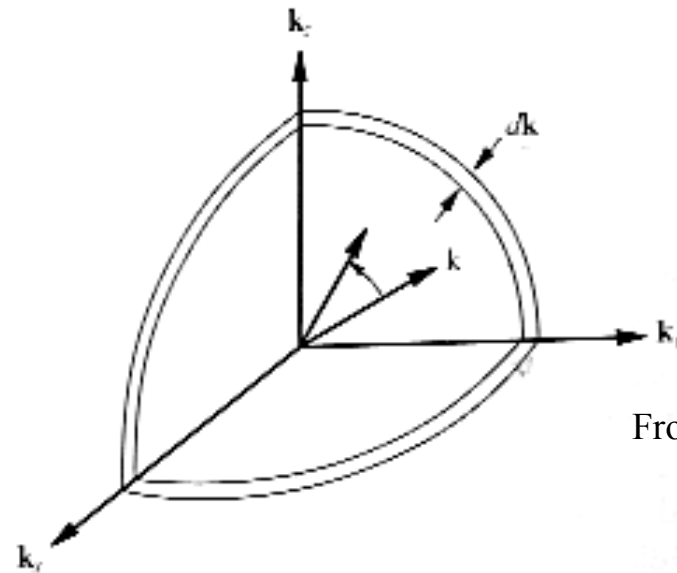
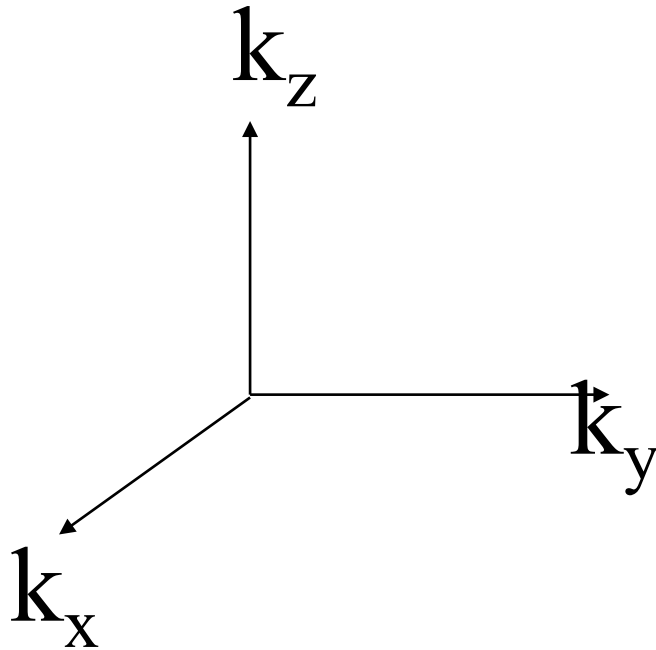


From Verdeyen

Density of states

Number of states between k , $k+dk$:

$$N_k dk = ?$$



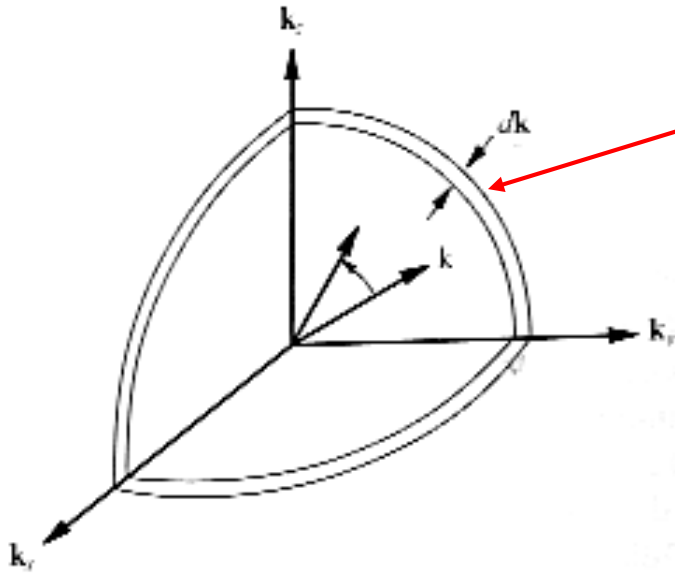
$$k \equiv \sqrt{k_x^2 + k_y^2 + k_z^2}$$

$$k_{n_x} = n_x \pi / L$$

$$k_{n_y} = n_y \pi / L$$

$$k_{n_z} = n_z \pi / L$$

$$N_k dk = ?$$



Volume of spherical shell
 $= 4\pi k^2 dk / 8$

8 is for upper right quadrant

Number of states in volume =
 Volume x States/volume

States/volume = $1 / (\pi/L)^3$:

$$N_k dk = \left(4\pi k^2 dk / 8 \right) \cdot \left(\frac{1}{(\pi/L)^3} \right) \cdot 2 = L^3 \frac{k^2 dk}{\pi^2}$$

$$\rho_k dk \equiv \frac{N_k dk}{\text{volume}} = \frac{k^2 dk}{\pi^2}$$

HW you will do calculation for 2 dimensional world.

$\rho(E)dE = ?$

We use:

$$\rho_k dk = \rho(E) dE$$

$$\rho_k dk = \frac{k^2 dk}{\pi^2}$$

$$E = \frac{\hbar^2 k^2}{2m} \Rightarrow k = \sqrt{\frac{2mE}{\hbar^2}} \Rightarrow dk = \sqrt{\frac{2m}{\hbar^2}} \frac{dE}{2\sqrt{E}}$$

$$\rho(E)dE = \frac{2^{3/2} m^{3/2}}{\pi^2 \hbar^{3/2}} \cdot E^{1/2} dE$$

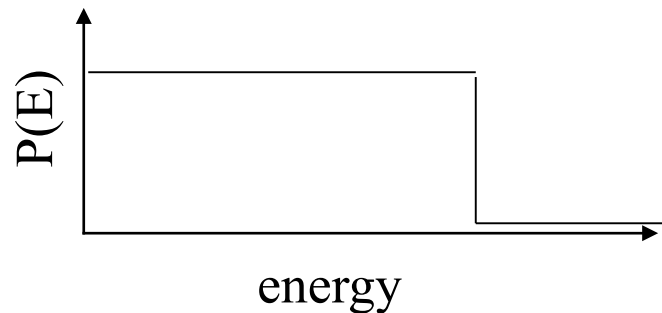
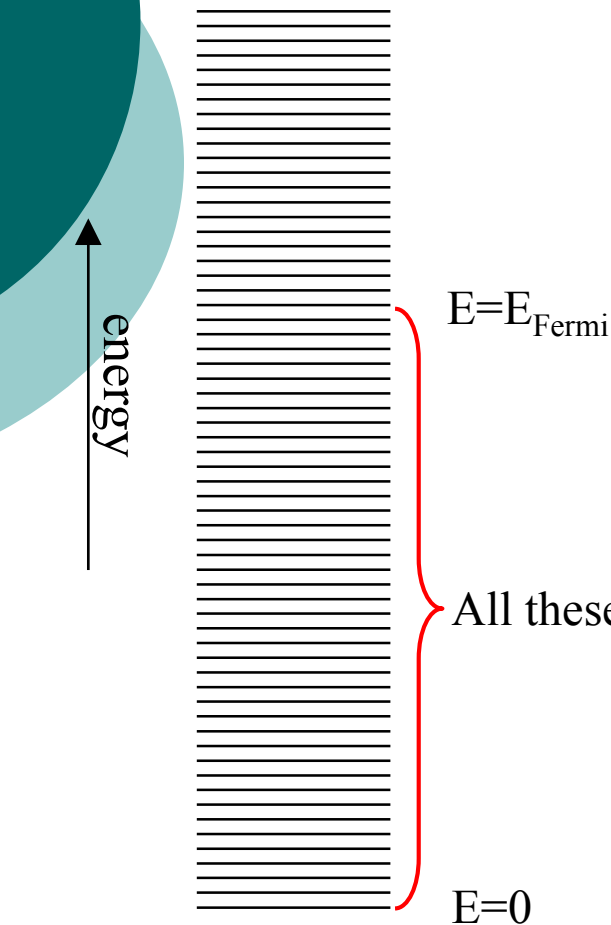
Fermi gas

At zero temperature, as we add electrons to the box, we gradually fill up all the states.
(DISCUSS PAULI EXCLUSION PRINCIPLE -IMPORTANT!)

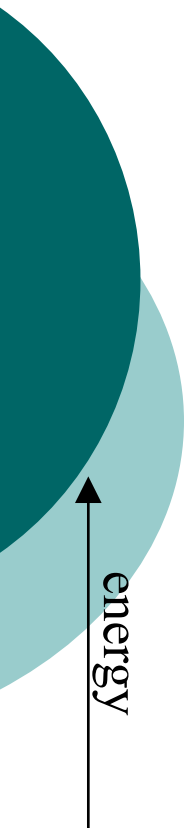
When we are done filling the box, the energy of the last electron is called the “Fermi energy.”

“Gas” means we neglect electron-electron interactions.

All these states are filled with electrons.



Fermi energy



$$\# \text{ electrons} = \int_0^{E_f} N_E dE = \int_0^{E_f} L^3 \frac{2^{1/2} m^{3/2}}{\pi^2 \hbar^{3/2}} \cdot E^{1/2} dE$$

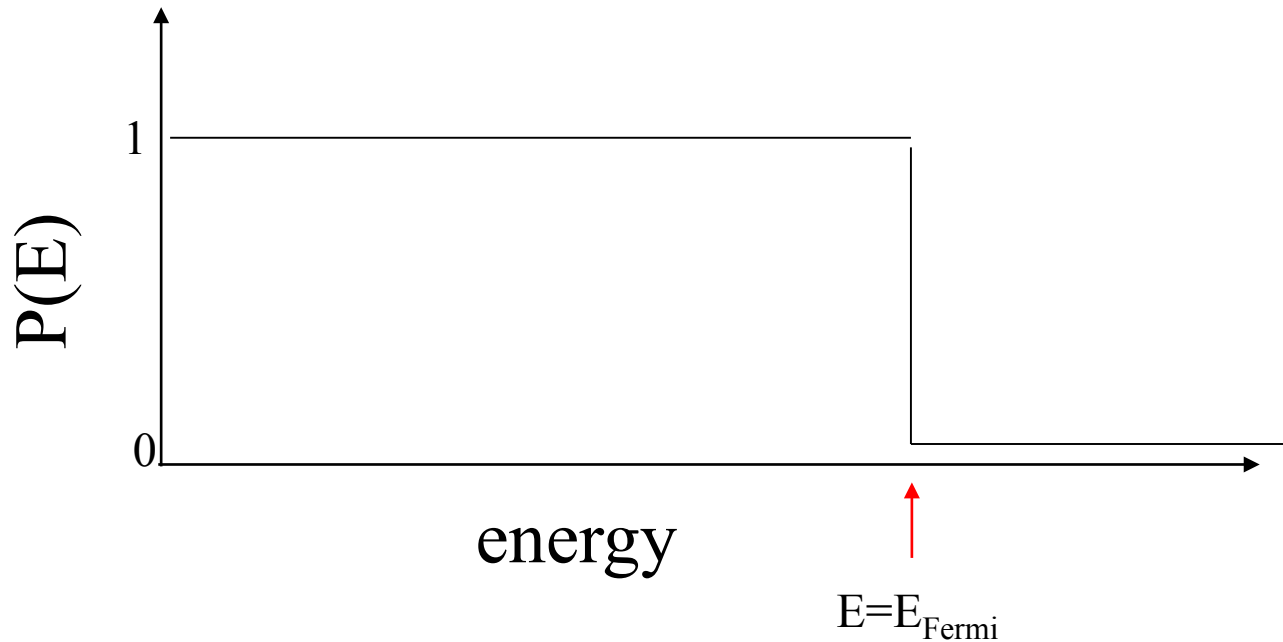
$$\# \text{ electrons} = L^3 \frac{2^{1/2} m^{3/2}}{\pi^2 \hbar^{3/2}} \frac{2}{3} E_f^{3/2}$$

$$\Rightarrow E_f = \frac{\hbar^2 3^{2/3} \pi^{4/3}}{2m} \left(\frac{\# \text{ electrons}}{L^3} \right)^{2/3}$$

All these states are filled with electrons.

In a typical metal, 1 electron / (0.1 nm)³.
 $E_f \sim 10 \text{ eV}$

Occupation probability



$P(E)$ = probability of occupying a state with energy E

What about finite temperature?

Boltzmann

Recall Boltzmann factor $P(\varepsilon)$:

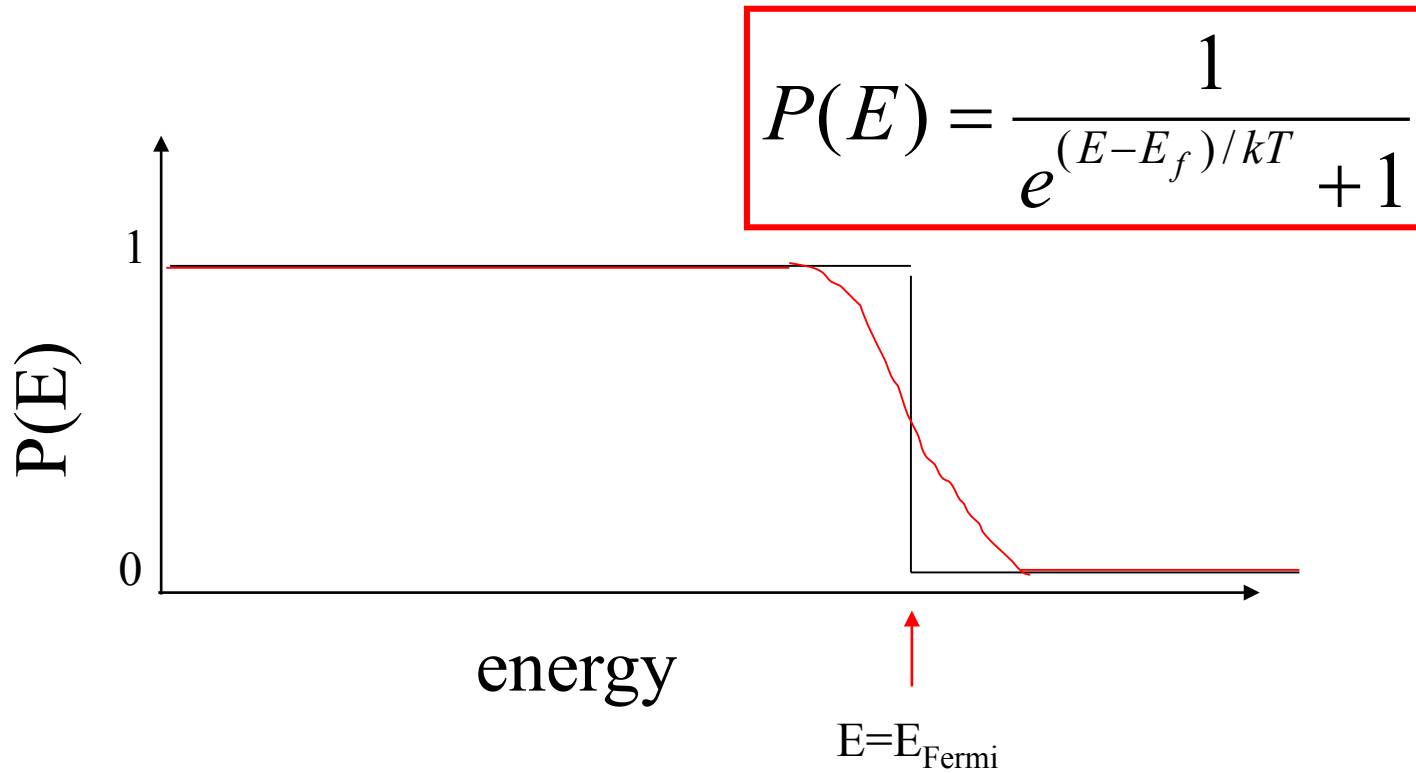
“The probability for a physical system to be in a state with energy ε is proportional to $e^{-\varepsilon/kT}$.”

This is actually not quite true. It is classical.
A quantum calculation shows for electrons:

$$P(E) = \frac{1}{e^{(E-E_f)/kT} + 1}$$

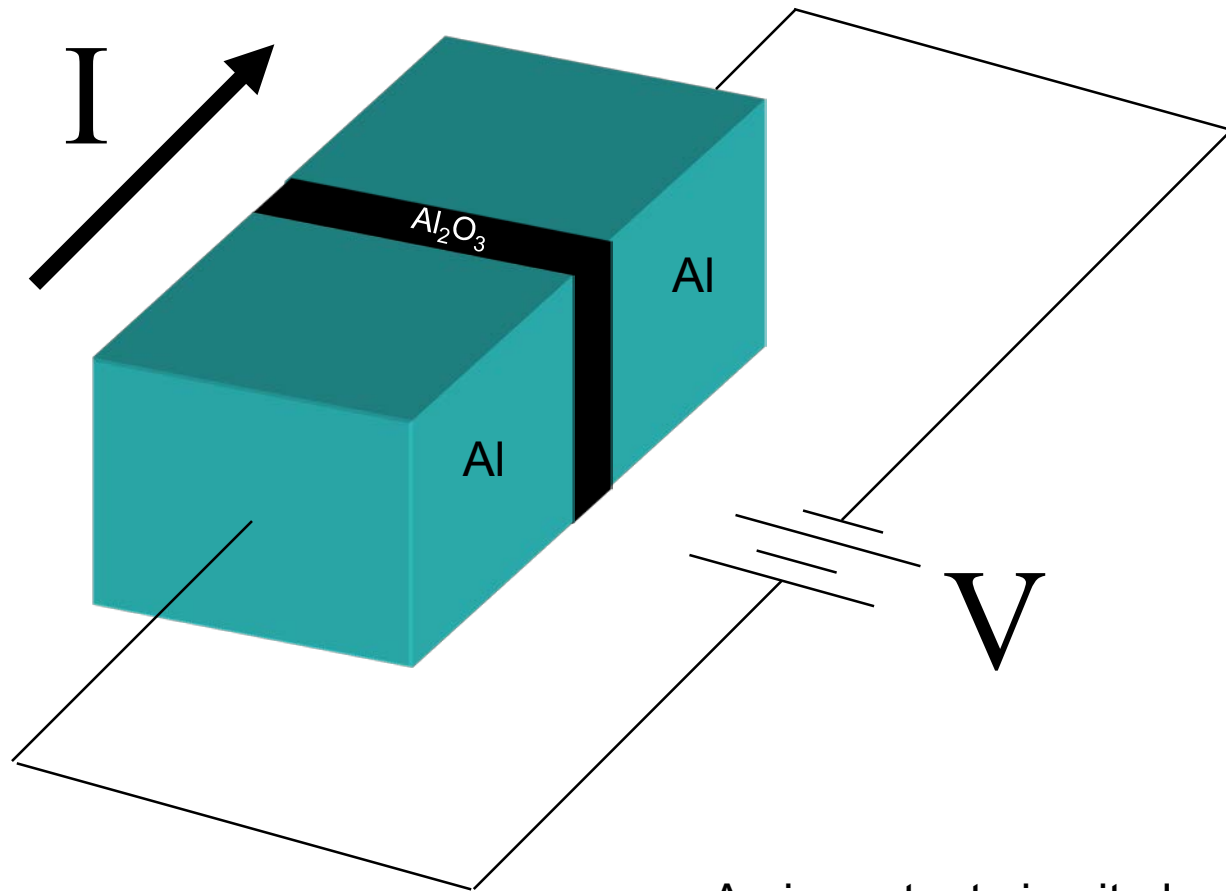
Called Fermi-Dirac distribution function.
Boltzmann is high-energy limit (discuss!)

Fermi-Dirac



$P=1/2$ at E_f for all temperatures.

Tunnel junctions



An important circuit element in
single electron transistors.

Readings this lecture covers

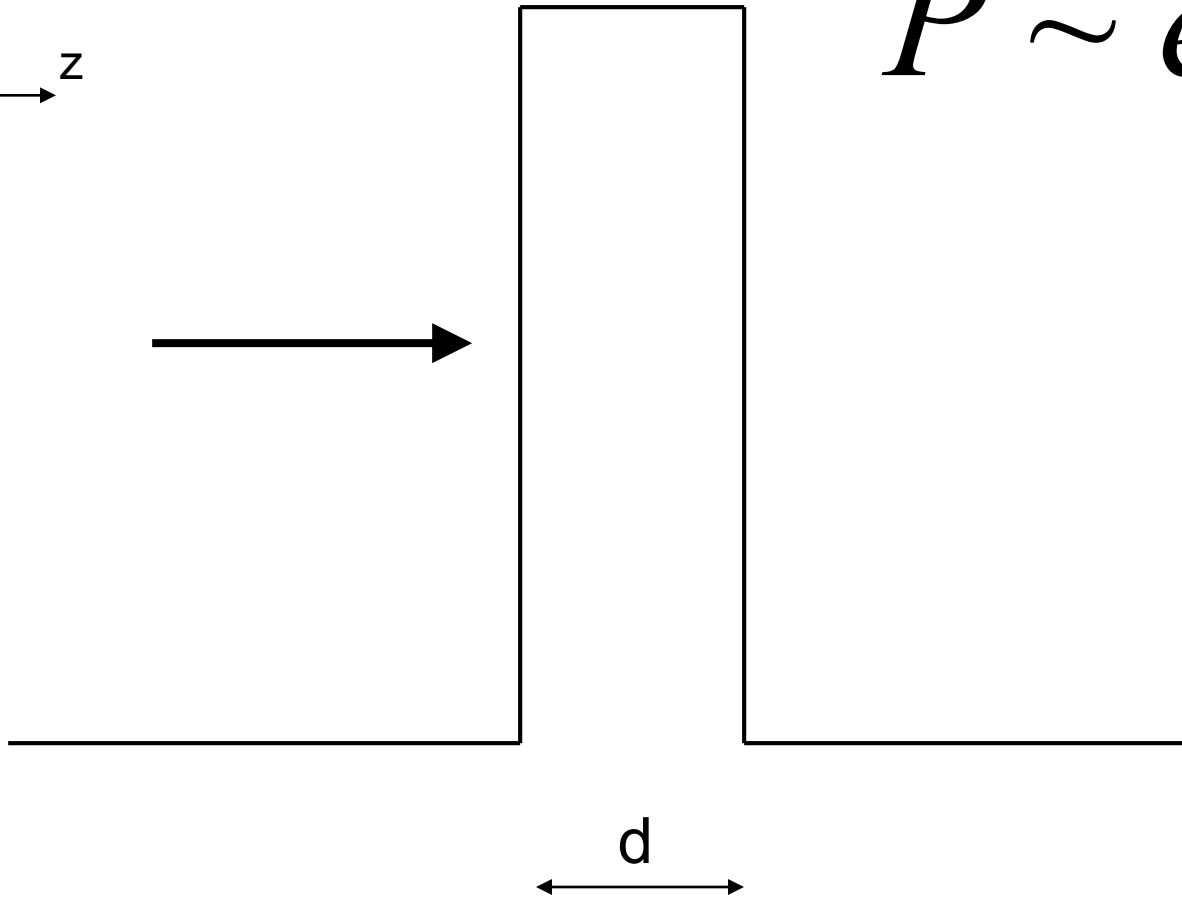
- Ferry pp. 91-101, 114-117
- Reference: Hanson Ch. 6

Quantum tunnel probability

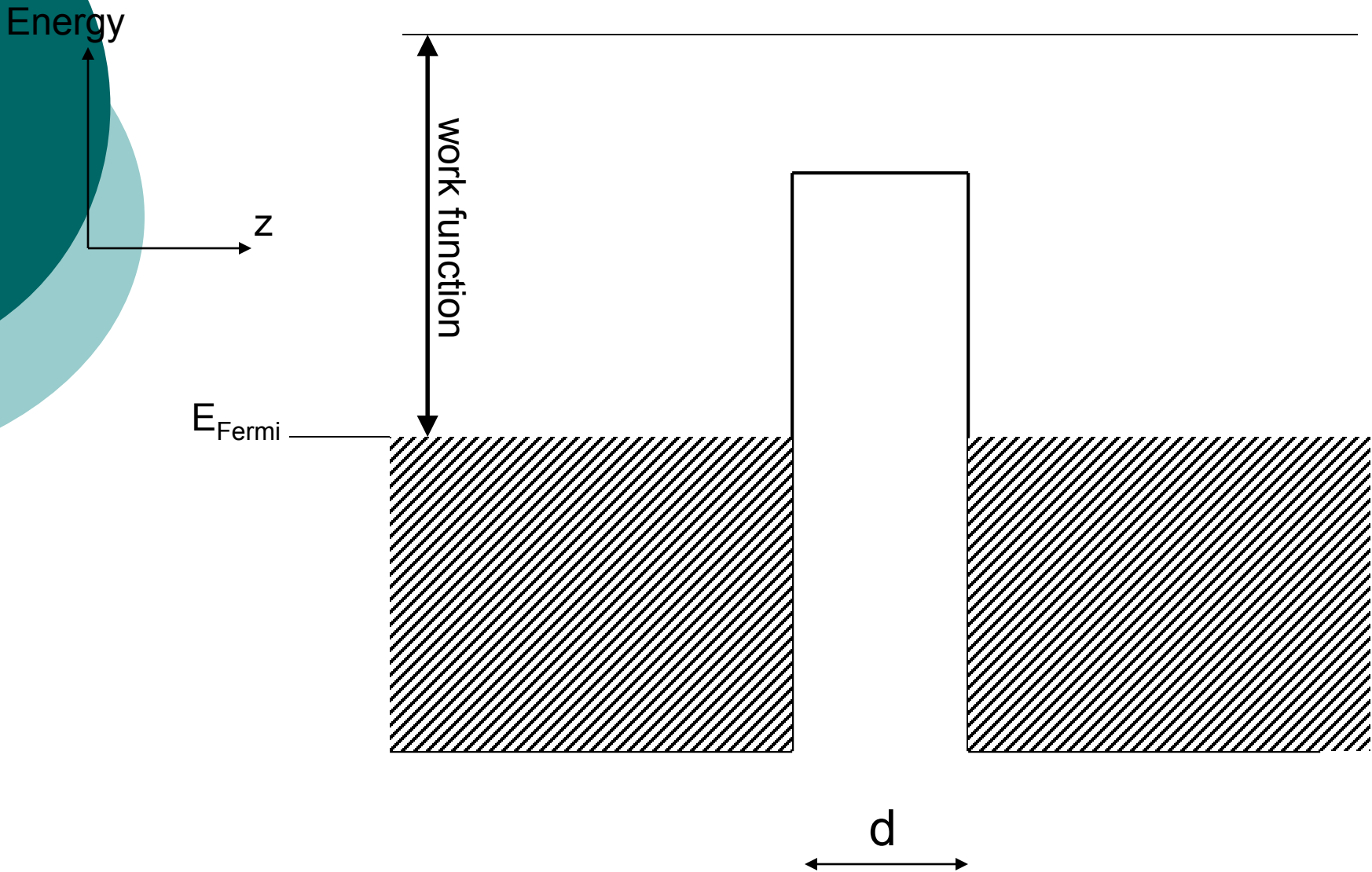
Energy

z

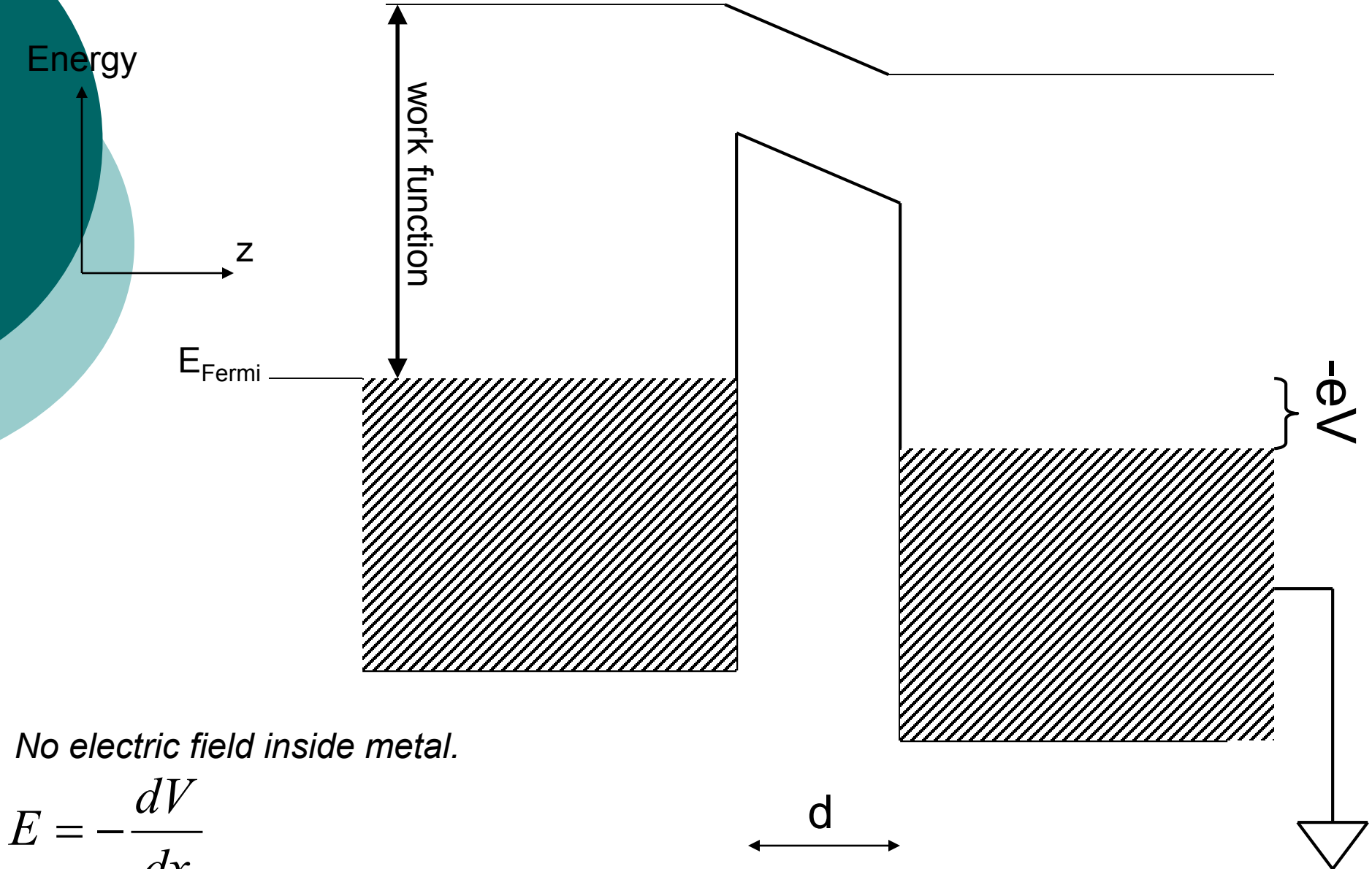
$$P \sim e^{-d}$$



Band diagram for tunnel junction



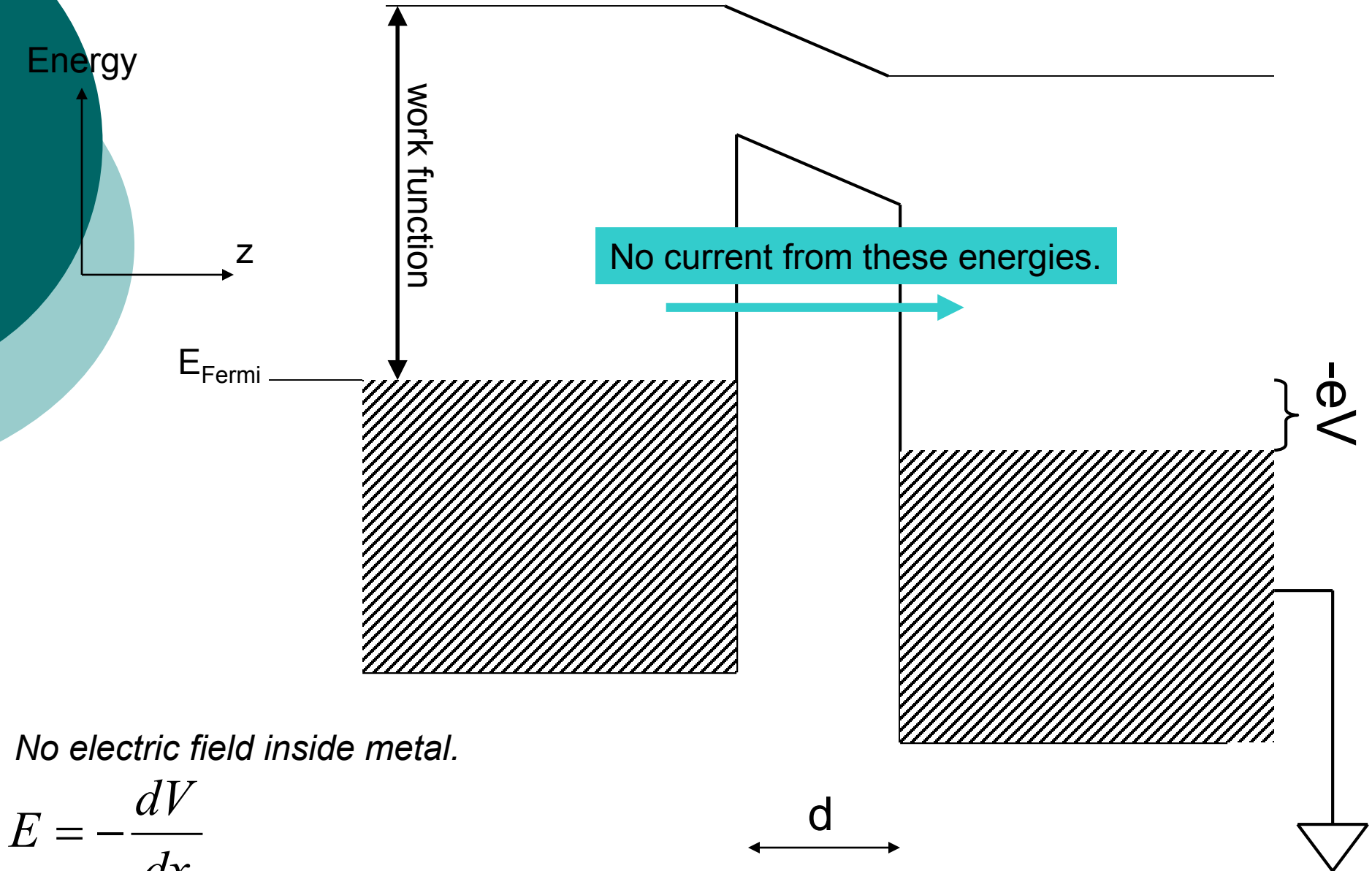
Band diagram under bias



No electric field inside metal.

$$E = -\frac{dV}{dx}$$

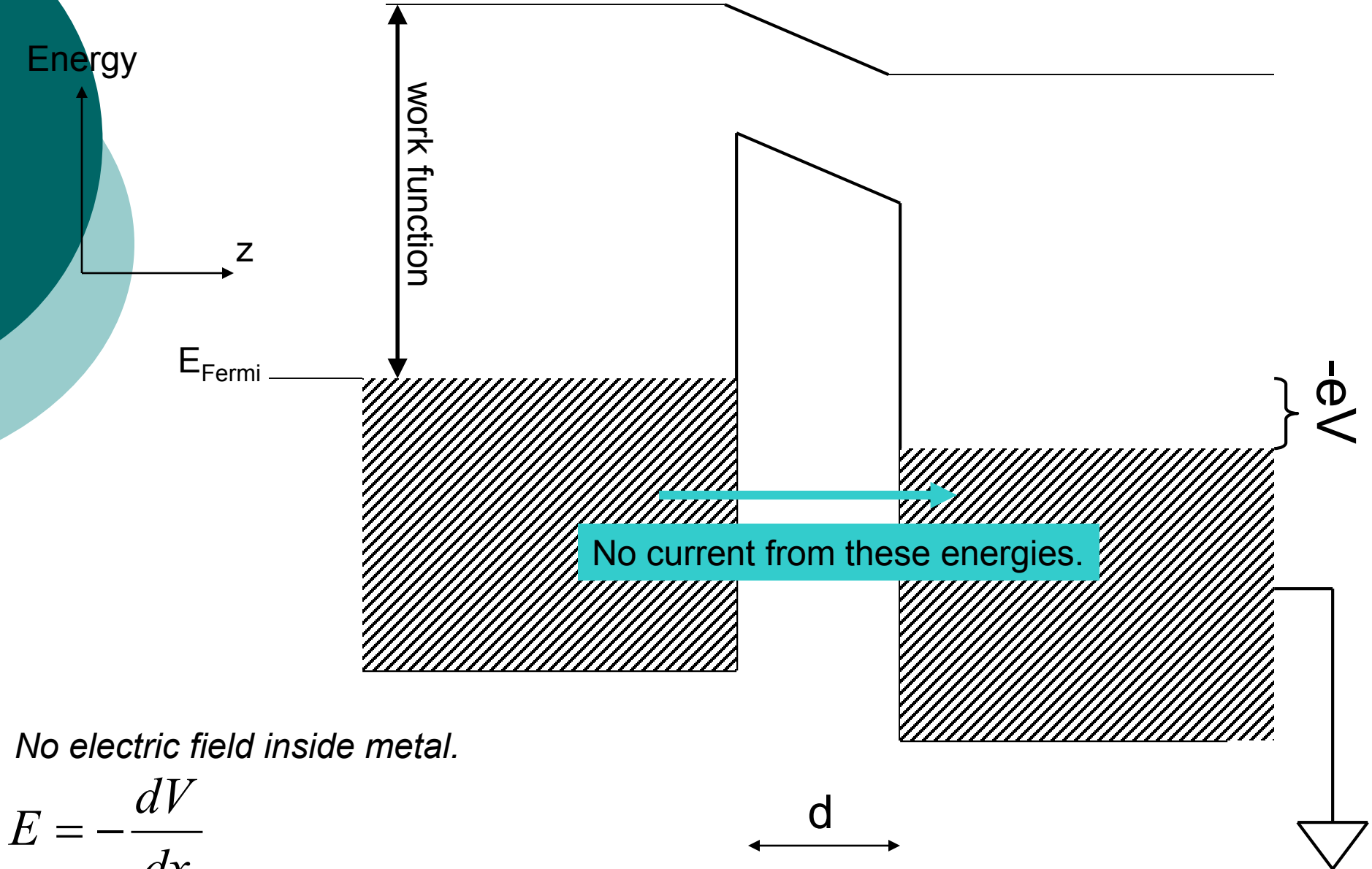
Band diagram under bias



No electric field inside metal.

$$E = -\frac{dV}{dx}$$

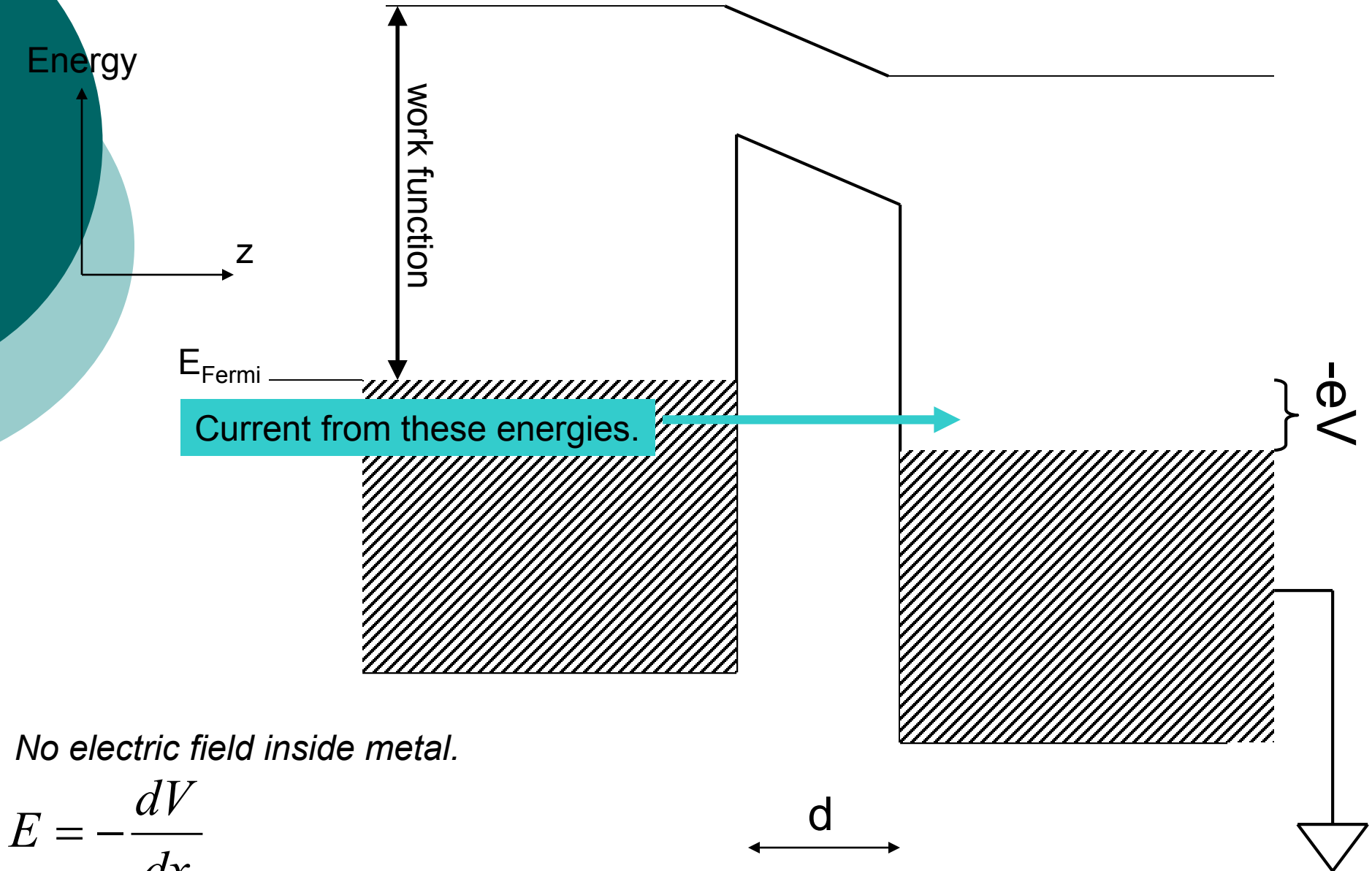
Band diagram under bias



No electric field inside metal.

$$E = -\frac{dV}{dx}$$

Band diagram under bias



$$E = -\frac{dV}{dx}$$

I-V curve

$$I = e \left(\frac{\# \text{ electrons}}{\text{second}} \Big|_{R-L} - \frac{\# \text{ electrons}}{\text{second}} \Big|_{L-R} \right)$$

$$\frac{\# \text{ electrons}}{\text{second}} \Big|_{L-R} = \sum_{\text{left electron states}} \sum_{\text{right electron states}} \left(\text{Pr ob}_{\text{left electron state occupied}} \right) \left(\text{Pr ob}_{\text{right electron state empty}} \right) T$$

Treat particles in left as “particle in a box”
 Recall our way of labeling states, and each state has energy:

$$E = \frac{\hbar^2 (\pi / L)^2}{2m} (n_x^2 + n_y^2 + n_z^2)$$

$$\frac{\# \text{ electrons}}{\text{second}} \Big|_{L-R} \rightarrow \sum_{n_x, n_y, n_z} \sum_{m_x, m_y, m_z} \left(\text{Pr ob}_{\text{left electron state occupied}} \right) \left(\text{Pr ob}_{\text{right electron state empty}} \right) T$$

$$\rightarrow \sum_{n_x, n_y, n_z} \sum_{m_x, m_y, m_z} \left(P_{n_x, n_y, n_z} \right) \left(1 - P_{m_x, m_y, m_z} \right) T$$

I-V curve

$$\left. \frac{\# \text{electrons}}{\text{second}} \right|_{L-R} = \sum_{n_x, n_y, n_z} \sum_{m_x, m_y, m_z} \left(P_{n_x, n_y, n_z} \right) \left(1 - P_{m_x, m_y, m_z} \right) T$$

Energy and momentum are conserved in physics so:

$$T = 0 \text{ unless}$$

$$n_x = m_x$$

$$n_y = m_y$$

$$E_{\text{left}} - eV = E_{\text{right}}$$

$$E_{\text{left}} - eV = E_{\text{right}}$$

$$\Rightarrow \frac{\hbar^2 (\pi / L)^2}{2m} (n_x^2 + n_y^2 + n_z^2) - eV = \frac{\hbar^2 (\pi / L)^2}{2m} (m_x^2 + m_y^2 + m_z^2)$$

$$\Rightarrow \frac{\hbar^2 (\pi / L)^2}{2m} n_z^2 - eV = \frac{\hbar^2 (\pi / L)^2}{2m} m_z^2$$

I-V curve

$$\left. \frac{\# \text{ electrons}}{\text{second}} \right|_{L-R} = \sum_{n_x, n_y, n_z} \sum_{m_x, m_y, m_z} \left(P_{n_x, n_y, n_z} \right) \left(1 - P_{m_x, m_y, m_z} \right) T$$

$$\rightarrow \sum_{n_x, n_y, n_z} \left(P_{n_x, n_y, n_z} \right) \left(1 - P_{n_x, n_y, m_z} \right) T$$

$$P_{n_x, n_y, n_z} = \frac{1}{1 + e^{\left(\frac{\hbar^2 (\pi/L)^2 (n_x^2 + n_y^2 + n_z^2) - E_f}{kT} \right)}} = f(E_L)$$

$$P_{n_x, n_y, m_z} = \frac{1}{1 + e^{\left(\frac{\hbar^2 (\pi/L)^2 (n_x^2 + n_y^2 + m_z^2) - E_f}{kT} \right)}} = \frac{1}{1 + e^{\left(\frac{\hbar^2 (\pi/L)^2 (n_x^2 + n_y^2 + n_z^2) + eV - E_f}{kT} \right)}} = \frac{1}{1 + e^{\left(\frac{E_L + eV - E_f}{kT} \right)}} = f(E_L + eV)$$

$$\left. \frac{\# \text{ electrons}}{\text{second}} \right|_{L-R} \rightarrow \sum_{n_x, n_y, n_z} \left(f(E_L) \right) \left(1 - f(E_L + eV) \right) T$$

I-V curve

$$\left. \frac{\# \text{electrons}}{\text{second}} \right|_{L-R} \rightarrow \sum_{n_x, n_y, n_z} (f(E_L))(1 - f(E_L + eV))T$$

A similar calculation shows:

$$\left. \frac{\# \text{electrons}}{\text{second}} \right|_{R-L} \rightarrow \sum_{n_x, n_y, n_z} (f(E_L + eV))(1 - f(E_L))T$$

Since:

$$I = e \left(\left. \frac{\# \text{electrons}}{\text{second}} \right|_{R-L} - \left. \frac{\# \text{electrons}}{\text{second}} \right|_{L-R} \right)$$

We have:

$$I = e \sum_{n_x, n_y, n_z} \left[(f(E_L) - f(E_L + eV)) \right] T$$

A nice, simple result.

I-V curve

$$I = e \sum_{n_x, n_y, n_z} \left[(f(E_L) - f(E_L + eV)) \right] T$$

$$I = e \sum_{n_x, n_y} \sum_{n_z} \left[(f(E_L) - f(E_L + eV)) \right] T$$

In the macro world, states are very finely spaced and we have (discuss):
(Later in the class we will see that this fails in nanosized circuits.)

$$\sum_{n_x} \rightarrow \int dn_x \quad \sum_{n_y} \rightarrow \int dn_y \quad \sum_{n_z} \rightarrow \int dn_z$$

$$I \rightarrow e \int dn_x \int dn_y \int dn_z \left[(f(E_L) - f(E_L + eV)) \right] T$$

I-V curve

$$I \rightarrow e \int dn_x \int dn_y \int dn_z \left[(f(E_L) - f(E_L + eV)) \right] T$$

$$I \rightarrow e \int dn_x \int dn_y \int \frac{m}{\hbar^2 (\pi/L)^2} \frac{1}{\sqrt{E_L - \frac{\hbar^2 (\pi/L)^2}{2m} (n_x^2 + n_y^2)}} dE_L \left[(f(E_L) - f(E_L + eV)) \right] T$$

$$I \approx e \int dn_x \int dn_y \frac{m}{\hbar^2 (\pi/L)^2} \frac{1}{\sqrt{E_F - \frac{\hbar^2 (\pi/L)^2}{2m} (n_x^2 + n_y^2)}} T \int dE_L \left[(f(E_L) - f(E_L + eV)) \right]$$

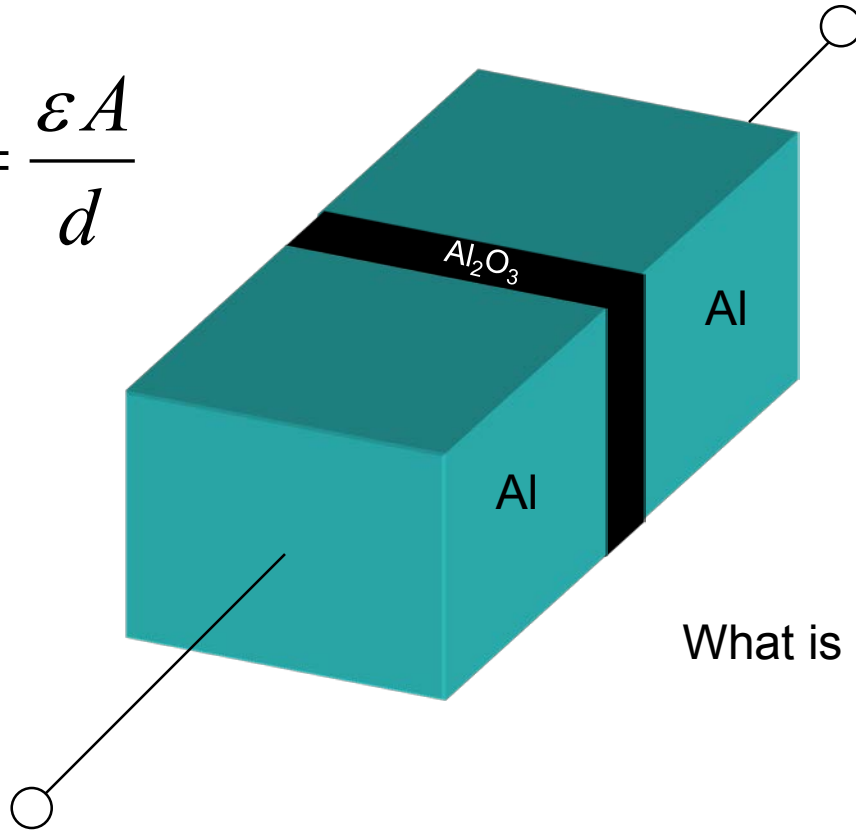
$$\int dE_L \left[(f(E_L) - f(E_L + eV)) \right] \approx eV \quad (\text{show on board})$$

$$I \approx (eV) eT \frac{m}{\hbar^2 (\pi/L)^2} \int_0^\infty dn_x \int_0^\infty dn_y \frac{1}{\sqrt{E_F - \frac{\hbar^2 (\pi/L)^2}{2m} (n_x^2 + n_y^2)}}$$

$$I \approx (eV) (\text{constant})$$

Lecture 5: Coulomb blockade

$$C = \frac{\epsilon A}{d}$$



What is charge on this capacitor?

Readings this lecture covers

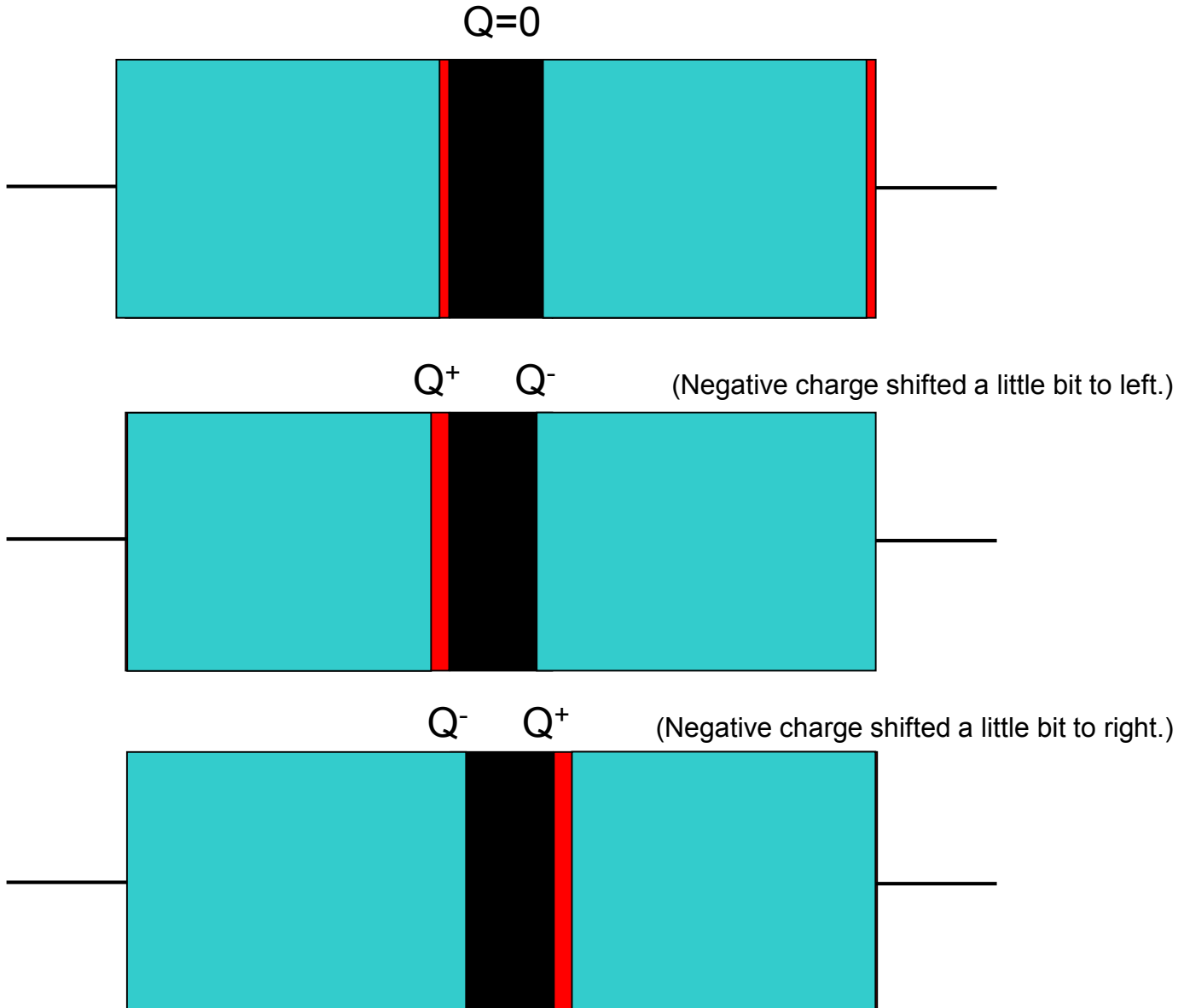
- Ferry pp. 226-244
- Hanson, pp. 212-244
- Cleland PRL, PRB (reading packet)
- Devoret chapter in *Single Charge Tunneling* (reading packet)
- Grabert chapter (reading packet)
- These chapters are covered all the way to (and including) lecture 8

Charge on capacitor continuous

-ve charge



+ve charge



Is tunneling allowed?

-ve charge



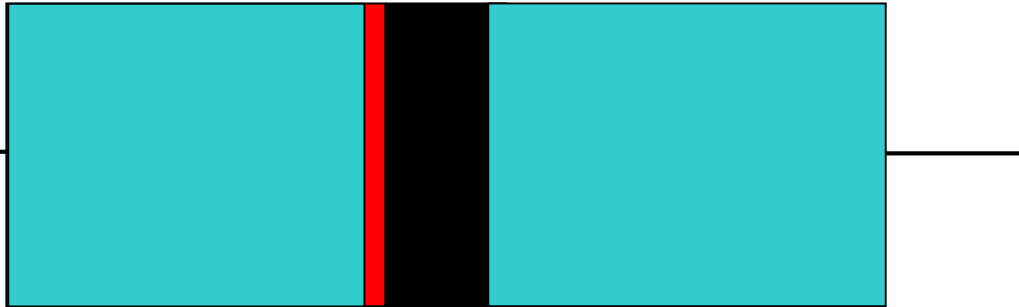
+ve charge



(Negative charge shifted a little bit to left.)

Q^+

Q^-



$$E = \frac{Q^2}{2C}$$

Is tunneling allowed?

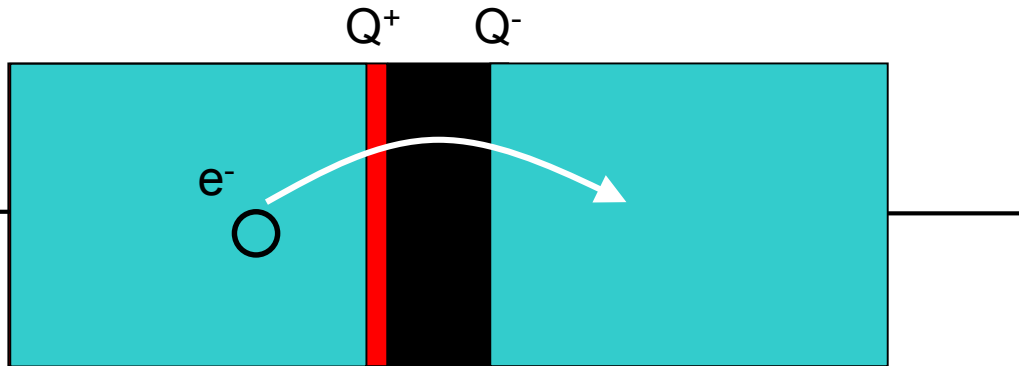
-ve charge



+ve charge



(Negative charge shifted a little bit to left.)



$$E = \frac{Q^2}{2C}$$

Is tunneling allowed?

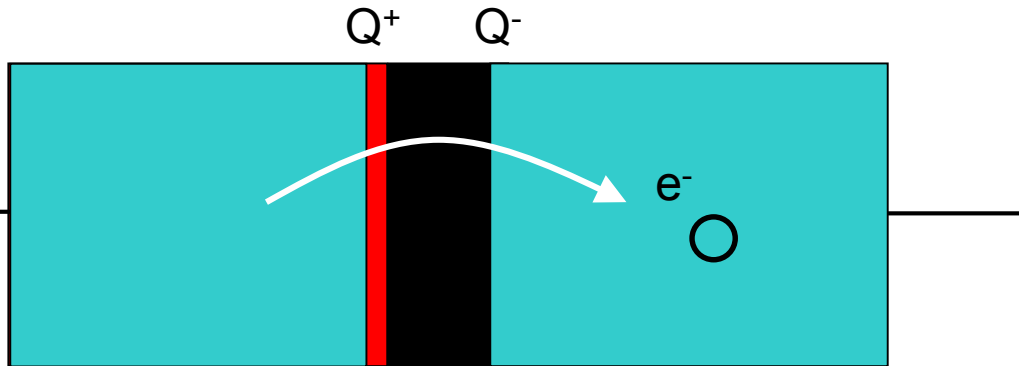
-ve charge



+ve charge

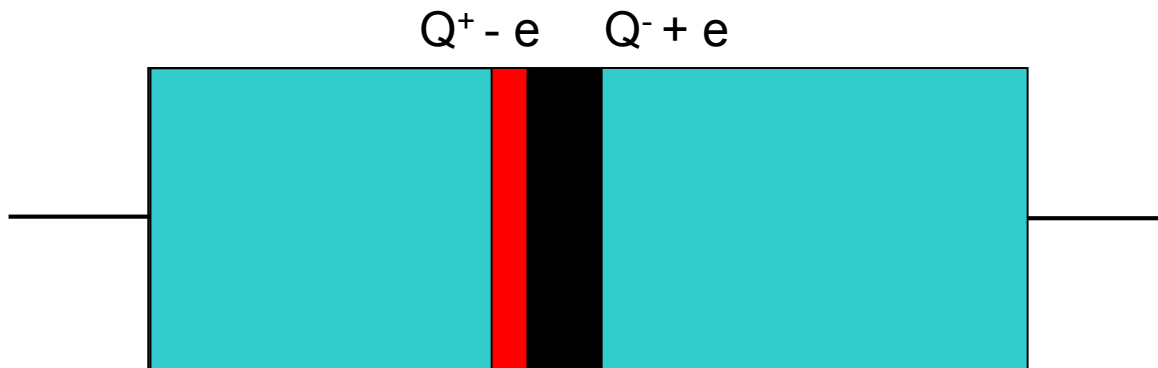


(Negative charge shifted a little bit to left.)



$$E = \frac{Q^2}{2C}$$

After electron tunnels:



$$E = \frac{(Q - e)^2}{2C}$$

$$\Delta E = \frac{e(Q - e/2)}{C}$$

Coulomb gap

-ve charge



+ve charge



$$\Delta E = \frac{e(Q - e/2)}{C} > 0$$

$$\Rightarrow Q - e/2 > 0$$

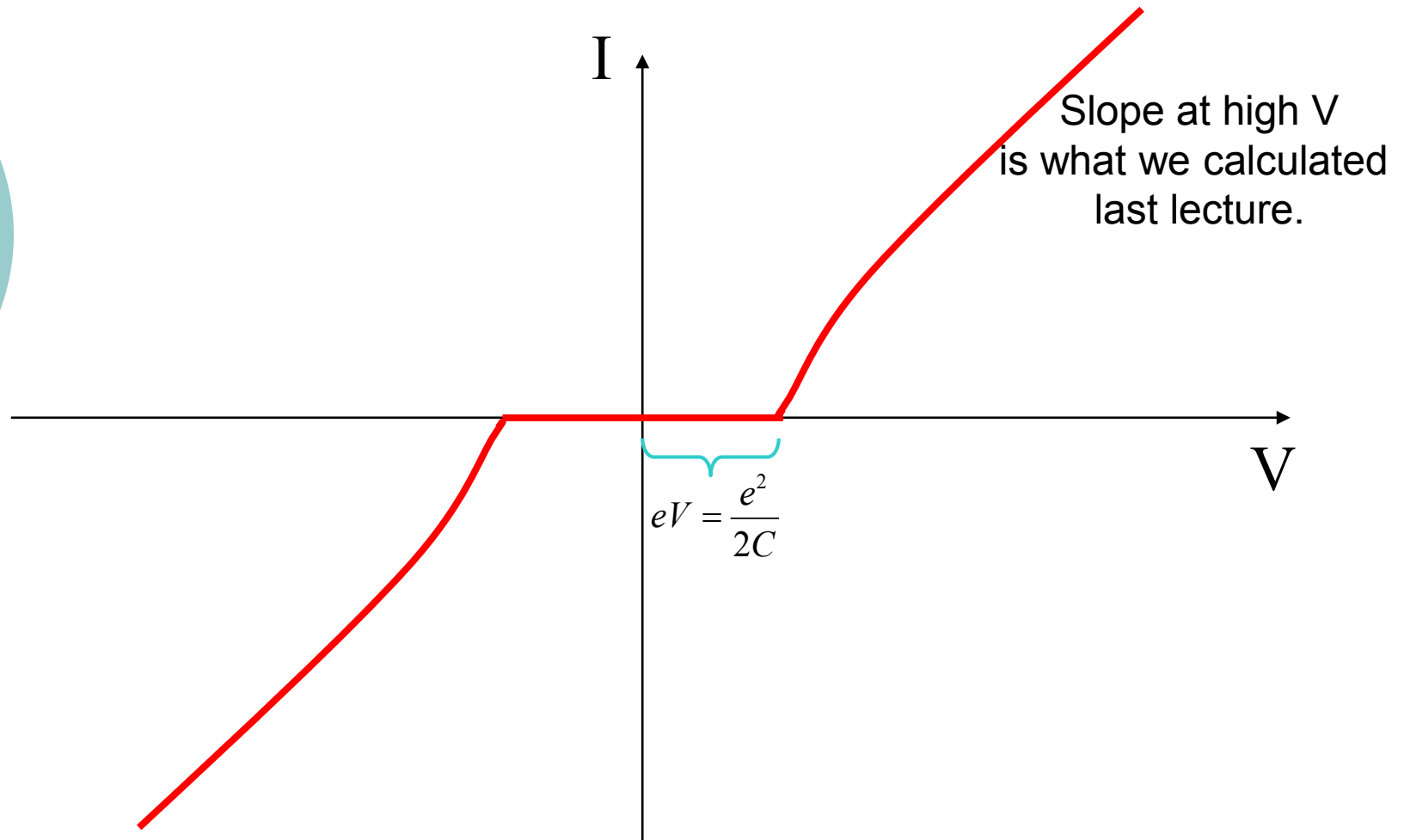
$$\Rightarrow Q > e/2$$

$$\Rightarrow C|V| > e/2 \Rightarrow |V| > \frac{e}{2C}$$

$$\boxed{-\frac{e}{2C} < V < \frac{e}{2C}}$$

Tunneling only under these conditions, *otherwise no tunneling!*

I-V curve



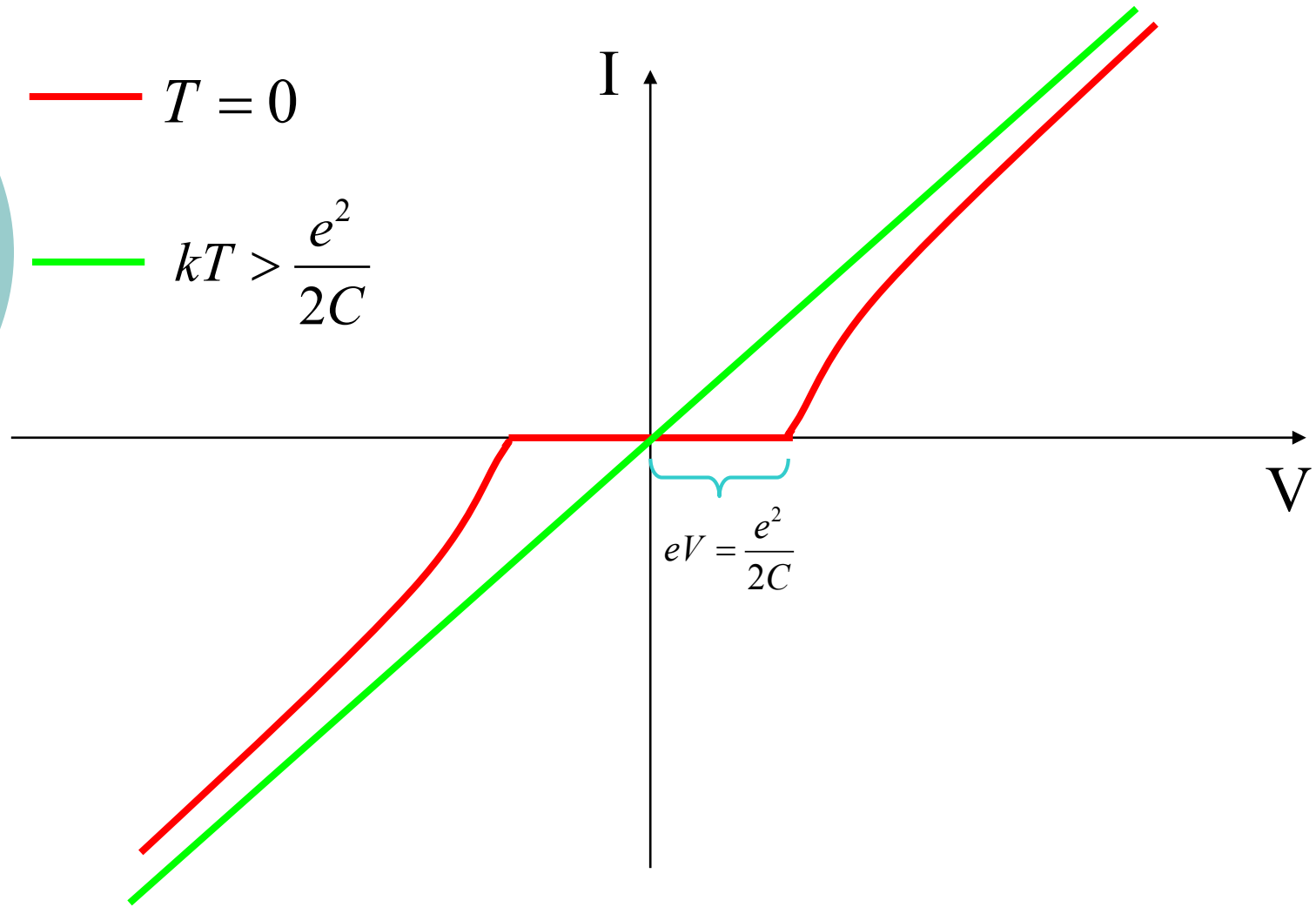
Temperature

$$\Delta E = \frac{e(Q - e/2)}{C} \quad \text{can be less than 0 if thermal energy available}$$

Criteria to observe coulomb gap behavior:

$$\frac{e^2}{C} > kT$$

I-V curve vs. temperature



Numbers

Class demo:

1 nm barrier, 1 mm x 1 mm junction:

$$C = \frac{\epsilon A}{d} = \frac{10 \cdot 8.85 \cdot 10^{-12} \text{ F/m} (10^{-3} \text{ m})^2}{10^{-9} \text{ m}} \approx 10^{-7} \text{ F}$$

$$\frac{e^2}{C} > kT \Rightarrow T < \frac{e^2}{Ck} = \frac{(1.6 \cdot 10^{-19} \text{ coulomb})^2}{10^{-7} \text{ F} \cdot 1.38 \cdot 10^{-23} \text{ J/K}} \approx 10^{-8} \text{ K}$$

Practically impossible.

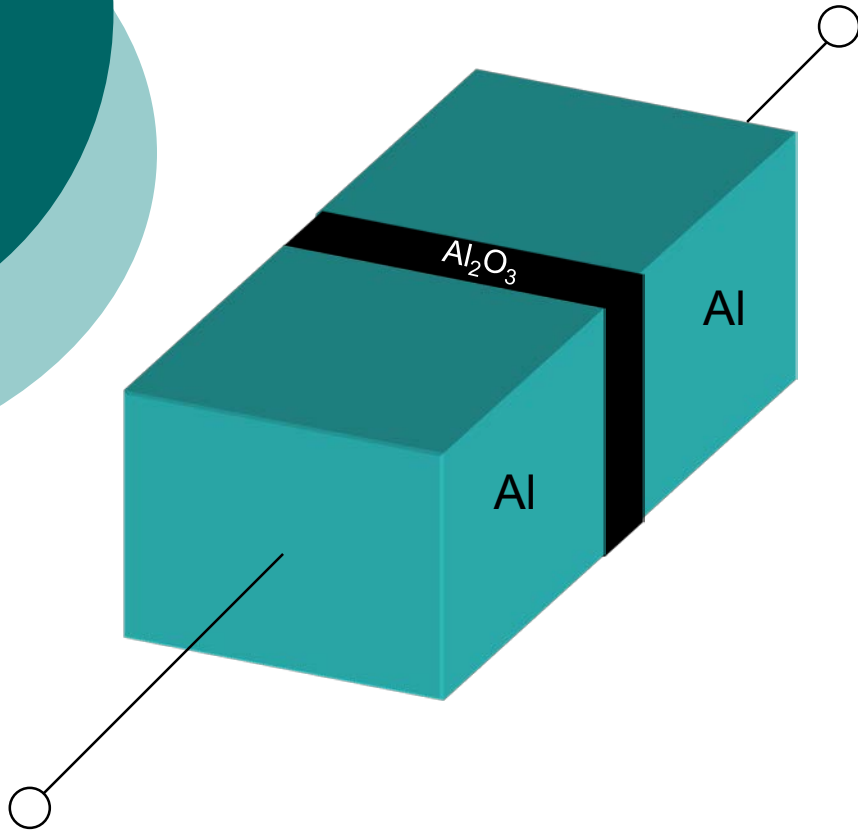
Best lithographic junction:

1 nm barrier, 100 nm x 100 nm junction:

$$C \approx 10^{-15} \text{ F} \Rightarrow T < 1 \text{ K}$$

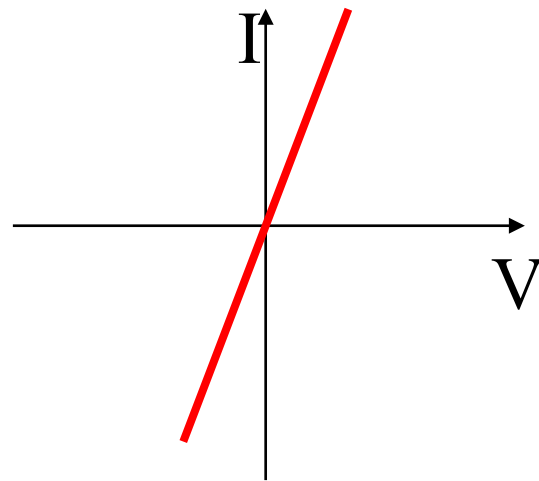
Possible to achieve in the lab.

Quantum mechanics



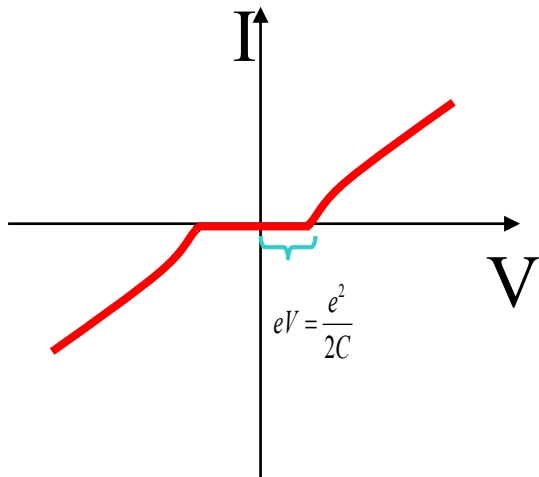
- For strong tunneling, electron can have a large probability to be on both sides at the same time.
- This means the system energy cannot be defined by localizing the electron on only one side.
- This makes coulomb blockade irrelevant.

I-V curve vs. tunnel strength



Strong tunneling

$$R_T < R_K \equiv \frac{h}{e^2} = 25 \text{ k}\Omega$$



Weak tunneling

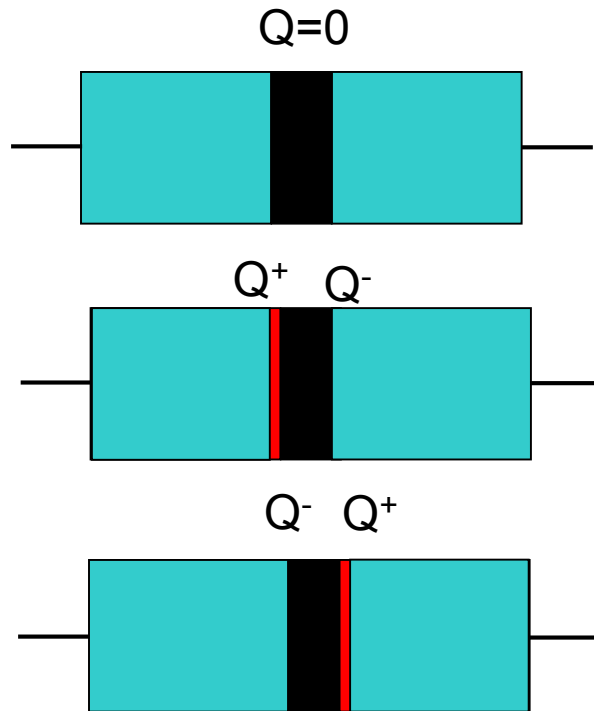
$$R_T > \frac{h}{e^2} = 25 \text{ k}\Omega$$

Charge on capacitor is a *quantum variable*

-ve charge

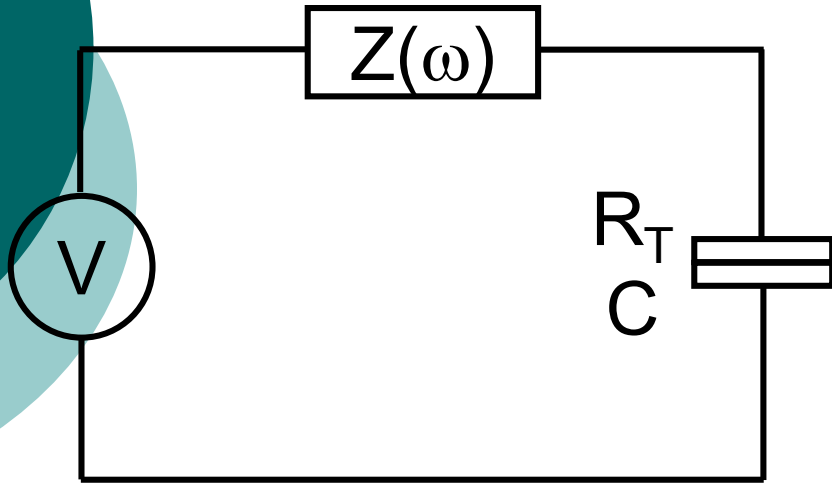


+ve charge



- We don't always know what Q is.
- Treating Q as a quantum variable, there is a certain probability for the system to have a certain value of Q .
- Should describe a "wave function" for Q : $\Psi(Q)$ just like wave function for position $\Psi(x)$
- Now, we need quantum theory of electric circuits.

Quantum theory of electric circuits



- At DC, can have current bias or voltage bias depending on $Z(\text{dc})$ vs. R_T .
- At AC, almost always have $Z(\omega) < R_T$ because of lead capacitance (typically pF).

Full quantum treatment beyond the scope of this class.

In order to see Coulomb blockage, need current bias all the way up to $1/(R_K C)$ which is typically 10 GHz, i.e.:

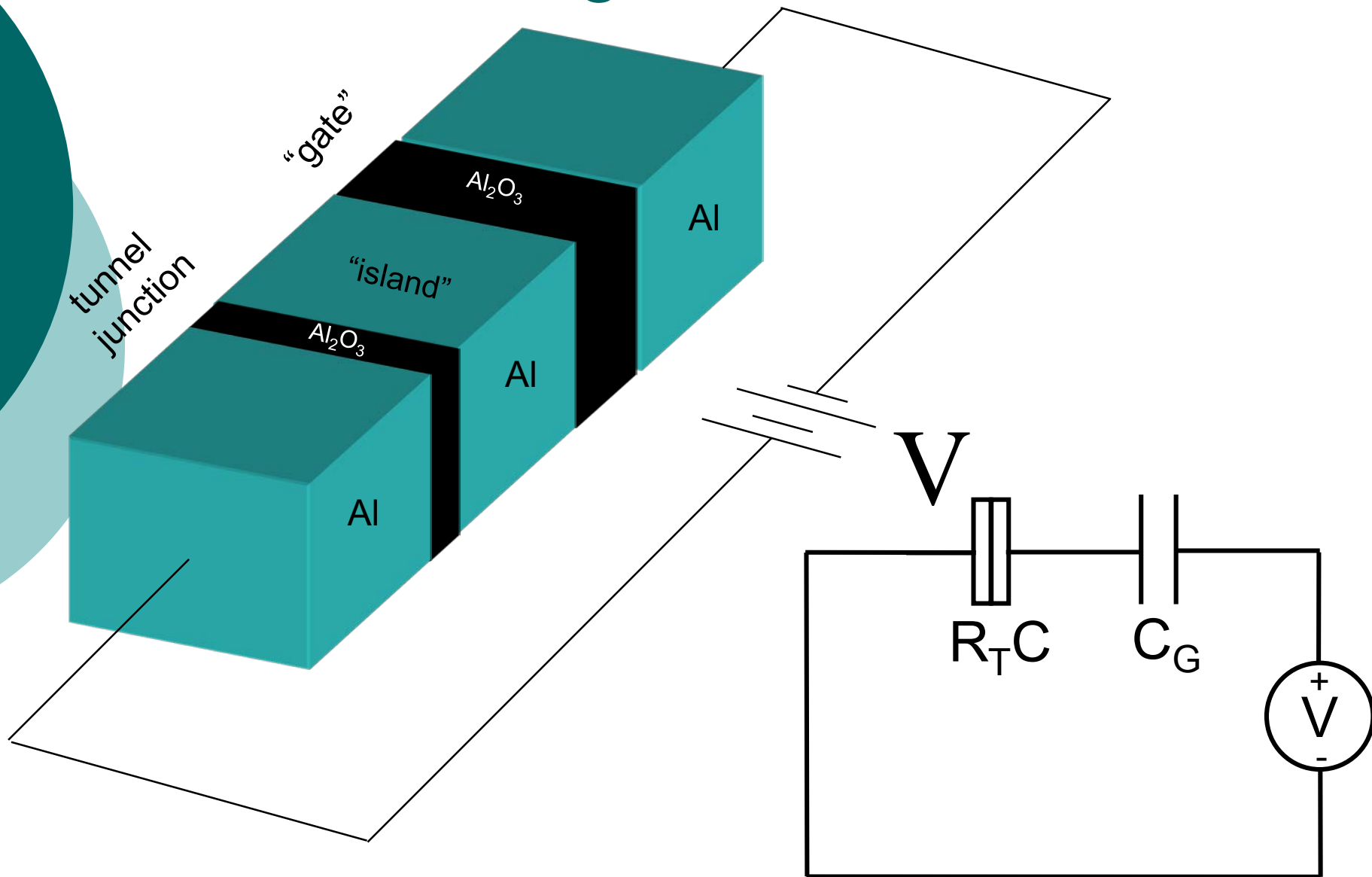
$$Z(\omega) > R_T \text{ for all } \omega \leq \frac{1}{R_K C} \sim 10 \text{ GHz}$$

Requirements for Coulomb blockade

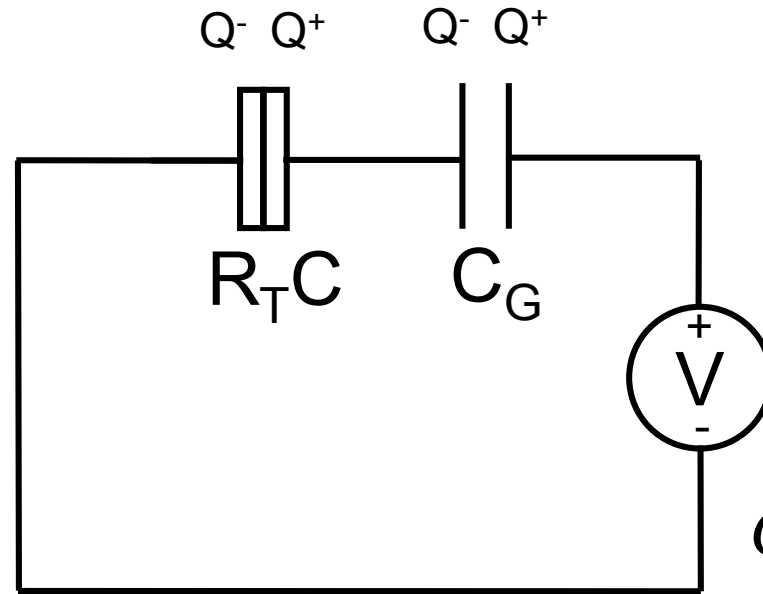
- $kT < e^2/C$ (hard)
- $R_T > R_K$ (25 k Ω)
(harder)
- $Z(\omega) > R_T$ at all frequencies up to $1/R_K C$
(hardest)

Achieved by Cleland PhD thesis, Berkeley 1992.
(Congratulations, Andrew.)

Lecture 6: Single electron box



Electrostatic energy (*no tunneling*)

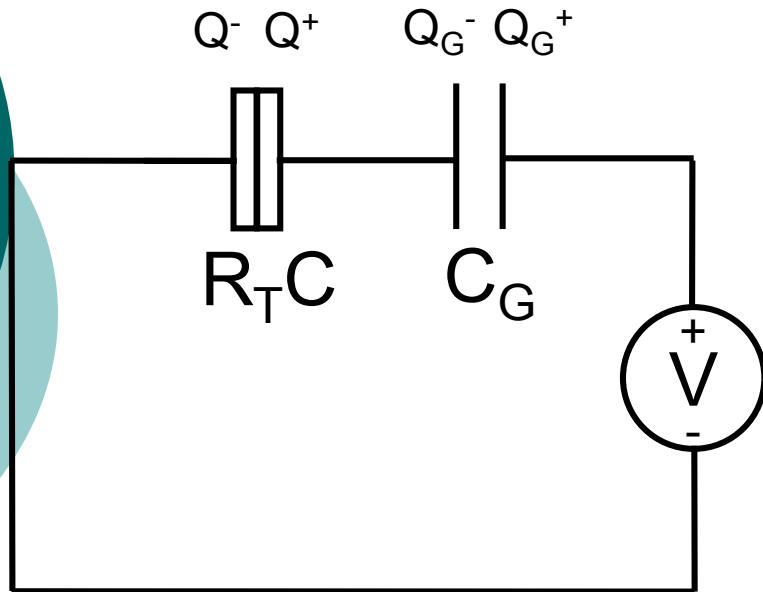


$$C_{series}^{-1} \equiv C^{-1} + C_G^{-1}$$

$$V = \frac{Q}{C} + \frac{Q}{C_G} = Q \left(\frac{1}{C} + \frac{1}{C_G} \right) = \frac{Q}{C_{series}}$$

$$E = \frac{Q^2}{2C} + \frac{Q^2}{2C_G} = \frac{Q^2}{2C_{series}} = \frac{1}{2} C_{series} V^2$$

Island charge



“Island charge”:

$$Q_i = Q - Q_G$$

Kirchoff:

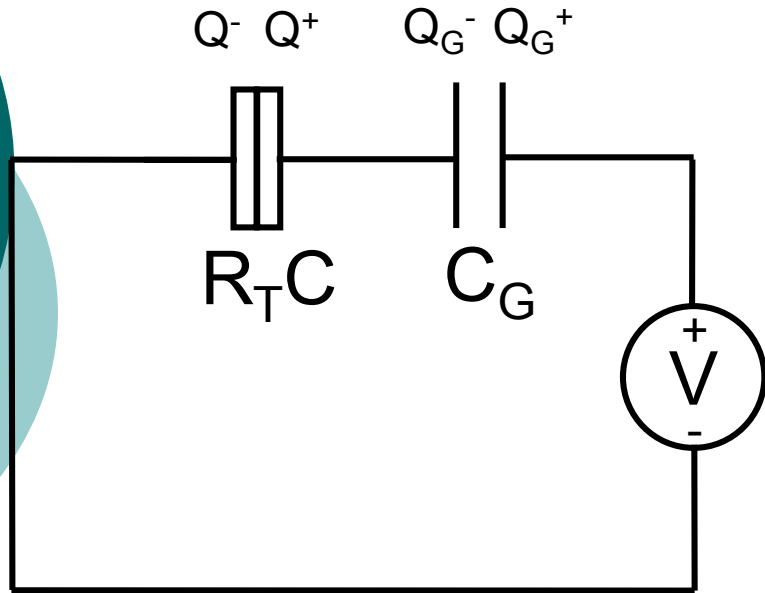
$$V = \frac{Q}{C} + \frac{Q_G}{C_G}$$

Solve for Q , Q_G :

$$Q = \frac{C(C_G V + Q_i)}{C + C_G}$$

$$Q_G = \frac{C_G(CV - Q_i)}{C + C_G}$$

Electrostatic energy (w/tunneling)



$$Q = \frac{C(C_G V + Q_i)}{C + C_G}$$

$$Q_G = \frac{C_G(CV - Q_i)}{C + C_G}$$

$$E = \frac{Q^2}{2C} + \frac{Q_G^2}{2C_G} = \frac{CC_G V^2 + Q_i^2}{2(C + C_G)}$$

Thermodynamics

Entropy:

$$S = S(E, V, N, \dots)$$

Energy:

$$E = E(S, V, N, \dots)$$

Entropy maximum \Leftrightarrow Energy minimum

Thermodynamic variables

Energy:

$$E = E(S, V, N, \dots)$$

Temperature:

$$\frac{1}{T} \equiv \left. \frac{\partial E}{\partial S} \right|_{V, N, \dots}$$

Pressure:

$$P \equiv - \left. \frac{\partial E}{\partial V} \right|_{E, N, \dots}$$

Thermodynamic potentials

Energy:

$$E = E(S, V, N, \dots)$$

Helmholtz potential (Helmholtz free energy):

$$F = E - TS$$

Minimized in presence of
“reservoir” with temperature T .

Enthalpy:

$$H = E + PV$$

Minimized in presence of
“reservoir” with pressure P .

Gibbs free energy:

$$G = E - TS + PV$$

Minimized in presence of
“reservoir” with pressure P ,
temperature T .

Thermodynamic potentials for circuits

Energy:

$$E = E(S, V, N, Q, \dots)$$

Gibbs free energy for electronic circuits:

$$G = E - Q_G V$$

Minimized in presence of
"reservoir" with voltage V.

↑
electrostatic
energy

↑
need to calculate

Q= how much charge has passed through the battery onto the gate

V= voltage of the battery

Free energy of single electron box:

$$G = E - Q_G V$$

From before:

$$E = \frac{CC_G V^2 + Q_i^2}{2(C + C_G)} \quad Q_G = \frac{C_G(CV - Q_i)}{C + C_G}$$

$$\begin{aligned} G &= \frac{CC_G V^2 + Q_i^2}{2(C + C_G)} - \frac{C_G(CV - Q_i)}{C + C_G} V \\ &= \frac{1}{2} \frac{(C_G V + Q_i)^2}{C + C_G} - \frac{1}{2} C_G V^2 \end{aligned}$$

(Note: The last minus sign agrees with Lafarge thesis, but not Ferry textbook.)

Charge of island

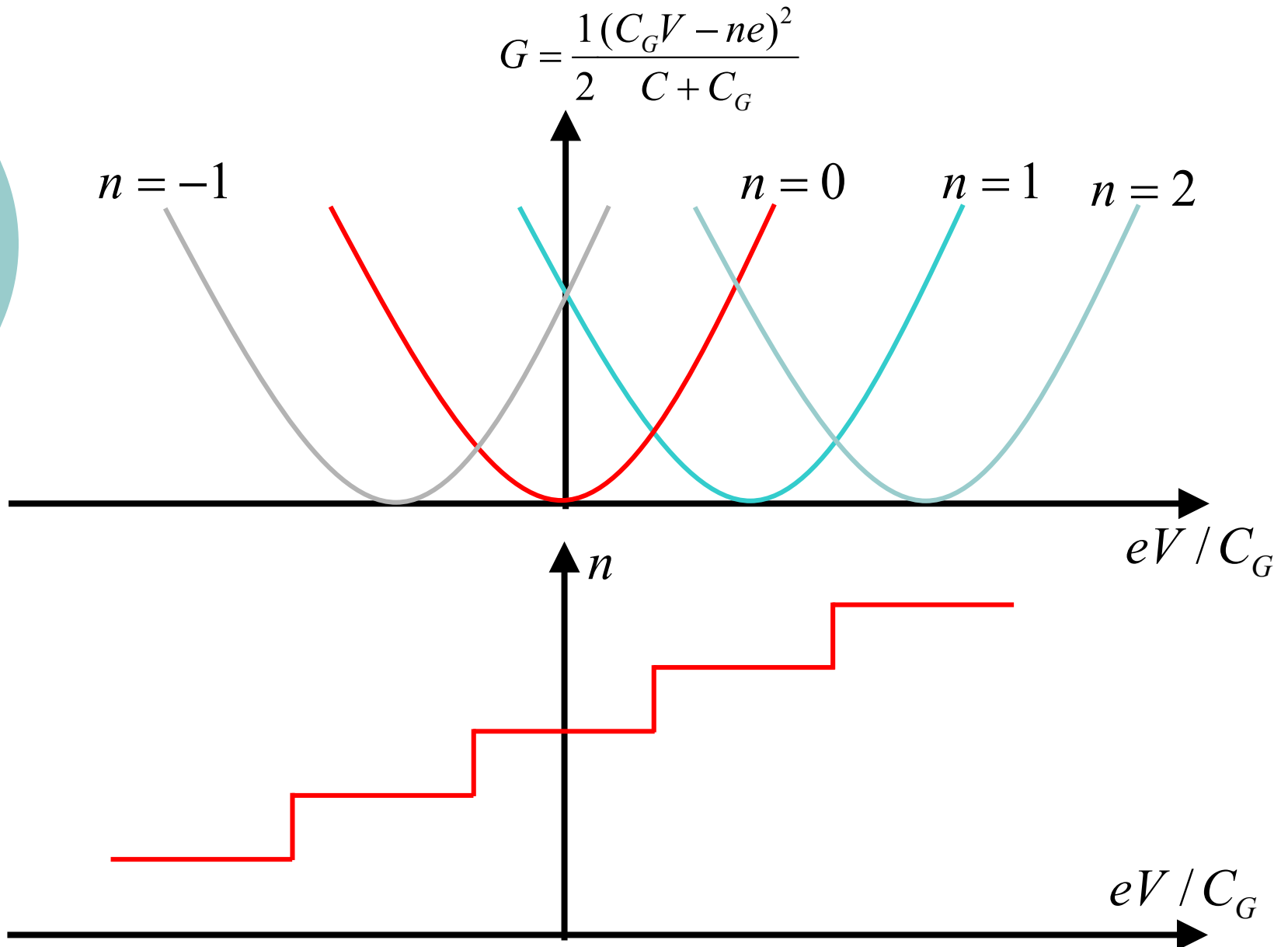
From last slide:

$$G = \frac{1}{2} \frac{(C_G V + Q_i)^2}{C + C_G} - \frac{1}{2} C_G V^2$$

$$Q_i = -ne \quad \text{only if } R_T \gg R_K$$

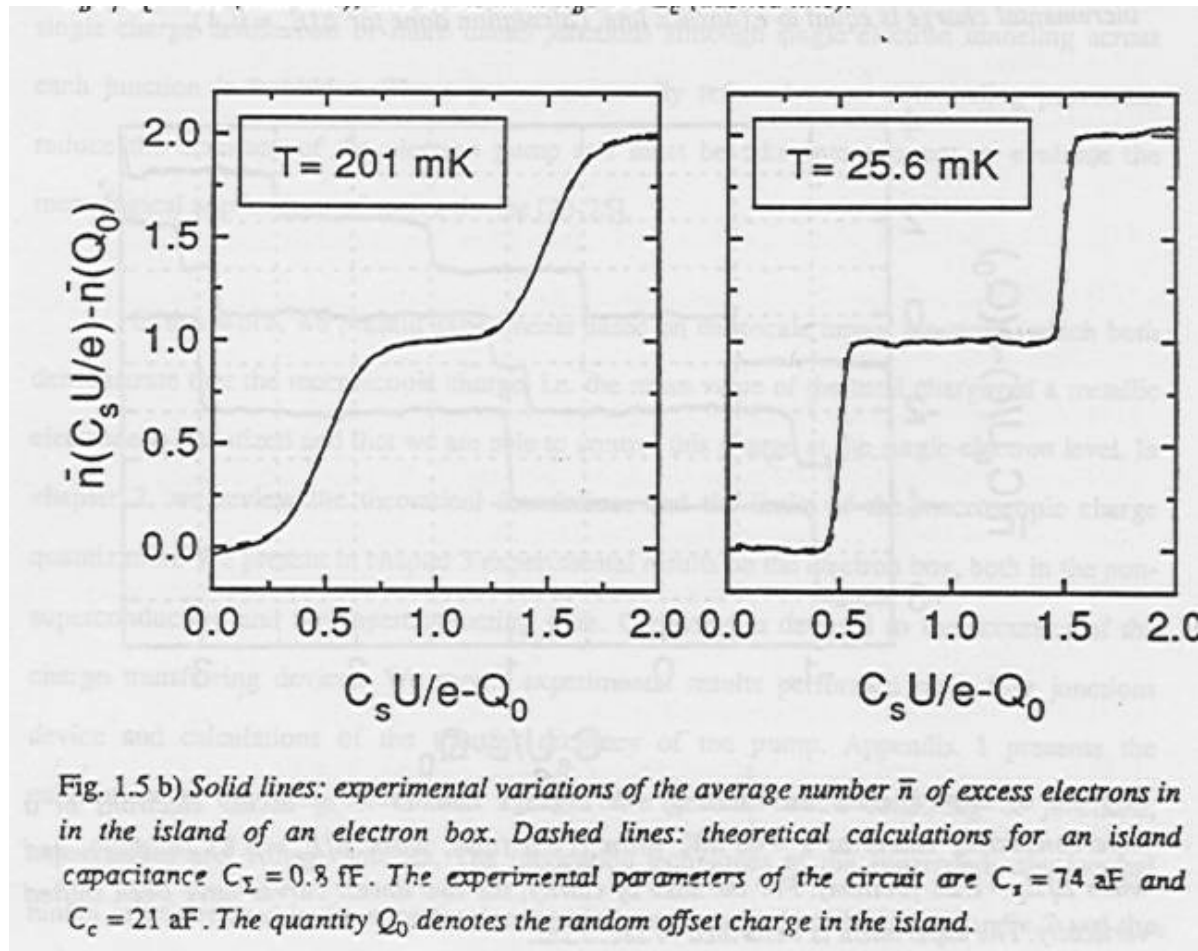
$$G = \frac{1}{2} \frac{(C_G V - ne)^2}{C + C_G} + \textit{const}$$

Charge of island



Finite temperatures

Need
 $kT \ll e^2/(C+C_G)$

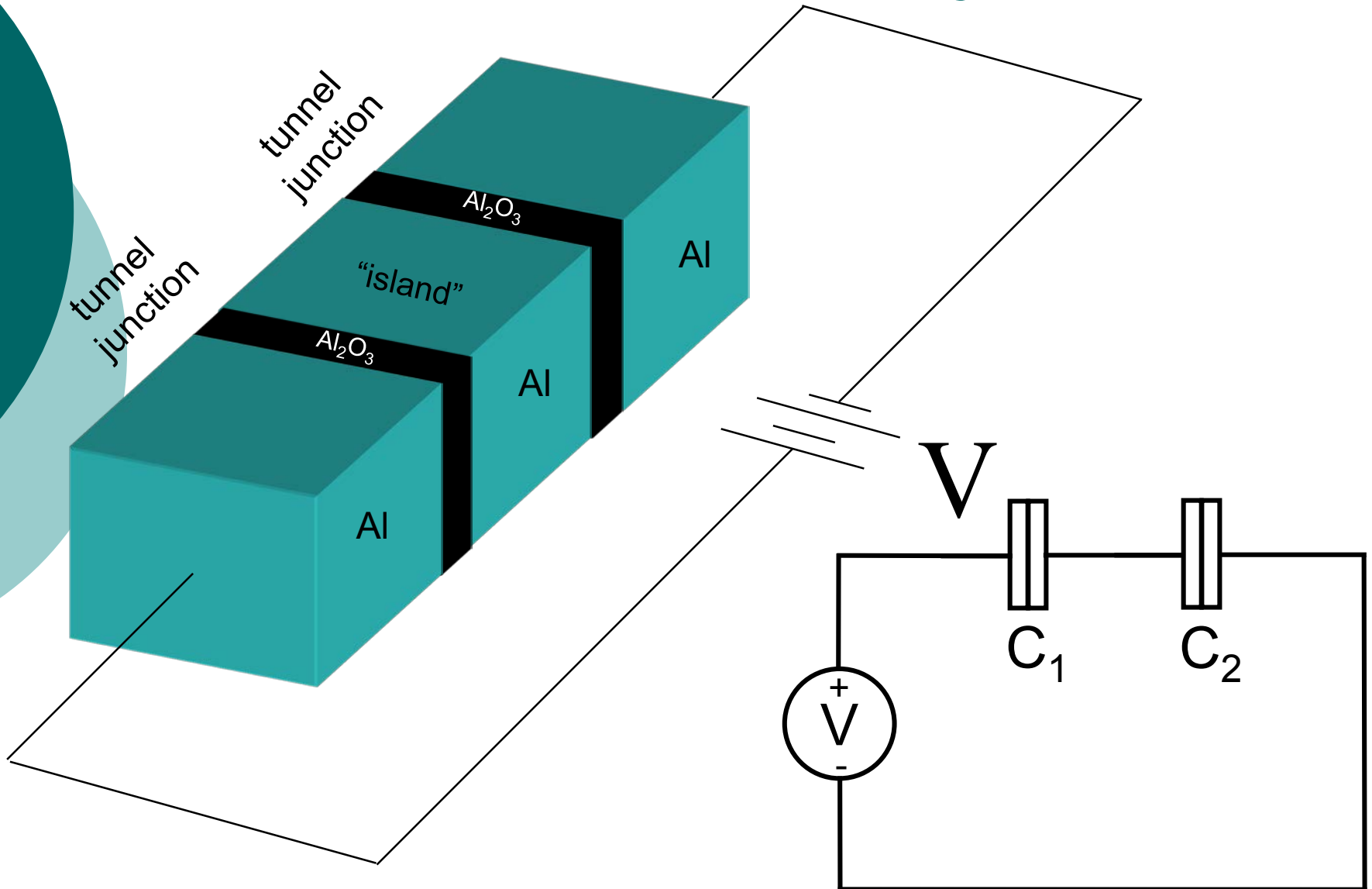


From Lafarge, PhD thesis, Universite Paris 6 (1993)

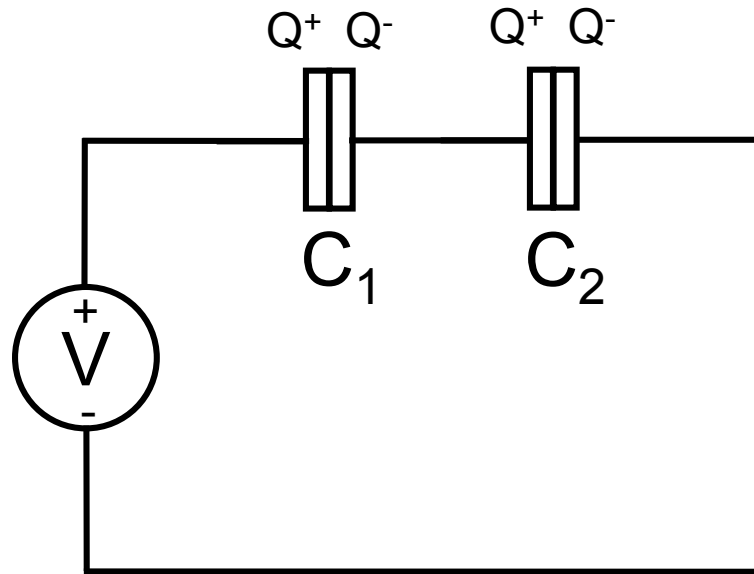
Quantum computing

- A single electron box has been proposed as a qu-bit
- $|0\rangle$ or $|1\rangle$ correspond to n or $n+1$ electrons
- Difficulty is fast (GHz) readout before decoherence sets in
- A superconducting box (for Cooper pairs) could have longer decoherence

Lecture 7: Double tunnel junction



Electrostatic energy (*no tunneling*)

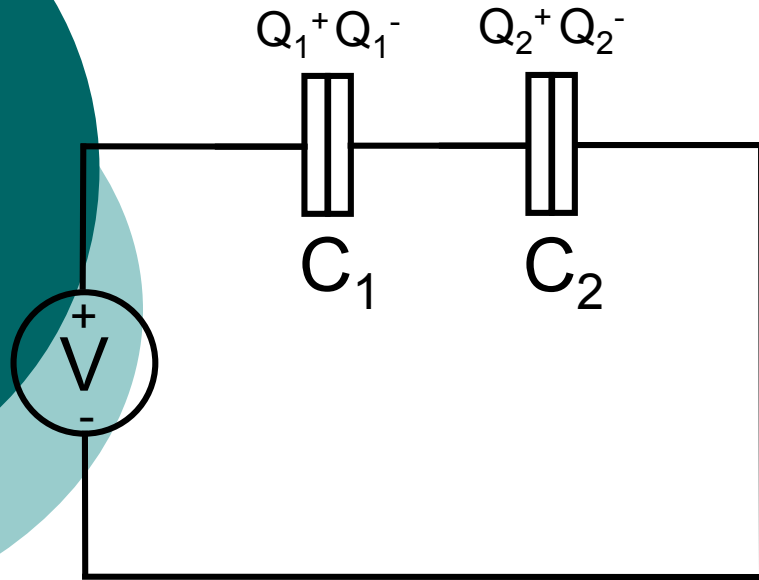


$$C_{series}^{-1} \equiv C^{-1} + C_G^{-1}$$

$$V = \frac{Q}{C_1} + \frac{Q}{C_2} = Q \left(\frac{1}{C_1} + \frac{1}{C_2} \right) = \frac{Q}{C_{series}}$$

$$E = \frac{Q^2}{2C_1} + \frac{Q^2}{2C_2} = \frac{Q^2}{2C_{series}} = \frac{1}{2} C_{series} V^2$$

Island charge



“Island charge”:

$$Q_i = Q_2 - Q_1$$

Kirchoff:

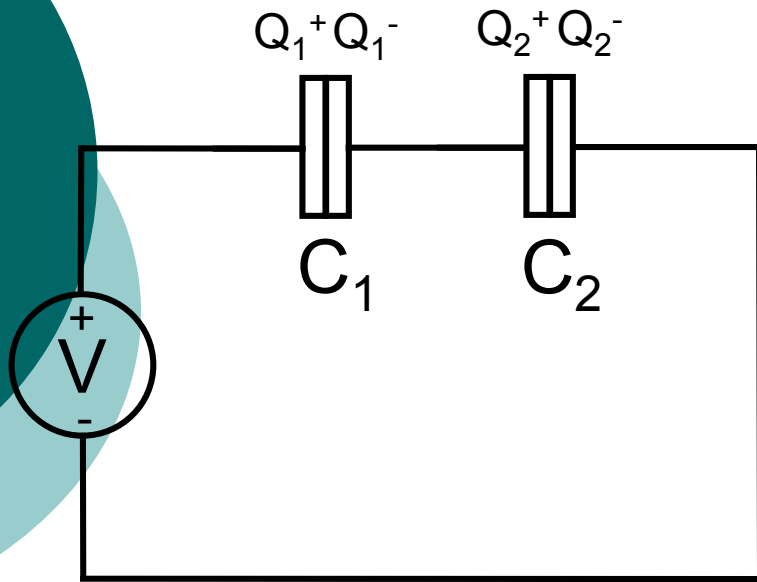
$$V = \frac{Q_1}{C_1} + \frac{Q_2}{C_2}$$

Solve for Q , Q_G :

$$Q_1 = \frac{C_1(C_2V - Q_i)}{C_1 + C_2}$$

$$Q_2 = \frac{C_2(C_1V + Q_i)}{C_1 + C_2}$$

Electrostatic energy (*with tunneling*)



$$Q_1 = \frac{C_1(C_2V - Q_i)}{C_1 + C_2}$$

$$Q_2 = \frac{C_2(C_1V + Q_i)}{C_1 + C_2}$$

$$E = \frac{Q_1^2}{2C_1} + \frac{Q_2^2}{2C_2} = \frac{C_1C_2V^2 + Q_i^2}{2(C_1 + C_2)}$$

Free energy :

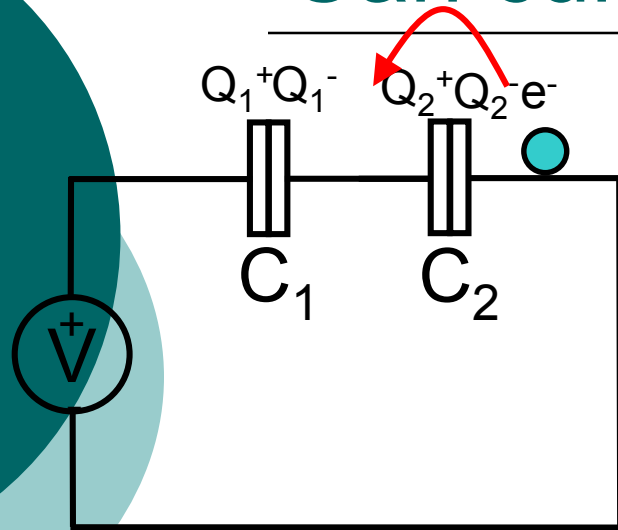
$$G = E - Q_1 V$$

From before:

$$E = \frac{C_1 C_2 V^2 + Q_i^2}{2(C_1 + C_2)} \quad Q_1 = \frac{C_1(C_2 V - Q_i)}{C_1 + C_2}$$

$$\begin{aligned} G &= \frac{C_1 C_2 V^2 + Q_i^2}{2(C_1 + C_2)} - \frac{C_1(C_2 V - Q_i)}{C_1 + C_2} V \\ &= \frac{1}{2} \frac{(C_1 V + Q_i)^2}{C_1 + C_2} - \frac{1}{2} C_1 V^2 \end{aligned}$$

Can current flow?



$$\Delta G = \Delta E - V \Delta Q_1$$

Before:

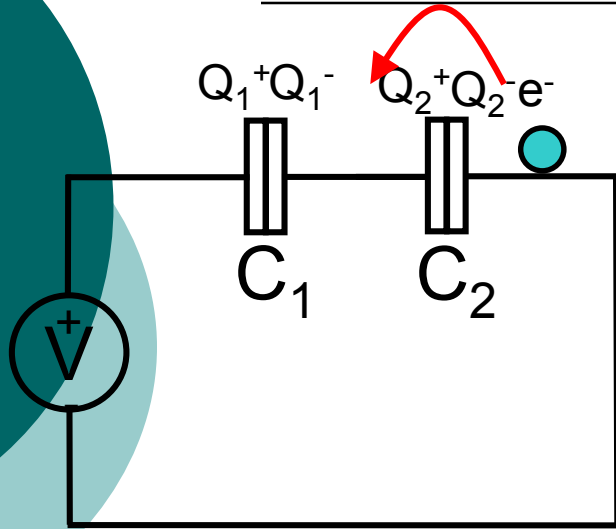
$$Q_i = -n_0 e$$

After:

$$Q_i = -n_0 e - e$$

$$\begin{aligned} \Delta E &= \frac{C_1 C_2 V^2 + (-n_0 e)^2}{2(C_1 + C_2)} - \frac{C_1 C_2 V^2 + (-n_0 e - e)^2}{2(C_1 + C_2)} = \\ &= \frac{(-n_0 e)^2}{2(C_1 + C_2)} - \frac{(-n_0 e - e)^2}{2(C_1 + C_2)} = \frac{-2n_0 e^2 - e^2}{2(C_1 + C_2)} \end{aligned}$$

Can current flow?



$$\Delta G = \Delta E - V \Delta Q_1$$

Before:

$$Q_i = -n_0 e$$

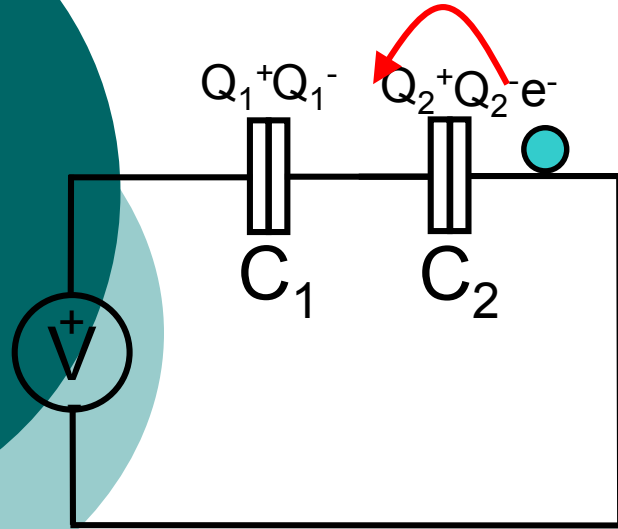
$$Q_1 = \frac{C_1(C_2 V - (-n_0 e))}{C_1 + C_2}$$

After:

$$Q_i = -n_0 e - e \quad Q_1 = \frac{C_1(C_2 V - (-n_0 e - e))}{C_1 + C_2}$$

$$\Delta Q_1 = -\frac{C_1 e}{C_1 + C_2}$$

Can current flow?



$$\Delta G = \Delta E - V \Delta Q_1$$

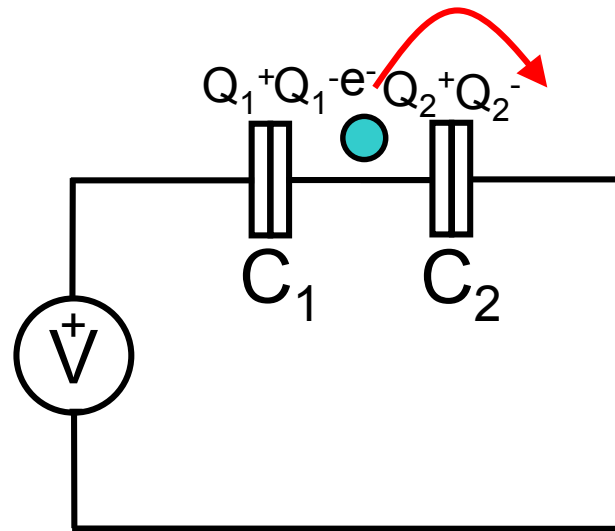
$$\Delta E = \frac{-2n_0e^2 - e^2}{2(C_1 + C_2)}$$

$$\Delta Q_1 = -\frac{C_1e}{C_1 + C_2}$$

$$\Delta G = \frac{-2n_0e^2 - e^2}{2(C_1 + C_2)} + V \frac{C_1e}{C_1 + C_2} = \frac{e}{C_1 + C_2} \left[-n_0e - \frac{e}{2} + C_1V \right] > 0$$

$$V > \frac{e}{C_1} \left(n_0 + \frac{1}{2} \right)$$

Similarly:

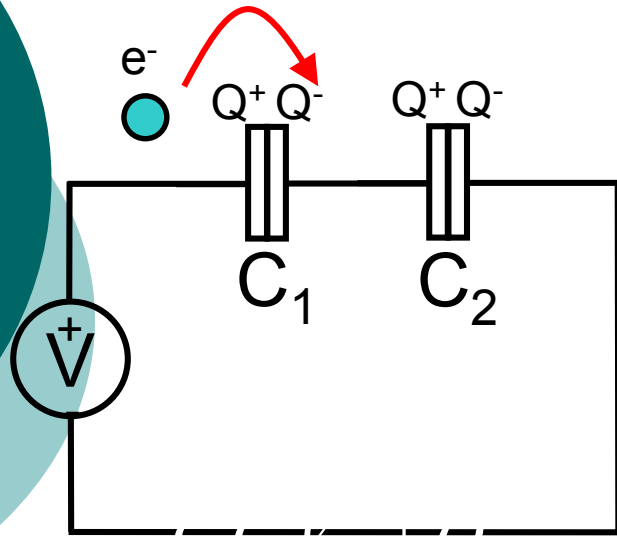


Allowed only if:

$$V < \frac{e}{C_1} \left(n_0 - \frac{1}{2} \right)$$

n_0 is the number of electrons on the island *before* the tunnel event.

Can current flow?



$$\Delta G = \Delta E - V \Delta Q_1$$

Before:

$$Q_i = -n_0 e$$

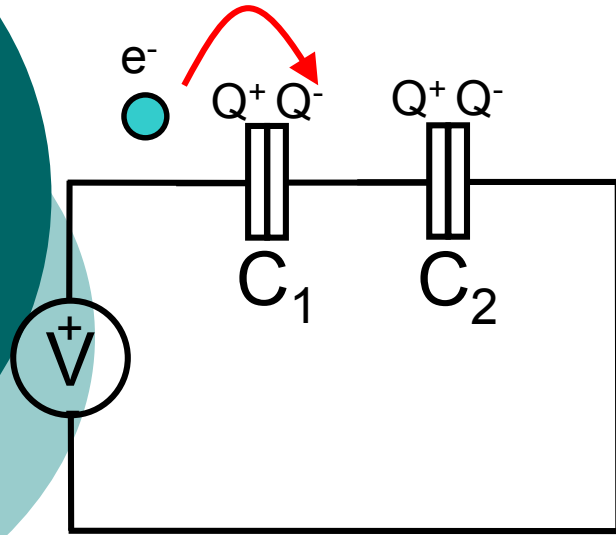
After:

$$Q_i = -n_0 e - e$$

$$\Delta E = \frac{C_1 C_2 V^2 + (-n_0 e)^2}{2(C_1 + C_2)} - \frac{C_1 C_2 V^2 + (-n_0 e - e)^2}{2(C_1 + C_2)} =$$

$$= \frac{(-n_0 e)^2}{2(C_1 + C_2)} - \frac{(-n_0 e - e)^2}{2(C_1 + C_2)} = \frac{-2n_0 e^2 - e^2}{2(C_1 + C_2)}$$

Can current flow?



$$\Delta G = \Delta E - V \Delta Q_1$$

Before:

$$Q_i = -n_0 e \quad Q_1 = \frac{C_1(C_2 V - (-n_0 e))}{C_1 + C_2}$$

After:

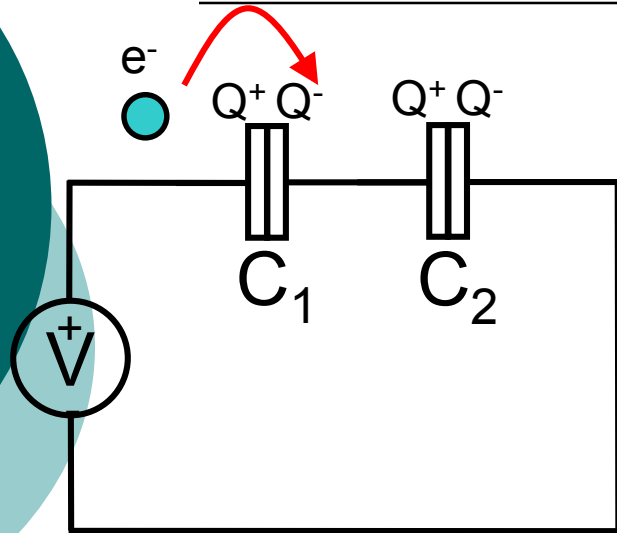
$$Q_i = -n_0 e - e \quad Q_1 = \frac{C_1(C_2 V - (-n_0 e - e))}{C_1 + C_2}$$

$$\Delta Q_{1,polarization} = -\frac{C_1 e}{C_1 + C_2}$$

“But...” $\Delta Q_{1,tunnel} = e$

$$\Delta Q_{1,total} = e - \frac{C_1 e}{C_1 + C_2} = \frac{C_1 + C_2}{C_1 + C_2} e - \frac{C_1 e}{C_1 + C_2} = \frac{C_2 e}{C_1 + C_2}$$

Can current flow?



$$\Delta G = \Delta E - V \Delta Q_1$$

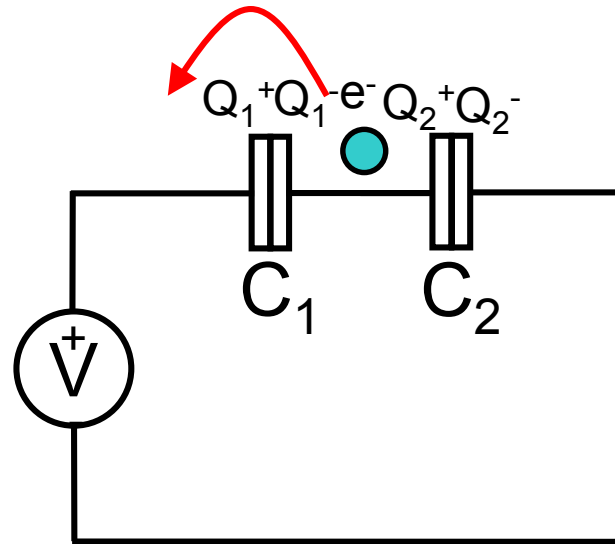
$$\Delta Q_{1,total} = \frac{C_2 e}{C_1 + C_2}$$

$$\Delta E = \frac{-2n_0 e^2 - e^2}{2(C_1 + C_2)}$$

$$\Delta G = \frac{-2n_0 e^2 - e^2}{2(C_1 + C_2)} + V \frac{C_2 e}{C_1 + C_2} = \frac{e}{C_1 + C_2} \left[-n_0 e - \frac{e}{2} - C_2 V \right] > 0$$

$$V < -\frac{e}{C_2} \left(n_0 + \frac{1}{2} \right)$$

Similarly:

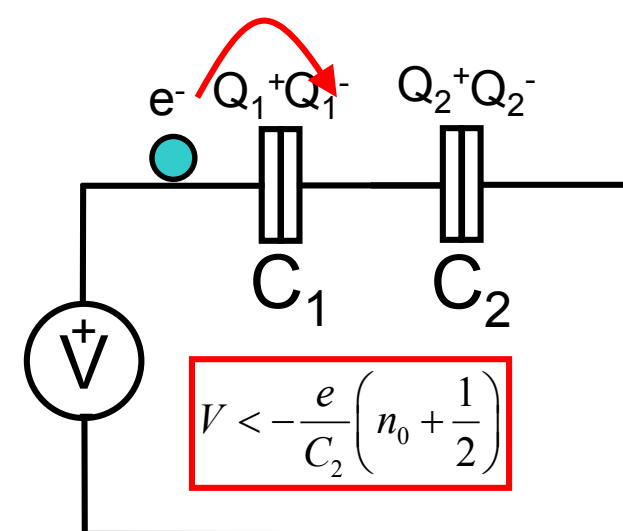
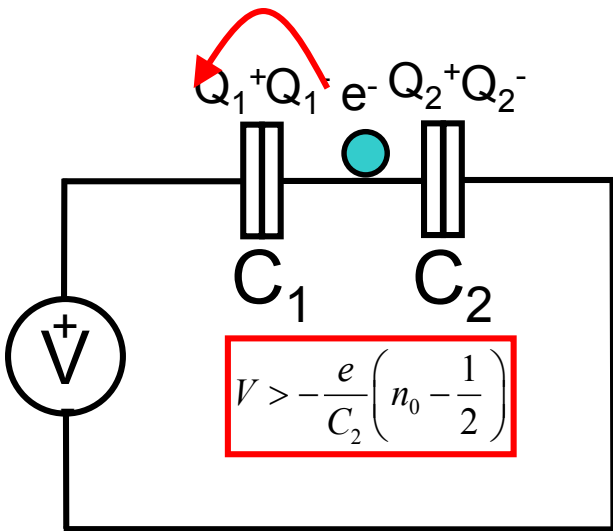
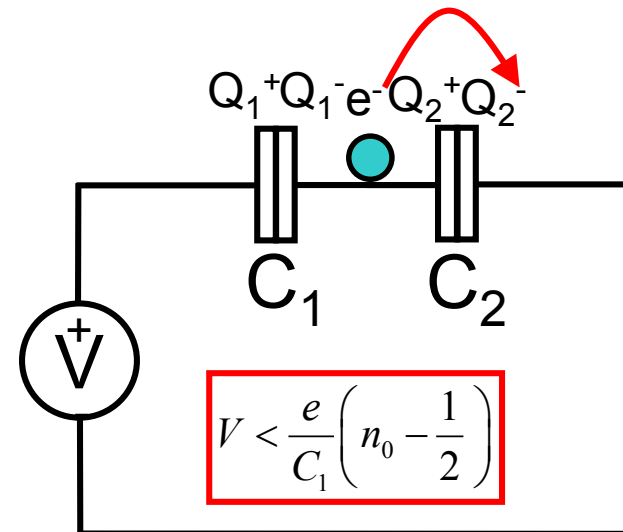
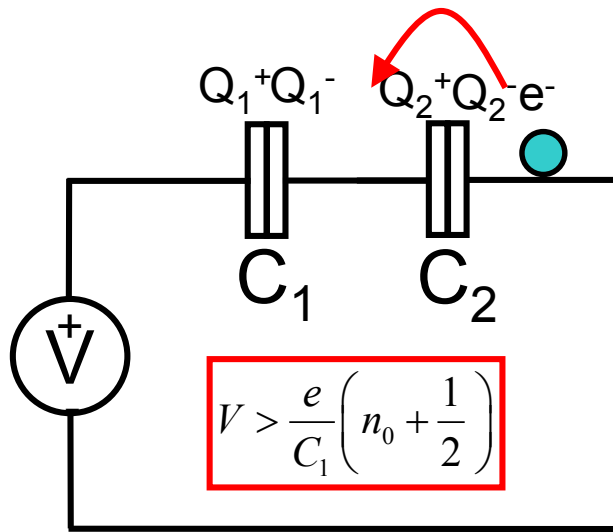


Allowed only if:

$$V > -\frac{e}{C_2} \left(n_0 - \frac{1}{2} \right)$$

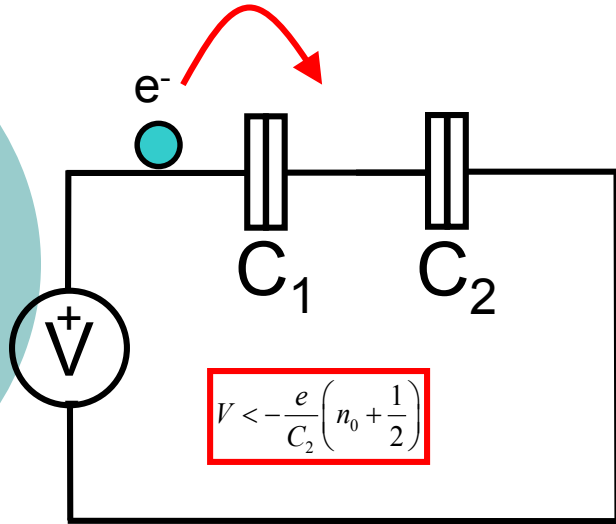
n_0 is the number of electrons on the island *before* the tunnel event.

Summary



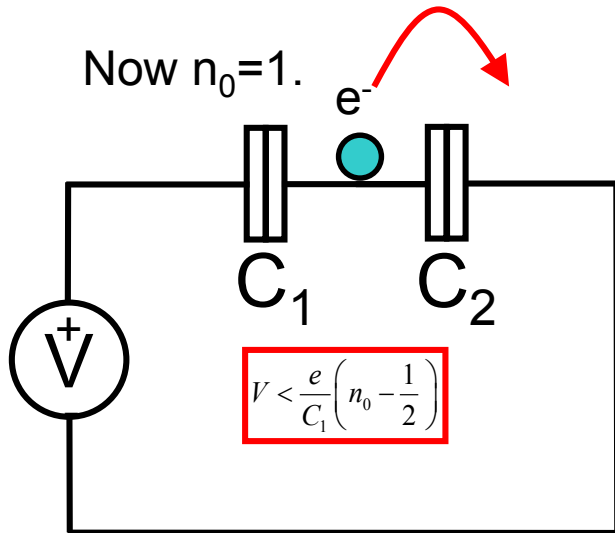
Current

Let $n_0=0$. Let $C_1 = C_2$



$$V < -\frac{e}{2C_2}$$

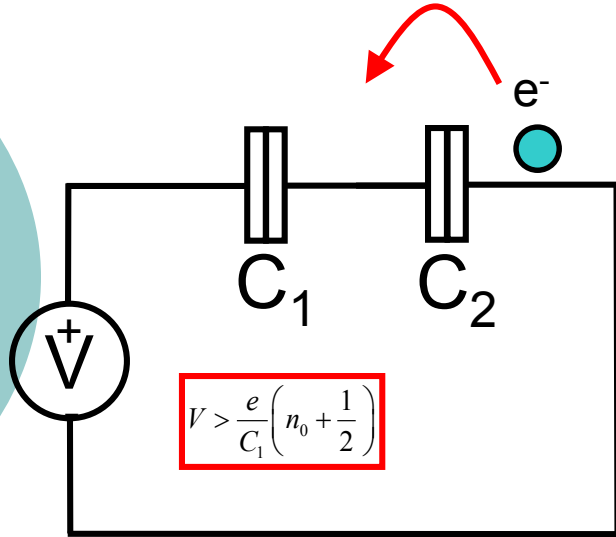
Now $n_0=1$.



$$V < \frac{e}{2C_2}$$

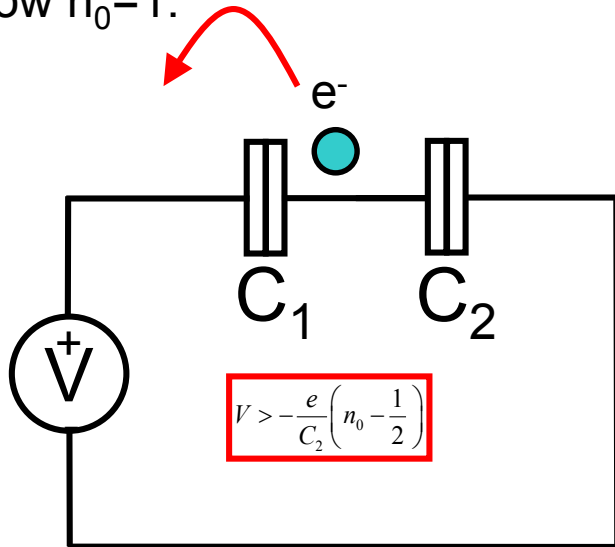
Current

Let $n_0=0$. Let $C_1 = C_2$



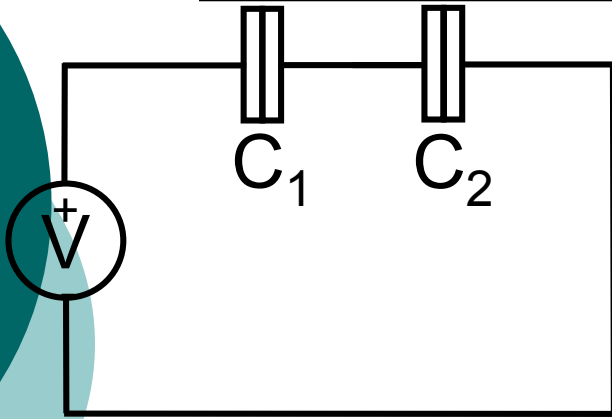
$$V > \frac{e}{2C_2}$$

Now $n_0=1$.



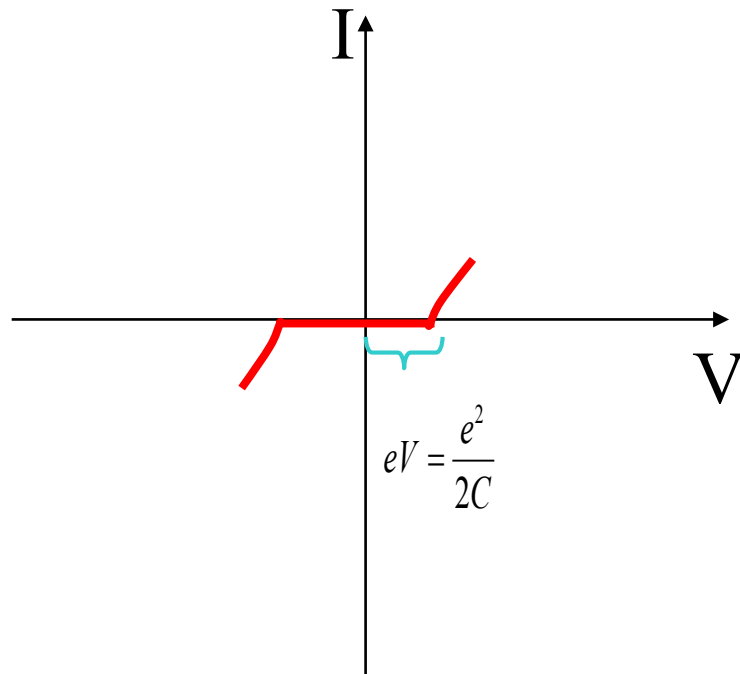
$$V > -\frac{e}{2C_2}$$

Coulomb blockade



Let $C_1 = C_2$
No current:

$$-\frac{e}{2C_2} < V < \frac{e}{2C_2}$$

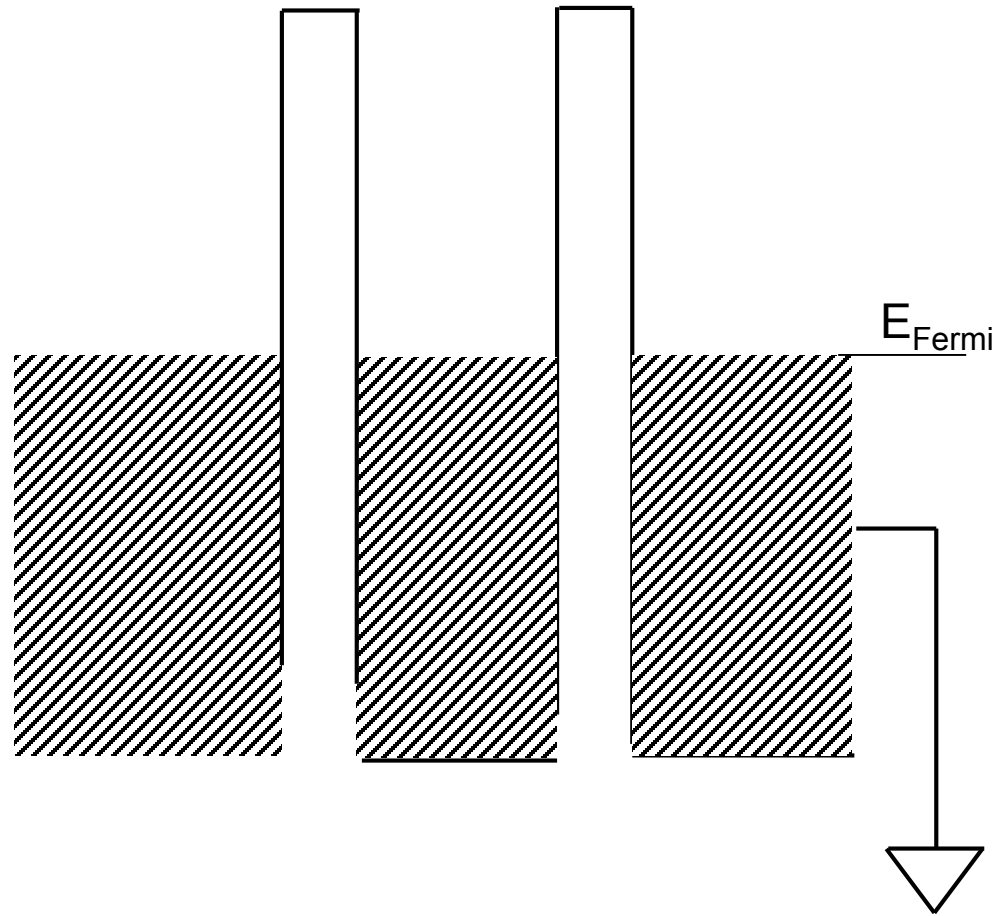


From quantum circuit theory,
works even when voltage biased.

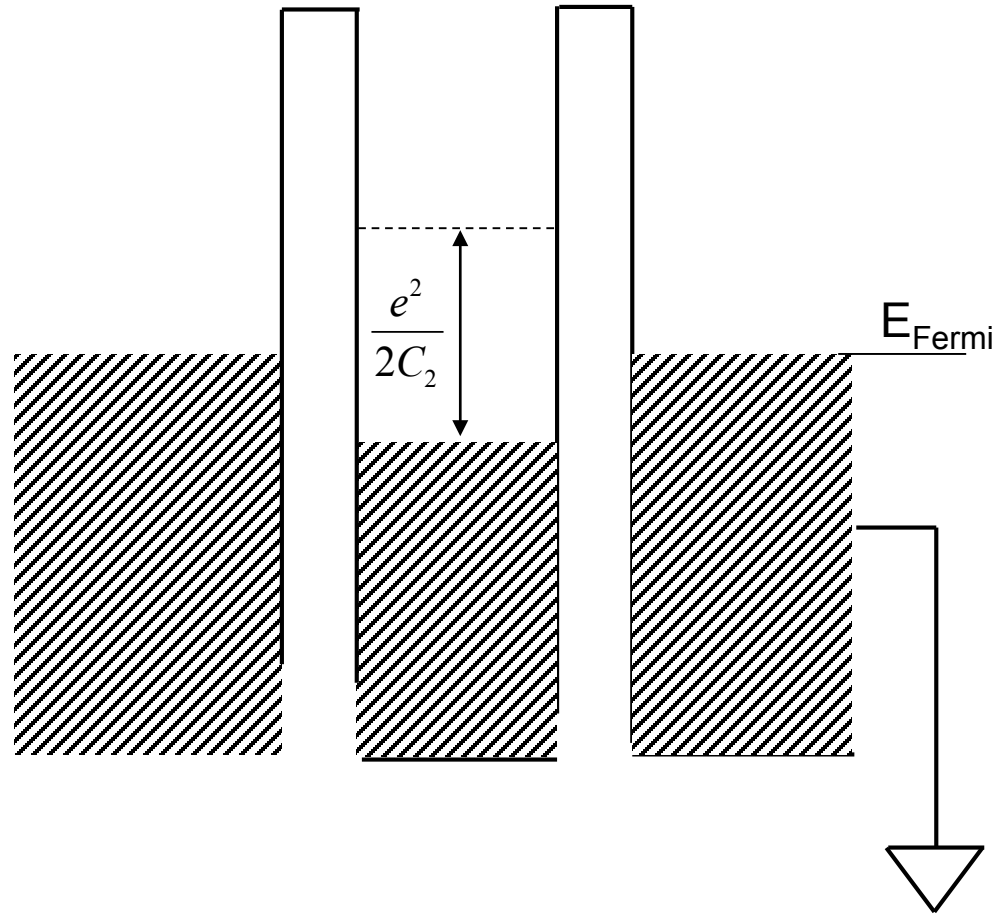
In single junction, Coulomb
blockade *hard* to observe.

In double junction, Coulomb
blockade *easy* to observe.

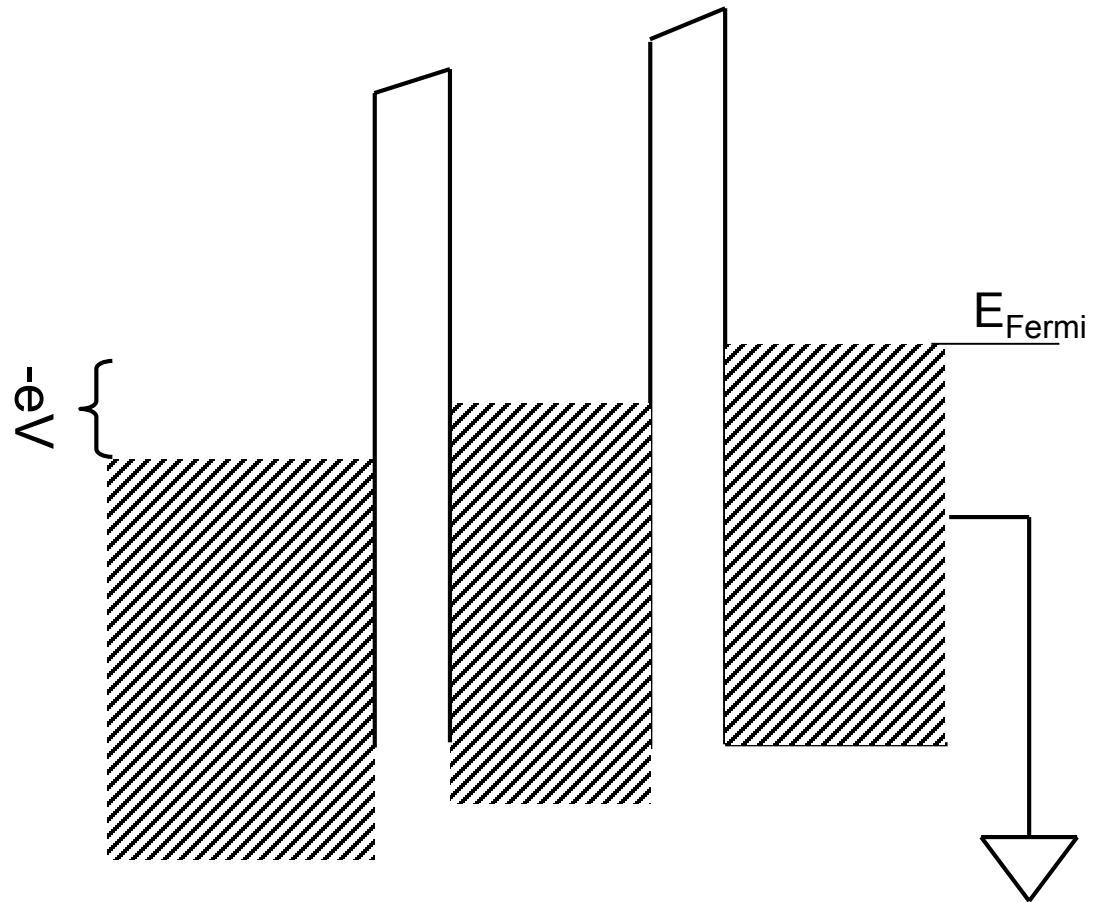
Band diagram



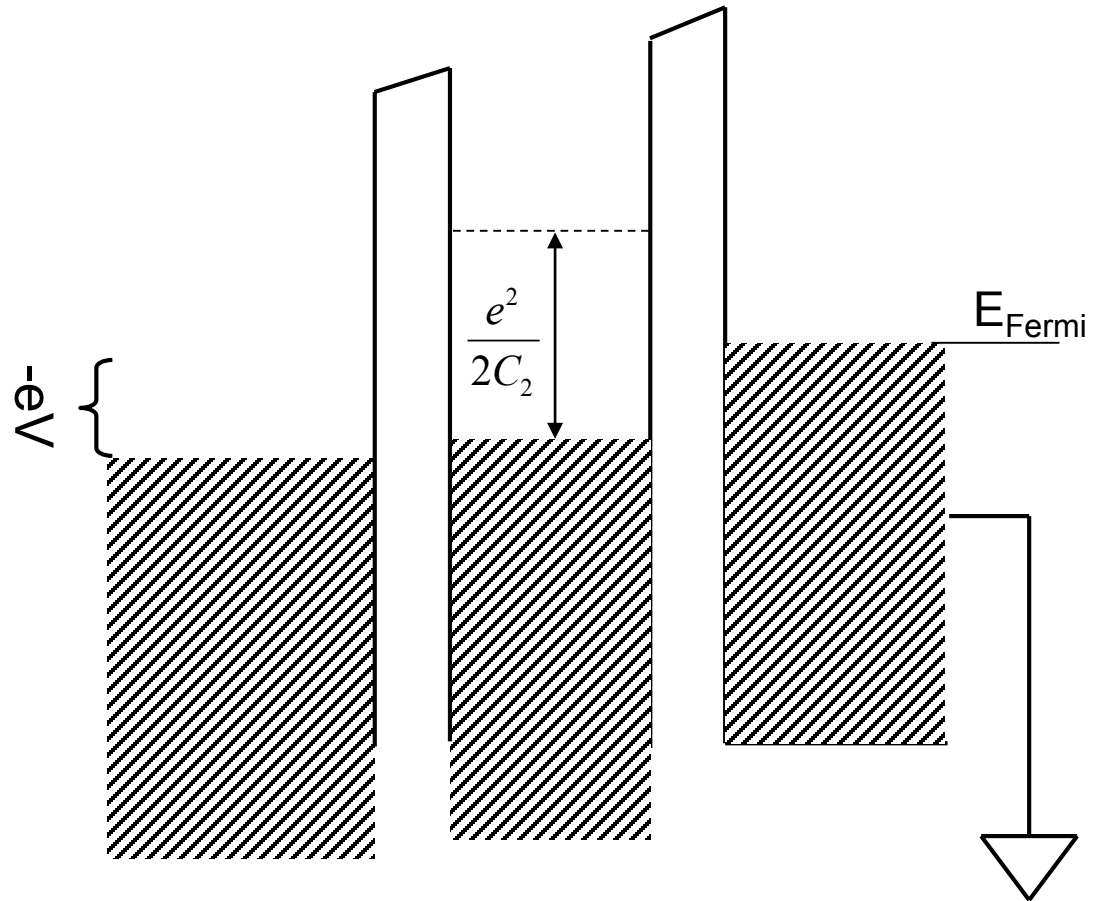
Band diagram with Coulomb "gap"



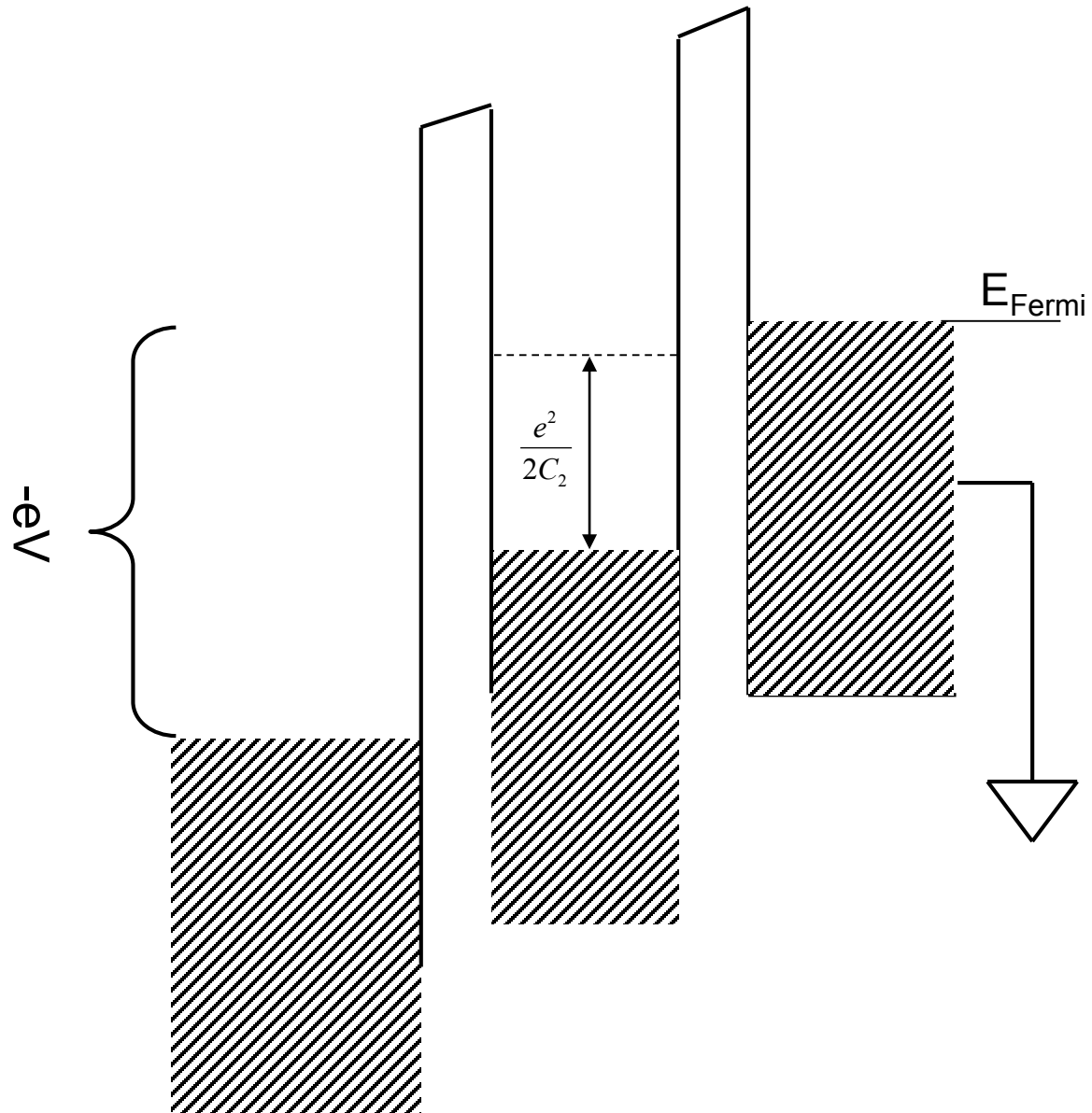
Band diagram under bias



Band diagram with Coulomb "gap"

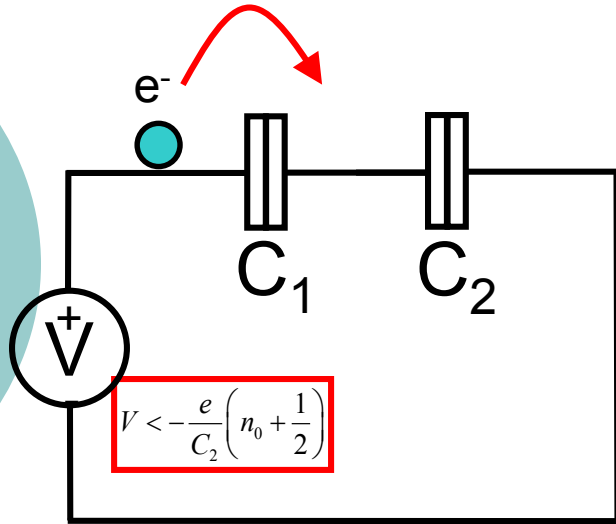


Band diagram with Coulomb "gap"



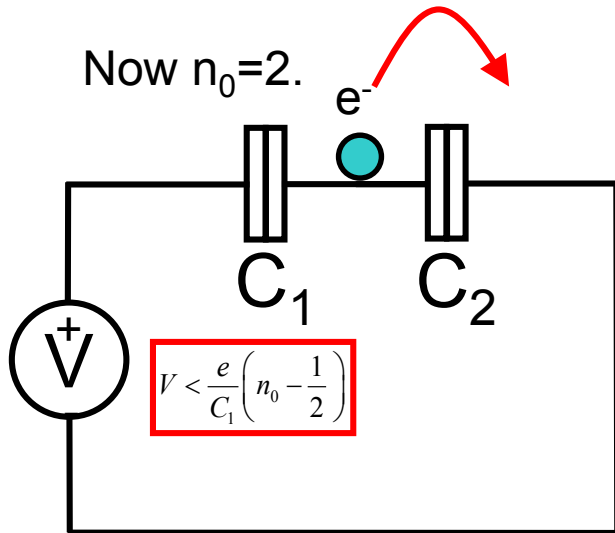
Higher voltages

Let $n_0=1$. Let $C_1 = C_2$



$$V < -\frac{3e}{2C_2}$$

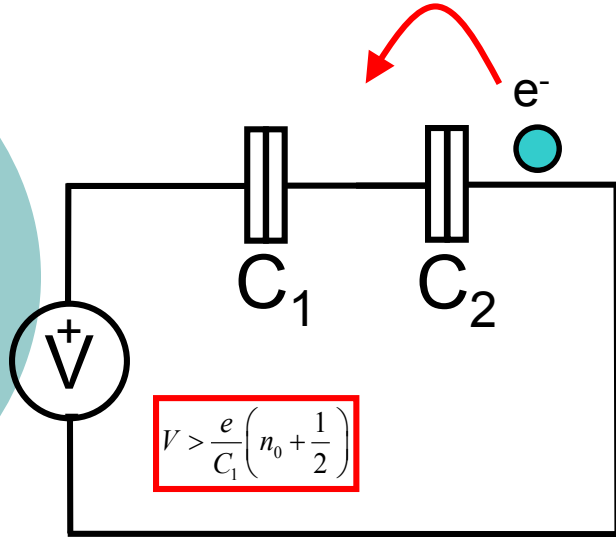
Now $n_0=2$.



$$V < -\frac{3e}{2C_2}$$

Higher voltages

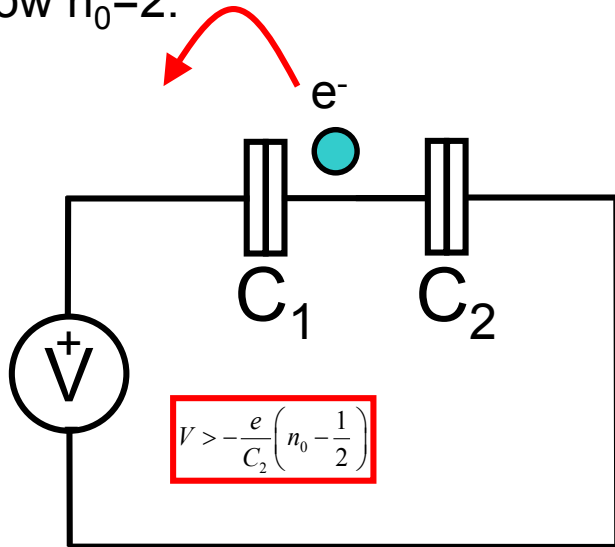
Let $n_0=1$. Let $C_1 = C_2$



$$V > \frac{e}{C_1} \left(n_0 + \frac{1}{2} \right)$$

$$V > \frac{3e}{2C_2}$$

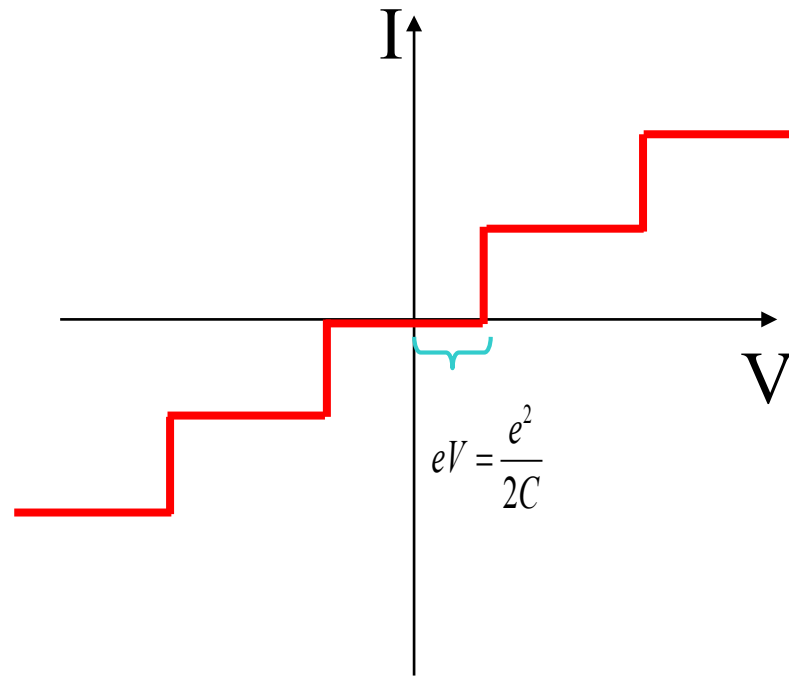
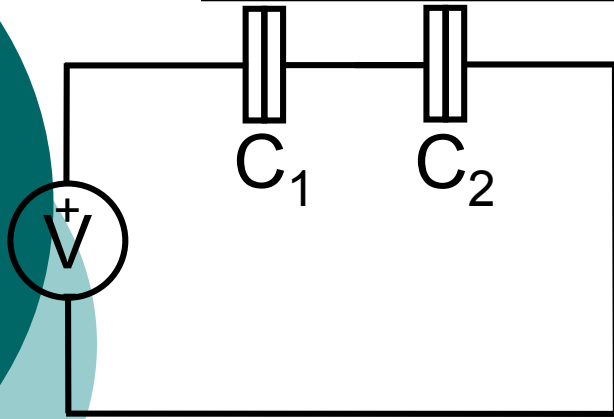
Now $n_0=2$.



$$V > -\frac{e}{C_2} \left(n_0 - \frac{1}{2} \right)$$

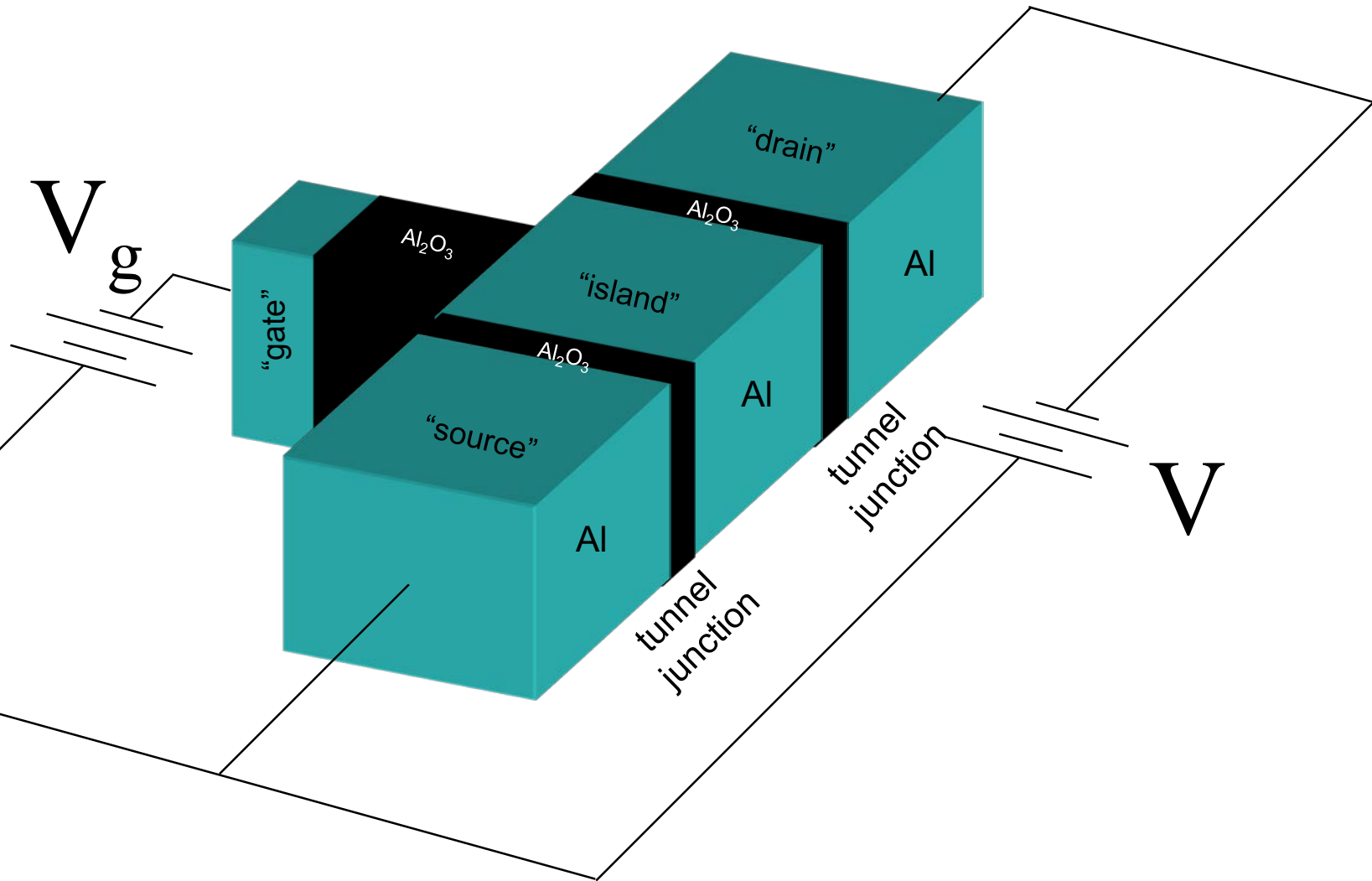
$$V > \frac{3e}{2C_2}$$

Coulomb staircase

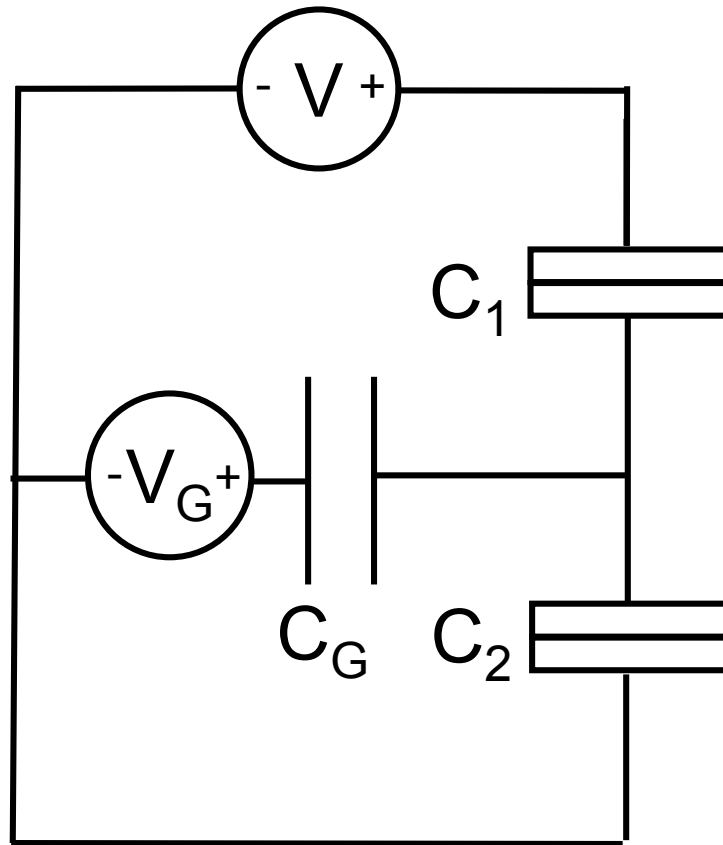


Overall slope is R_{tunnel} , which is *large*.

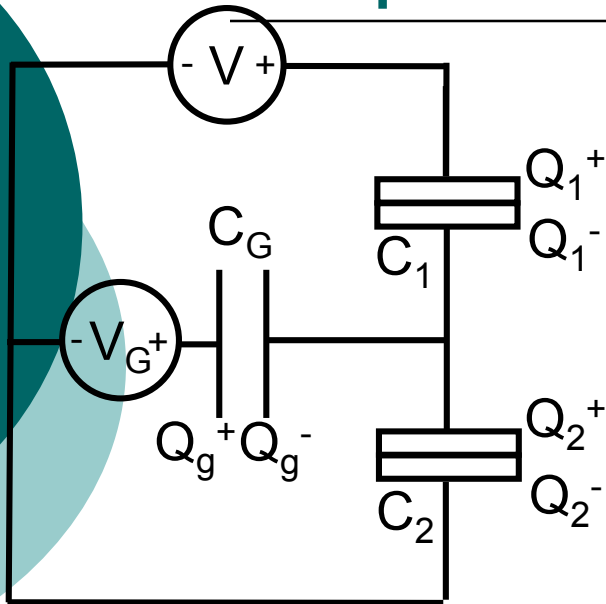
Lecture 8: Single electron transistor



Single electron transistor circuit



Capacitor charges



Kirchoff:
$$V = \frac{Q_1}{C_1} + \frac{Q_2}{C_2}$$

$$V_g = \frac{Q_g}{C_g} + \frac{Q_2}{C_2}$$

Island charge:
$$Q_i = Q_2 - Q_1 - Q_g$$

3 equations, 3 unknowns, solve:

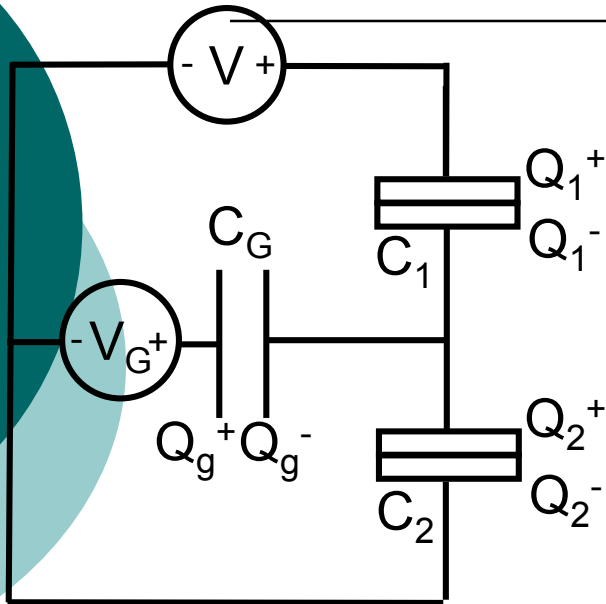
$$Q_1 = \frac{C_1 V (C_2 + C_g) - C_1 C_g (Q_i + V_g)}{C_\Sigma}$$

$$C_\Sigma \equiv C_1 + C_2 + C_g$$

$$Q_2 = \frac{C_2 Q_i + C_1 C_2 V + C_g C_2 V_g}{C_\Sigma}$$

$$Q_2 = \frac{-C_g Q_i - C_1 C_g V + C_g V_g (C_1 + C_2)}{C_\Sigma}$$

Electrostatic energy



$$E = \frac{Q_1^2}{2C_1} + \frac{Q_2^2}{2C_2} + \frac{Q_G^2}{2C_G}$$

$$Q_1 = \frac{C_1 V (C_2 + C_g) - C_1 C_g V_g - C_1 Q_i}{C_\Sigma}$$

$$Q_2 = \frac{C_2 Q_i + C_1 C_2 V + C_g C_2 V_g}{C_\Sigma}$$

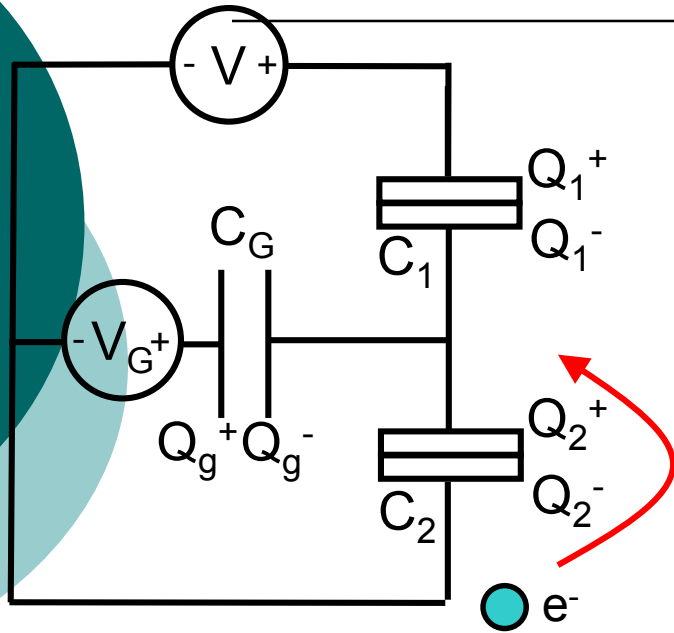
$$Q_G = \frac{-C_g Q_i - C_1 C_g V + C_g V_g (C_1 + C_2)}{C_\Sigma}$$

$$E = \frac{1}{2C_\Sigma} \left[C_G C_1 + (V - V_G)^2 + C_1 C_2 V^2 + C_G C_2 V_G^2 + Q_i^2 \right]$$

Free energy :

$$G = E - Q_1 V - Q_G V_G$$

Can current flow?



$$\Delta G = \Delta E - V \Delta Q_1 - V_G \Delta Q_G$$

Before:

$$Q_i = -n_0 e$$

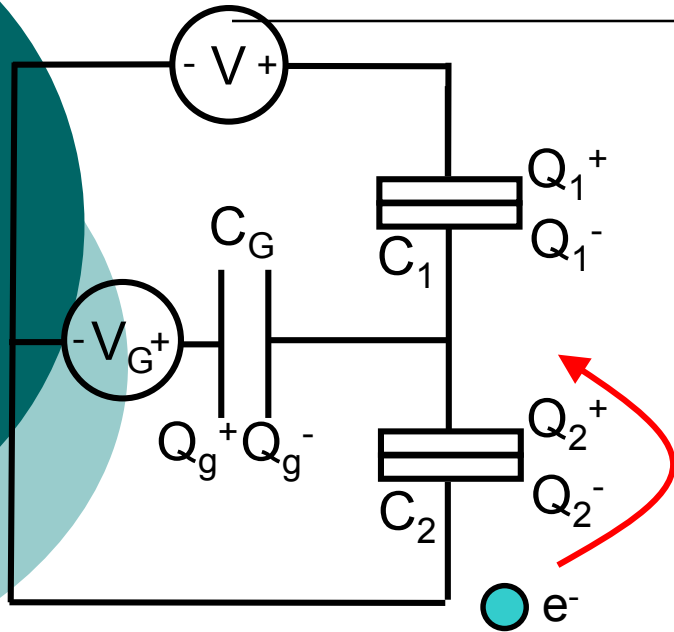
After:

$$Q_i = -n_0 e - e$$

$$E = \frac{1}{2C_\Sigma} \left[C_G C_1 + (V - V_G)^2 + C_1 C_2 V^2 + C_G C_2 V_G^2 + Q_i^2 \right]$$

$$\Delta E = \frac{-2n_0 e^2 - e^2}{2C_\Sigma}$$

Can current flow?



$$\Delta G = \Delta E - V \Delta Q_1 - V_G \Delta Q_G$$

Before: $Q_i = -n_0 e$

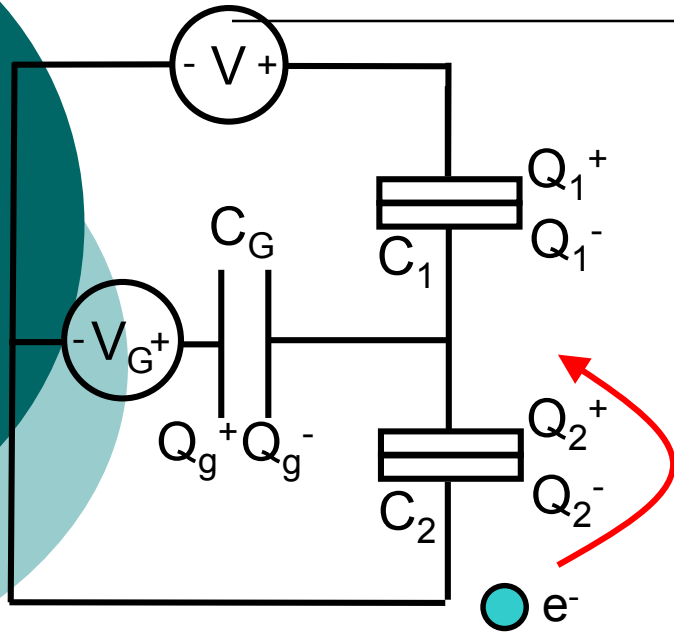
After: $Q_i = -n_0 e - e$

$$Q_1 = \frac{C_1 V (C_2 + C_g) - C_1 C_G V_G - C_1 Q_i}{C_\Sigma}$$

$$\Delta Q_1 = \Delta \frac{C_1 V (C_2 + C_g) - C_1 C_G V_G - C_1 Q_i}{C_\Sigma} = \frac{-C_1 (-n_0 e)}{C_\Sigma} - \frac{-C_1 (-n_0 e - e)}{C_\Sigma}$$

$$\Delta Q_1 = \frac{-e C_1}{C_\Sigma}$$

Can current flow?



$$\Delta G = \Delta E - V \Delta Q_1 - V_G \Delta Q_G$$

Before: $Q_i = -n_0 e$

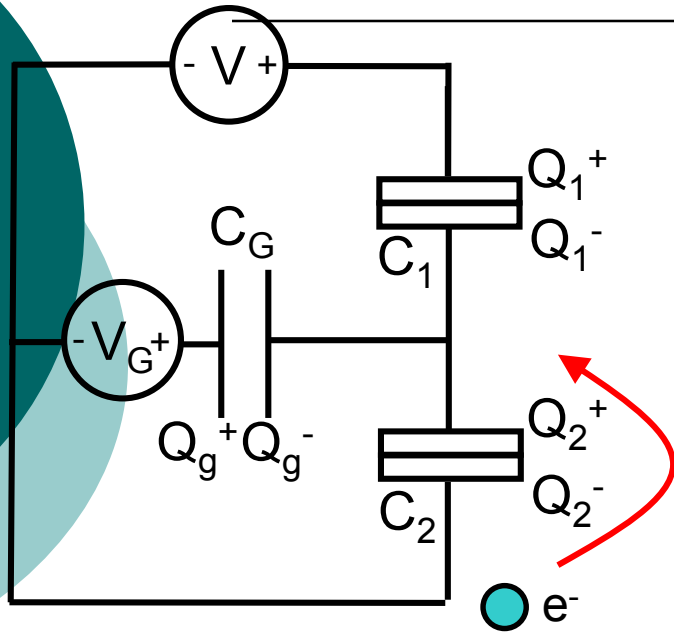
After: $Q_i = -n_0 e - e$

$$Q_G = \frac{-C_g Q_i - C_1 C_g V + C_g V_g (C_1 + C_2)}{C_\Sigma}$$

$$\Delta Q_G = \Delta \frac{-C_g Q_i - C_1 C_g V + C_g V_g (C_1 + C_2)}{C_\Sigma} = \frac{-C_g (-n_0 e)}{C_\Sigma} - \frac{-C_g (-n_0 e - e)}{C_\Sigma}$$

$$\Delta Q_G = \frac{-e C_g}{C_\Sigma}$$

Can current flow?



$$\Delta G = \Delta E - V \Delta Q_1 - V_G \Delta Q_G$$

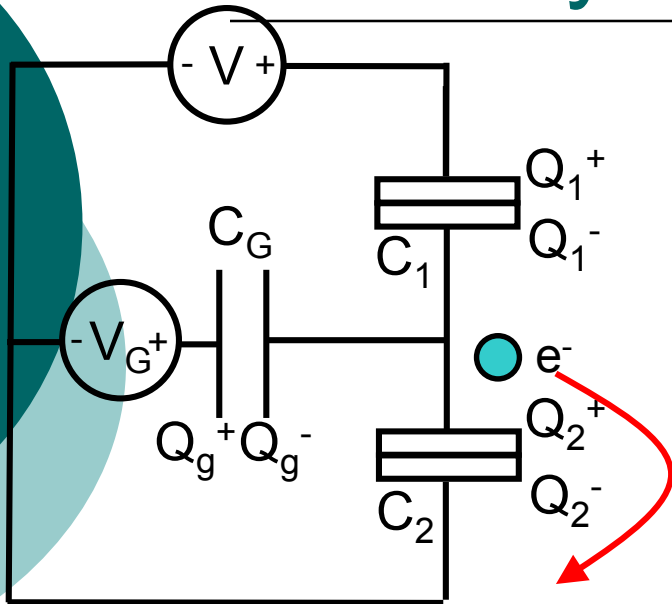
$$\Delta E = \frac{-2n_0 e^2 - e^2}{2C_\Sigma}$$

$$\Delta Q_1 = \frac{-eC_1}{C_\Sigma} \quad \Delta Q_G = \frac{-eC_g}{C_\Sigma}$$

$$\Delta G = \frac{-2n_0 e^2 - e^2}{2C_\Sigma} + V \frac{eC_1 C_g}{C_\Sigma} + V_G \frac{eC_g}{C_\Sigma}$$

$$\Delta G = \frac{e}{C_\Sigma} \left[-n_0 e - \frac{e}{2} + C_1 V + C_g V_G \right] > 0$$

Similarly

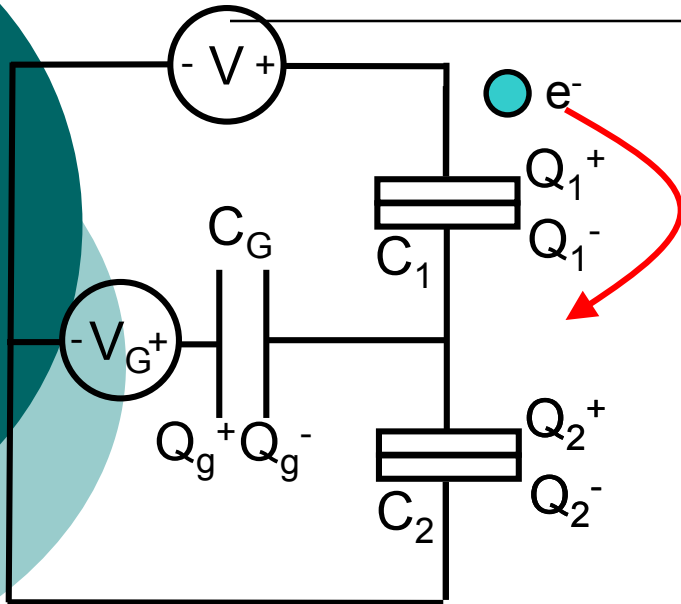


Allowed only if:

$$\Delta G = \frac{e}{C_\Sigma} \left[+n_0 e - \frac{e}{2} - C_1 V - C_g V_G \right] > 0$$

n_0 is the number of electrons on the island *before* the tunnel event.

Can current flow?



$$\Delta G = \Delta E - V \Delta Q_1 - V_G \Delta Q_G$$

Before:

$$Q_i = -n_0 e$$

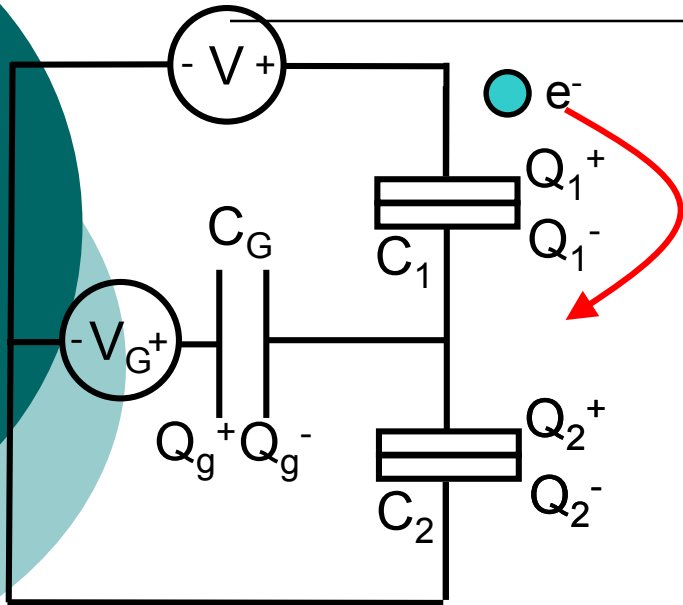
After:

$$Q_i = -n_0 e + e$$

$$E = \frac{1}{2C_\Sigma} \left[C_G C_1 + (V - V_G)^2 + C_1 C_2 V^2 + C_G C_2 V_G^2 + Q_i^2 \right]$$

$$\Delta E = \frac{-2n_0 e^2 - e^2}{2C_\Sigma}$$

Can current flow?



$$\Delta G = \Delta E - V \Delta Q_1 - V_G \Delta Q_G$$

Before:

$$Q_i = -n_0 e$$

After:

$$Q_i = -n_0 e + e$$

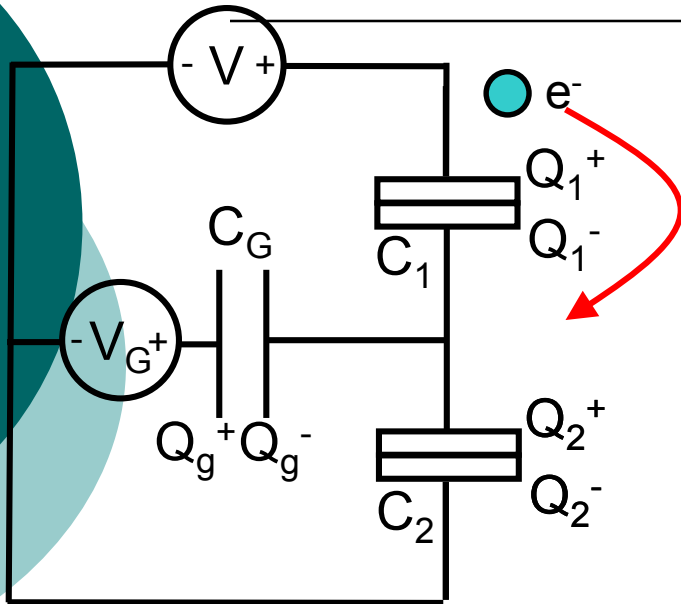
$$Q_1 = \frac{C_1 V (C_2 + C_g) - C_1 C_G V_G - C_1 Q_i}{C_\Sigma}$$

$$\Delta Q_1 = \Delta \frac{C_1 V (C_2 + C_g) - C_1 C_G V_G - C_1 Q_i}{C_\Sigma} = \frac{-C_1 (-n_0 e)}{C_\Sigma} - \frac{-C_1 (-n_0 e - e)}{C_\Sigma}$$

$$\Delta Q_{1,polarization} = \frac{-e C_1}{C_\Sigma} \quad \Delta Q_{1,tunnel} = e$$

$$\Delta Q_{1,total} = \Delta Q_{1,polarization} + \Delta Q_{1,tunnel} = \frac{-e C_1}{C_\Sigma} + e = \frac{-e C_1}{C_1 + C_2 + C_G} + \frac{e C_1 + e C_2 + e C_G}{C_1 + C_2 + C_G} = e \frac{C_2 + C_G}{C_\Sigma}$$

Can current flow?



$$\Delta G = \Delta E - V \Delta Q_1 - V_G \Delta Q_G$$

Before:

$$Q_i = -n_0 e$$

After:

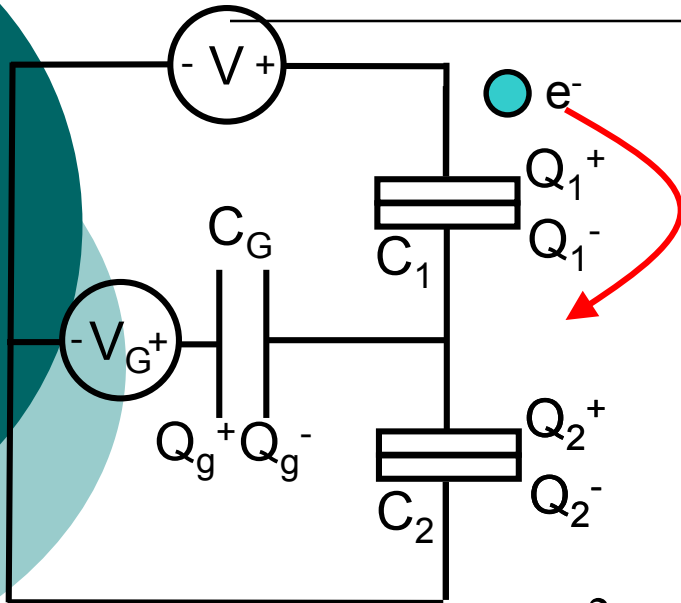
$$Q_i = -n_0 e + e$$

$$Q_G = \frac{-C_g Q_i - C_1 C_g V + C_g V_g (C_1 + C_2)}{C_\Sigma}$$

$$\Delta Q_G = \Delta \frac{-C_g Q_i - C_1 C_g V + C_g V_g (C_1 + C_2)}{C_\Sigma} = \frac{-C_g (-n_0 e)}{C_\Sigma} - \frac{-C_g (-n_0 e - e)}{C_\Sigma}$$

$$\Delta Q_G = \frac{-e C_g}{C_\Sigma}$$

Can current flow?



$$\Delta G = \Delta E - V \Delta Q_1 - V_G \Delta Q_G$$

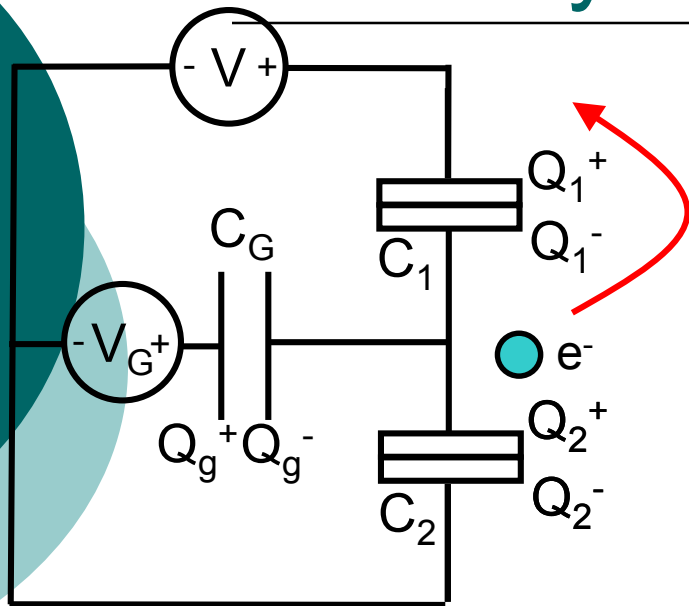
$$\Delta E = \frac{-2n_0 e^2 - e^2}{2C_\Sigma}$$

$$\Delta Q_{1,\text{total}} = e \frac{C_2 + C_G}{C_\Sigma} \quad \Delta Q_G = \frac{-eC_g}{C_\Sigma}$$

$$\Delta G = \frac{-2n_0 e^2 - e^2}{2C_\Sigma} - V e \frac{C_2 + C_G}{C_\Sigma} + V_G \frac{eC_g}{C_\Sigma}$$

$$\Delta G = \frac{e}{C_\Sigma} \left[-n_0 e - \frac{e}{2} - V (C_2 + C_G) + V_G C_g \right] > 0$$

Similarly:



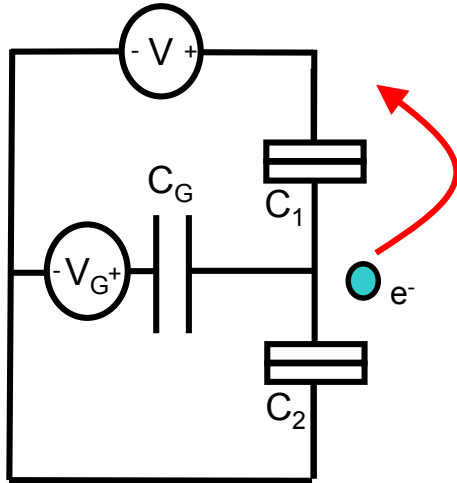
Allowed only if:

$$\Delta G = \frac{e}{C_\Sigma} \left[+n_0 e - \frac{e}{2} + V (C_2 + C_G) - V_G C_g \right] > 0$$

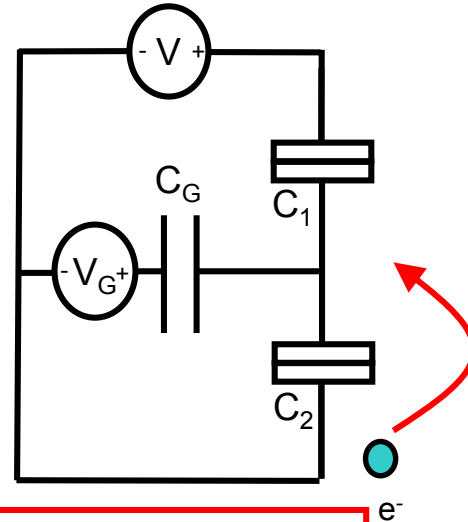
n_0 is the number of electrons on the island *before* the tunnel event.

Summary:

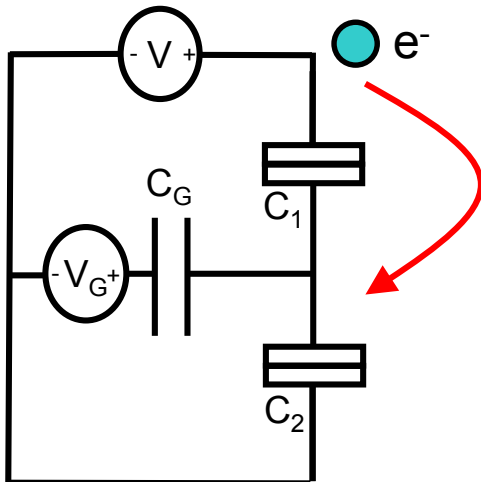
$$+n_0e - \frac{e}{2} + V(C_2 + C_G) - V_G C_g > 0$$



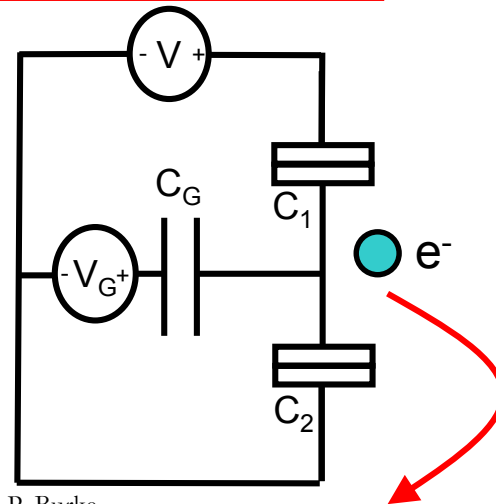
$$-n_0e - \frac{e}{2} + C_1V + C_gV_G > 0$$



$$-n_0e - \frac{e}{2} - V(C_2 + C_G) + V_G C_g > 0$$

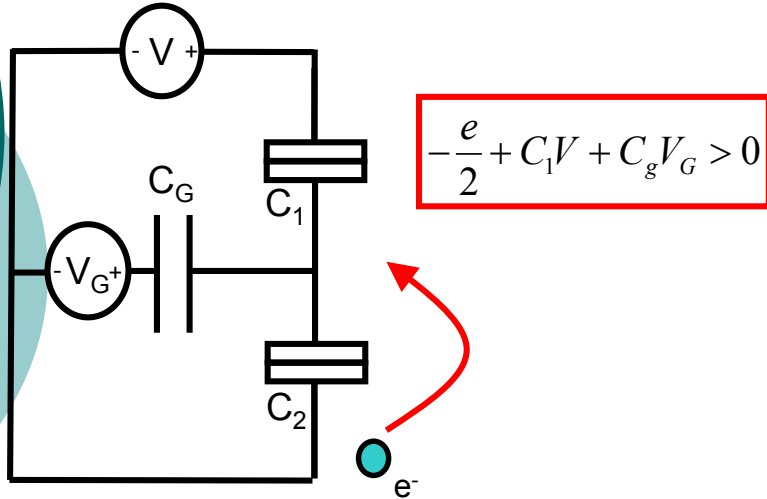


$$+n_0e - \frac{e}{2} - C_1V - C_gV_G > 0$$



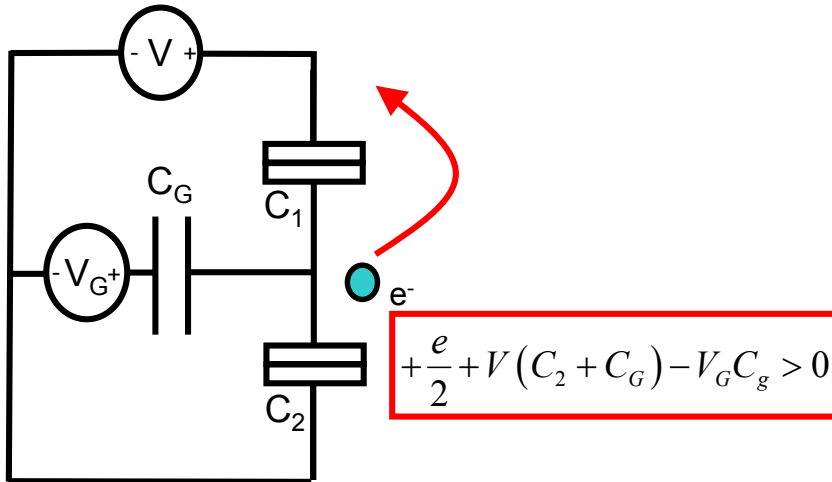
Current?

Let $n_0=0$.



$$V > \frac{e}{2C_1} - \frac{C_g}{C_1}V_G$$

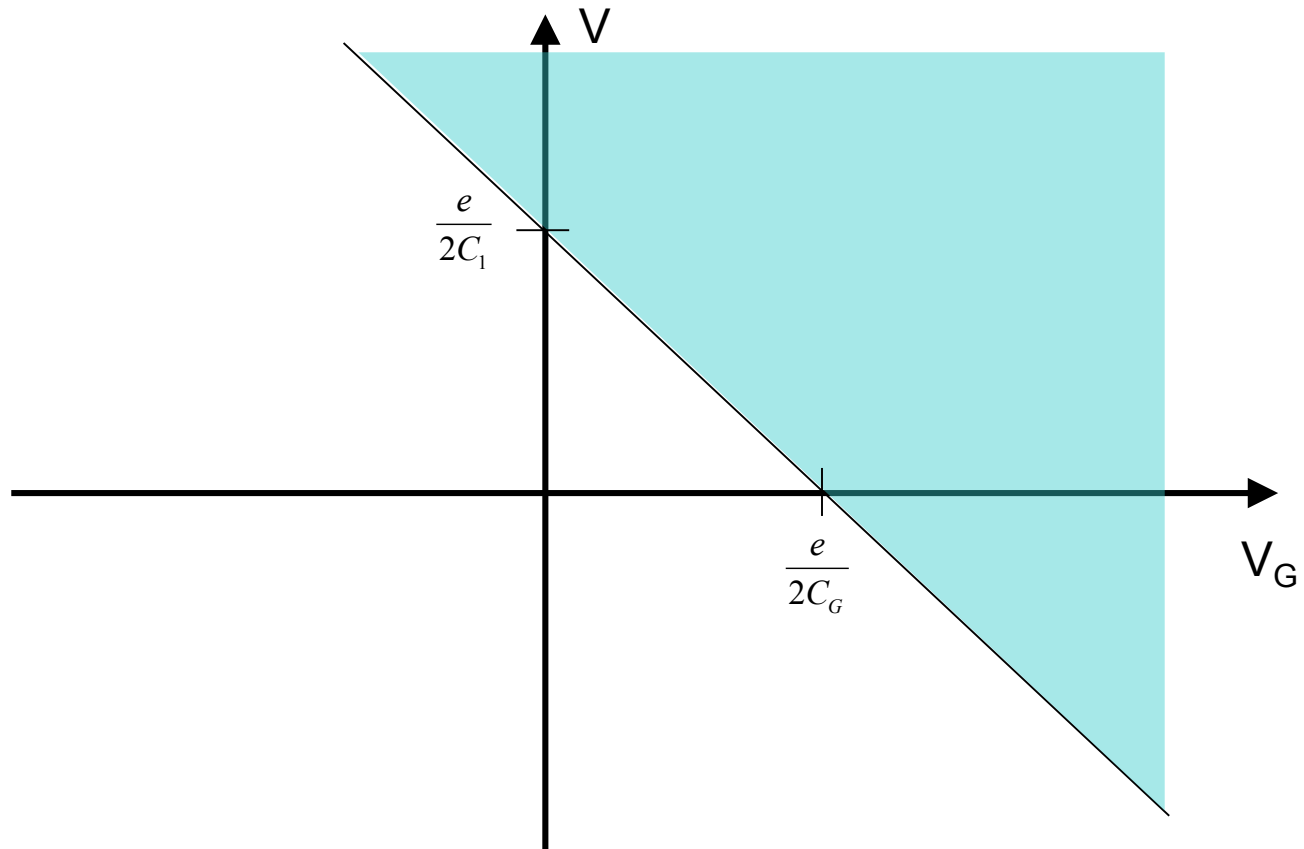
Now $n_0=1$.



$$V > \frac{C_g}{(C_2 + C_g)}V_G - \frac{e}{2(C_2 + C_g)}$$

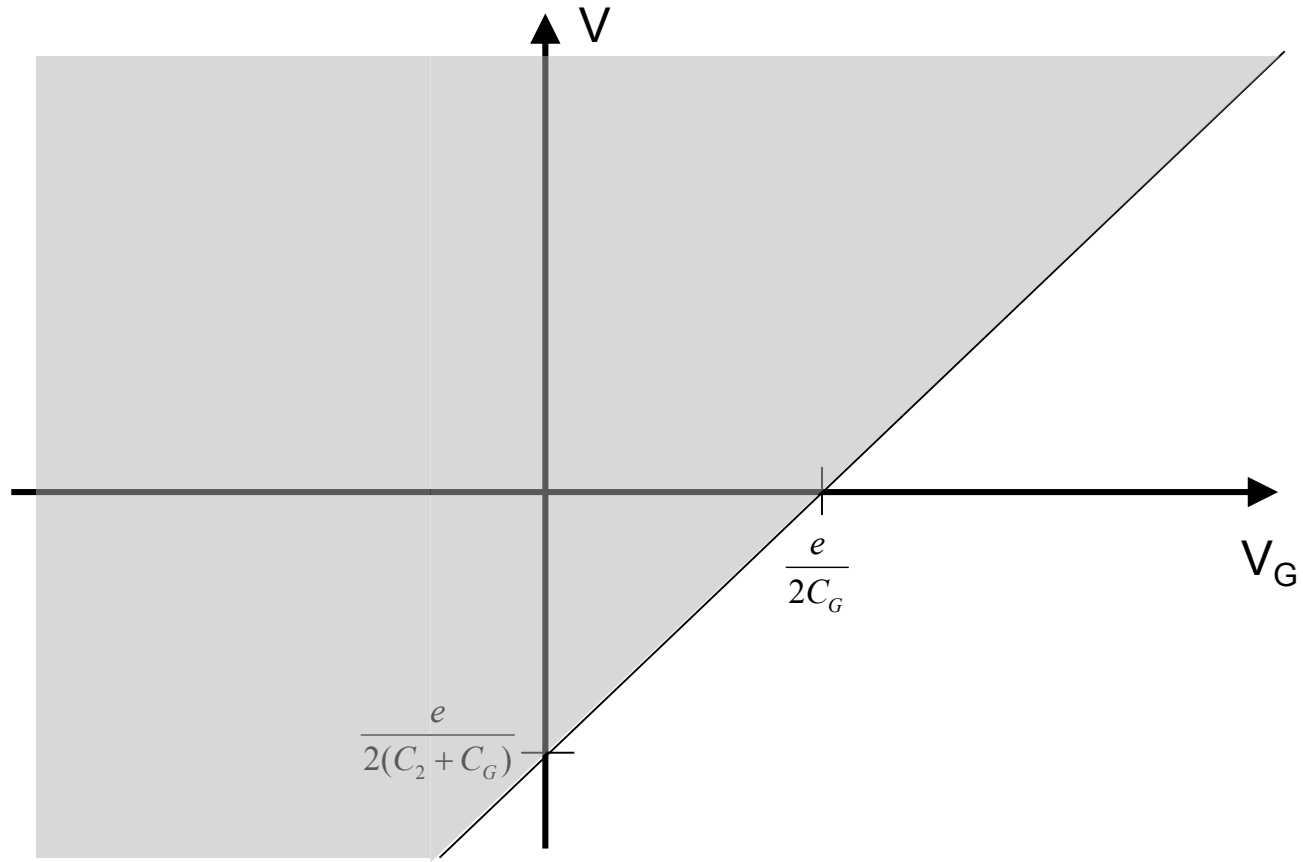
Current?

$$V > \frac{e}{2C_1} - \frac{C_g}{C_1} V_G$$



Current?

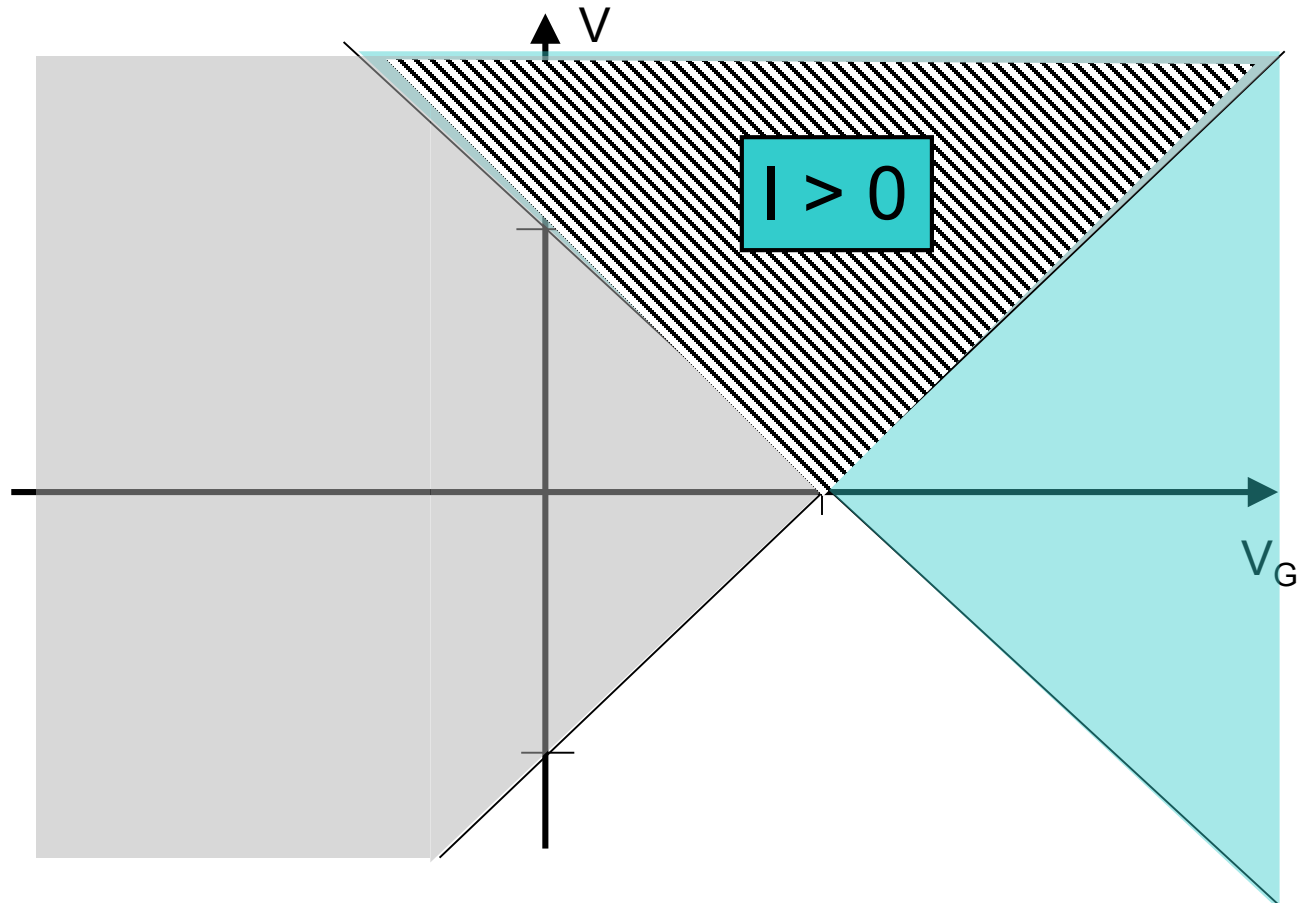
$$V > \frac{C_g}{(C_2 + C_G)} V_G - \frac{e}{2(C_2 + C_G)}$$



Current?

$$V > \frac{e}{2C_1} - \frac{C_g}{C_1} V_G$$

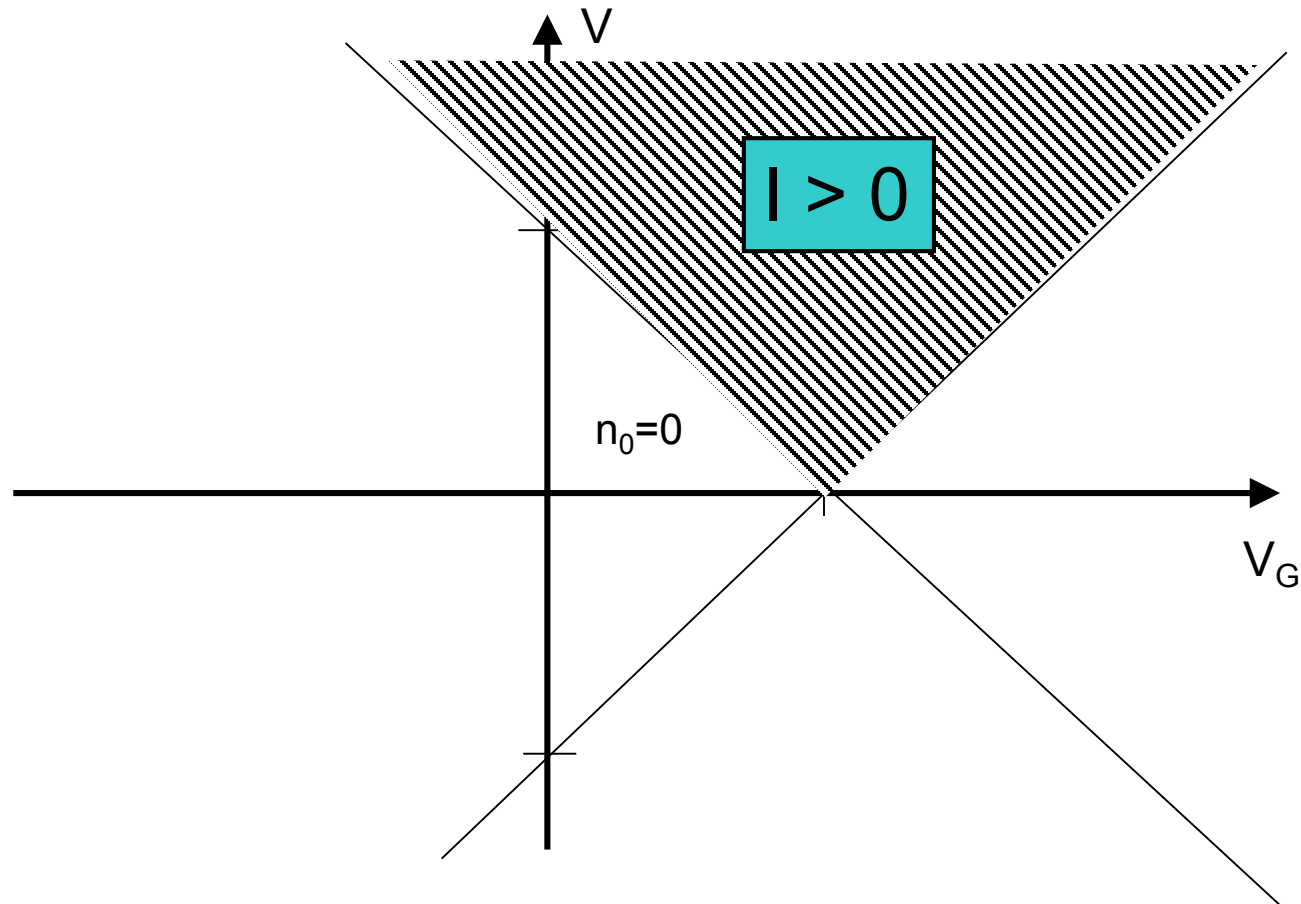
$$V > \frac{C_g}{(C_2 + C_G)} V_G - \frac{e}{2(C_2 + C_G)}$$



Current?

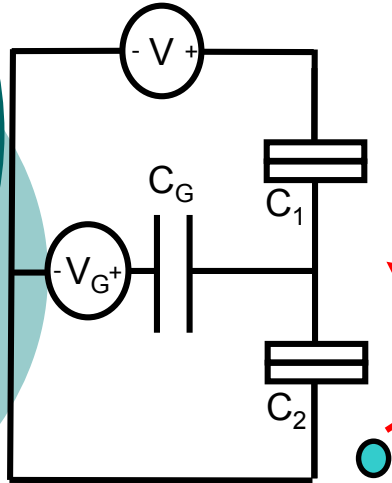
$$V > \frac{e}{2C_1} - \frac{C_g}{C_1} V_G$$

$$V > \frac{C_g}{(C_2 + C_G)} V_G - \frac{e}{2(C_2 + C_G)}$$



Current for 1 electrons on island:

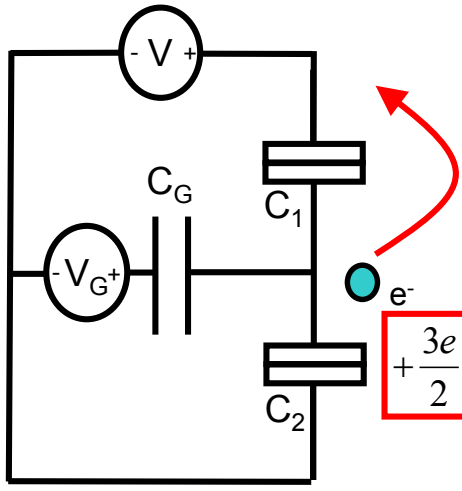
Let $n_0=1$.



$$-\frac{3e}{2} + C_1 V + C_g V_G > 0$$

$$V > \frac{3e}{2C_1} - \frac{C_g}{C_1} V_G$$

Now $n_0=2$.

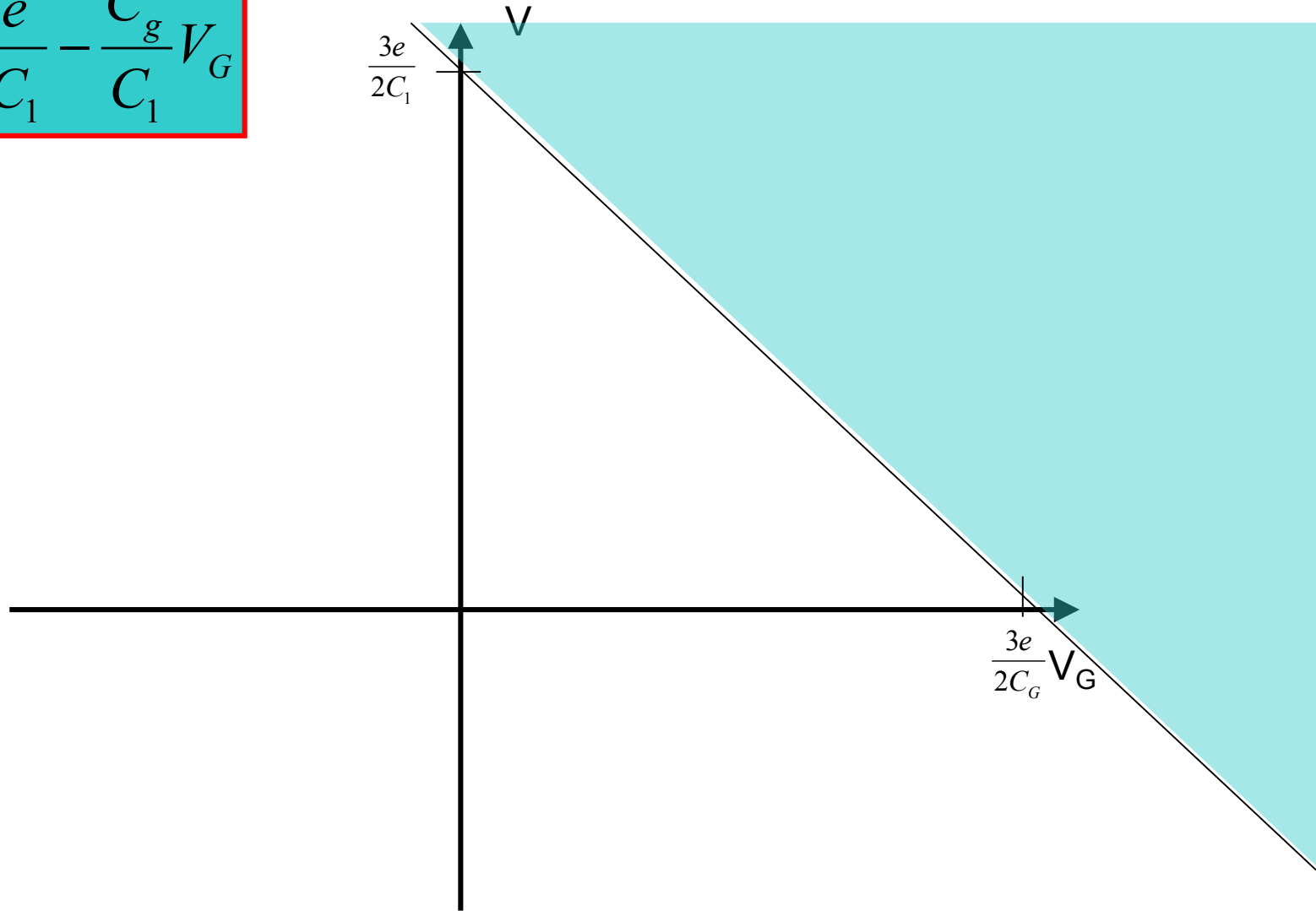


$$+\frac{3e}{2} + V(C_2 + C_G) - V_G C_g > 0$$

$$V > \frac{C_g}{(C_2 + C_G)} V_G - \frac{3e}{2(C_2 + C_G)}$$

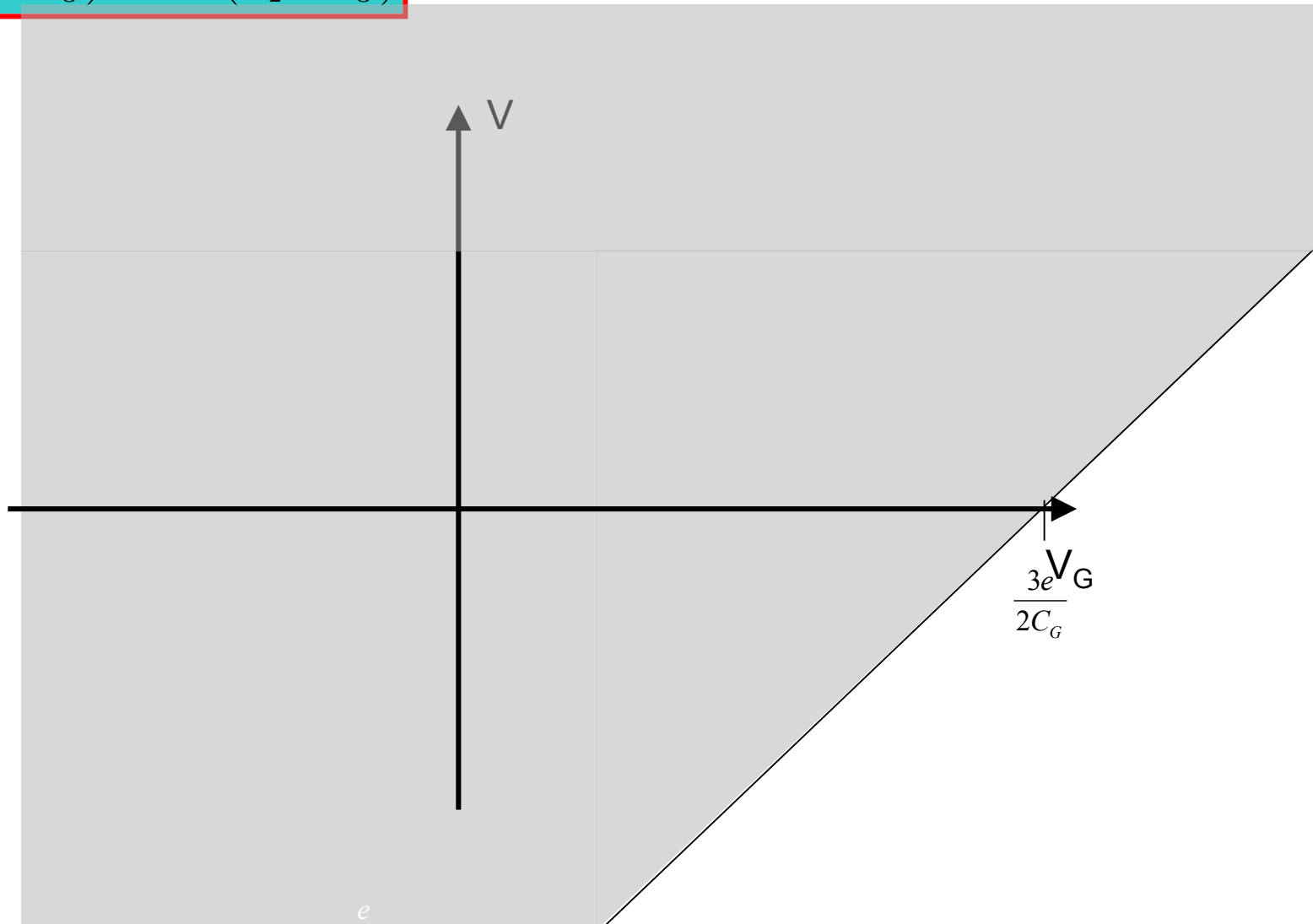
Current?

$$V > \frac{3e}{2C_1} - \frac{C_g}{C_1} V_G$$

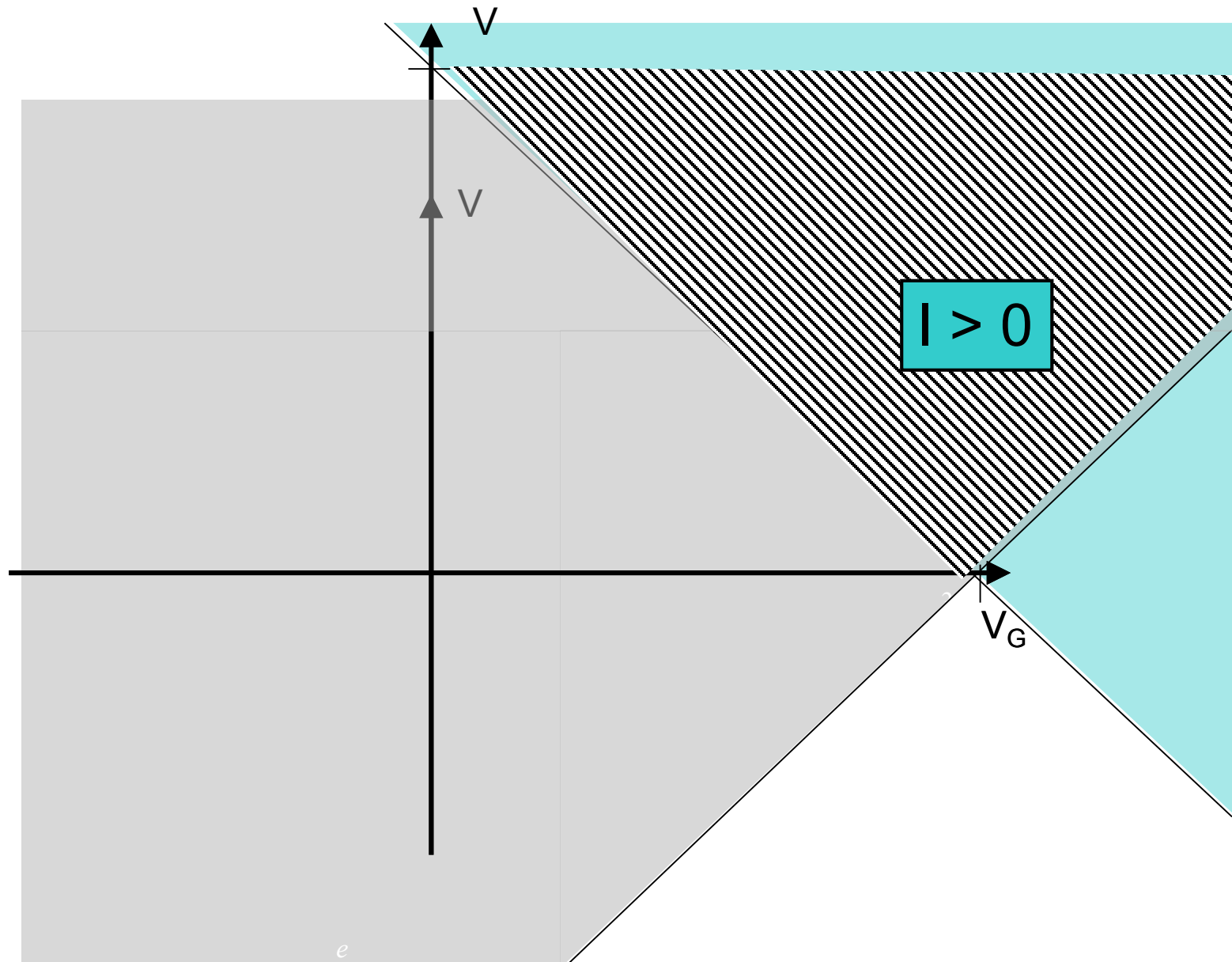


Current?

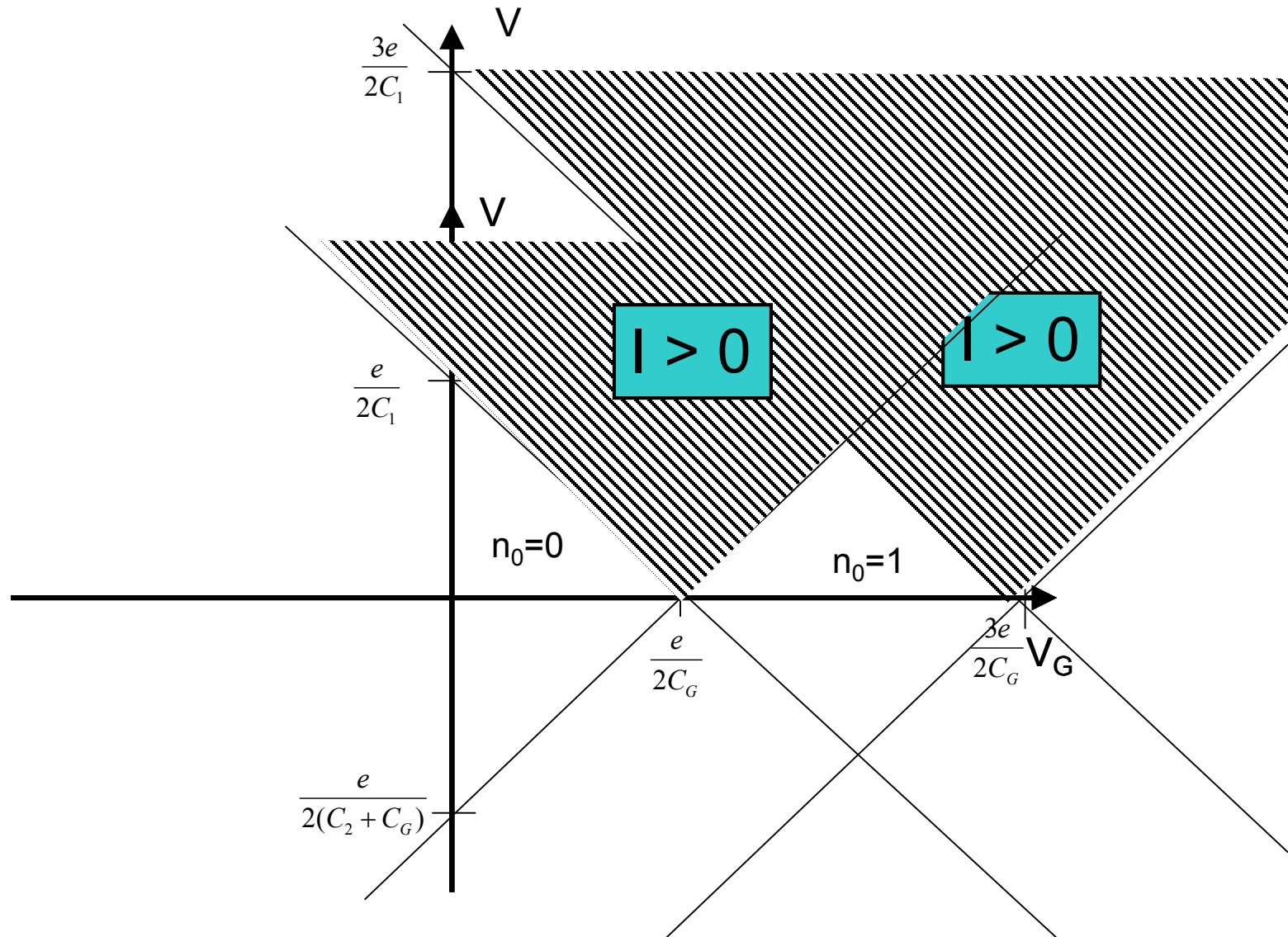
$$V > \frac{C_g}{(C_2 + C_G)} V_G - \frac{3e}{2(C_2 + C_G)}$$



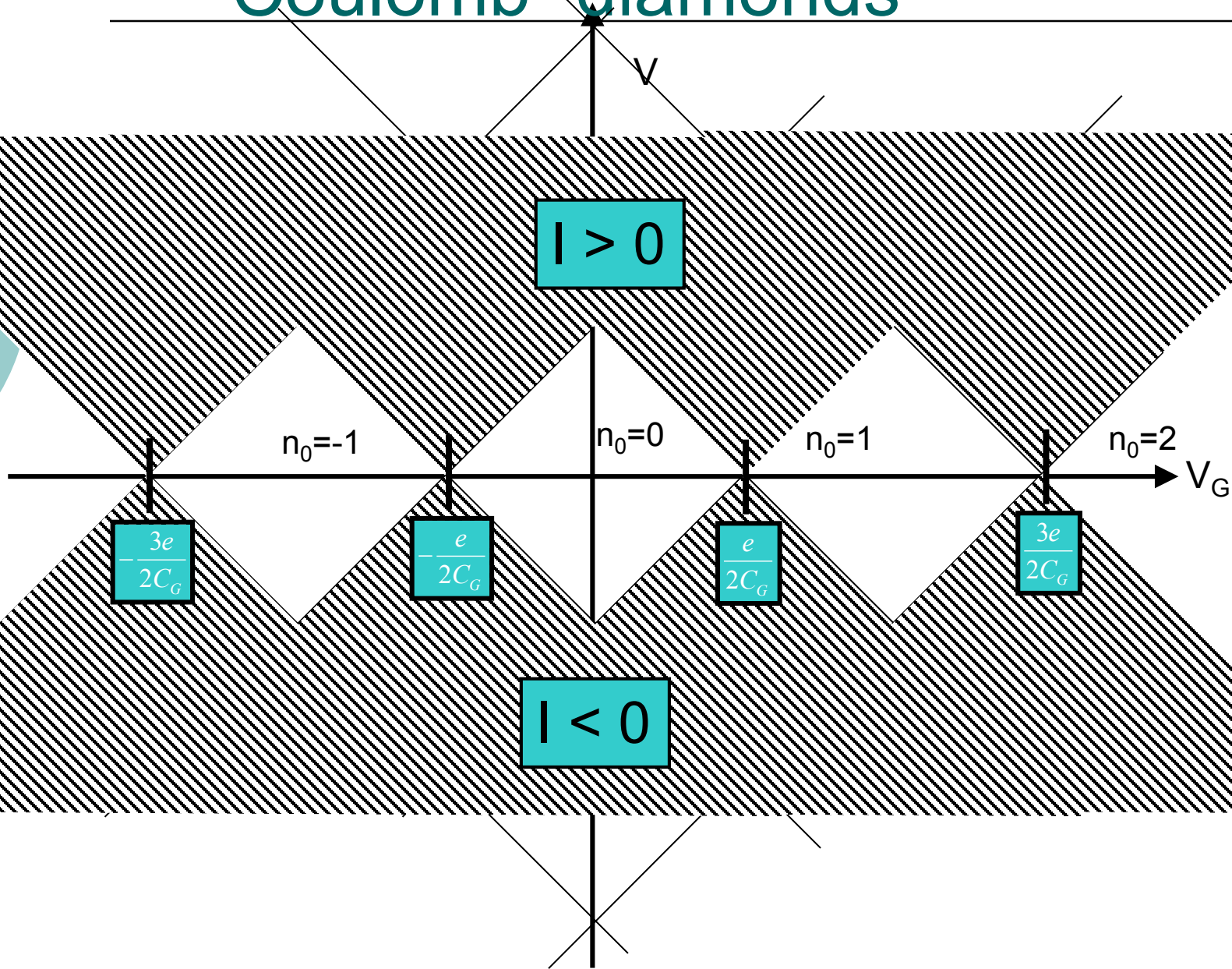
Current?



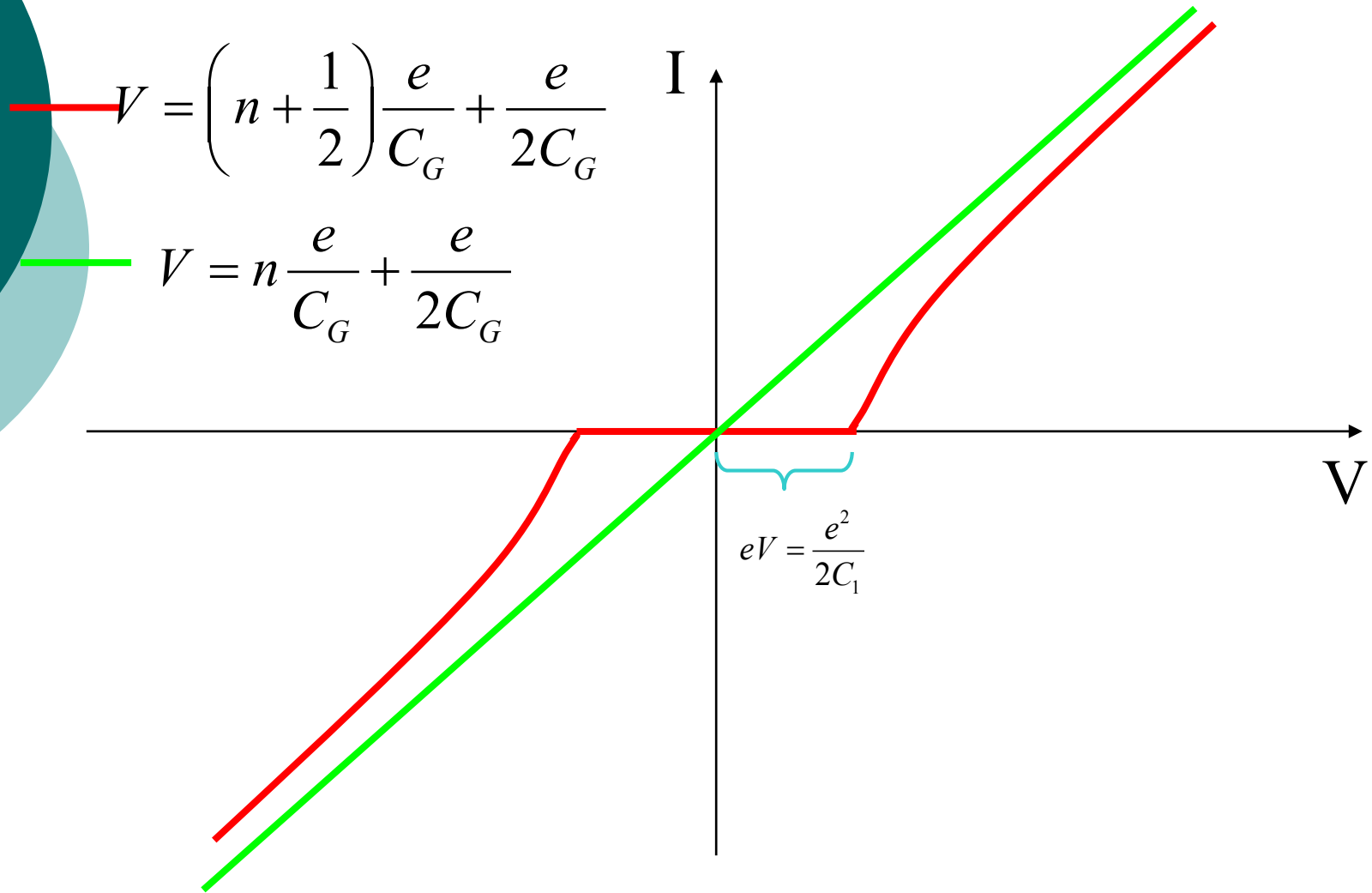
Current?



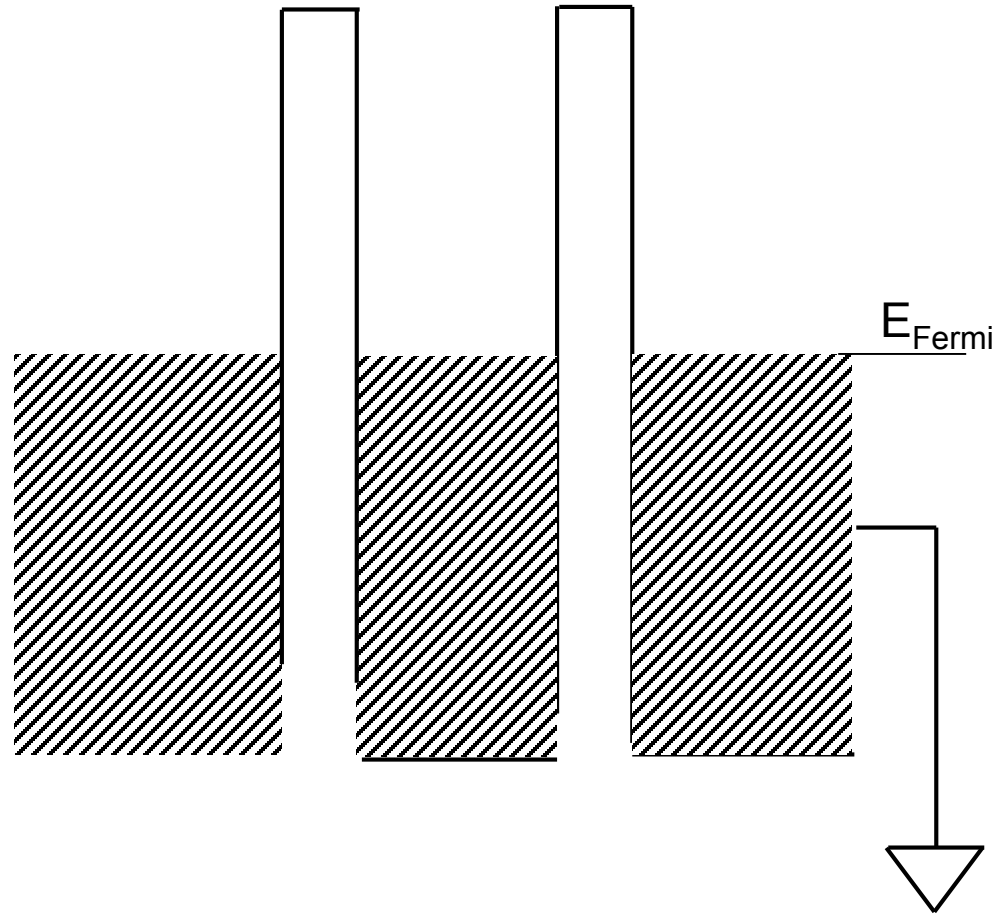
Coulomb "diamonds"



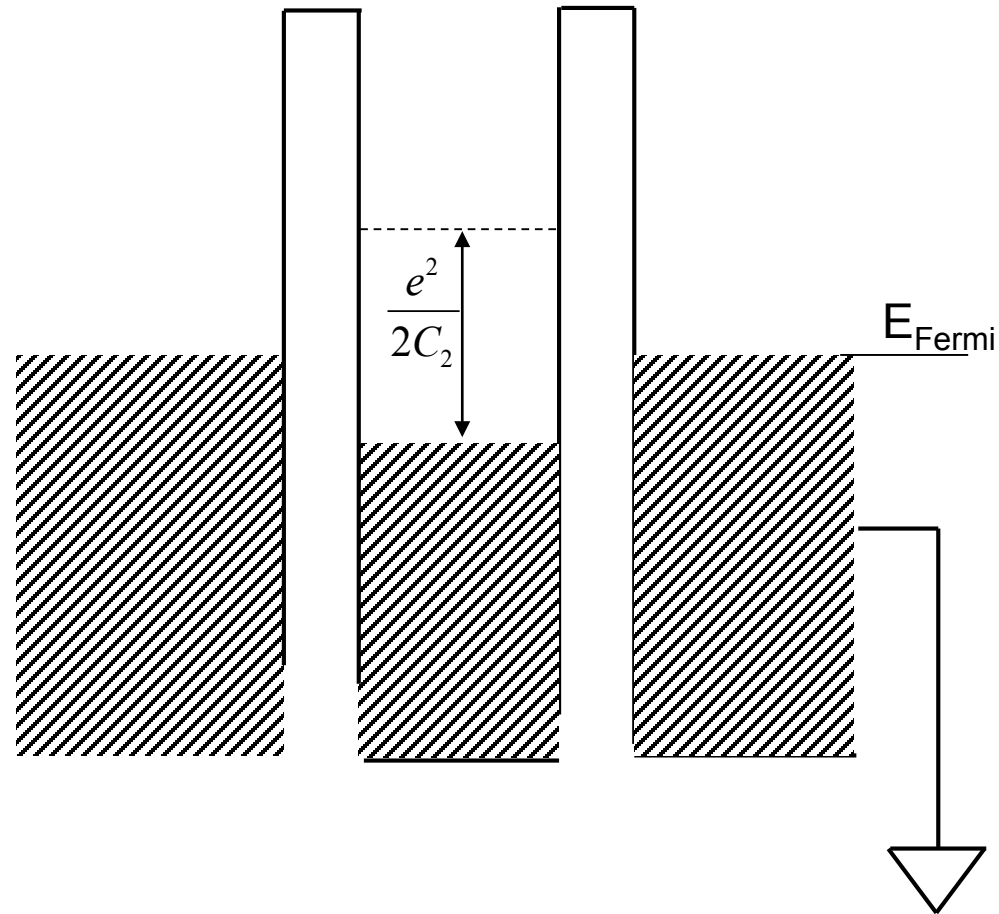
SET I-V curve vs. gate voltage



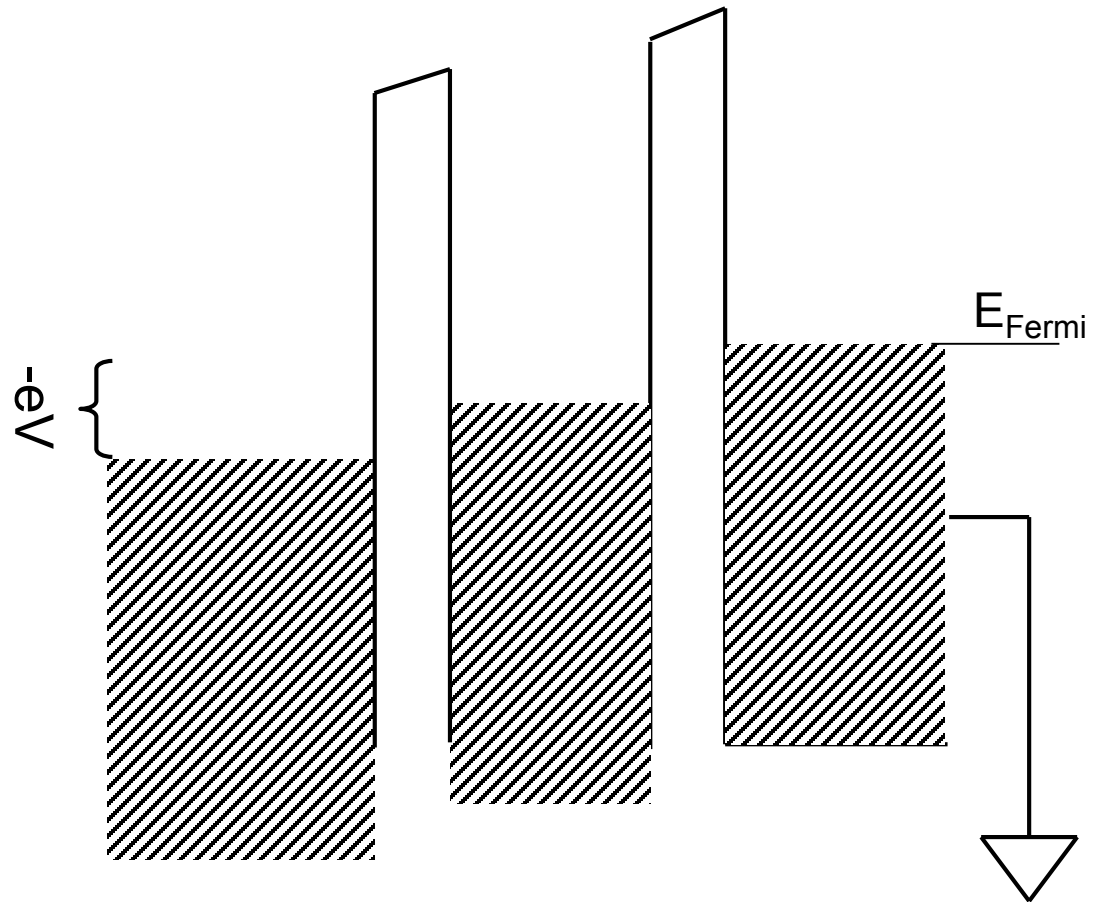
Band diagram



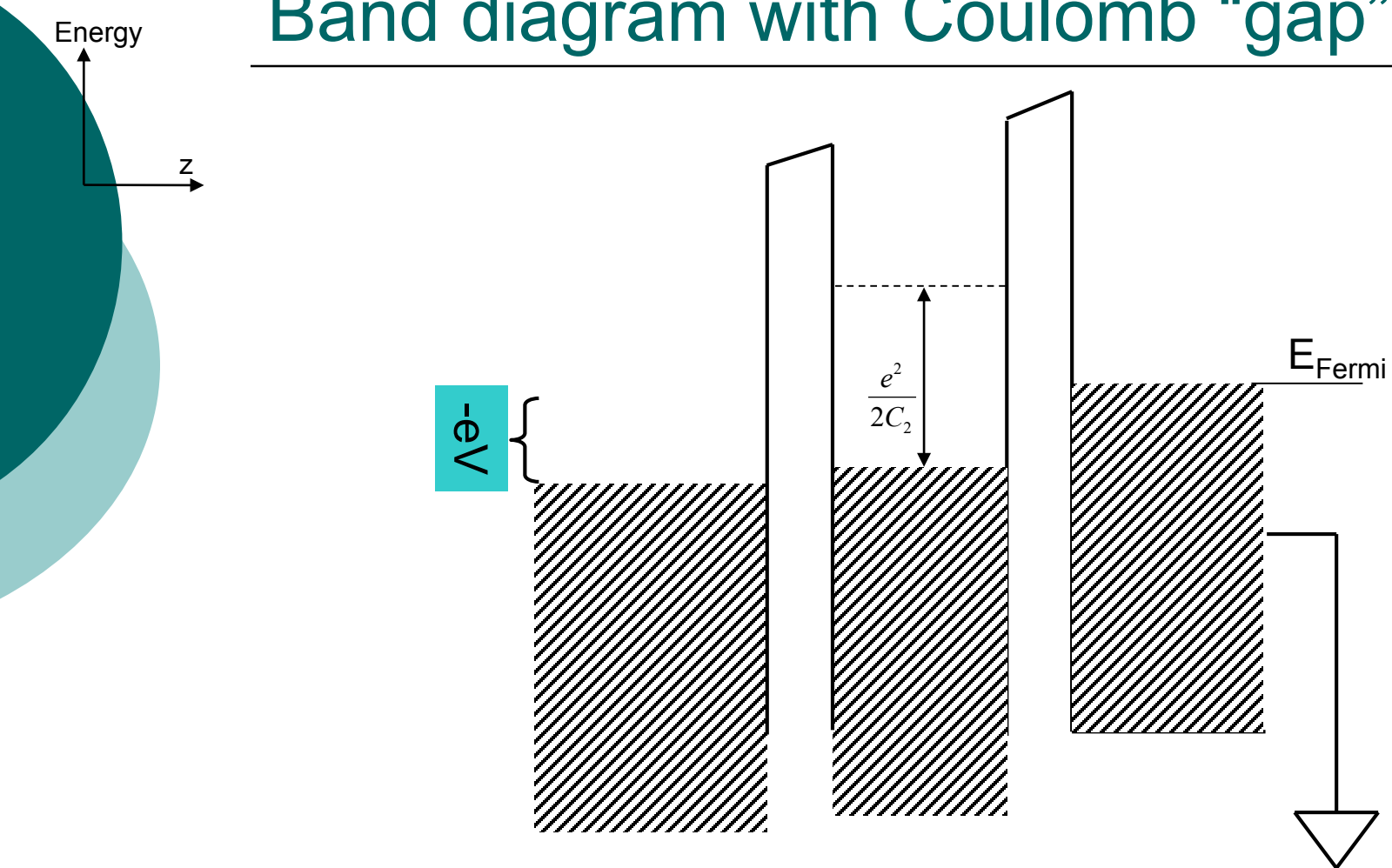
Band diagram with Coulomb "gap"



Band diagram under bias

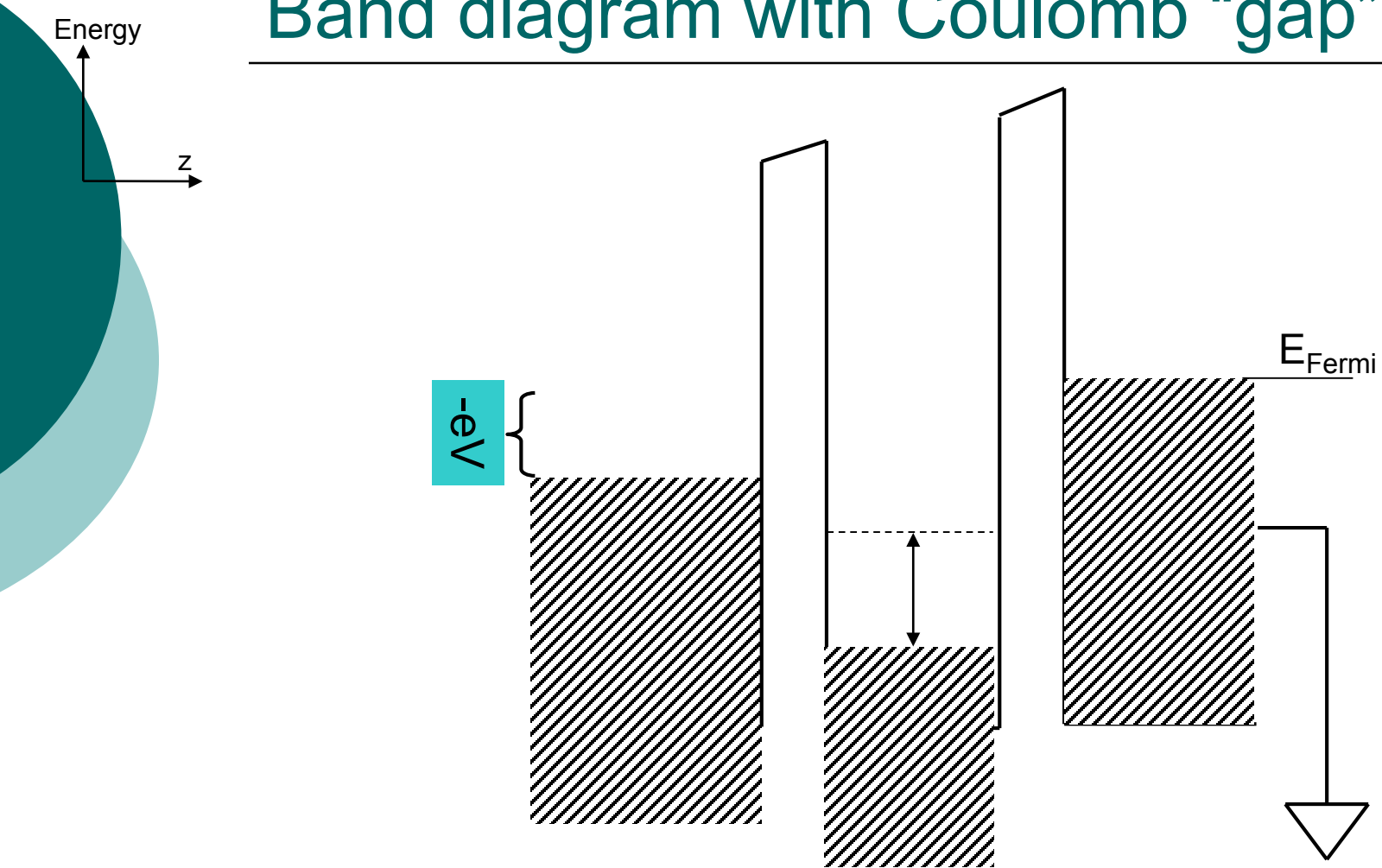


Band diagram with Coulomb "gap"



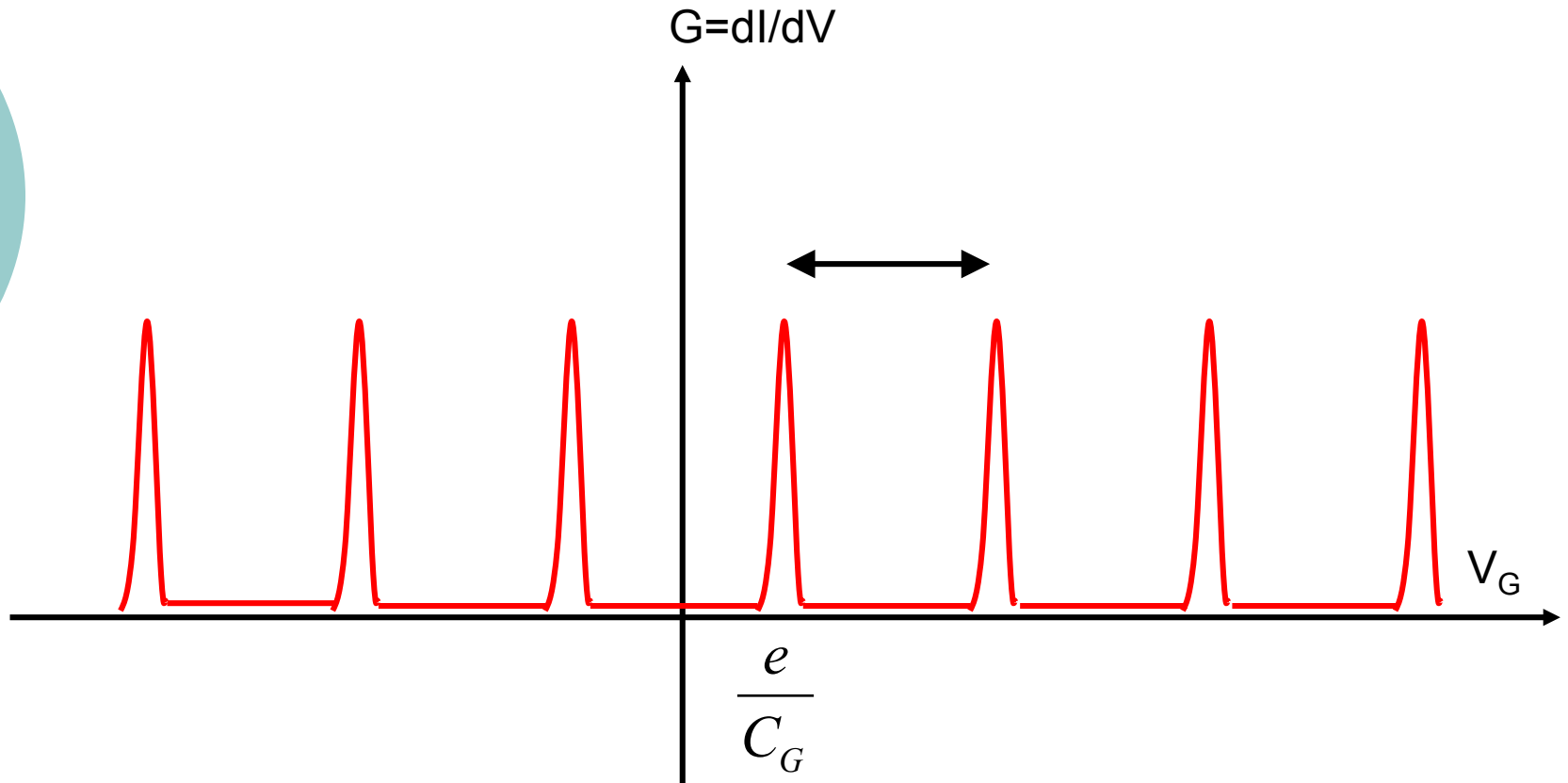
Gate voltage like a "plunger"
Moves island up/down by e^2/V_G

Band diagram with Coulomb "gap"



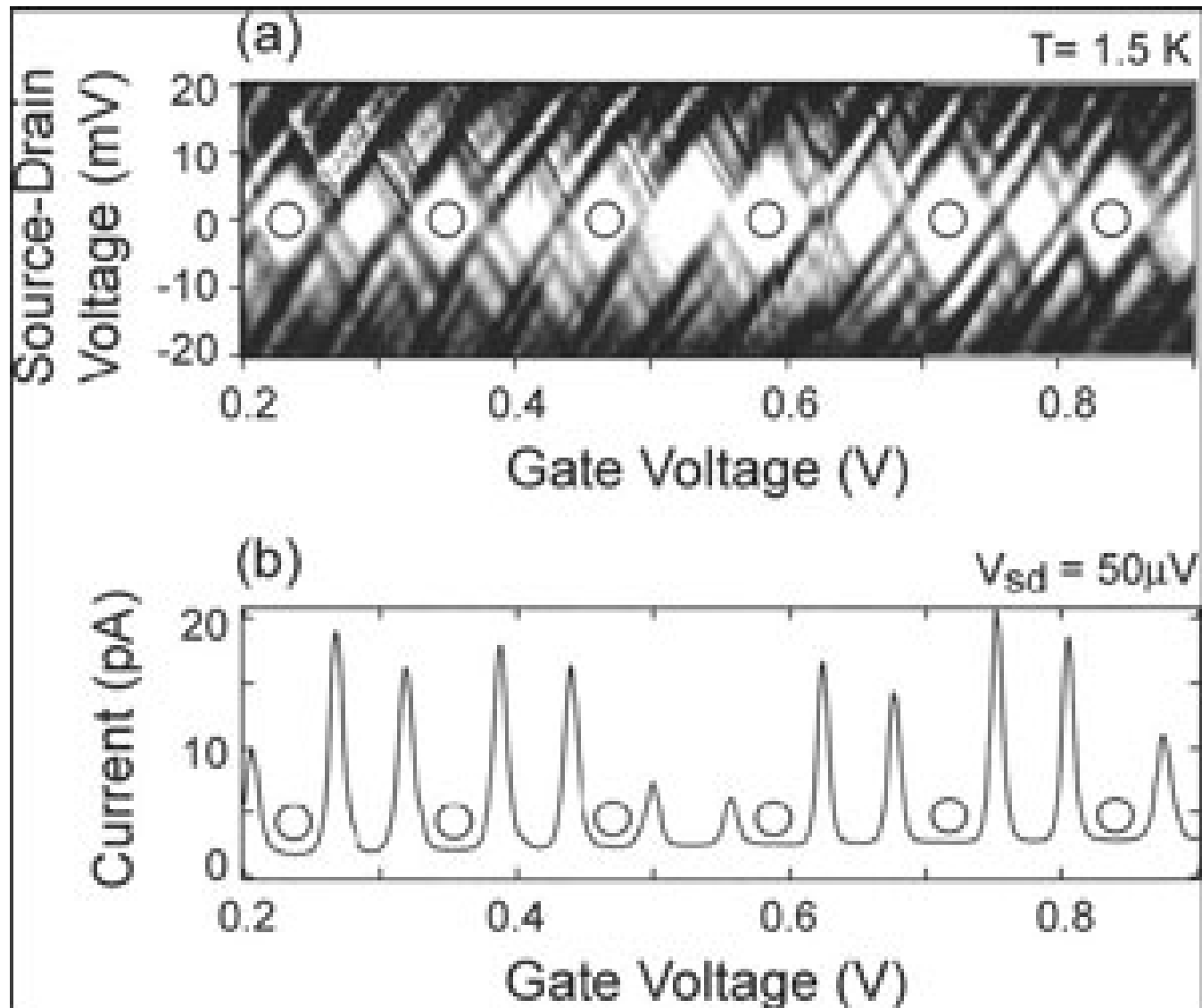
Gate voltage like a "plunger"
Moves island up/down by e^2/V_G

Zero bias conductance



Width of peaks set by temperature.

Coulomb diamond





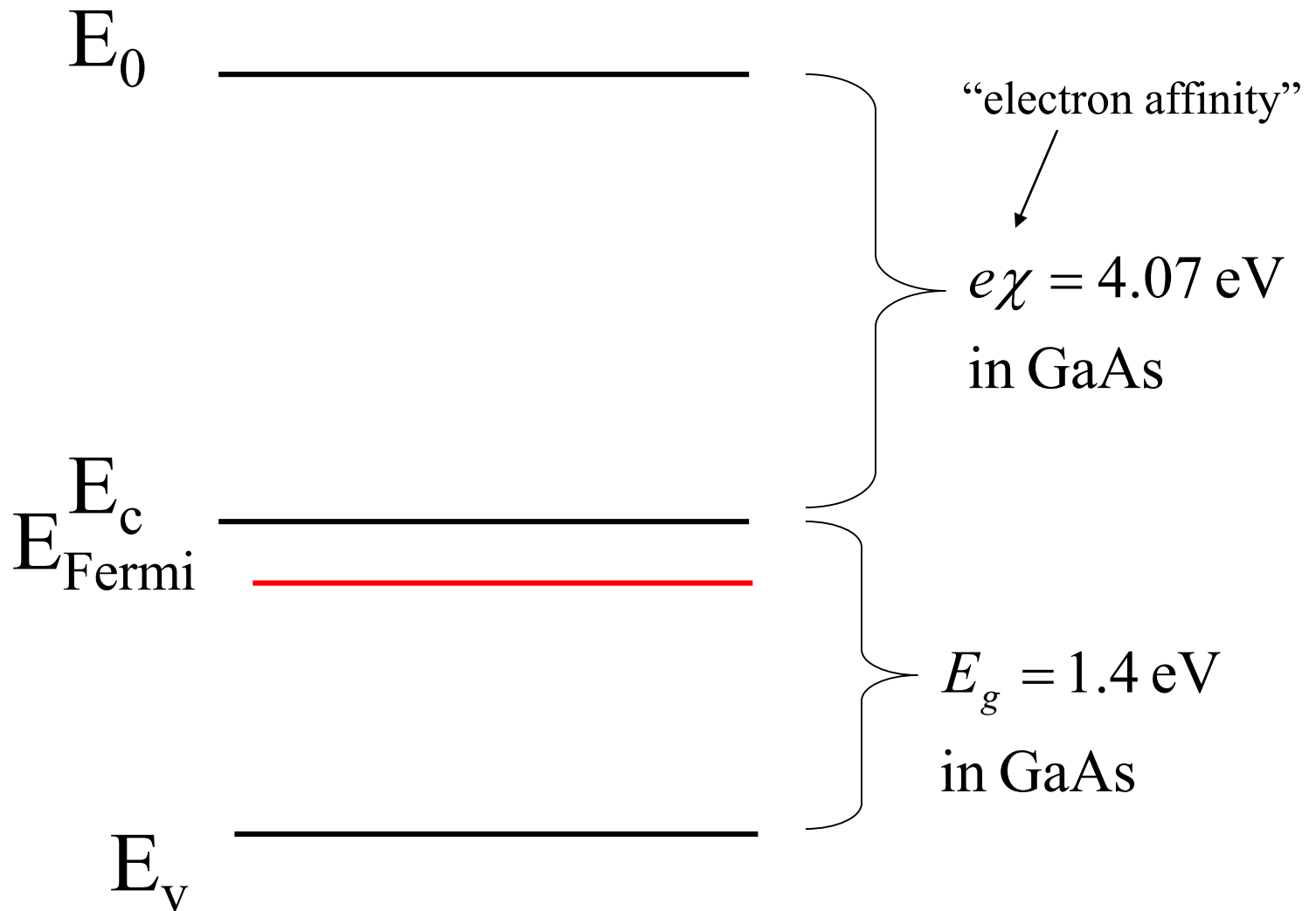
Lecture 9

2 dimensional electron gas (2DEG)

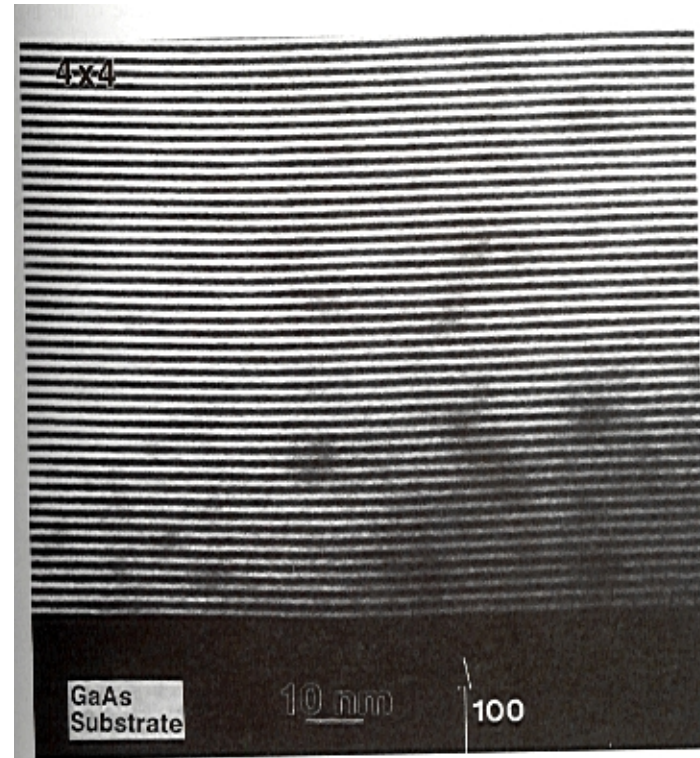
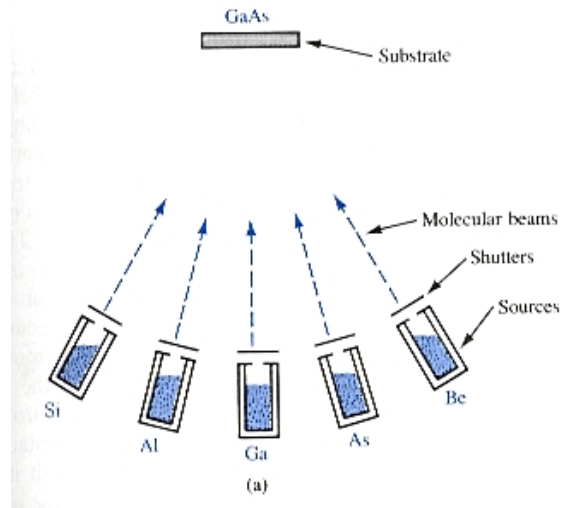
Readings this lecture covers

- Ferry, pp. 23-39
- Hanson, pp. 118-123

Vacuum level



MBE

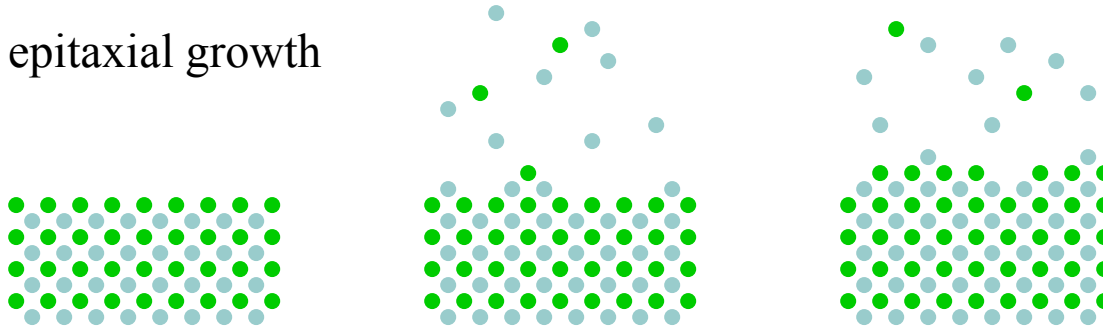


4 atom per layer!

(From Streetman, Solid State Electronic Devices)

MBE

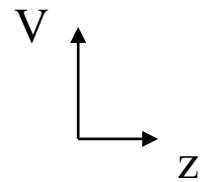
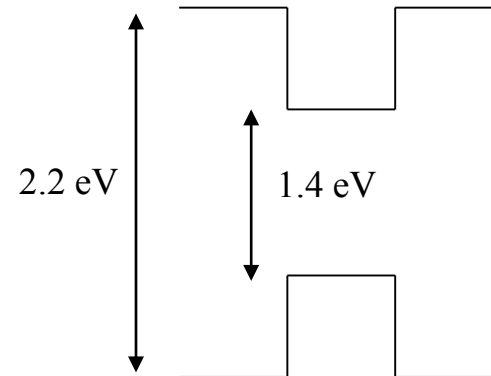
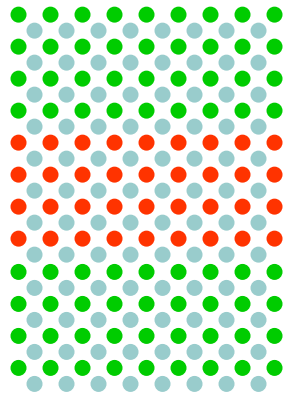
epitaxial growth



AlAs

GaAs

AlAs



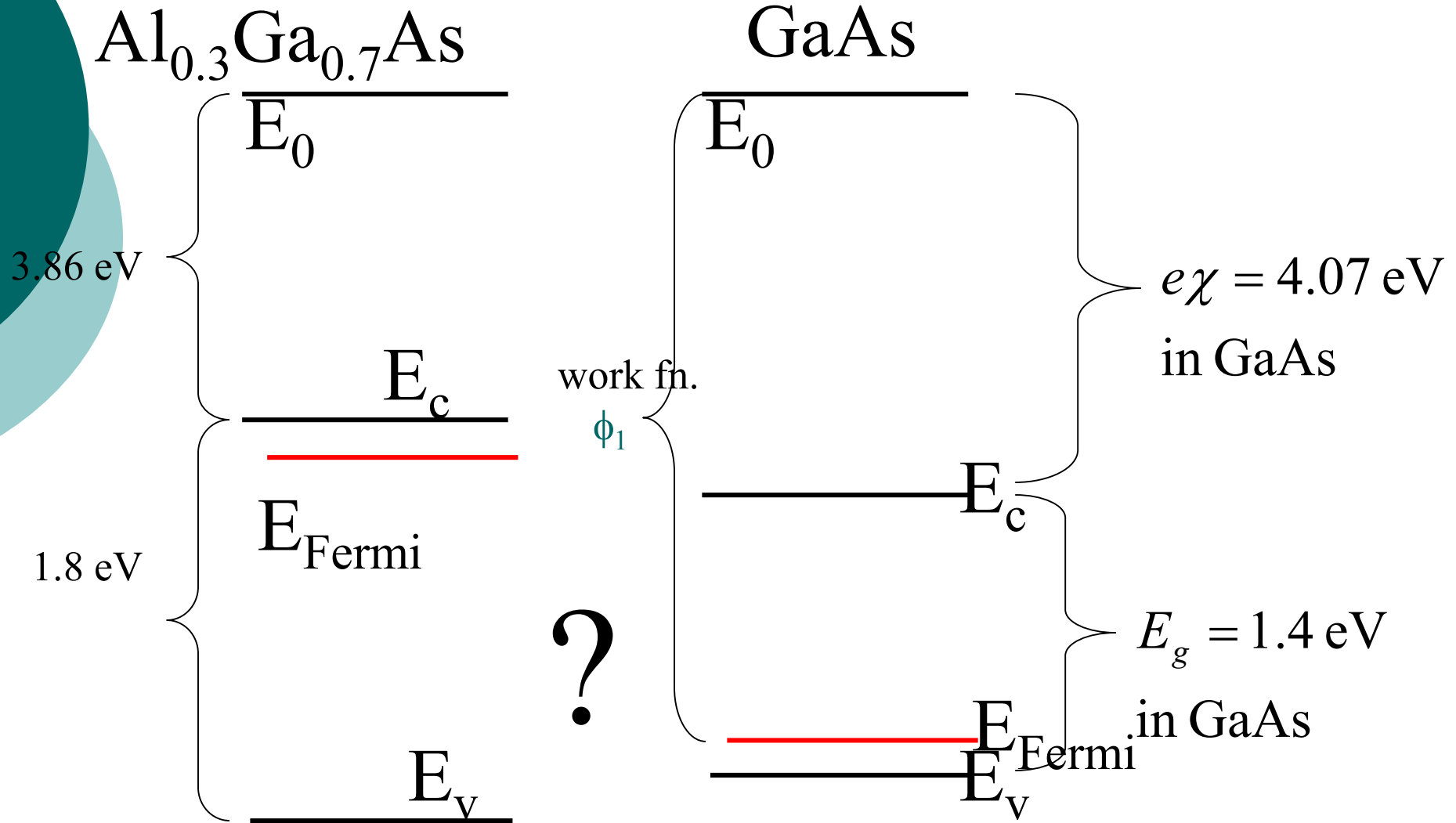
Also InP, InGaAs, InAlAs, InGaAsP ...

Picture adapted from M. Lilly.

Heterojunction band diagrams

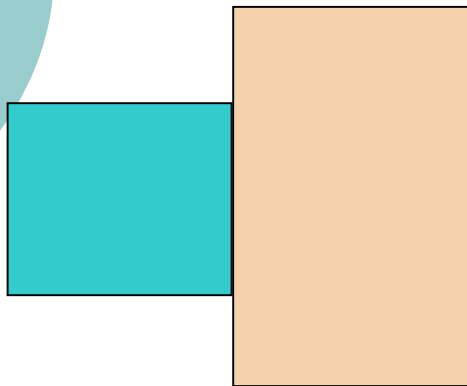
- Determine $\Delta E_c = \chi_1 - \chi_2$
(Vacuum levels line up)
- Determine $\Delta E_v = \Delta E_g - \Delta E_c$
- There will be some charge transfer and built-in electric field/voltage as in p-n homojunction
- Built in voltage $\phi = \phi_1 - \phi_2$
- Draw the diagram (You will in HW#2)

Intrinsic heterojunction



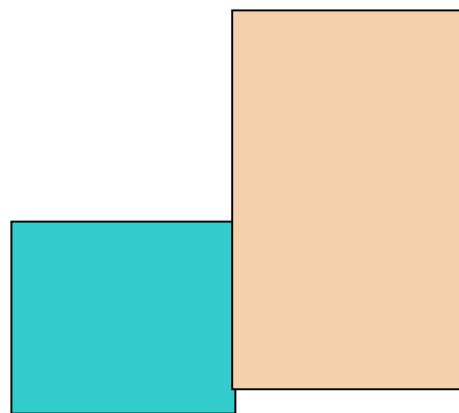
Types

I



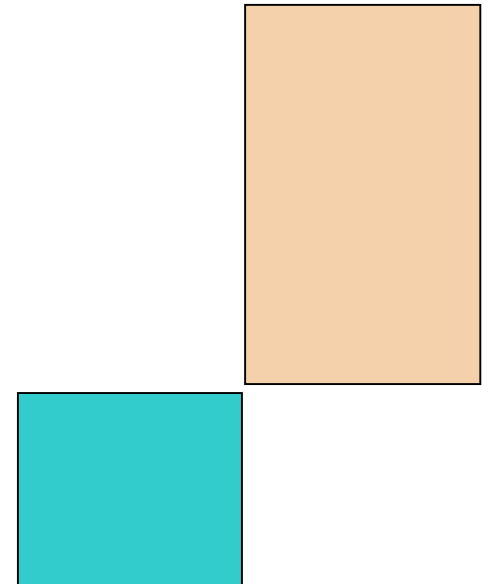
most common

II



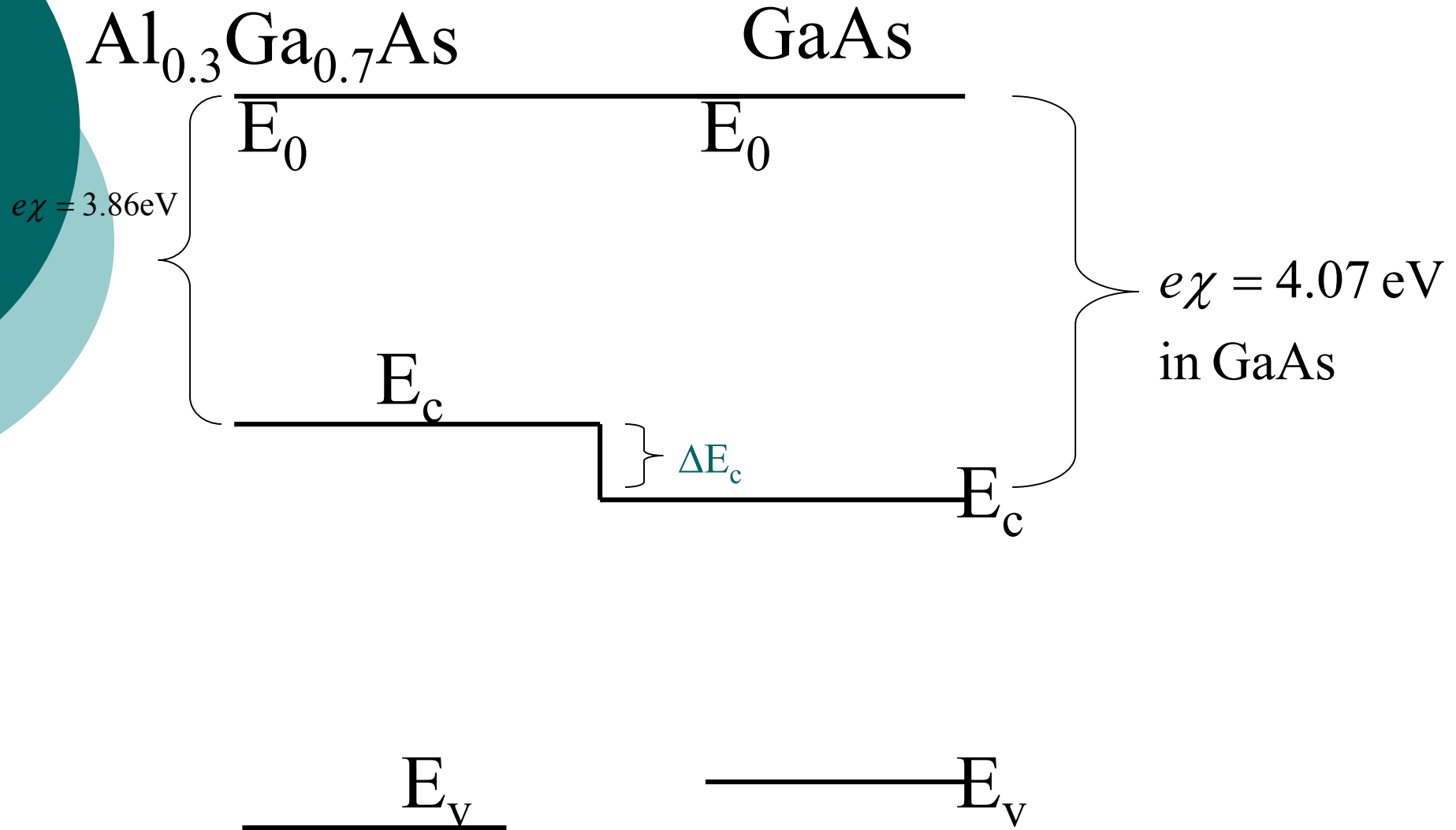
less common

III

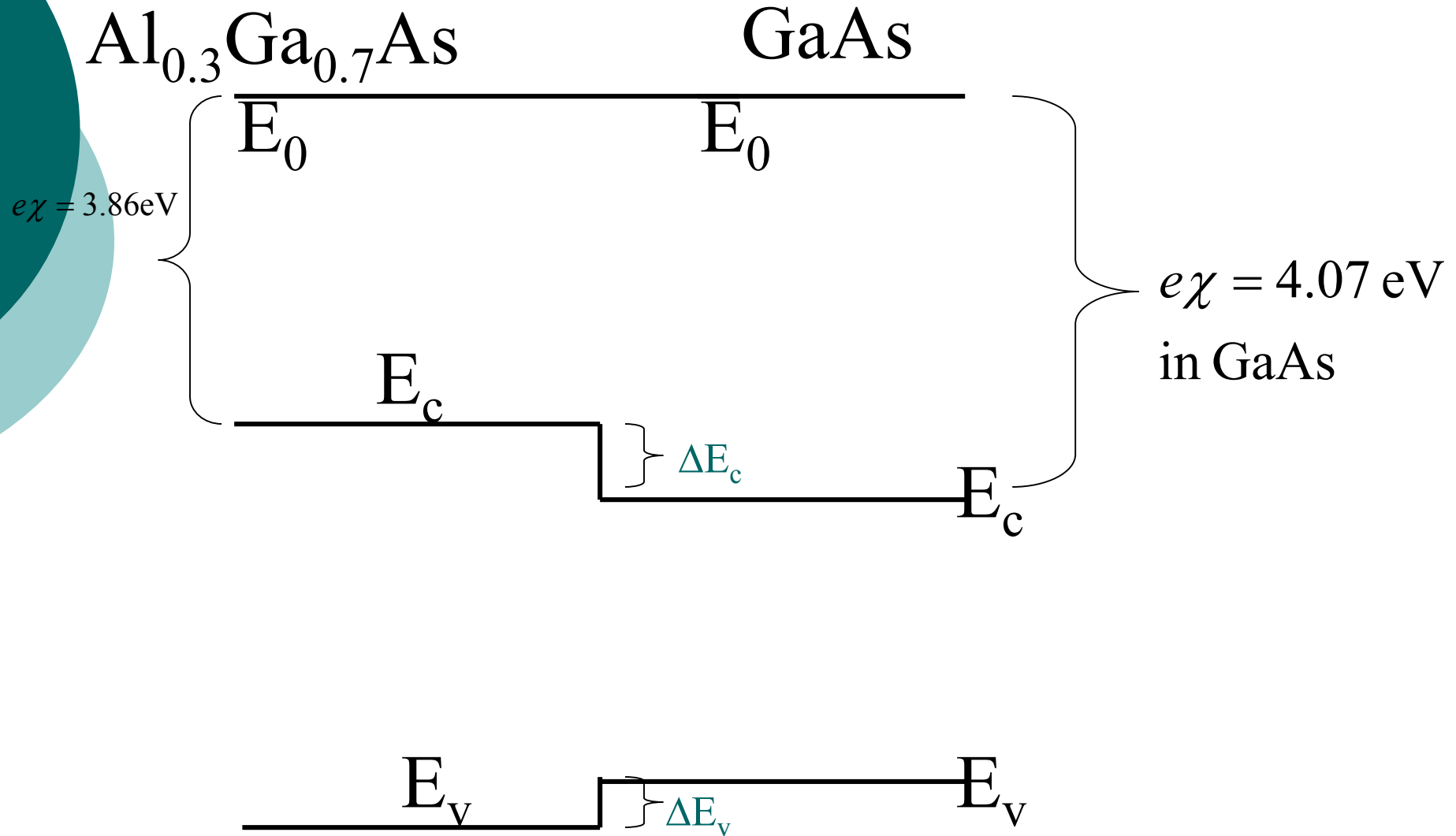


Only GaSb-InAs

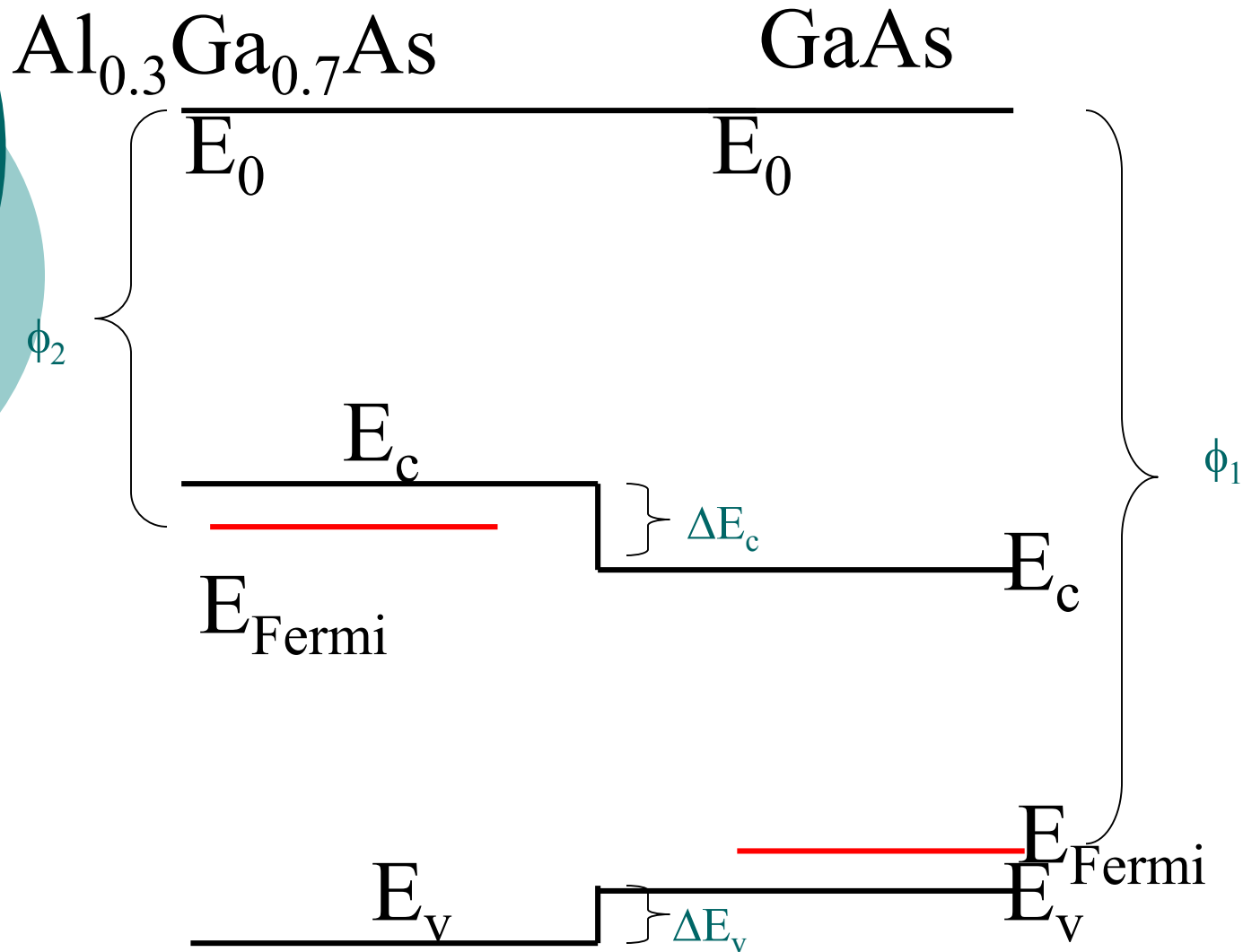
Determine $\Delta E_c = \chi_1 - \chi_2$



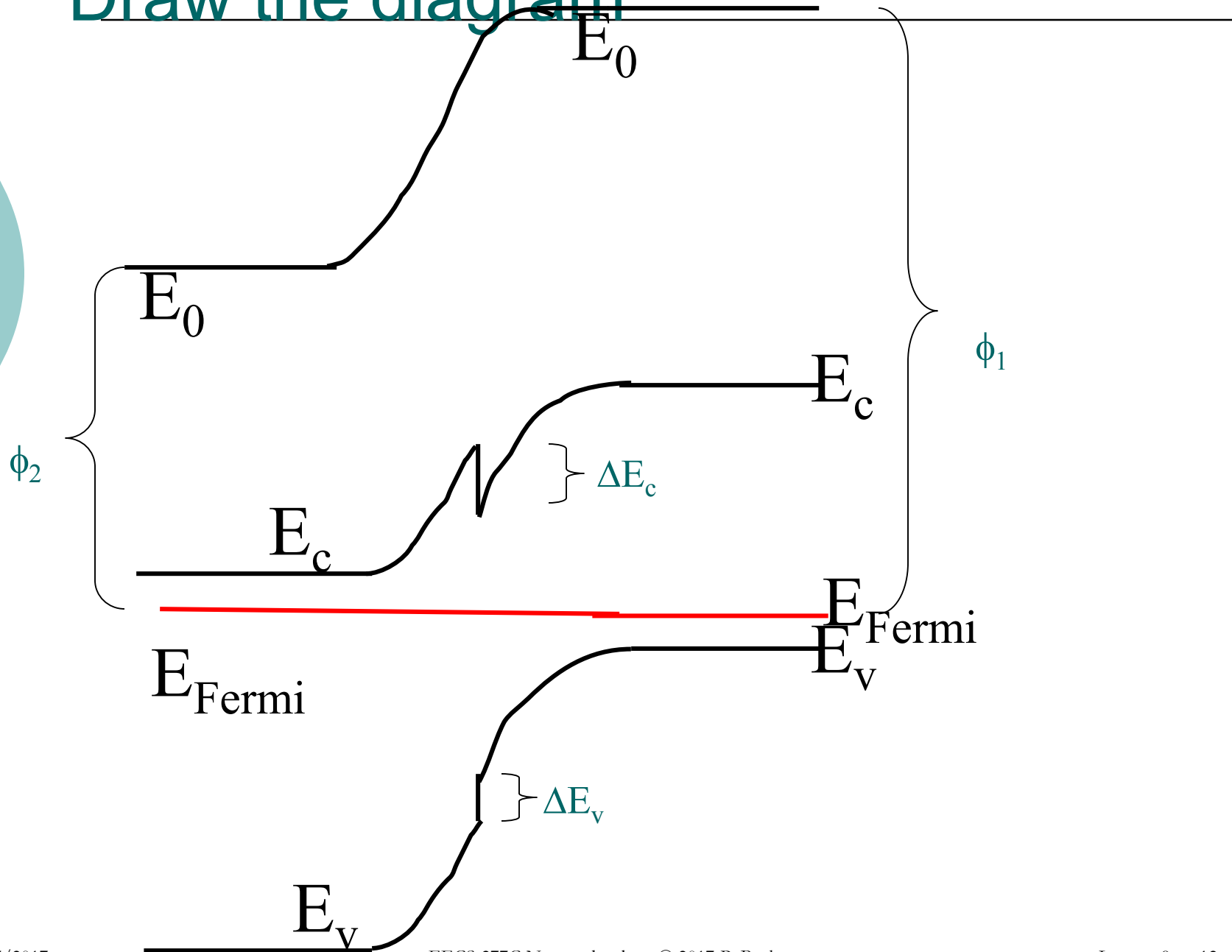
Determine $\Delta E_v = \Delta E_g - \Delta E_c$



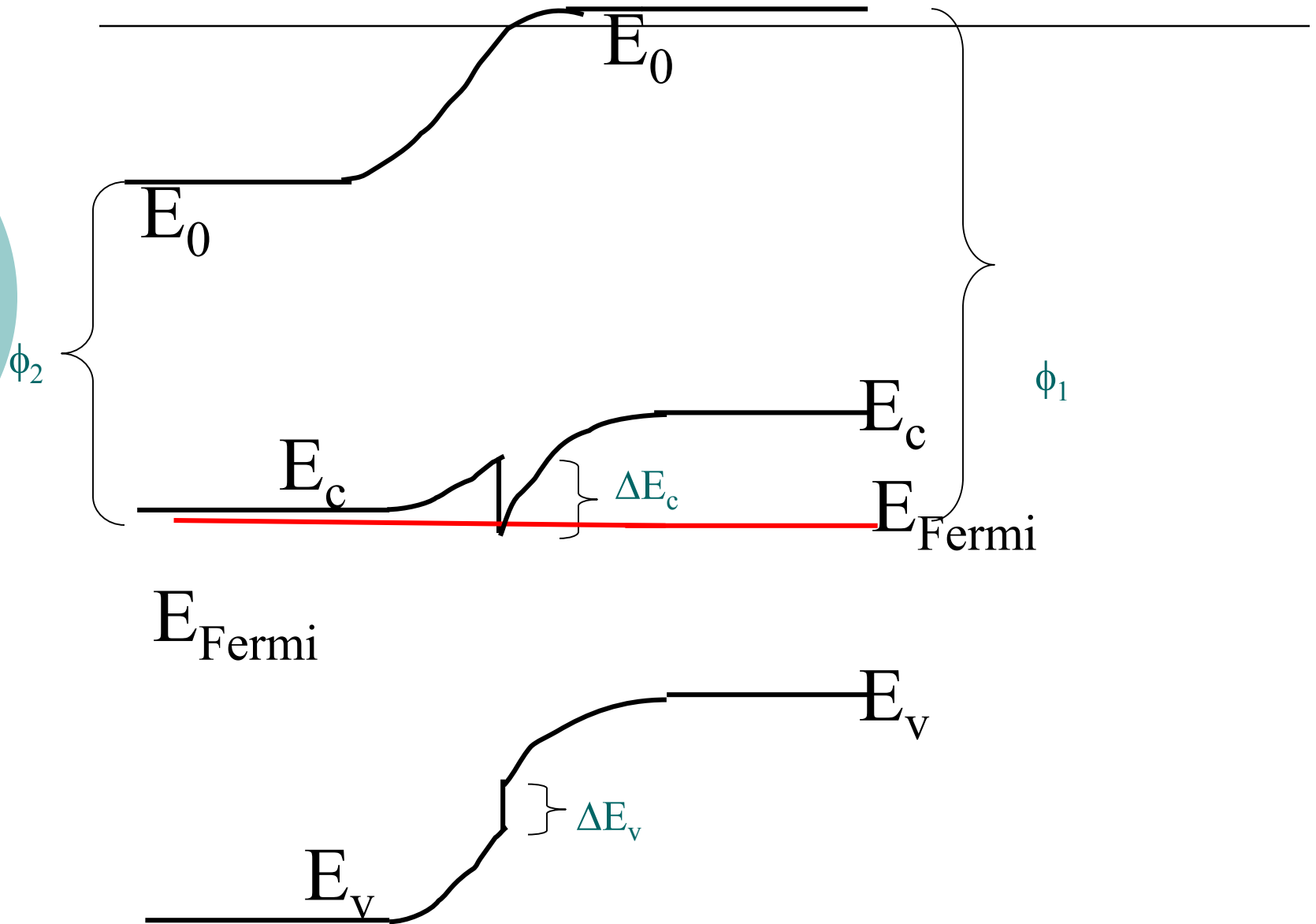
Built in voltage $\phi = \phi_1 - \phi_2$



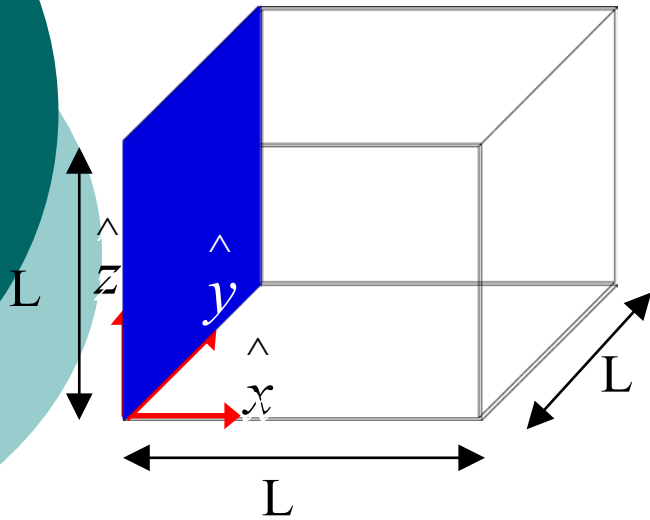
Draw the diagram



2DEG



Particle in a box:



$$\psi(\vec{r}) = (2i)^3 A \cdot \sin(k_{n_x} x) \cdot \sin(k_{n_y} y) \cdot \sin(k_{n_z} z)$$

$$k_{n_x} = n_x \pi / L$$

$$k_{n_y} = n_y \pi / L$$

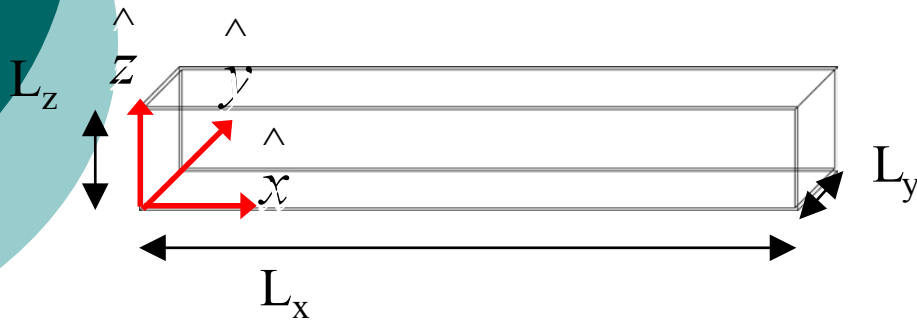
$$k_{n_z} = n_z \pi / L$$

$$E = \frac{\hbar^2 (k_{n_x}^2 + k_{n_y}^2 + k_{n_z}^2)}{2m} = \frac{\hbar^2 (\pi / L)^2}{2m} (n_x^2 + n_y^2 + n_z^2)$$

These are the allowed energy levels, or “quantum states”

Particle in a box

$$\psi(\vec{r}) = (2i)^3 A \cdot \sin(k_{n_x} x) \cdot \sin(k_{n_y} y) \cdot \sin(k_{n_z} z)$$



$$k_{n_x} = n_x \pi / L$$

$$k_{n_y} = n_y \pi / L$$

$$k_{n_z} = n_z \pi / L$$

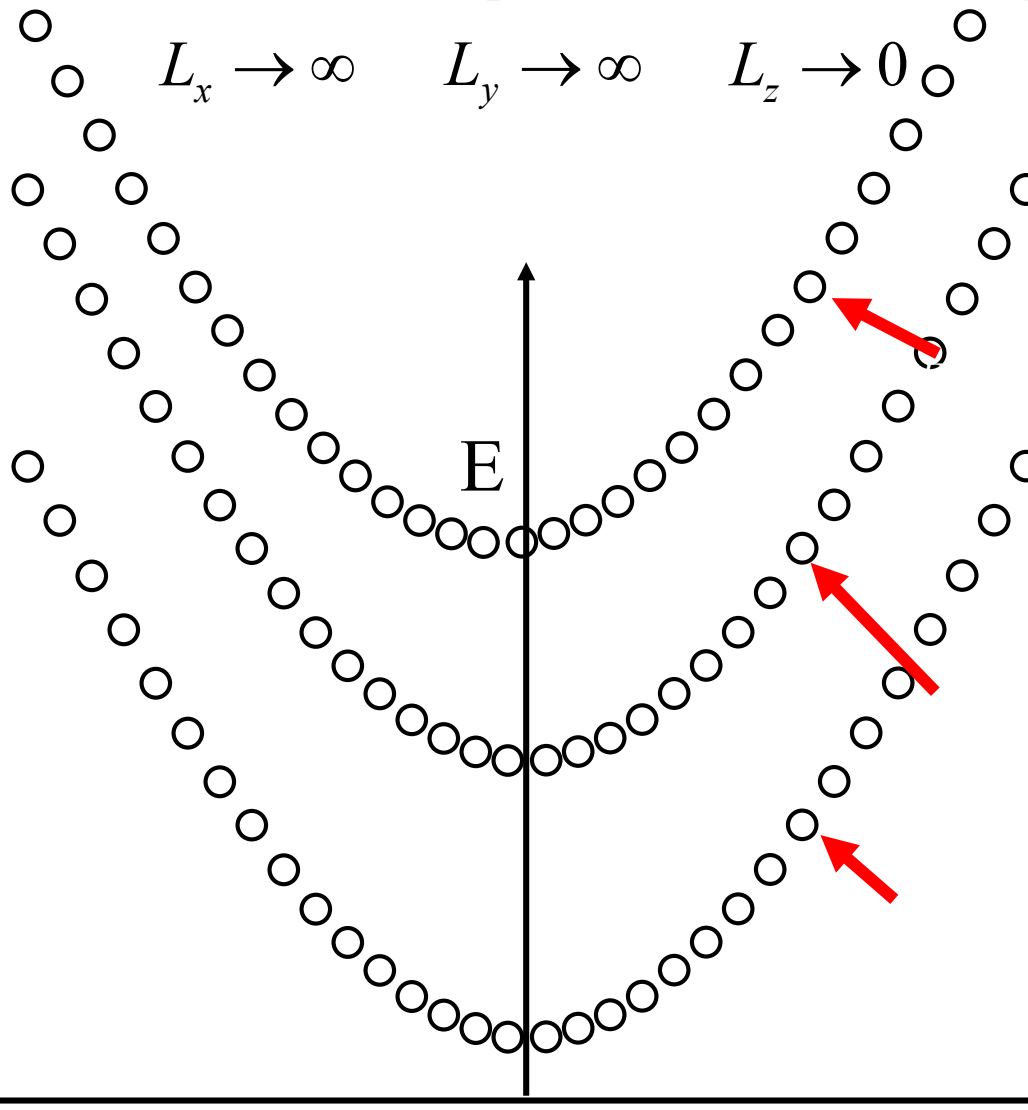
$$E = \frac{\hbar^2 (k_{n_x}^2 + k_{n_y}^2 + k_{n_z}^2)}{2m} = \frac{\hbar^2}{2m} \left[\left(\frac{\pi}{L_x} \right)^2 n_x^2 + \left(\frac{\pi}{L_y} \right)^2 n_y^2 + \left(\frac{\pi}{L_z} \right)^2 n_z^2 \right]$$

These are the allowed energy levels, or “quantum states”

Limit:

$$E = \frac{\hbar^2(k_{n_x}^2 + k_{n_y}^2 + k_{n_z}^2)}{2m} = \frac{\hbar^2}{2m} \left[\left(\frac{\pi}{L_x} \right)^2 n_x^2 + \left(\frac{\pi}{L_y} \right)^2 n_y^2 + \left(\frac{\pi}{L_z} \right)^2 n_z^2 \right]$$

$$L_x \rightarrow \infty \quad L_y \rightarrow \infty \quad L_z \rightarrow 0$$

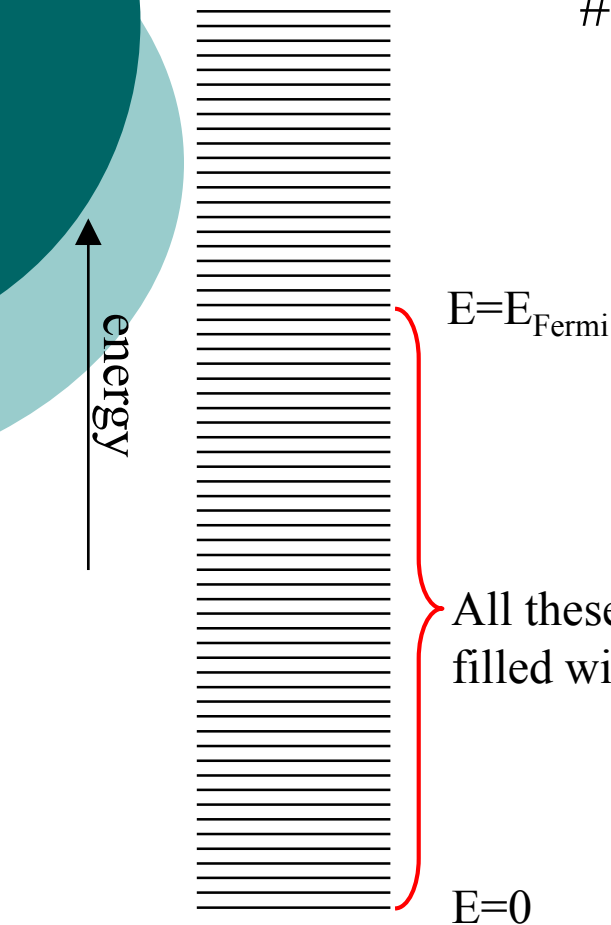


Fermi energy in 3 dimensions

$$\# \text{ electrons} = \int_0^{E_f} N_E dE = \int_0^{E_f} L^3 \frac{2^{1/2} m^{3/2}}{\pi^2 \hbar^{3/2}} \cdot E^{1/2} dE$$

$$\# \text{ electrons} = L^3 \frac{2^{1/2} m^{3/2}}{\pi^2 \hbar^{3/2}} \frac{2}{3} E_f^{3/2}$$

$$\Rightarrow E_f = \frac{\hbar^2 3^{2/3} \pi^{4/3}}{2m} \left(\frac{\# \text{ electrons}}{L^3} \right)^{2/3}$$

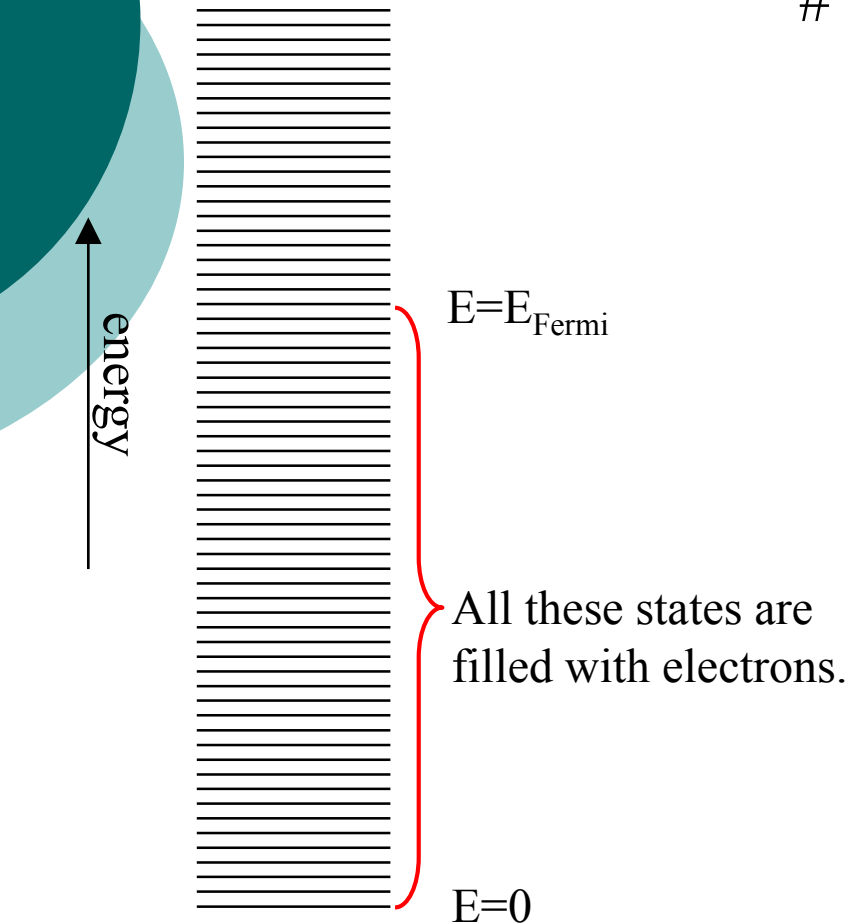


In a typical metal, $L \sim 0.1 \text{ nm}$.

$$E_f \sim 10 \text{ eV}$$

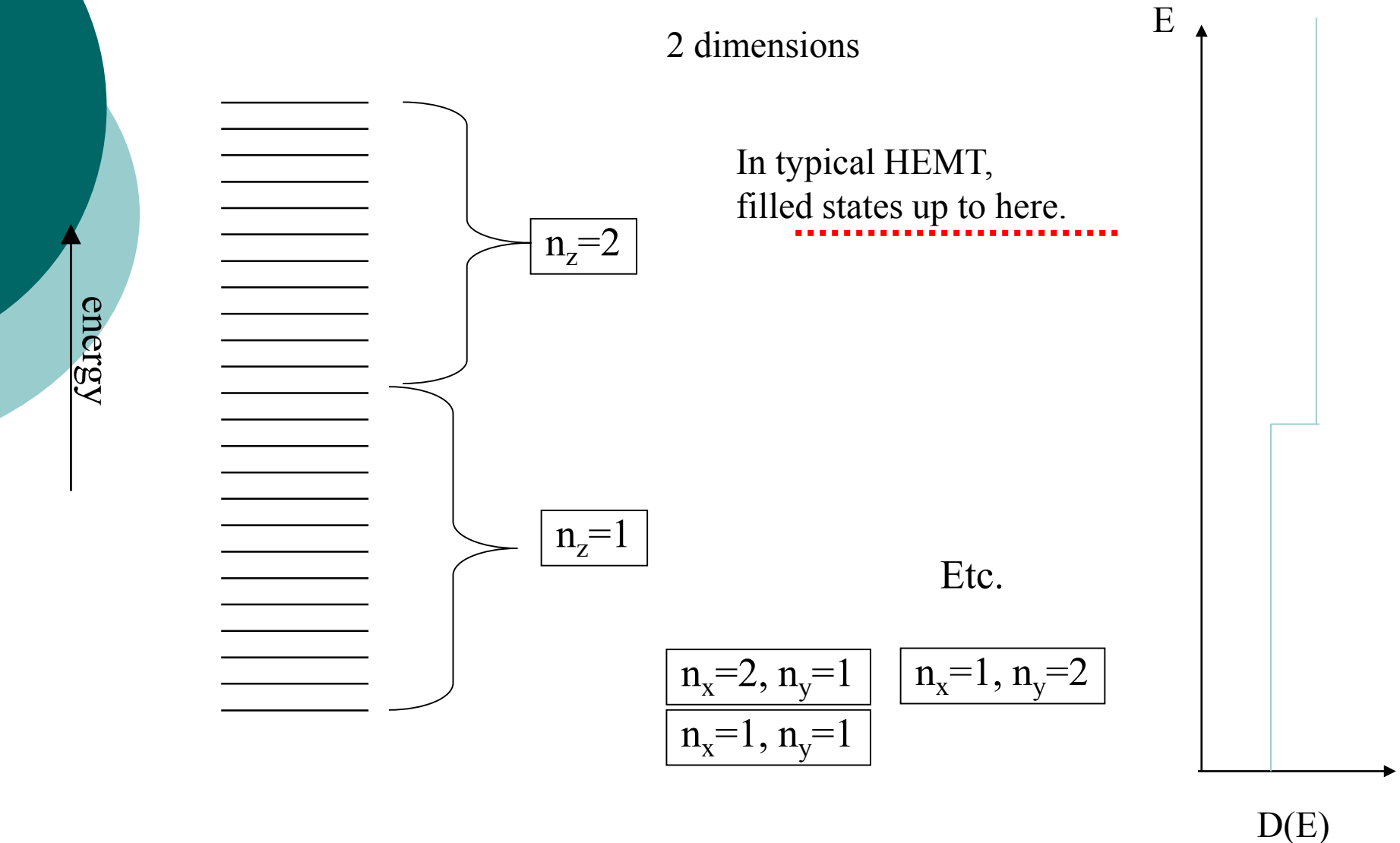
Fermi energy in 2 dimensions

$$\# \text{ electrons} = \int_0^{E_f} N_E f(E) dE = ?$$



Need to evaluate integral numerically, just as in 3d.

Energy spectrum of free particles

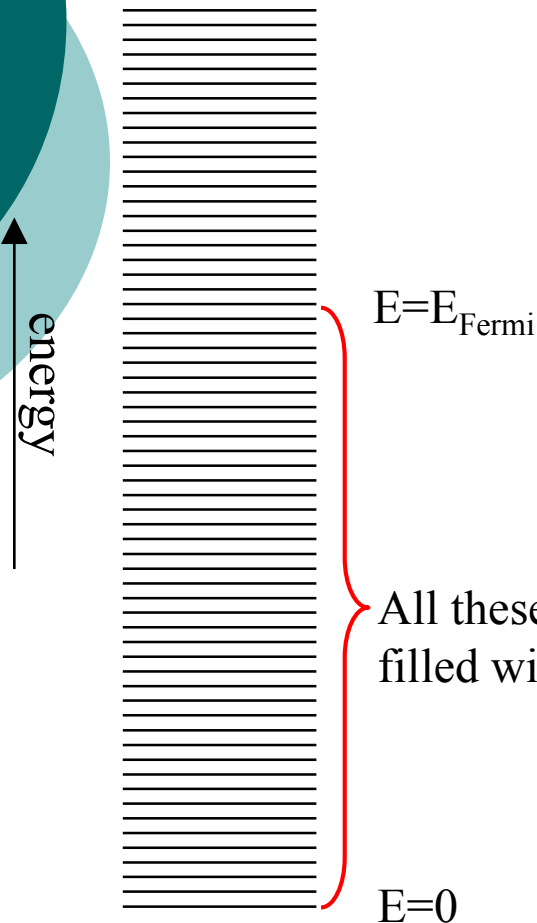


Fermi energy in 2d

$$\# \text{ electrons} = \int_0^{E_f} N_E dE = \int_0^{E_f} L^2 \frac{m}{\pi \hbar} dE$$

$$\# \text{ electrons} = L^2 \frac{m}{\pi \hbar} E_f$$

$$\Rightarrow E_f = \frac{\hbar \pi}{m} \left(\frac{\# \text{ electrons}}{L^2} \right)$$

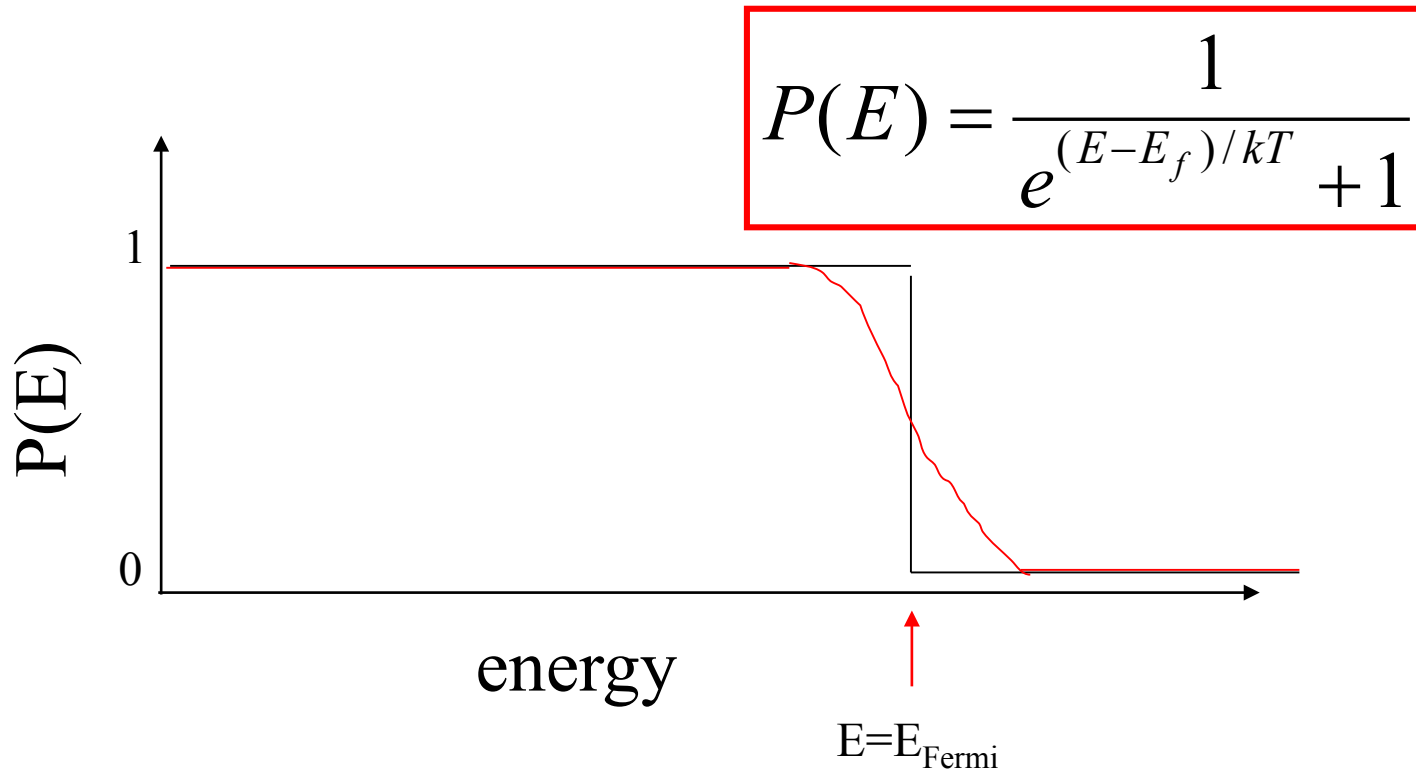


In GaAs, 10^{11}cm^{-2} gives
 $E_f \sim \text{meV}$

But 10^{12}cm^{-2} gives more than first subband.

Discuss “subband”, how above integral gets modified.

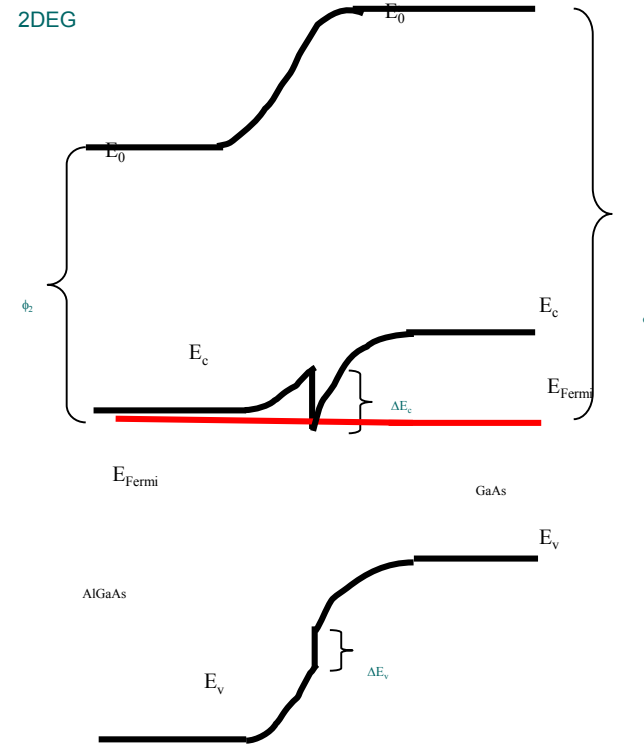
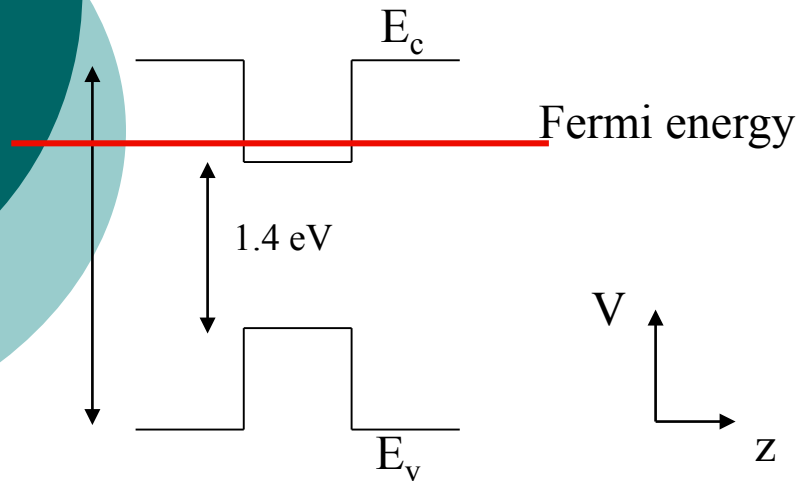
Fermi-Dirac



$P=1/2$ at E_f for all temperatures.

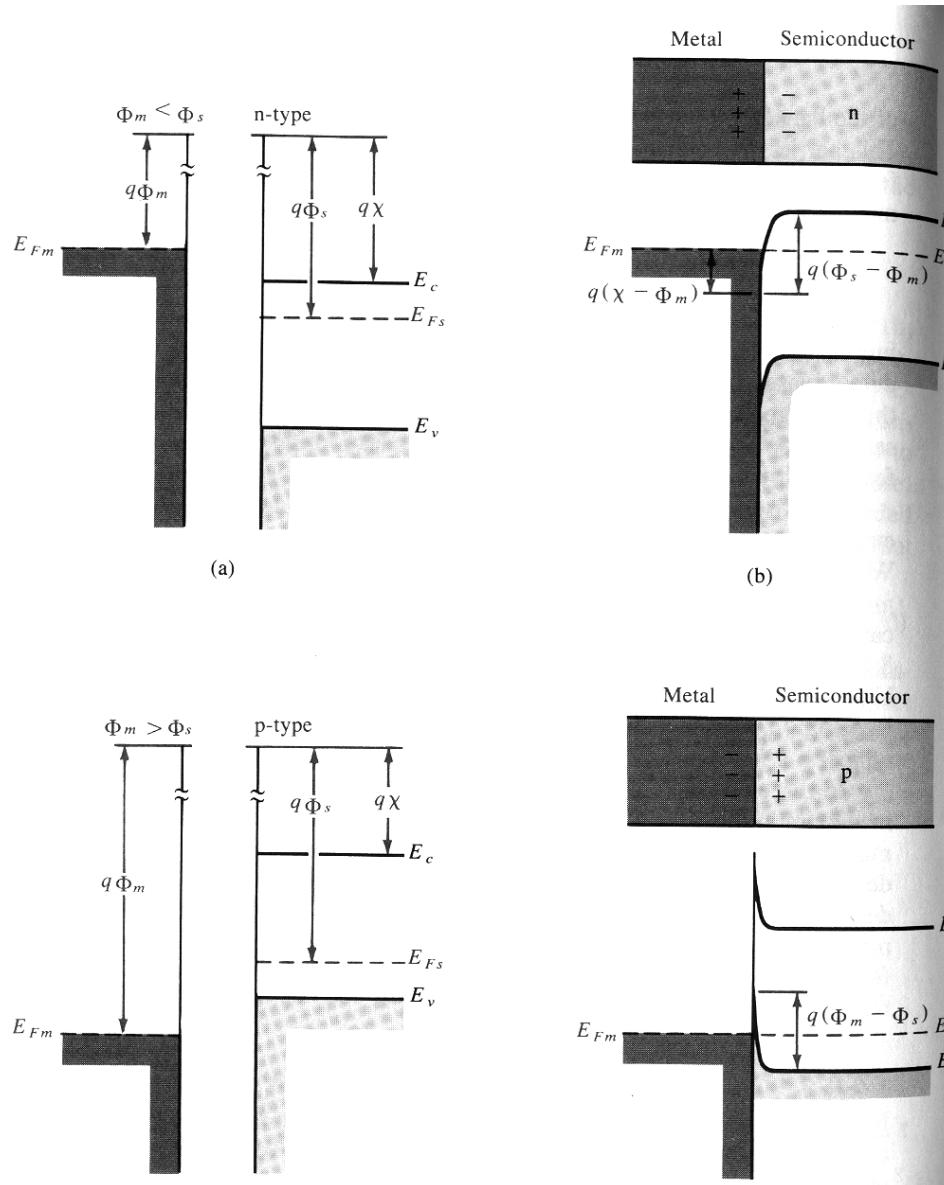
kT

Triangle vs. square well:



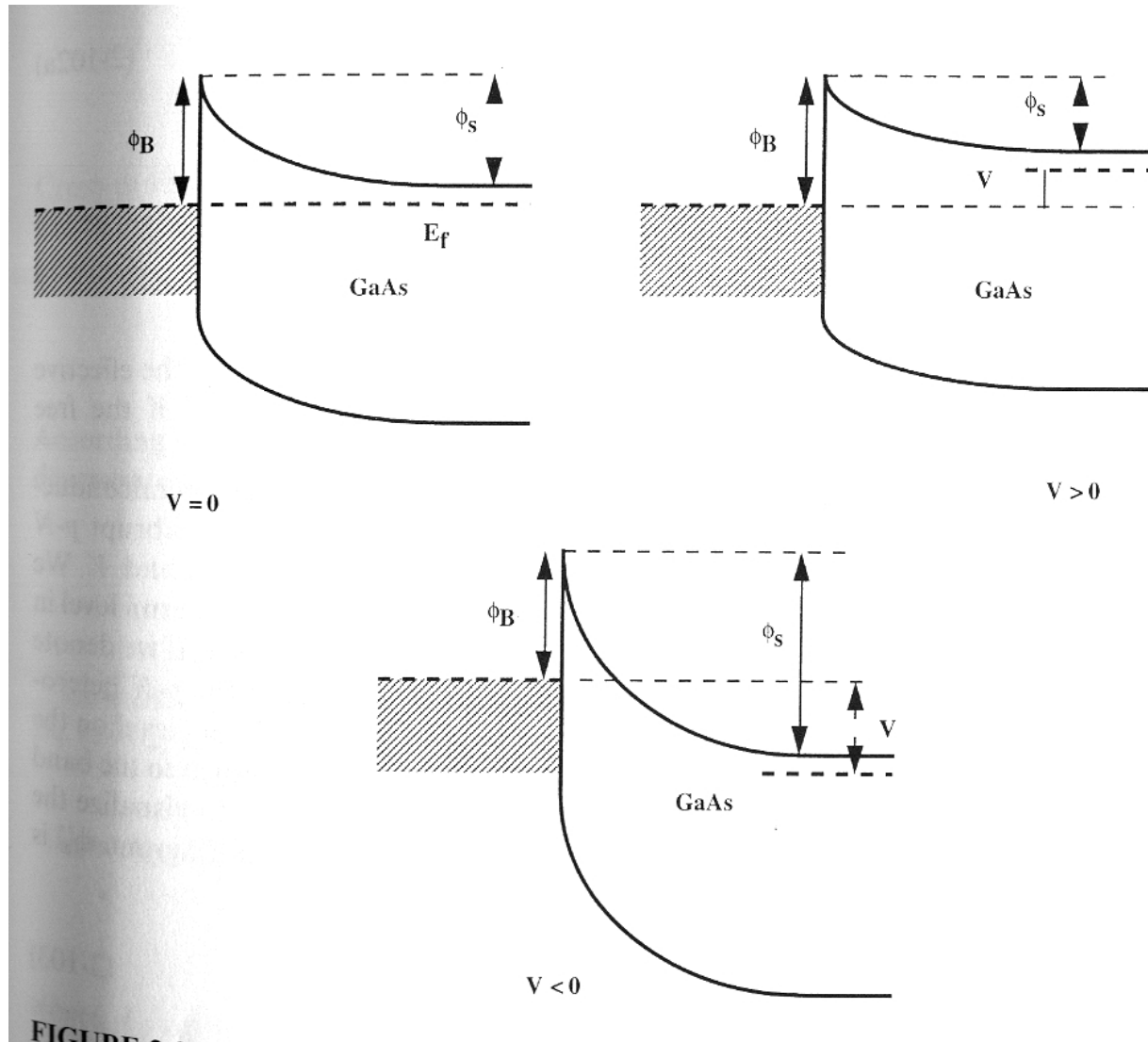
(Draw both bound states on board.
In particular discuss figure 5.21 from Liu.)
Also discuss shallow vs. wide wells on board.
(Typically 100 angstroms works.)
Discuss setback doping, mobility (time permitting).

Schottky barriers



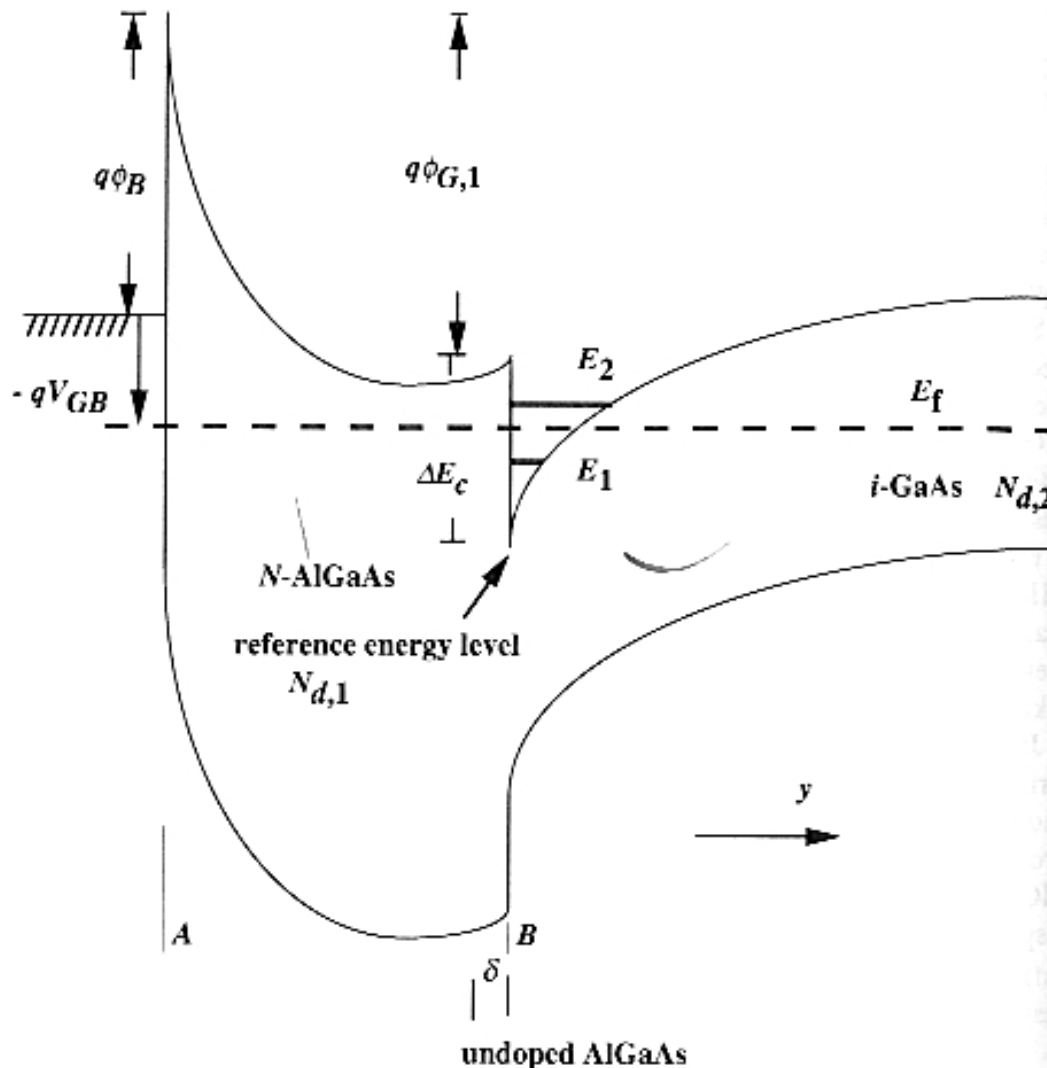
From Streetman

Schottky barriers



From Liu

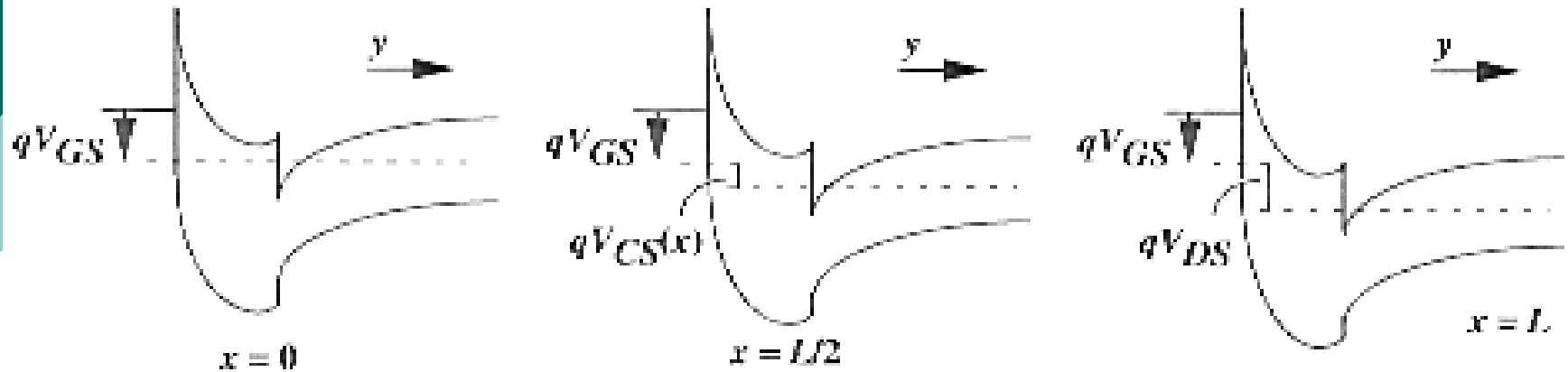
Band diagram



- Bias changes Fermi level
- hence density.
- Can “pinchoff”

From Liu.

Vary gate voltage



Changes Fermi energy which changes density.

(Draw better pictures on board.)

From Liu.

n_s vs E_f

After all that mumbo-jumbo, we know it is complicated.

We approximate it many times as:

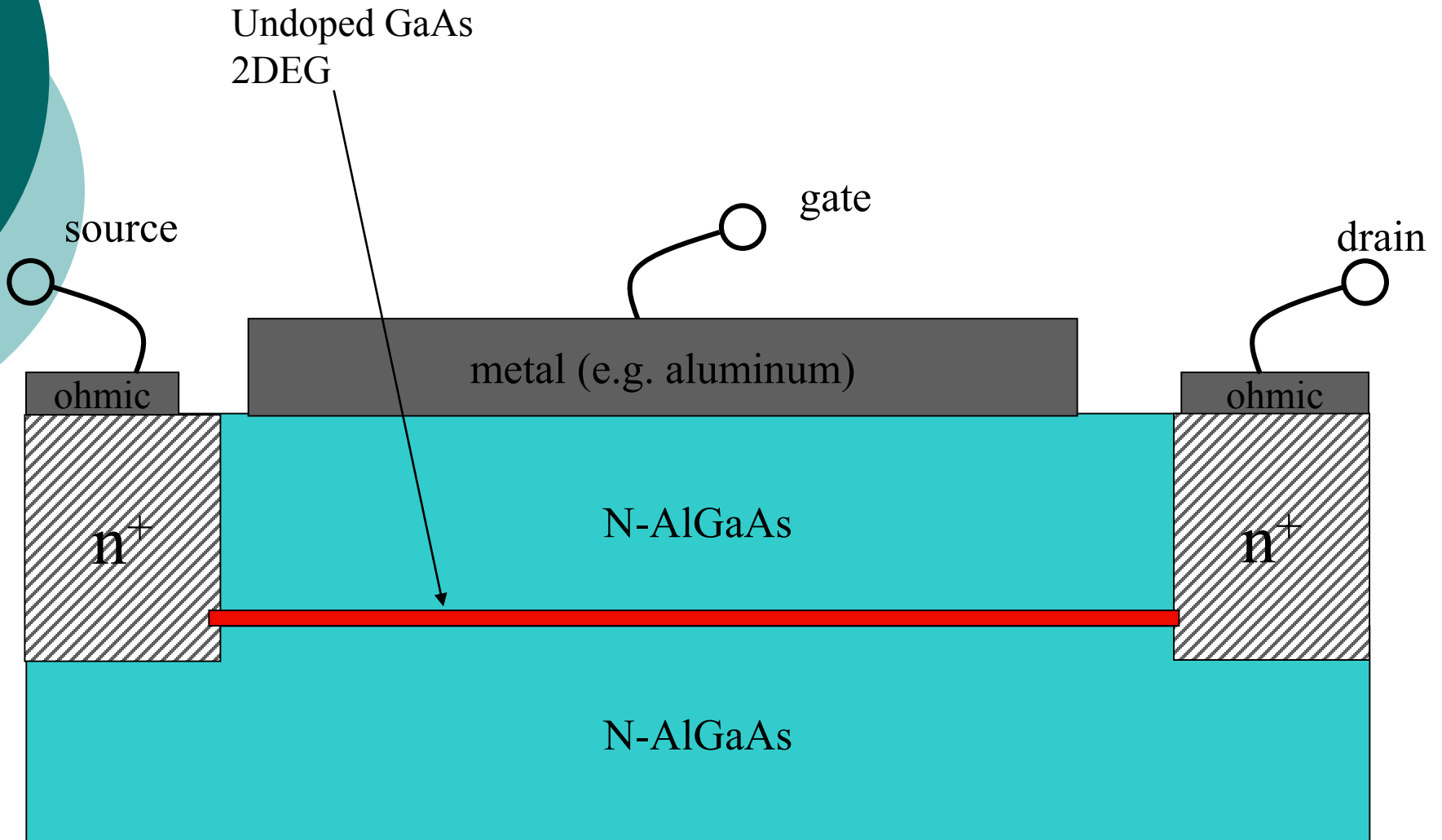
$$E_f(n_s) = E_{f,0} + a \cdot n_s$$

Density

$$en_s = \frac{\varepsilon}{t_b + \varepsilon a / e^2} (V_{GB} - V_T)$$

$$V_T \equiv \phi_B + \frac{E_{f,0}}{e} - \frac{eN_{d,1}}{2\varepsilon} (t_b - \delta)^2 - \frac{\Delta E_c}{e}$$

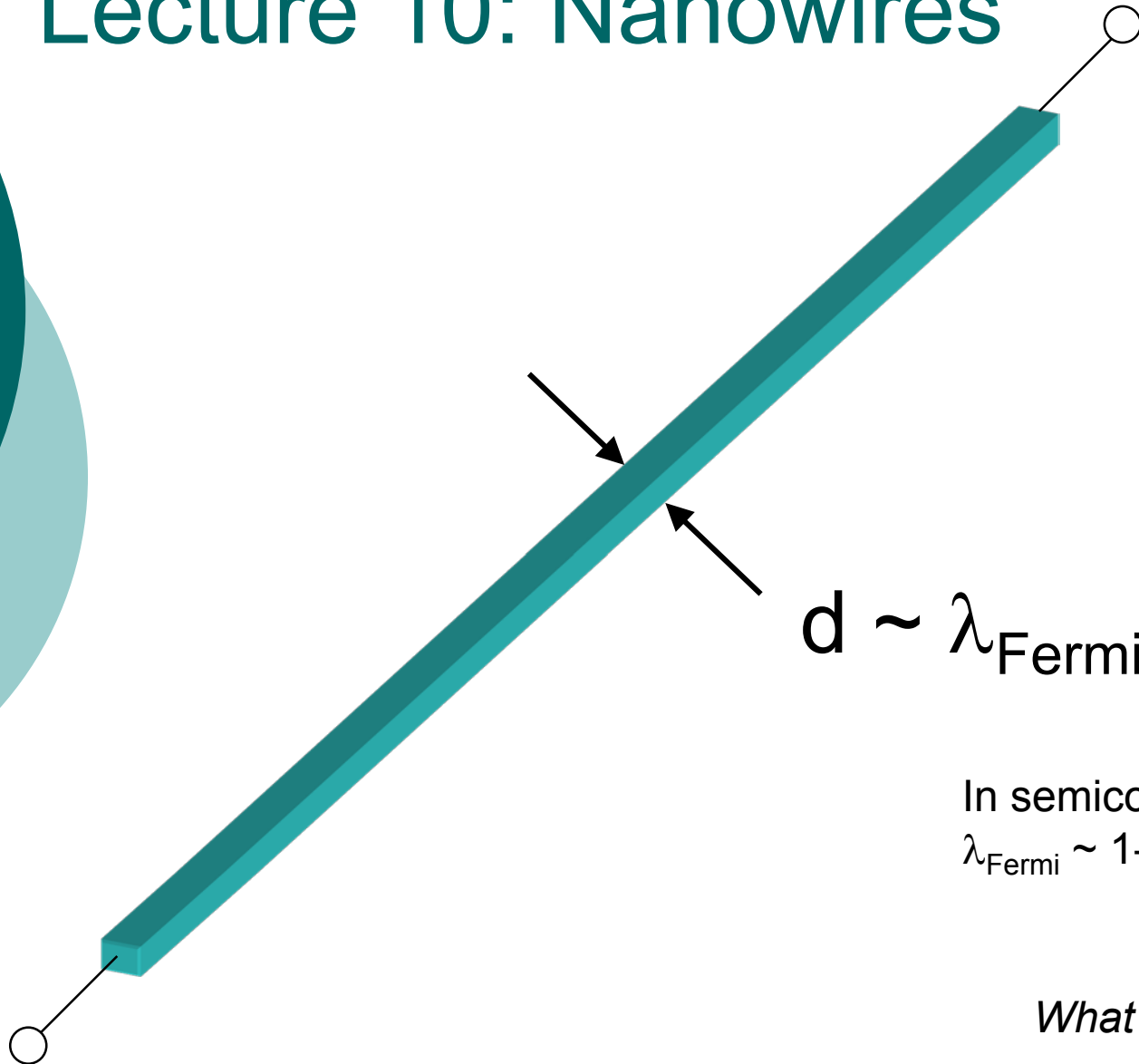
HEMT:



Tunneling

- Resonant tunnel diodes
 - Draw band diagram, I-V on board
 - Fast (> 700 GHz)
- Optical/IR detectors
 - Like photoelectric effect
- Quantum cascade lasers
 - Levels within quantum wells lase

Lecture 10: Nanowires



In semiconductors,
 $\lambda_{\text{Fermi}} \sim 1\text{-}10 \text{ nm}$

What is the resistance?

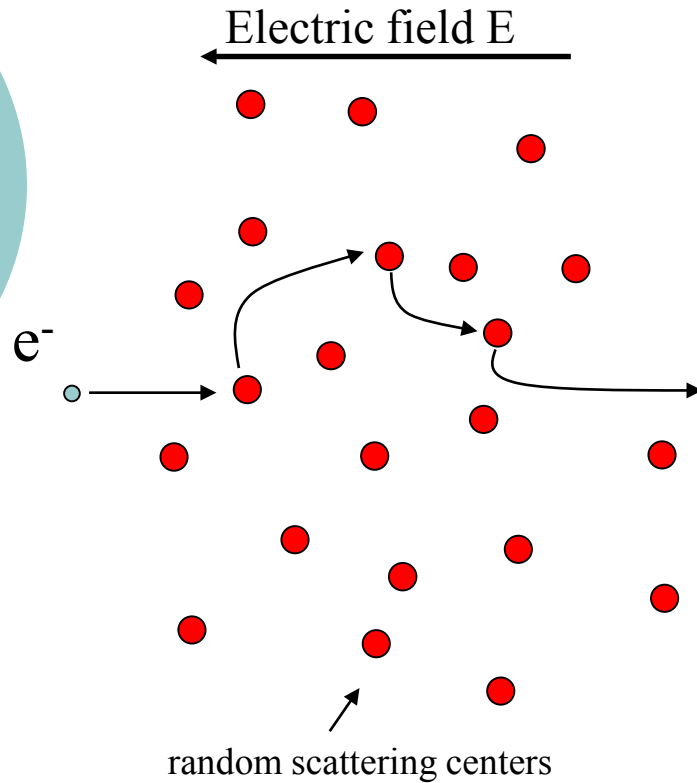
Readings this lecture covers

- Ferry pp. 39-46
- Hanson, pp. 124-125, 317-344

Drift current

- Caused by electric field
- Electron density constant
- Analogy: swarm of mosquitoes in the wind

Drift: Drude model



$$F = ma$$

$$eE = m \frac{\partial v}{\partial t}$$

$$v_{avg} = \underbrace{\frac{e\tau}{m}}_{\mu} E$$

$$j = ne v_{avg} = \underbrace{\frac{ne^2\tau}{m}}_{\sigma} E$$

Types of scattering

Electron-phonon:

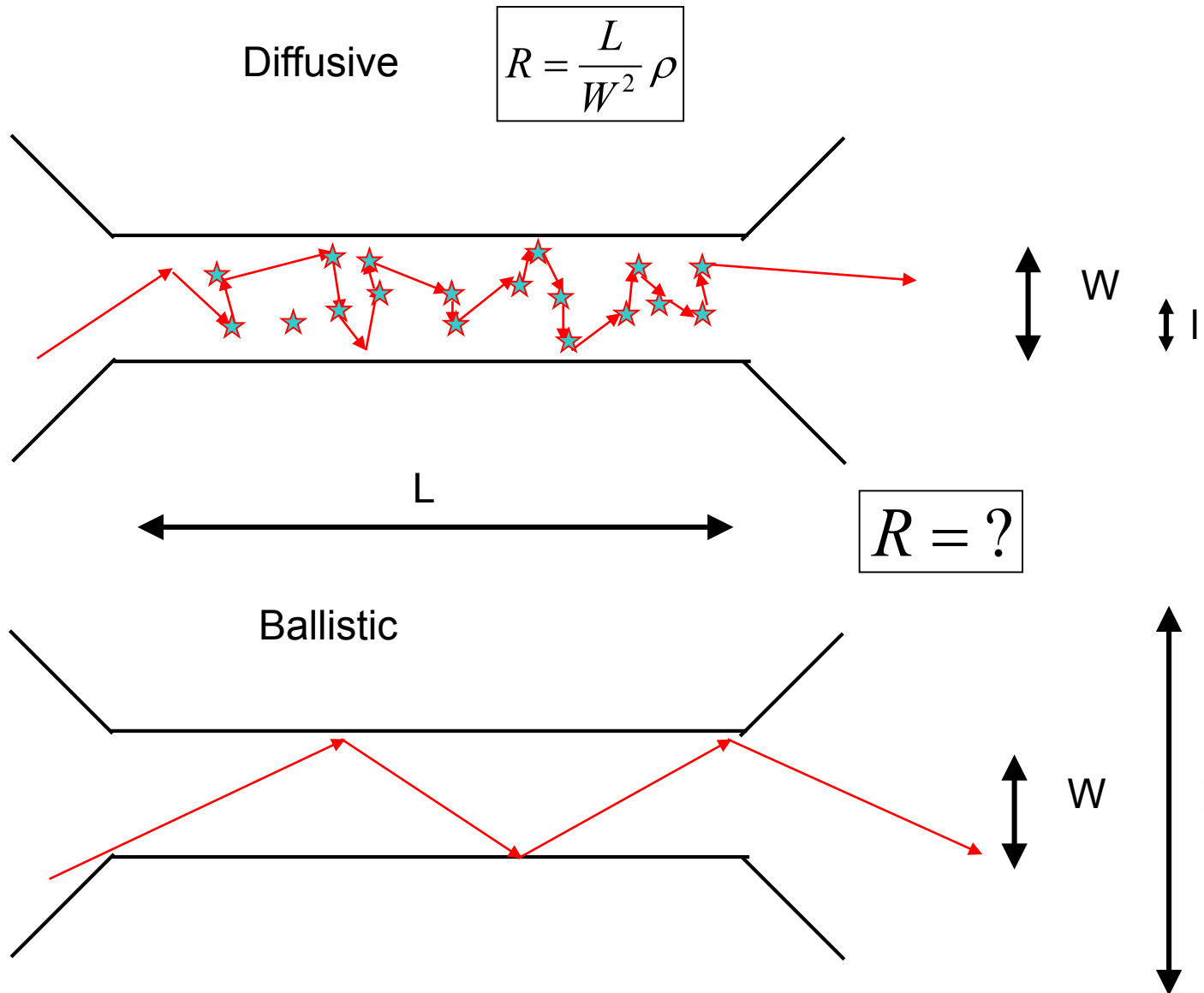
- Very temperature dependent
- Phonons are lattice vibrations
- At low temperatures, lattice is “perfectly still”

○ Impurity scattering

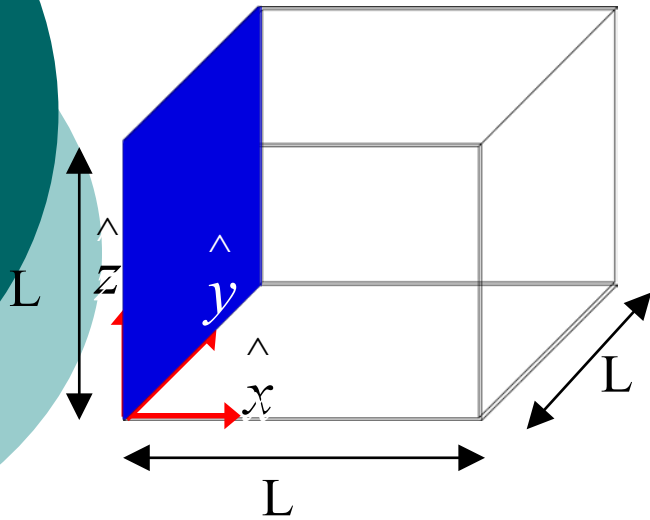
- Temperature independent
- Depends on impurity concentration

$$\frac{1}{\tau_{total}} = \frac{1}{\tau_{electron-phonon}} + \frac{1}{\tau_{impurity}}$$

Ballistic vs. diffusive transport



Particle in a box



$$\psi(\vec{r}) = (2i)^3 A \cdot \sin(k_{n_x} x) \cdot \sin(k_{n_y} y) \cdot \sin(k_{n_z} z)$$

$$k_{n_x} = n_x \pi / L$$

$$k_{n_y} = n_y \pi / L$$

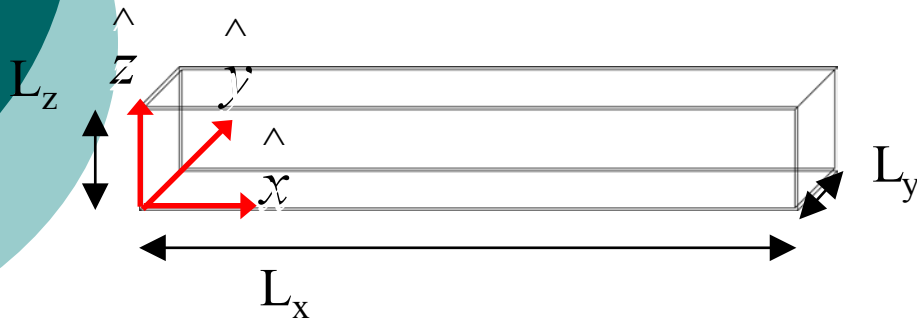
$$k_{n_z} = n_z \pi / L$$

$$E = \frac{\hbar^2 (k_{n_x}^2 + k_{n_y}^2 + k_{n_z}^2)}{2m} = \frac{\hbar^2 (\pi / L)^2}{2m} (n_x^2 + n_y^2 + n_z^2)$$

These are the allowed energy levels, or “quantum states”

Particle in a nanowire

$$\psi(\vec{r}) = (2i)^3 A \cdot \sin(k_{n_x} x) \cdot \sin(k_{n_y} y) \cdot \sin(k_{n_z} z)$$



$$k_{n_x} = n_x \pi / L$$

$$k_{n_y} = n_y \pi / L$$

$$k_{n_z} = n_z \pi / L$$

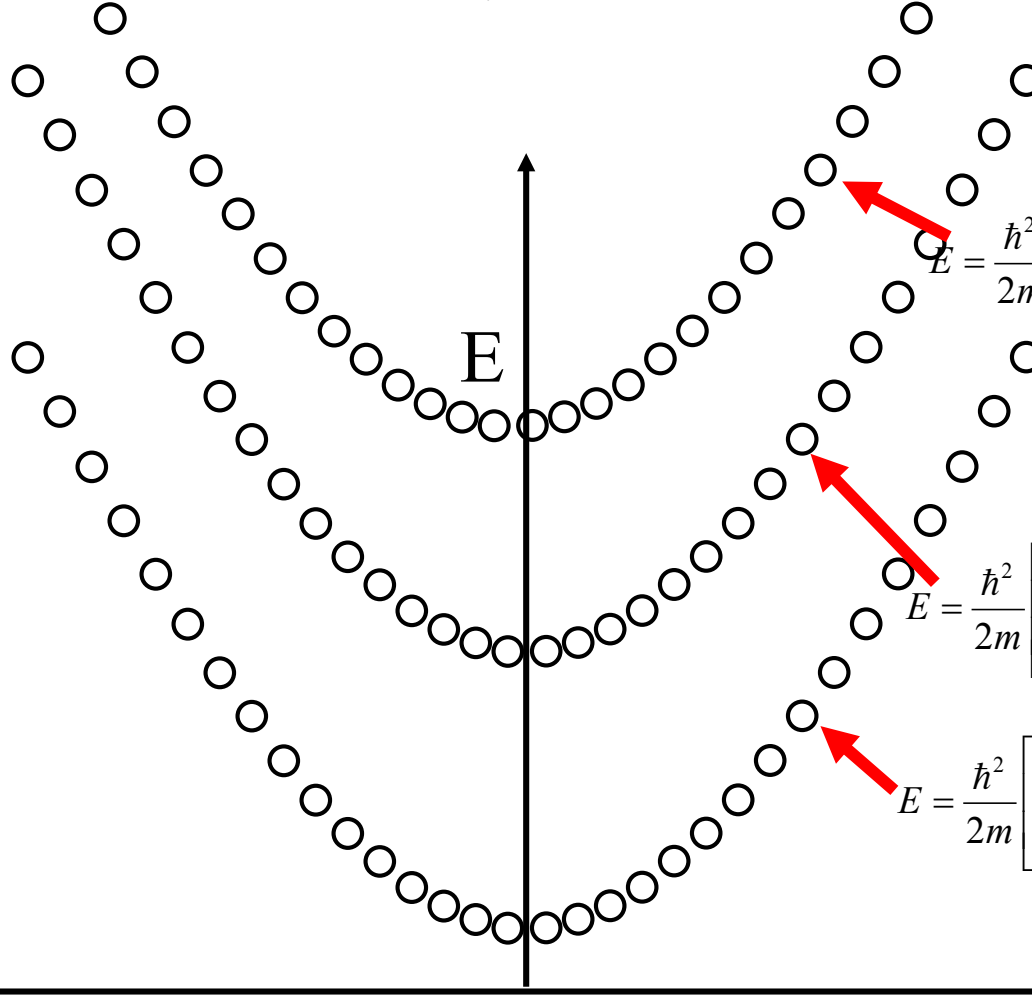
$$E = \frac{\hbar^2 (k_{n_x}^2 + k_{n_y}^2 + k_{n_z}^2)}{2m} = \frac{\hbar^2}{2m} \left[\left(\frac{\pi}{L_x} \right)^2 n_x^2 + \left(\frac{\pi}{L_y} \right)^2 n_y^2 + \left(\frac{\pi}{L_z} \right)^2 n_z^2 \right]$$

These are the allowed energy levels, or “quantum states”

Limits:

$$E = \frac{\hbar^2(k_{n_x}^2 + k_{n_y}^2 + k_{n_z}^2)}{2m} = \frac{\hbar^2}{2m} \left[\left(\frac{\pi}{L_x} \right)^2 n_x^2 + \left(\frac{\pi}{L_y} \right)^2 n_y^2 + \left(\frac{\pi}{L_z} \right)^2 n_z^2 \right]$$

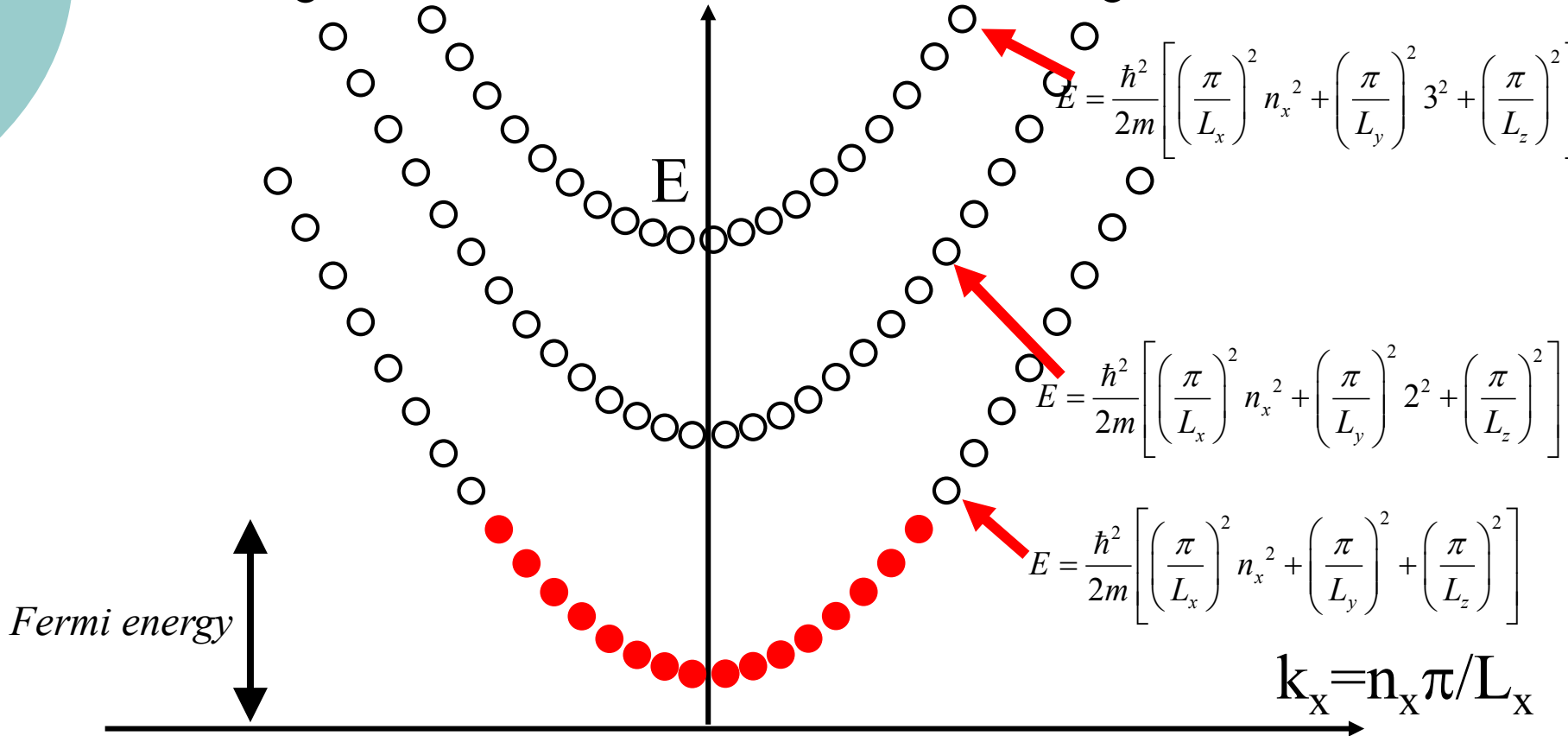
$$L_x \rightarrow \infty \quad L_y \rightarrow 0 \quad L_z \rightarrow 0$$



1d system:

$$E = \frac{\hbar^2(k_{n_x}^2 + k_{n_y}^2 + k_{n_z}^2)}{2m} = \frac{\hbar^2}{2m} \left[\left(\frac{\pi}{L_x} \right)^2 n_x^2 + \left(\frac{\pi}{L_y} \right)^2 n_y^2 + \left(\frac{\pi}{L_z} \right)^2 n_z^2 \right]$$

$$L_x \rightarrow \infty \quad L_y \rightarrow 0 \quad L_z \rightarrow 0$$



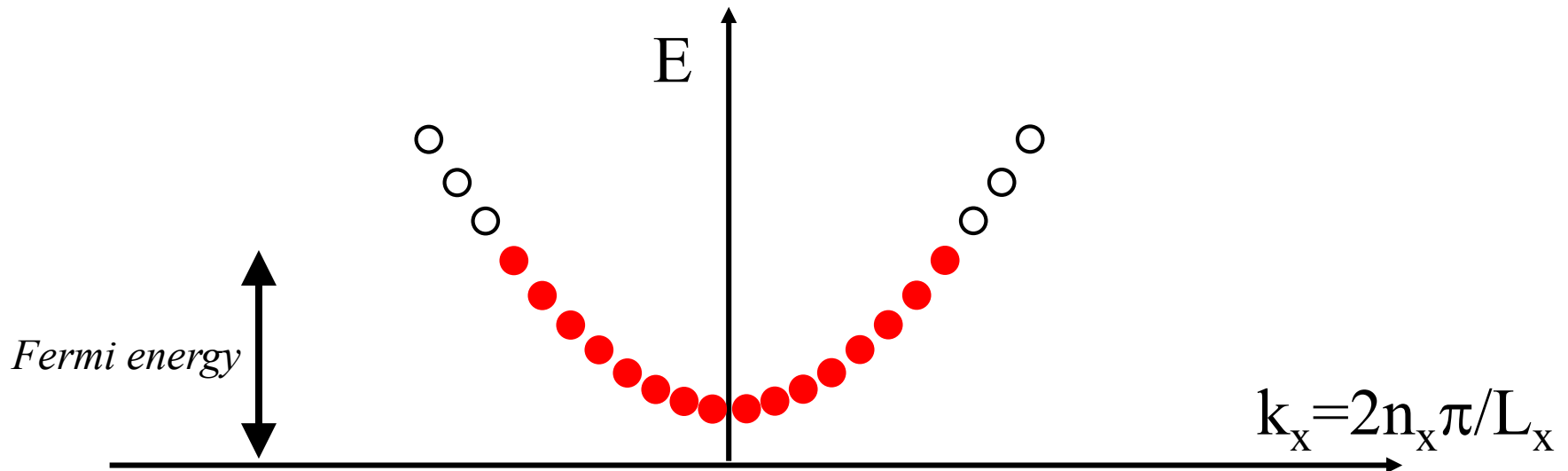
Positive and negative k-vectors:

Particle in a box: (positive k-vectors only)

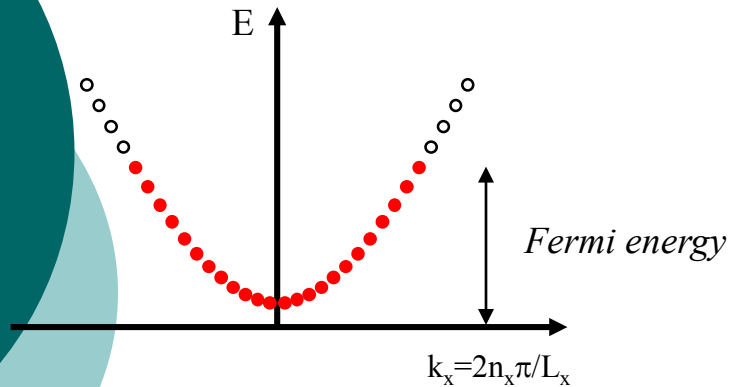
$$E = \frac{\hbar^2(k_{n_x}^2 + k_{n_y}^2 + k_{n_z}^2)}{2m} = \frac{\hbar^2}{2m} \left[\left(\frac{\pi}{L_x} \right)^2 n_x^2 + \left(\frac{\pi}{L_y} \right)^2 n_y^2 + \left(\frac{\pi}{L_z} \right)^2 n_z^2 \right]$$

“Born-Von Karman” boundary conditions: (positive *and* negative k-vectors)

$$E = \frac{\hbar^2}{2m} \left[\left(\frac{2\pi}{L_x} \right)^2 n_x^2 + \left(\frac{2\pi}{L_y} \right)^2 n_y^2 + \left(\frac{2\pi}{L_z} \right)^2 n_z^2 \right]$$



Single sub-band:



$$I = \frac{\text{charge}}{\text{time}} = e \cdot \frac{\#\text{elec}}{\text{time}} = e \cdot v \frac{\#\text{elec}}{\text{length}}$$

Different electrons have different velocities.

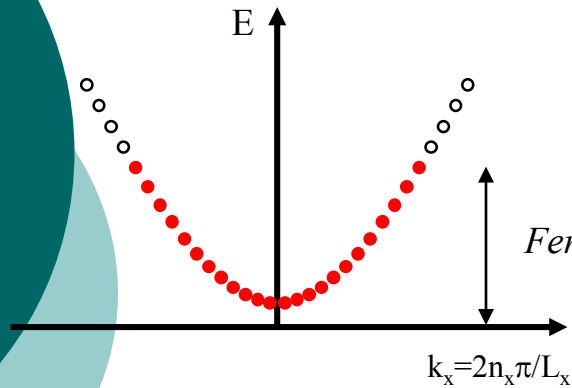
$$v = \frac{\text{momentum}}{\text{mass}} = \frac{p}{m} = \frac{\hbar k}{m}$$

$$I = I_{\text{right goers}} - I_{\text{left goers}}$$

$$I_{\text{right goers}} = \sum_{\text{right going electrons}} e v \frac{1}{\text{length}} = \sum_{\text{occupied states (right goers)}} e v \frac{1}{\text{length}}$$

$$I_{\text{right goers}} = \frac{e}{L_x} \sum_{k_x=0}^{k_F} \frac{\hbar k_x}{m} = \frac{e}{L_x} \sum_{n_x=0}^{n_F} \frac{\hbar (n_x 2\pi / L_x)}{m} = \frac{e 2\pi \hbar}{m L_x^2} \sum_{n_x=0}^{n_F} n_x$$

Single sub-band:



$$I_{\text{right goes}} = \frac{e2\pi\hbar}{mL_x^2} \sum_{n_x=0}^{n_F} n_x \rightarrow \frac{e2\pi\hbar}{mL_x^2} \int_0^{n_F} n_x dn_x$$

Change of variables:

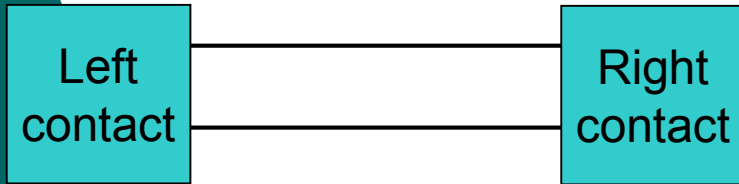
$$E = \frac{\hbar^2 k_x^2}{2m} = \frac{\hbar^2 (2n_x \pi / L_x)^2}{2m} \Rightarrow dE = \frac{4\hbar^2 (\pi / L_x)^2}{m} n_x dn_x$$

$$\Rightarrow n_x dn_x = \frac{m}{4\hbar^2 (\pi / L_x)^2} dE$$

$$I_{\text{right goes}} = \frac{e\pi\hbar}{2mL_x^2} \int_0^{n_F} n_x dn_x \rightarrow \frac{e\pi\hbar}{2mL_x^2} \frac{m}{\hbar^2 (\pi / L_x)^2} \int dE = \frac{e}{h} \int dE$$

Resistance quantum

Ballistic conductor



$$I_{\text{right goes}} = \frac{e}{h} \int dE \quad I_{\text{right goes}} = \frac{e}{h} \int dE$$

$$I = \frac{e}{h} \left[\int dE_{\text{right goes}} - \int dE_{\text{left goes}} \right]$$

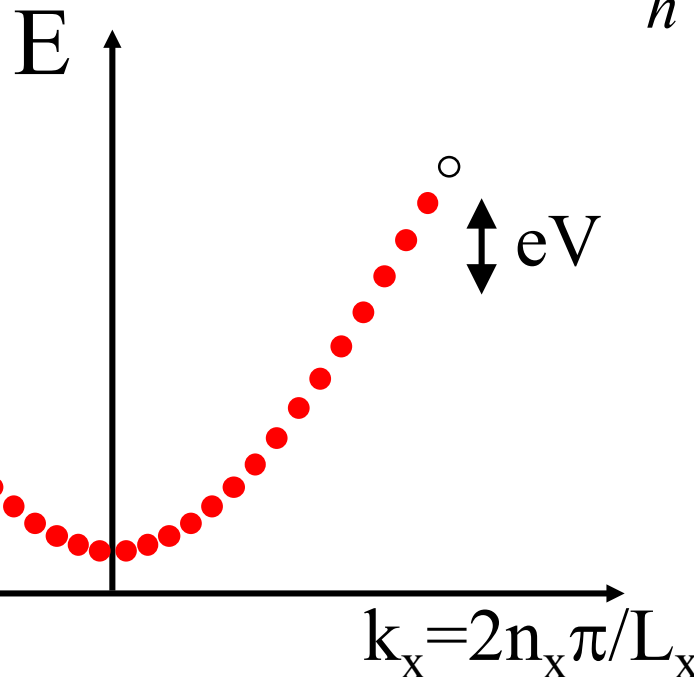
$$I = \frac{e}{h} [(E_F + eV) - E_F] = \frac{e^2}{h} V$$

$$V = I \frac{h}{e^2} = IR_{\text{quantum}}$$

$$R_{\text{quantum}} = \frac{h}{e^2} = 25 \text{ k}\Omega$$

With spin:

$$R_{\text{quantum}} = \frac{h}{2e^2} = 12.5 \text{ k}\Omega$$



Fermi energy

Lecture 11: Quantum point contact

Resistance is independent of length.



The diagram shows a long, thin, teal-colored rectangular bar representing a quantum point contact. The bar is oriented diagonally from the bottom-left to the top-right. At each end of the bar, there is a small white circle connected to the bar by a thin black line, representing electrical contacts. Two black arrows point towards the bar from the right side, indicating its width. To the left of the bar, there are two overlapping circular shapes, one dark teal and one light teal, representing gates or electrodes. The text 'Resistance is independent of length.' is written in italics above the bar. The equation $d \sim \lambda_{\text{Fermi}}$ is written to the right of the bar, with two arrows pointing to the width of the bar. A red-bordered box at the bottom right contains the equation $R_{\text{quantum}} = \frac{h}{2e^2} = 12.5 \text{ k}\Omega$.

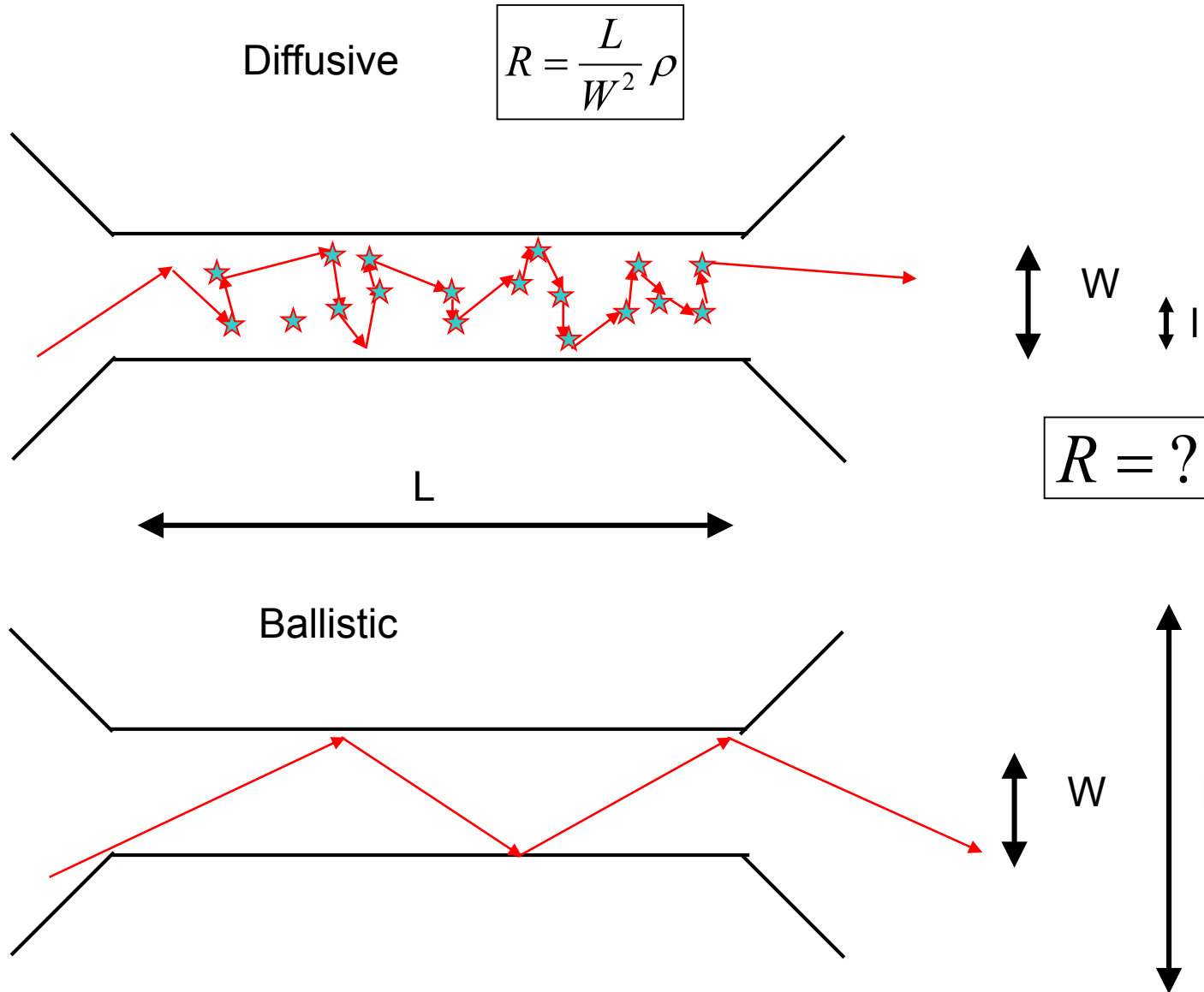
$$d \sim \lambda_{\text{Fermi}}$$

$$R_{\text{quantum}} = \frac{h}{2e^2} = 12.5 \text{ k}\Omega$$

Readings this lecture covers

- Ferry pp. 124-139
- Van Wees PRL (reading packet)
- Marcus APL (reading packet)
- Zhou APL (reading packet)

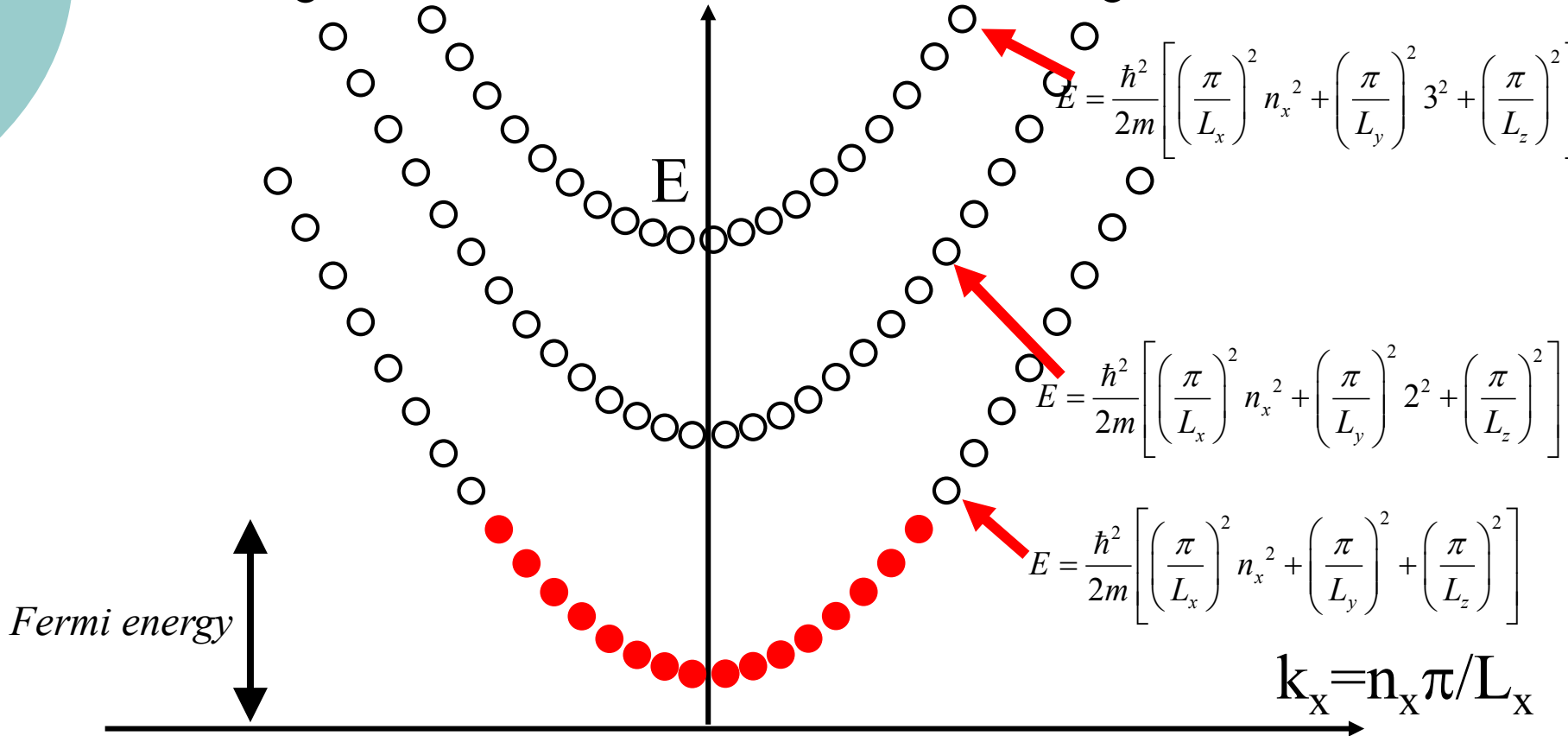
Ballistic vs. diffusive transport



1d system:

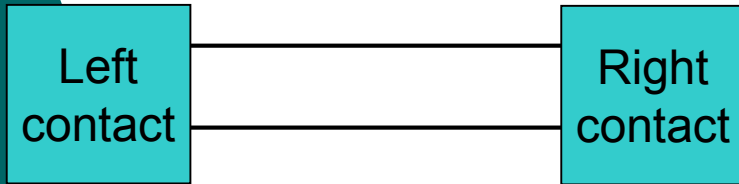
$$E = \frac{\hbar^2(k_{n_x}^2 + k_{n_y}^2 + k_{n_z}^2)}{2m} = \frac{\hbar^2}{2m} \left[\left(\frac{\pi}{L_x} \right)^2 n_x^2 + \left(\frac{\pi}{L_y} \right)^2 n_y^2 + \left(\frac{\pi}{L_z} \right)^2 n_z^2 \right]$$

$$L_x \rightarrow \infty \quad L_y \rightarrow 0 \quad L_z \rightarrow 0$$



Resistance quantum

Ballistic conductor



$$R_{\text{quantum}} = \frac{h}{e^2} = 25 \text{ k}\Omega$$

With spin:

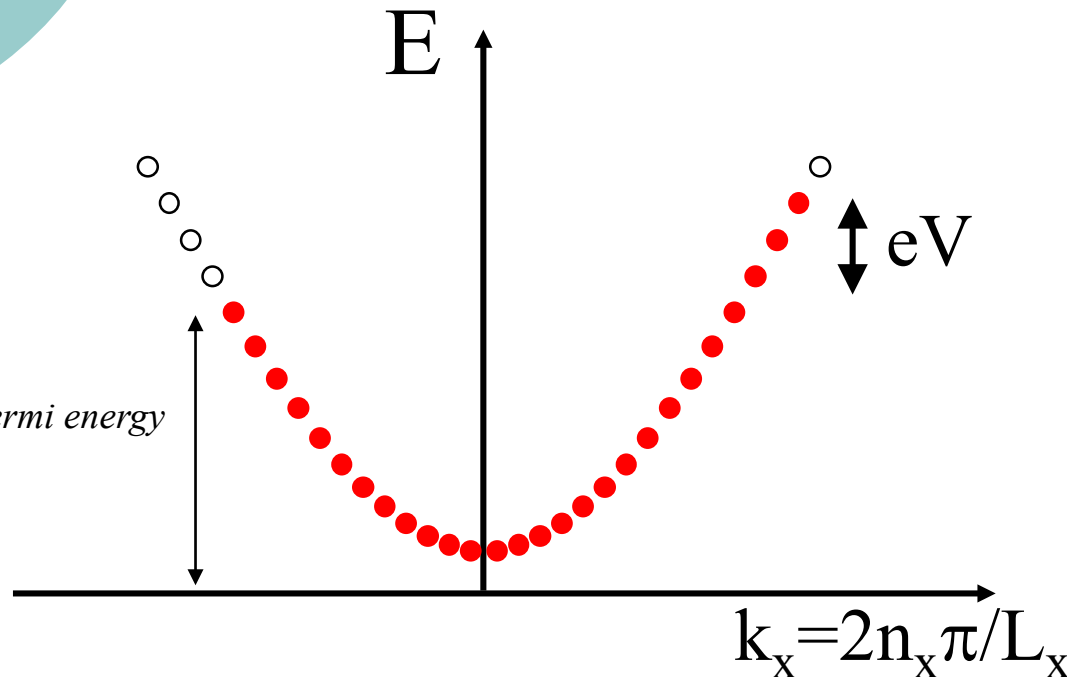
$$R_{\text{quantum}} = \frac{h}{2e^2} = 12.5 \text{ k}\Omega$$

$$G_{\text{quantum}} = \frac{2e^2}{h}$$

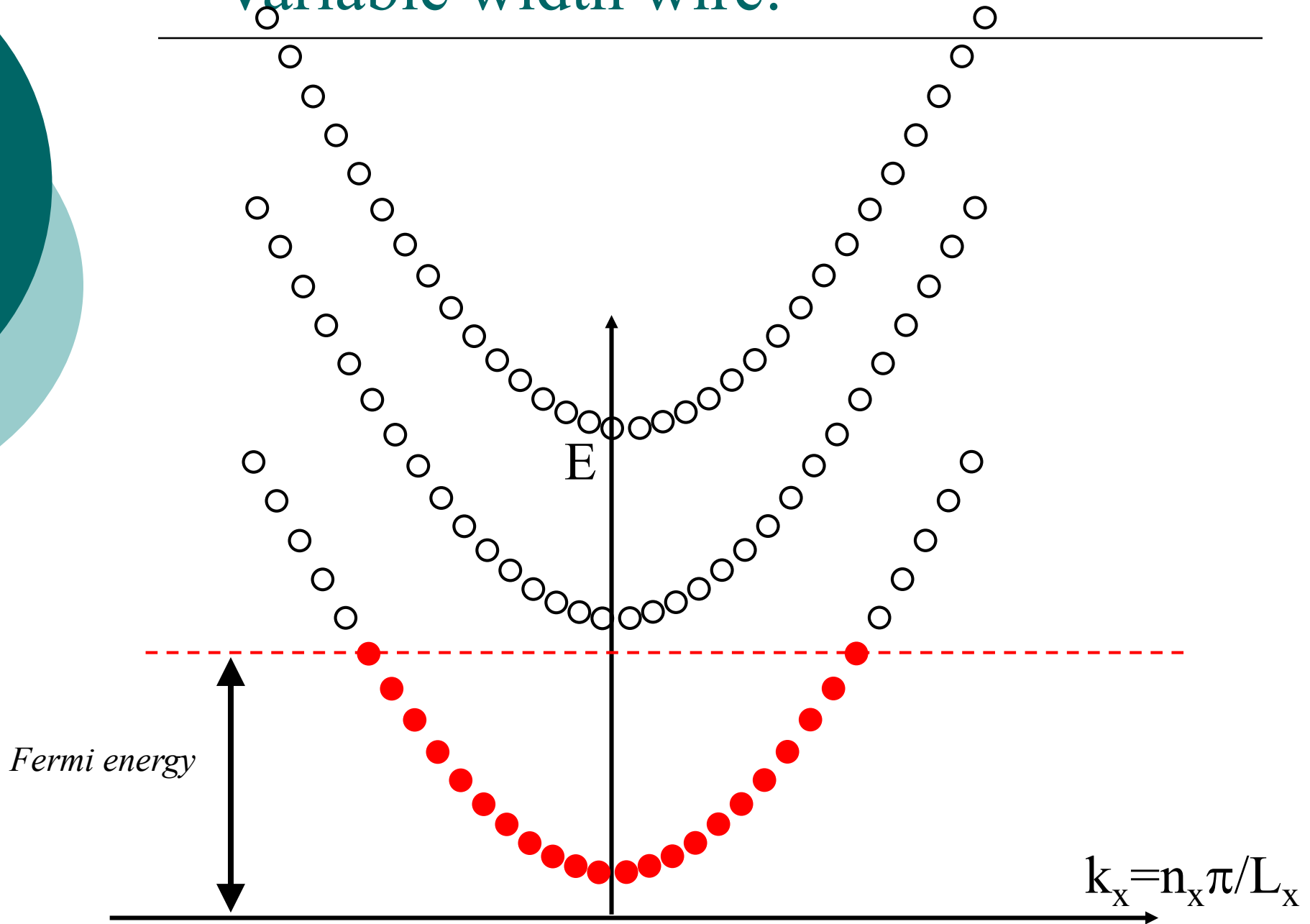
If injection from leads is not perfect:

$$G = T \frac{2e^2}{h}$$

T is the transmission probability.



Variable width wire:



Landauer formula:

$$G = n \frac{2e^2}{h}$$

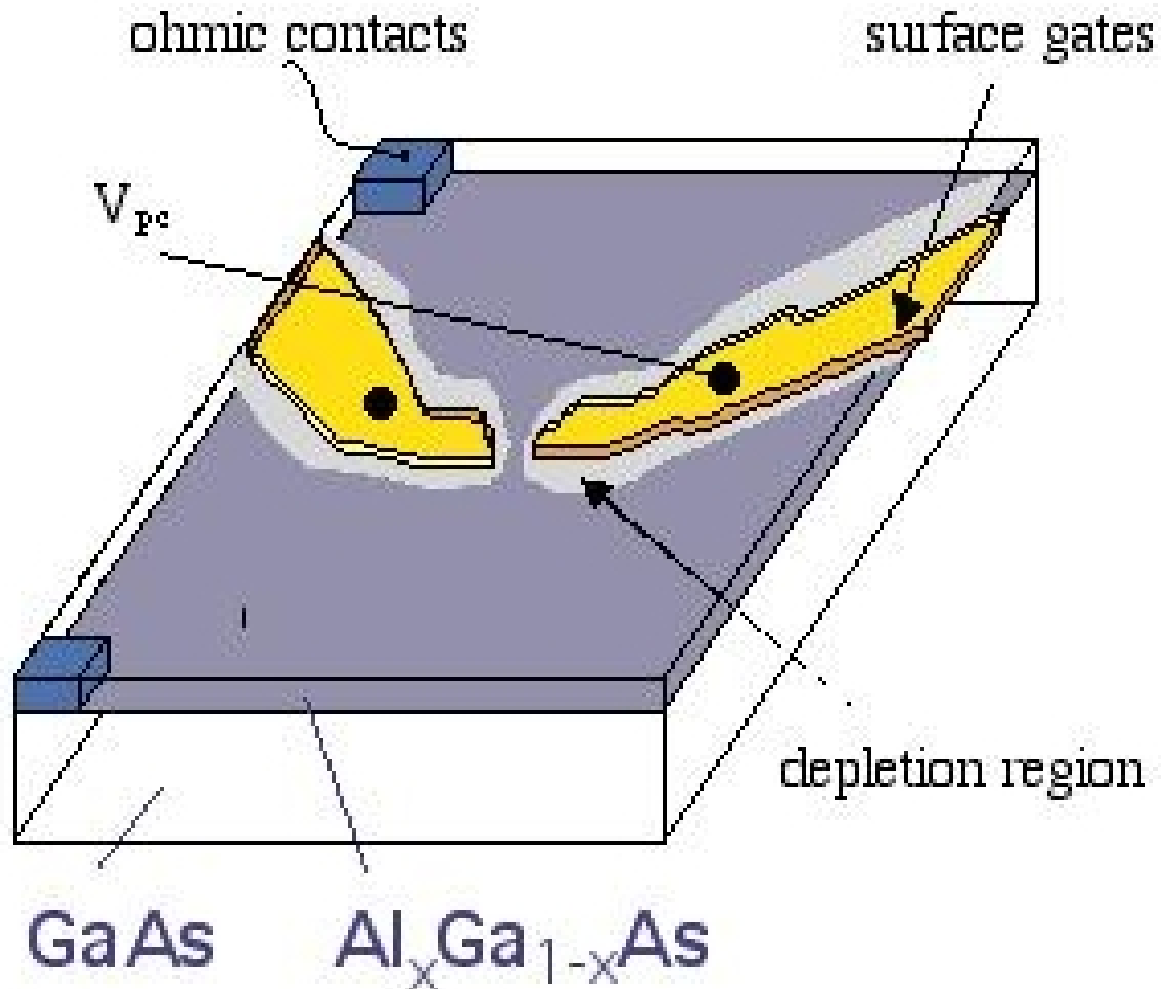
If the leads are not perfect injectors into each “channel” then:

$$G = \frac{2e^2}{h} \sum T_n$$

Experimental realizations:

- Pinch-off gate in semiconductor 2DEG (QPC)
- Break junction
- Electrochemical addition of atoms
- Scanning tunneling microscope

Quantum point contact



Quantum point contact

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PHYSICAL REVIEW LETTERS

29 FEBRUARY 1988

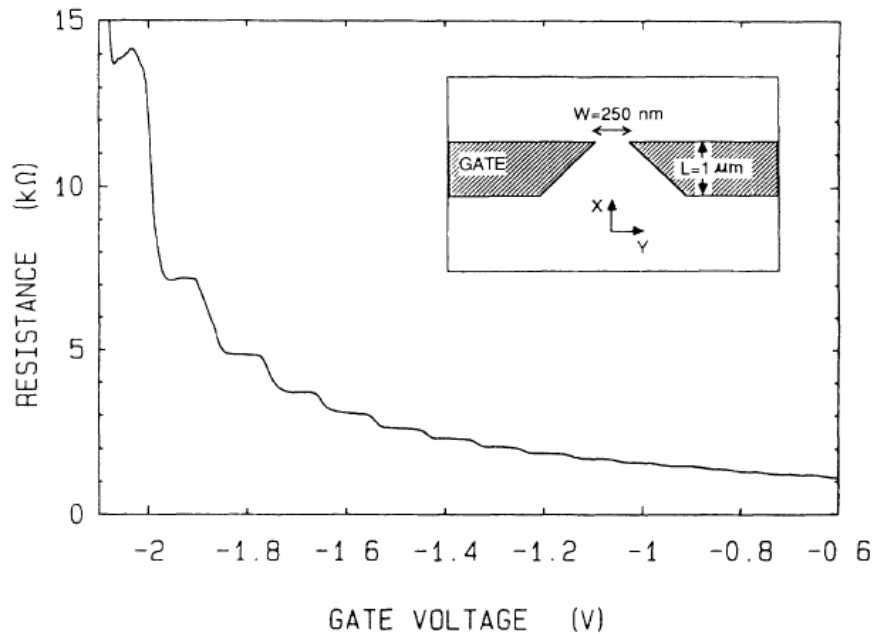


FIG. 1. Point-contact resistance as a function of gate voltage at 0.6 K. Inset: Point-contact layout.

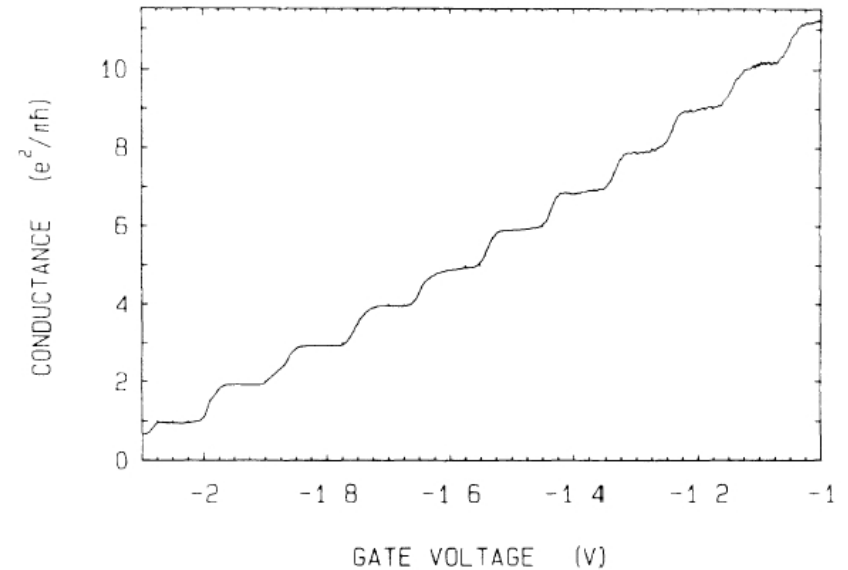


FIG. 2. Point-contact conductance as a function of gate voltage, obtained from the data of Fig. 1 after subtraction of the lead resistance. The conductance shows plateaus at multiples of $e^2/\pi h$.

B.J. van Wees et al. (1988), Phys. Rev. Lett., **60**, 848.

0.7 anomaly

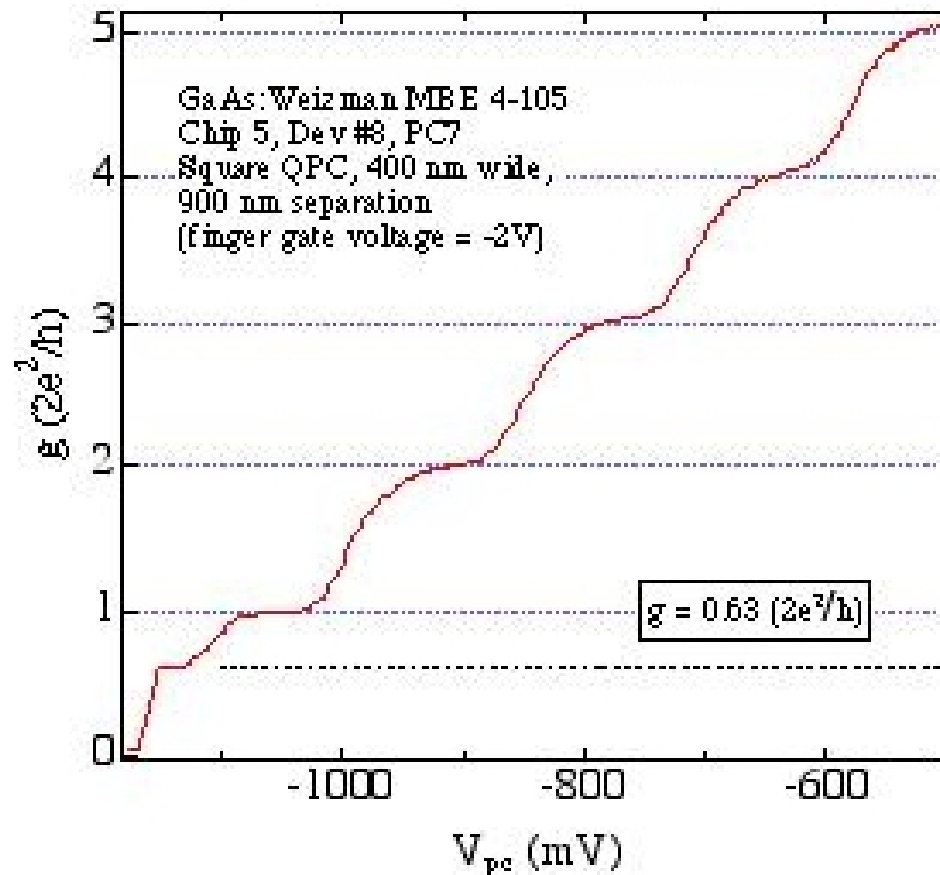
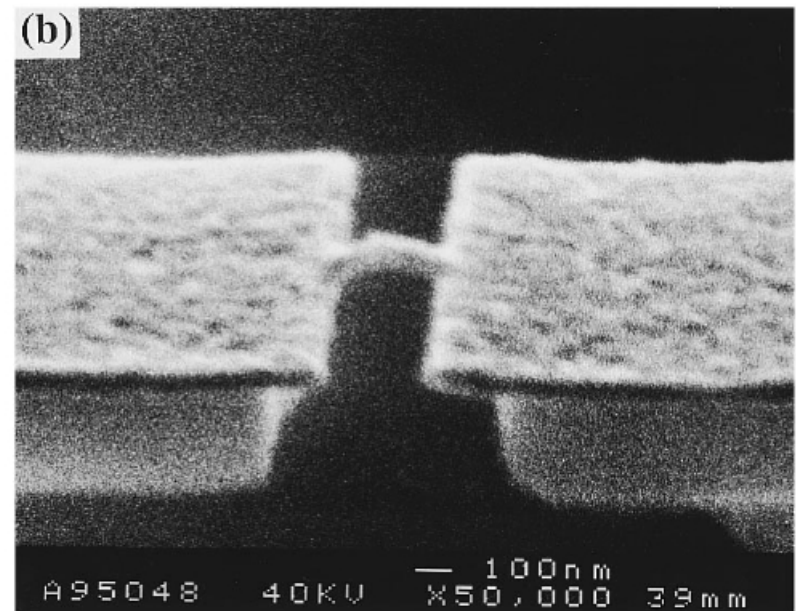
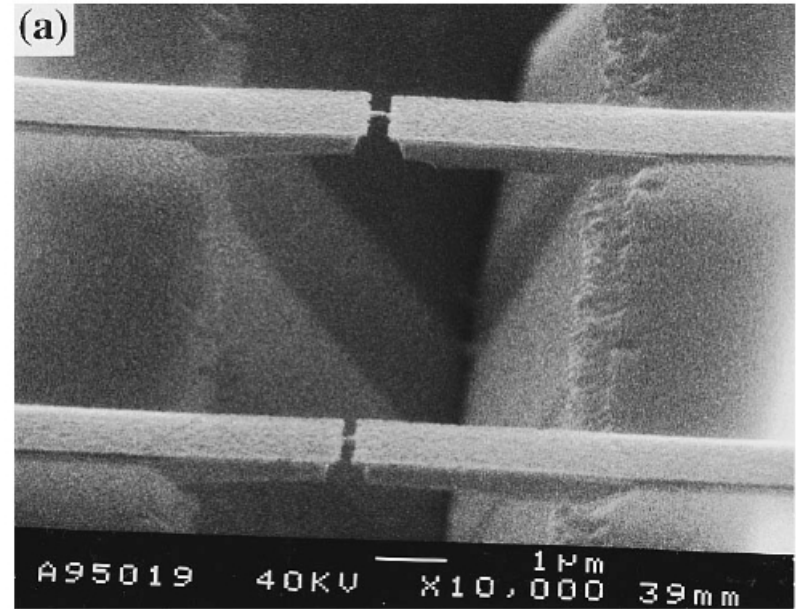
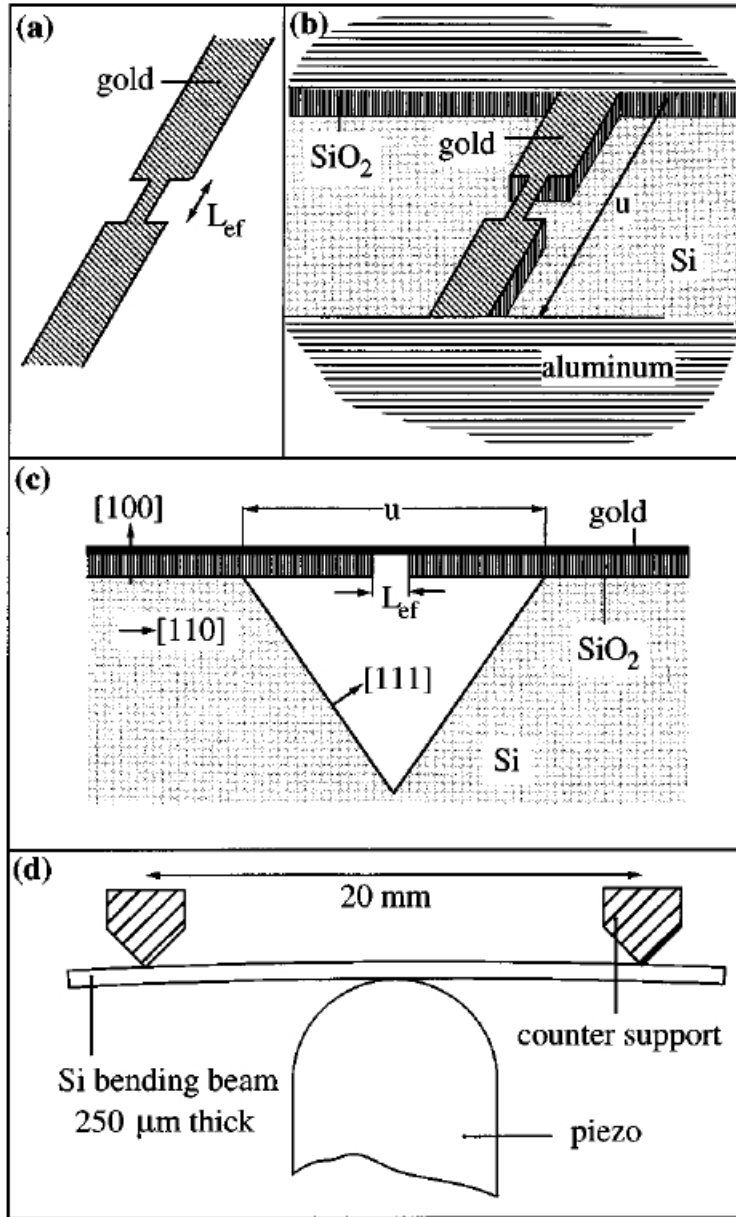


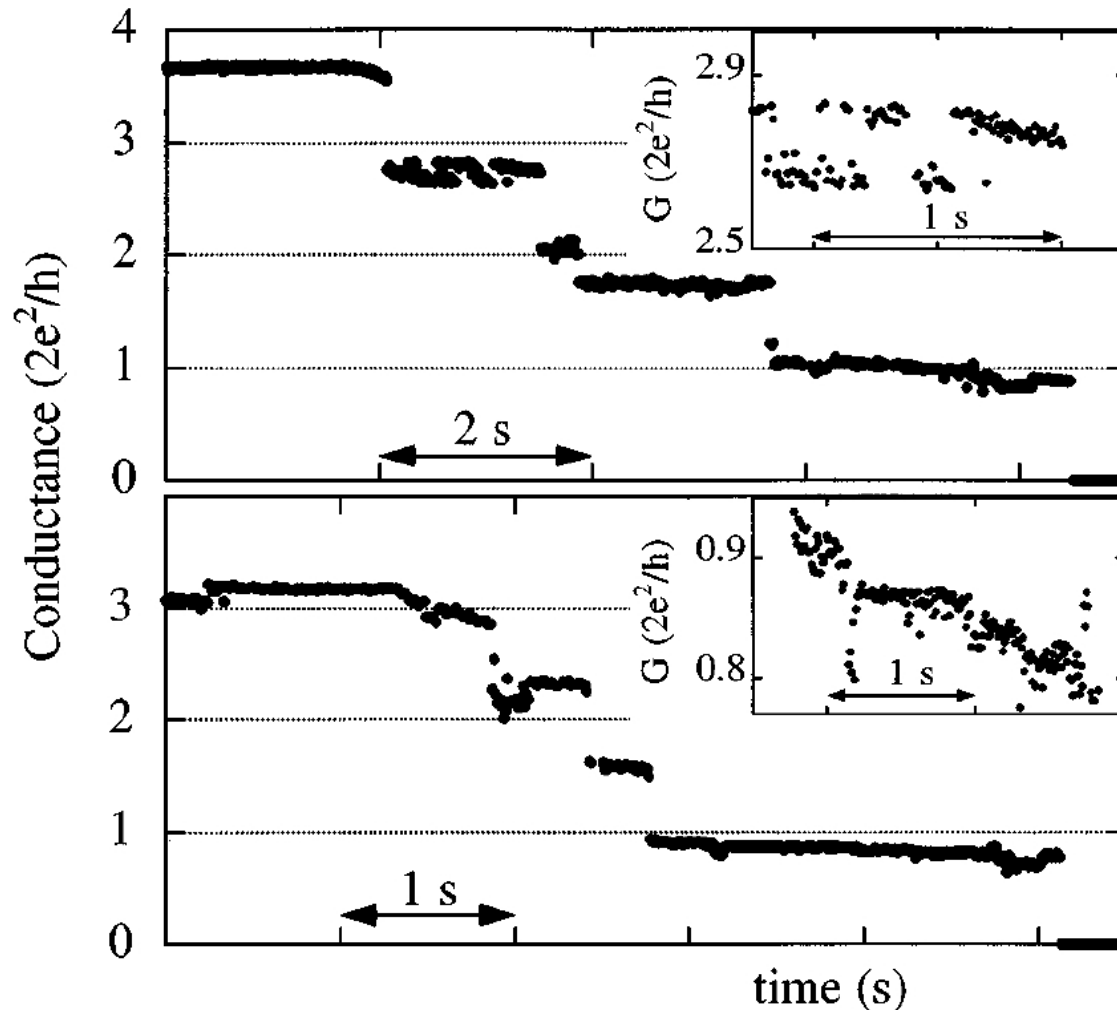
Figure 2: The conductance g through a point contact shows quantized plateaus at integer values of $2e^2/h$ with applied gate voltage, V_{pc} . This QPC shows a very prominent structure at $\sim 0.6 (2e^2/h)$. The gates of this QPC are 400 nm wide and 900 nm apart.

Break junction



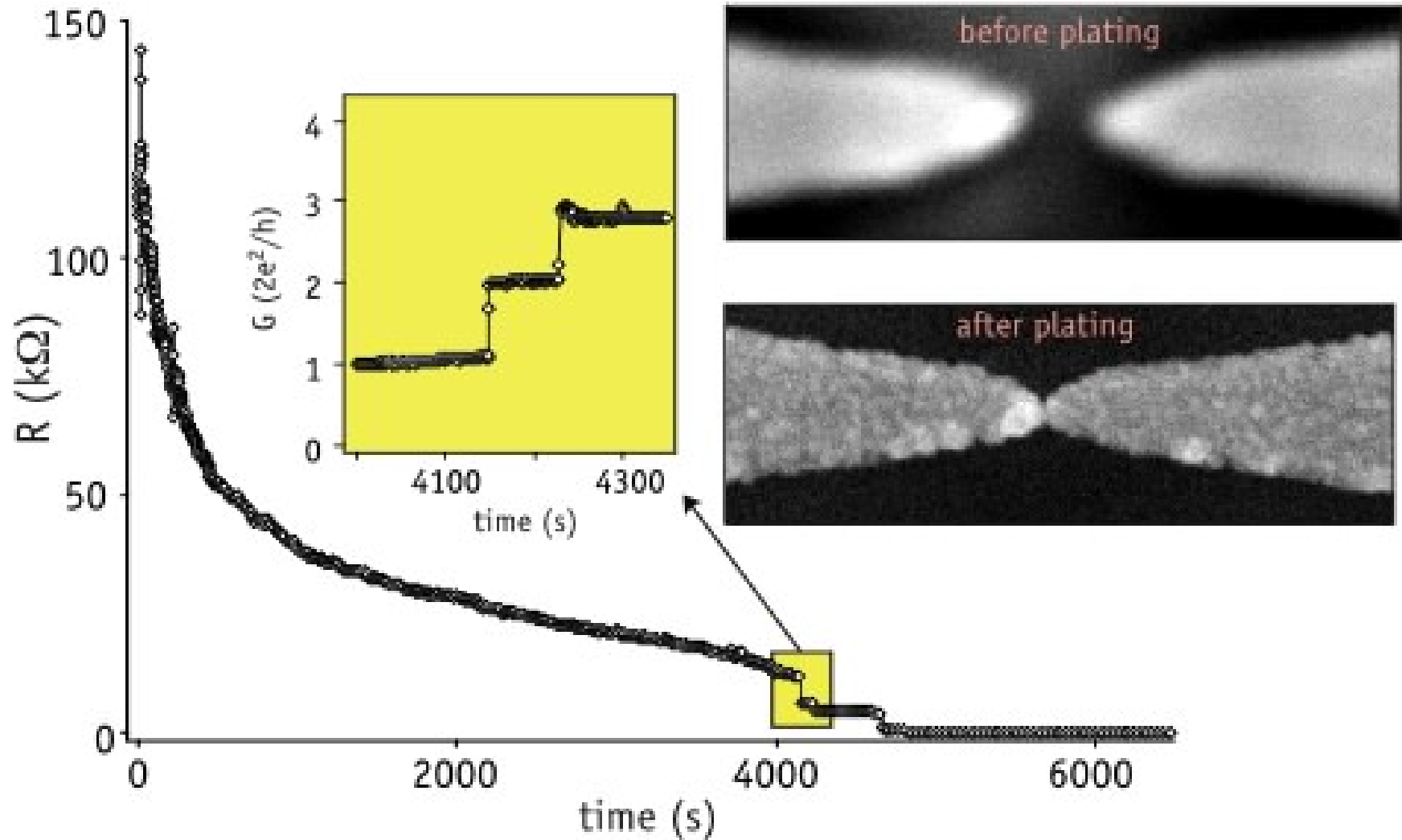
Microfabrication of a mechanically controllable break junction in silicon

C. Zhou, C. J. Muller, M. R. Deshpande, J. W. Sleight, and M. A. Reed
Center for Microelectronic Materials and Structures, Yale University, P.O. Box 208284, New Haven, Connecticut 06520-8284



Zhou, et al, Applied Physics Letters **67**, 8 (1995) p. 1160.

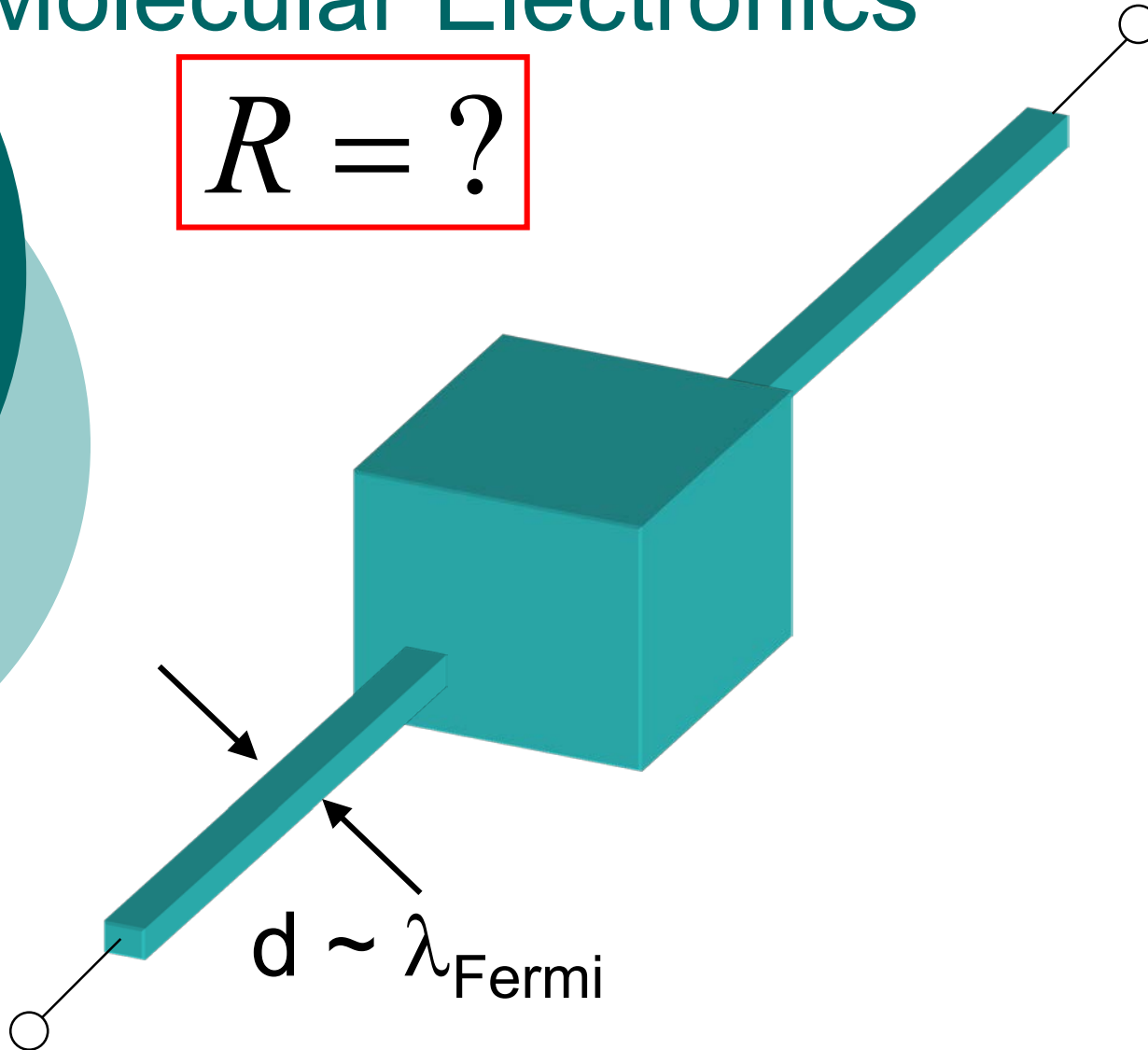
Electroplating



A.F.Morpurgo, C.M.Marcus and D. B. Robinson,
Controlled Fabrication of Metallic Electrodes with Atomic Separation, Appl. Phys. Lett. **74**, 2084 (1999).

Lecture 12: Quantum dots and Molecular Electronics

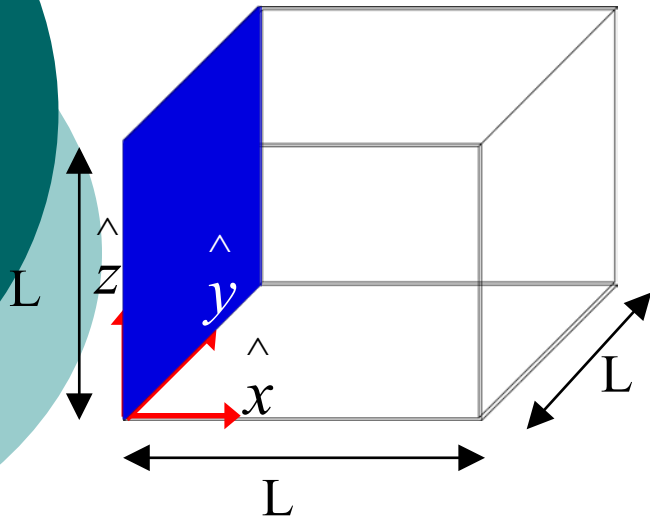
$$R = ?$$



Readings that cover this lecture

- Ferry, pp. 209-226
- Hanson, pp. 125-127

Particle in a box



We can do the same for y, z:

$$\psi(\vec{r}) = (2i)^3 A \cdot \sin(k_{n_x} x) \cdot \sin(k_{n_y} y) \cdot \sin(k_{n_z} z)$$

$$k_{n_x} = n_x \pi / L$$

$$k_{n_y} = n_y \pi / L$$

$$k_{n_z} = n_z \pi / L$$

$$E = \frac{\hbar^2 (k_{n_x}^2 + k_{n_y}^2 + k_{n_z}^2)}{2m} = \frac{\hbar^2 (\pi / L)^2}{2m} (n_x^2 + n_y^2 + n_z^2)$$

These are the allowed energy levels, or “quantum states”

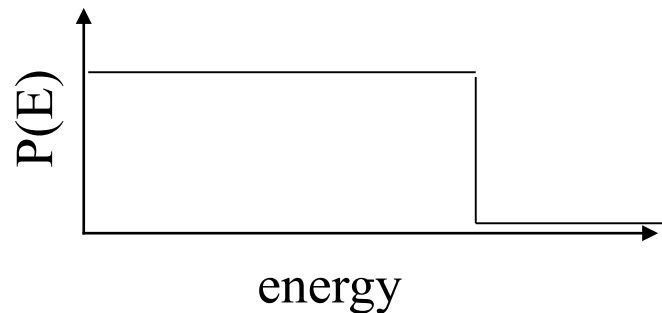
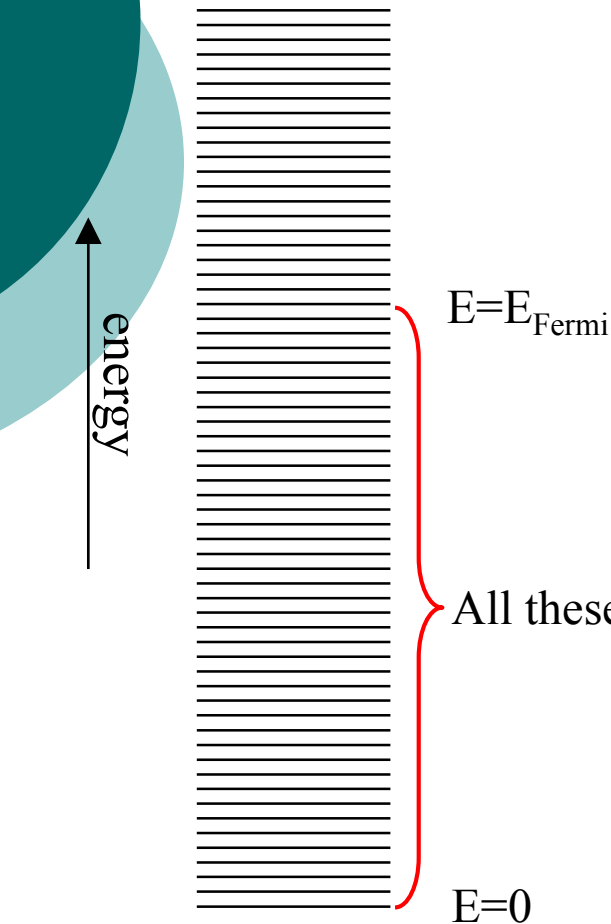
Fermi gas

At zero temperature, as we add electrons to the box, we gradually fill up all the states.
(DISCUSS PAULI EXCLUSION PRINCIPLE
-IMPORTANT!)

When we are done filling the box, the energy of the last electron is called the “Fermi energy.”

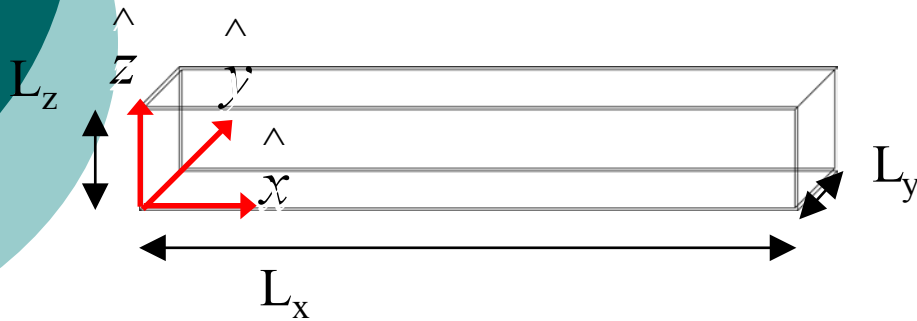
“Gas” means we neglect electron-electron interactions.

All these states are filled with electrons.



Particle in a box

$$\psi(\vec{r}) = (2i)^3 A \cdot \sin(k_{n_x} x) \cdot \sin(k_{n_y} y) \cdot \sin(k_{n_z} z)$$



$$k_{n_x} = n_x \pi / L$$

$$k_{n_y} = n_y \pi / L$$

$$k_{n_z} = n_z \pi / L$$

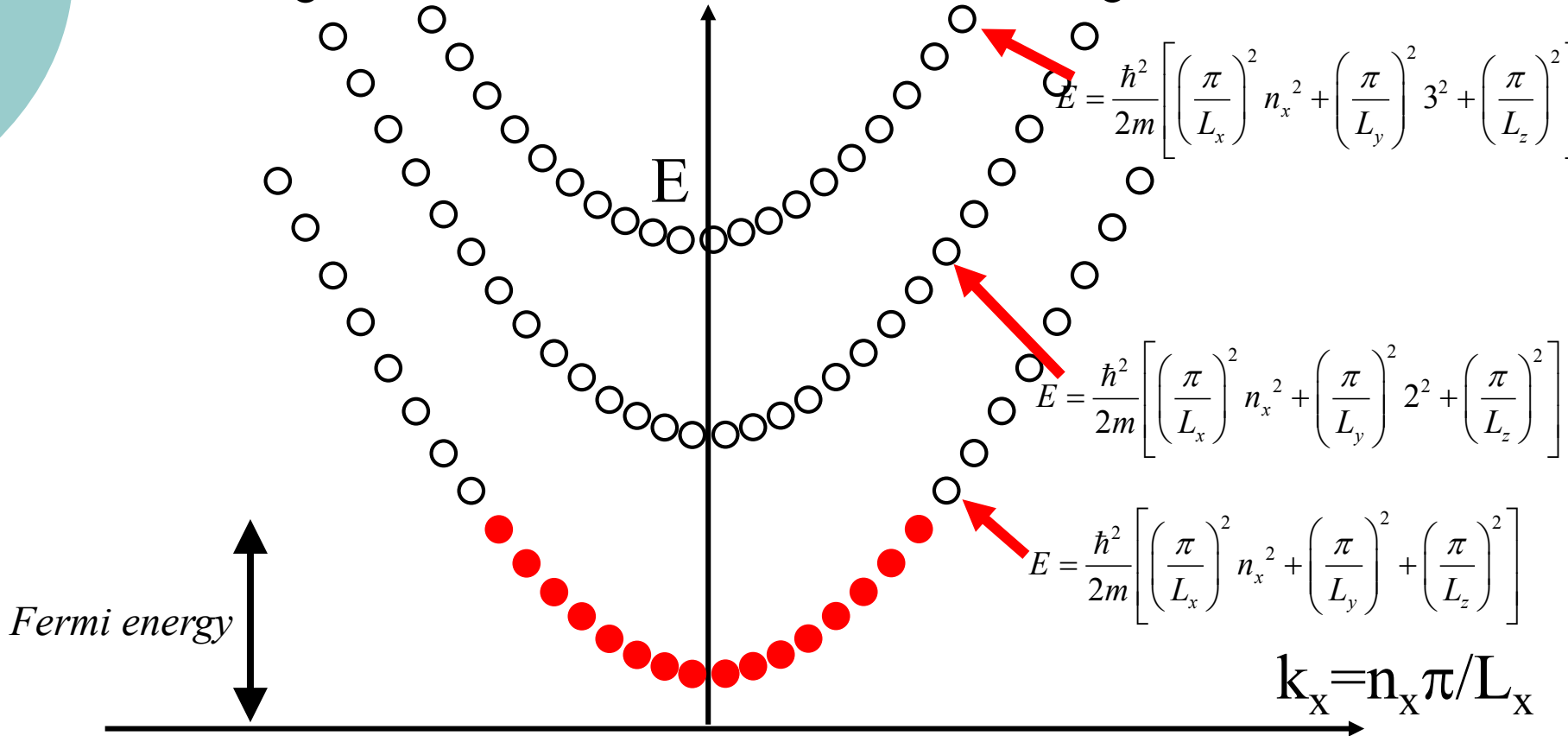
$$E = \frac{\hbar^2 (k_{n_x}^2 + k_{n_y}^2 + k_{n_z}^2)}{2m} = \frac{\hbar^2}{2m} \left[\left(\frac{\pi}{L_x} \right)^2 n_x^2 + \left(\frac{\pi}{L_y} \right)^2 n_y^2 + \left(\frac{\pi}{L_z} \right)^2 n_z^2 \right]$$

These are the allowed energy levels, or “quantum states”

1d system:

$$E = \frac{\hbar^2(k_{n_x}^2 + k_{n_y}^2 + k_{n_z}^2)}{2m} = \frac{\hbar^2}{2m} \left[\left(\frac{\pi}{L_x} \right)^2 n_x^2 + \left(\frac{\pi}{L_y} \right)^2 n_y^2 + \left(\frac{\pi}{L_z} \right)^2 n_z^2 \right]$$

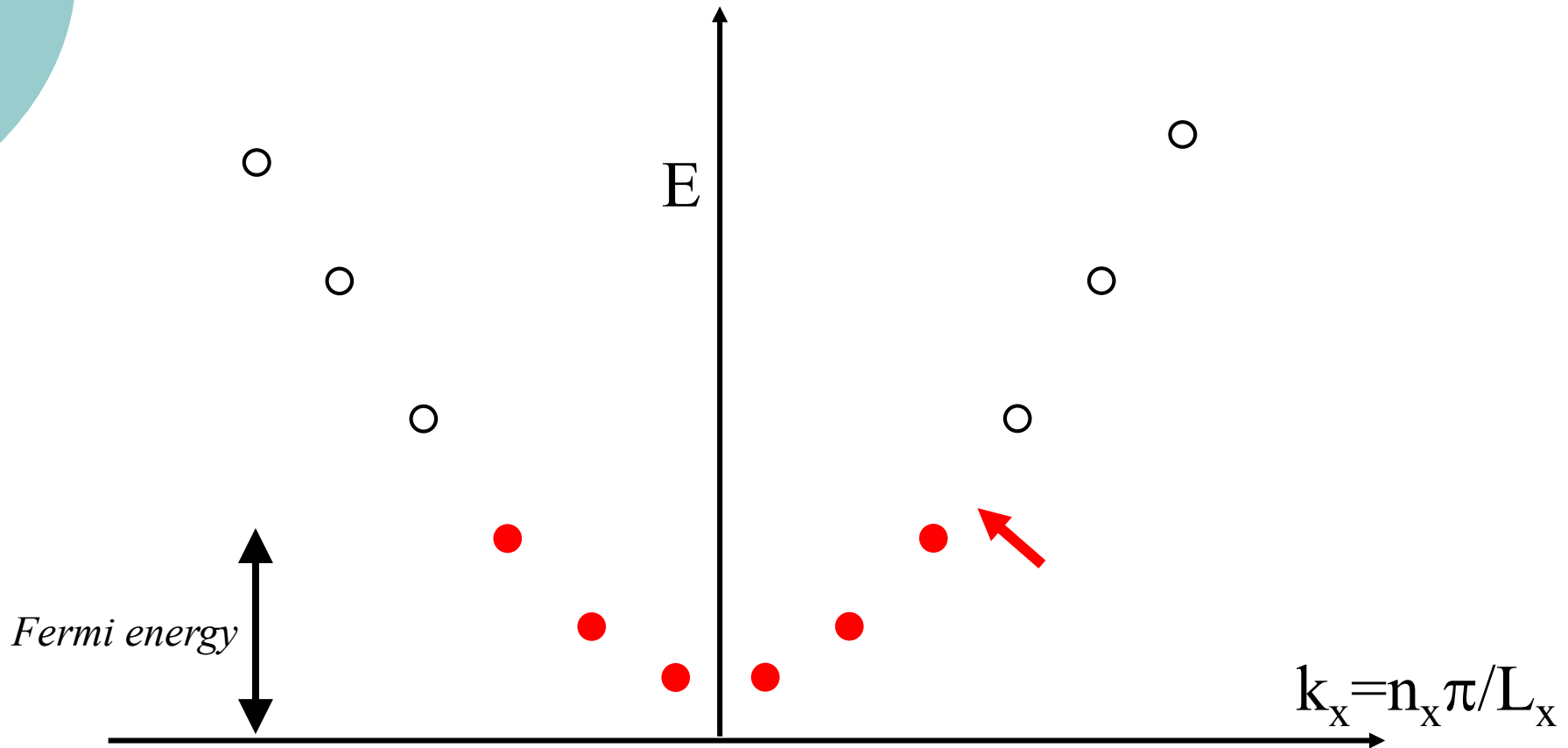
$$L_x \rightarrow \infty \quad L_y \rightarrow 0 \quad L_z \rightarrow 0$$



0d system

$$E = \frac{\hbar^2(k_{n_x}^2 + k_{n_y}^2 + k_{n_z}^2)}{2m} = \frac{\hbar^2}{2m} \left[\left(\frac{\pi}{L_x} \right)^2 n_x^2 + \left(\frac{\pi}{L_y} \right)^2 n_y^2 + \left(\frac{\pi}{L_z} \right)^2 n_z^2 \right]$$

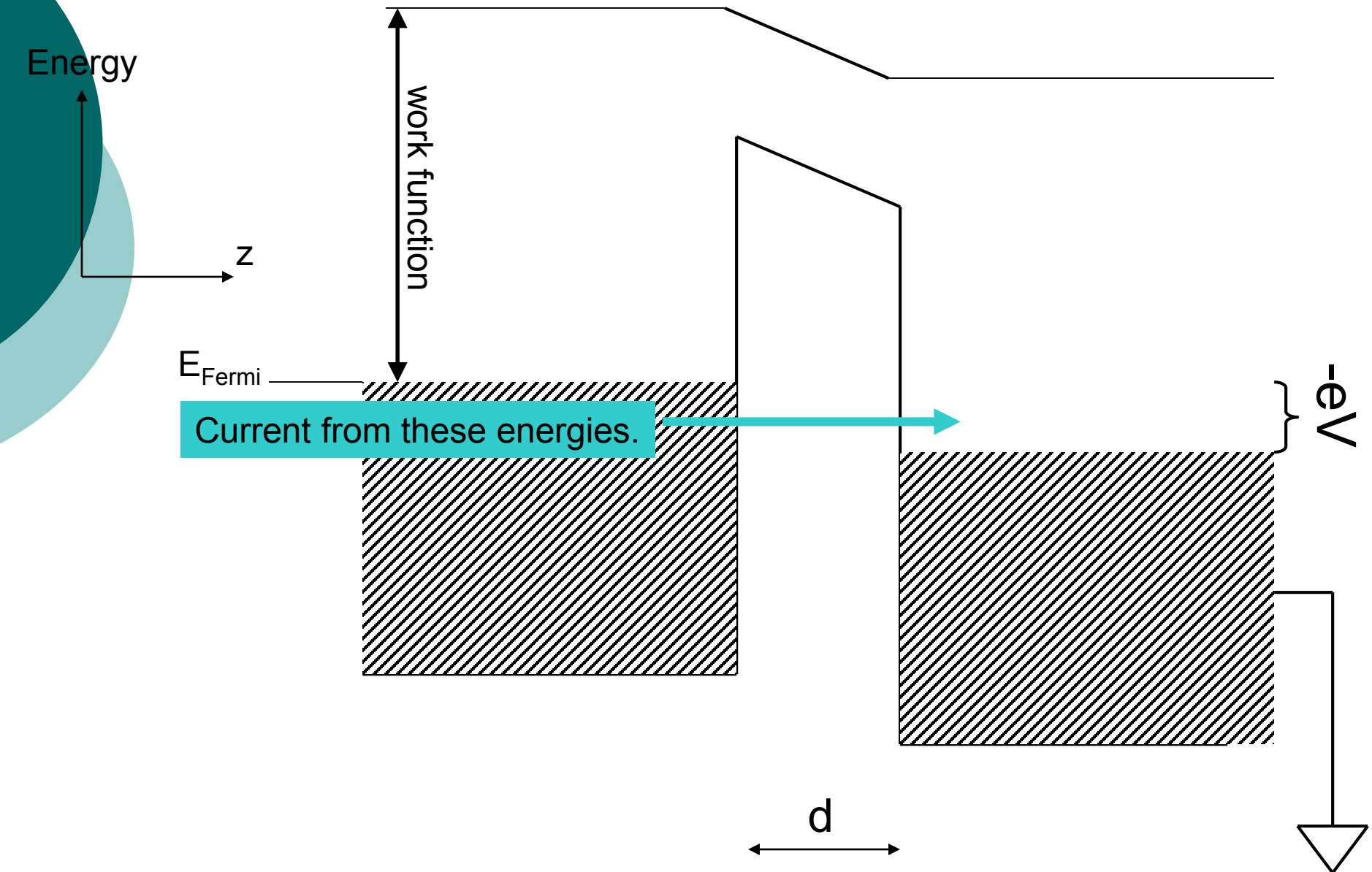
$$L_x \rightarrow 0 \quad L_y \rightarrow 0 \quad L_z \rightarrow 0$$



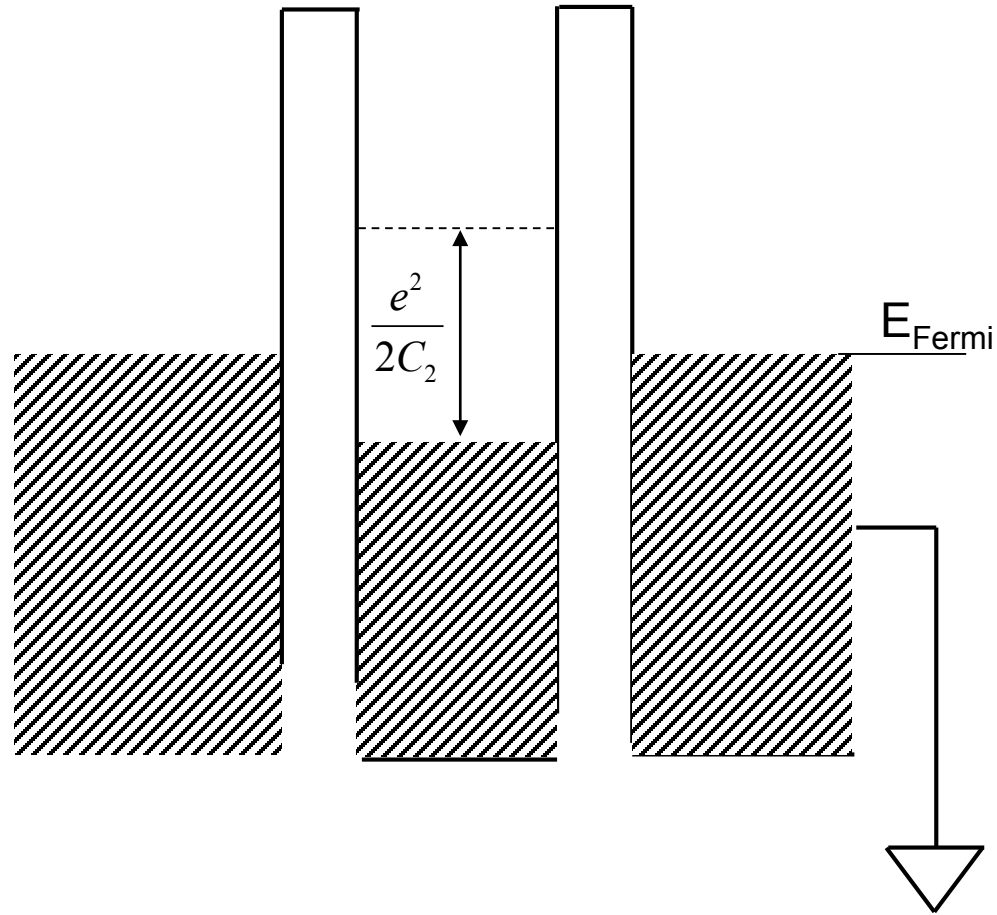
Energy scales

- Charging energy
- Single electron energy level spacing
- Temperature

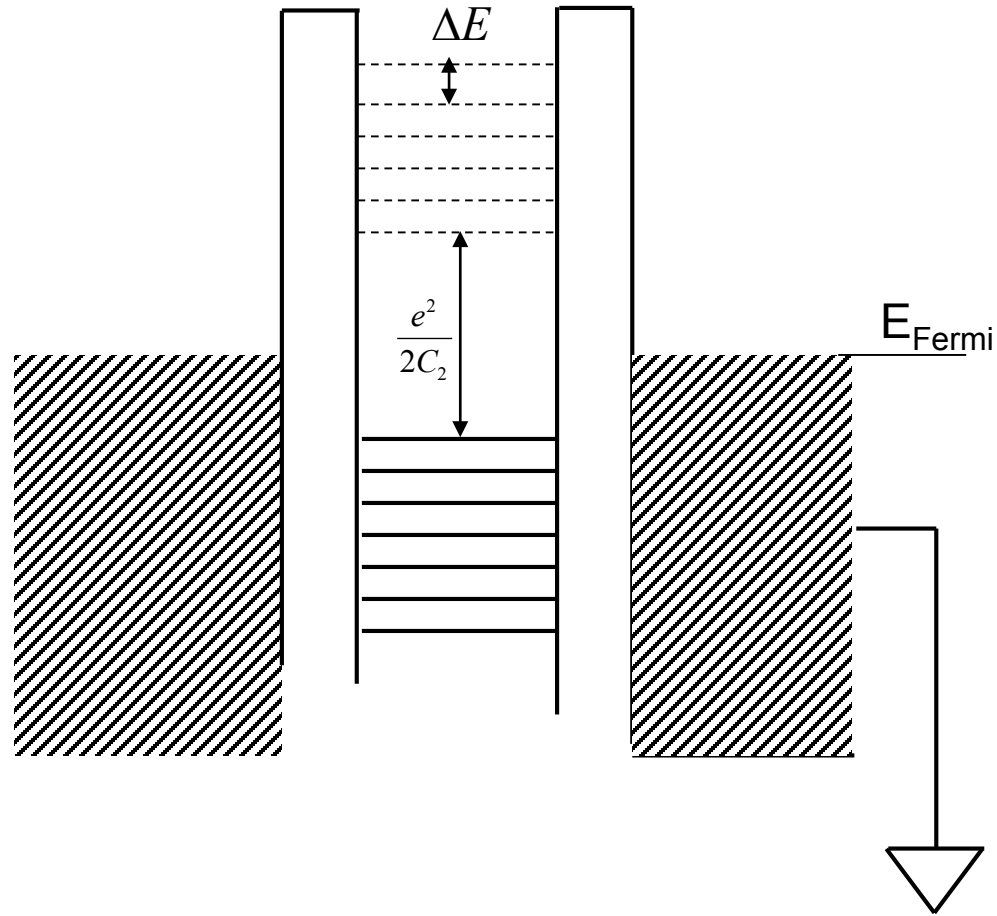
Continuum band diagrams like this no longer apply



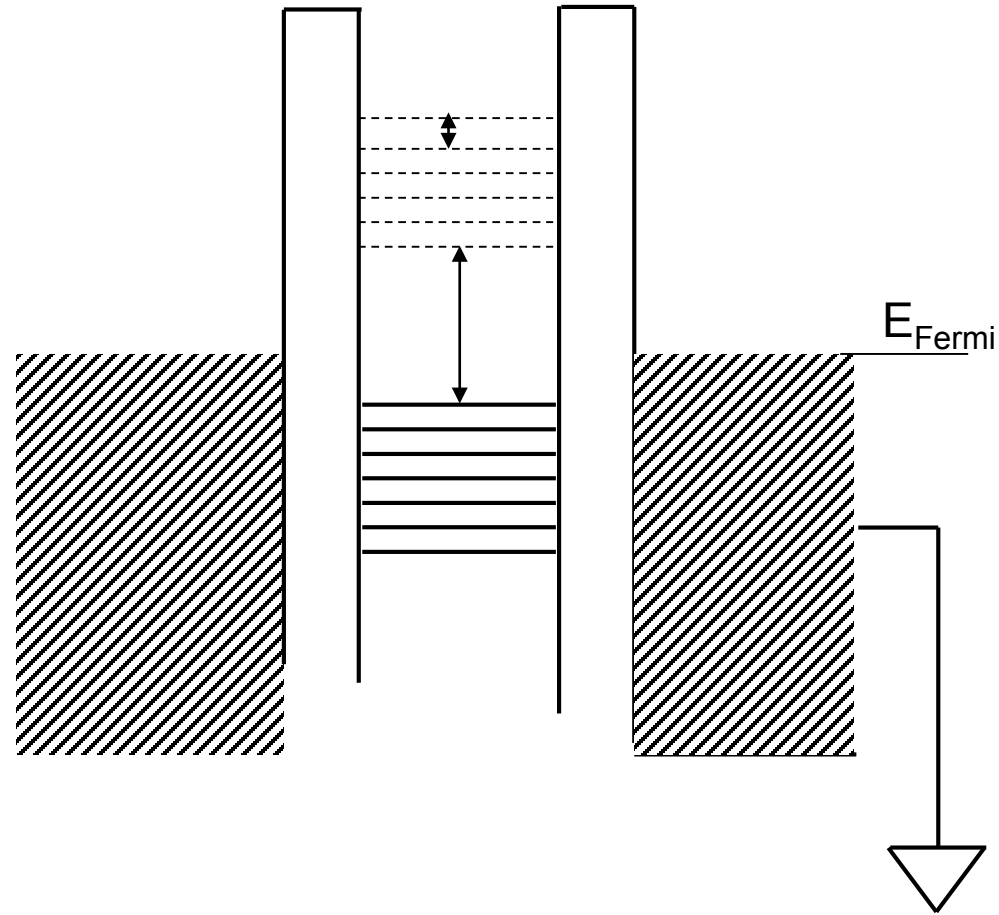
Band diagram with Coulomb "gap"



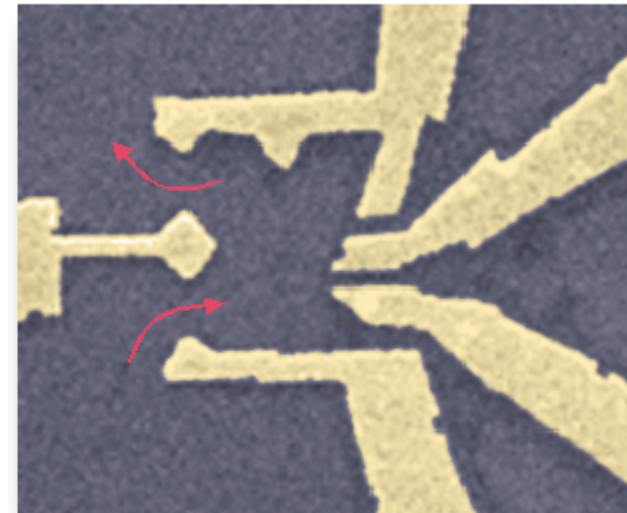
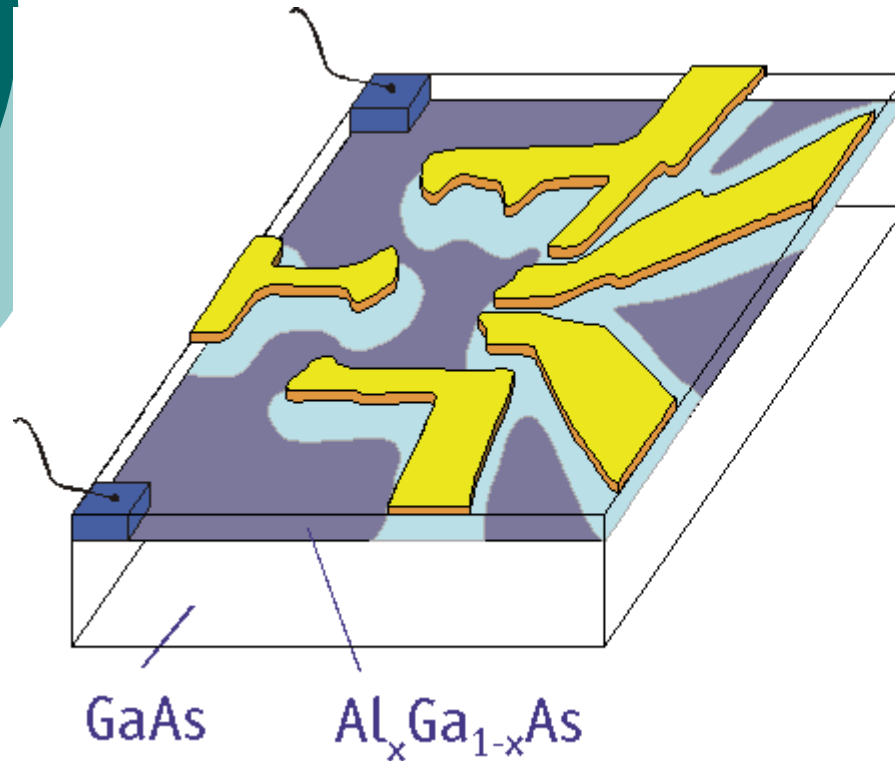
Band diagram with Coulomb “gap” and accounting for 0d states:



Band diagram with Coulomb "gap" and accounting for 0d states:

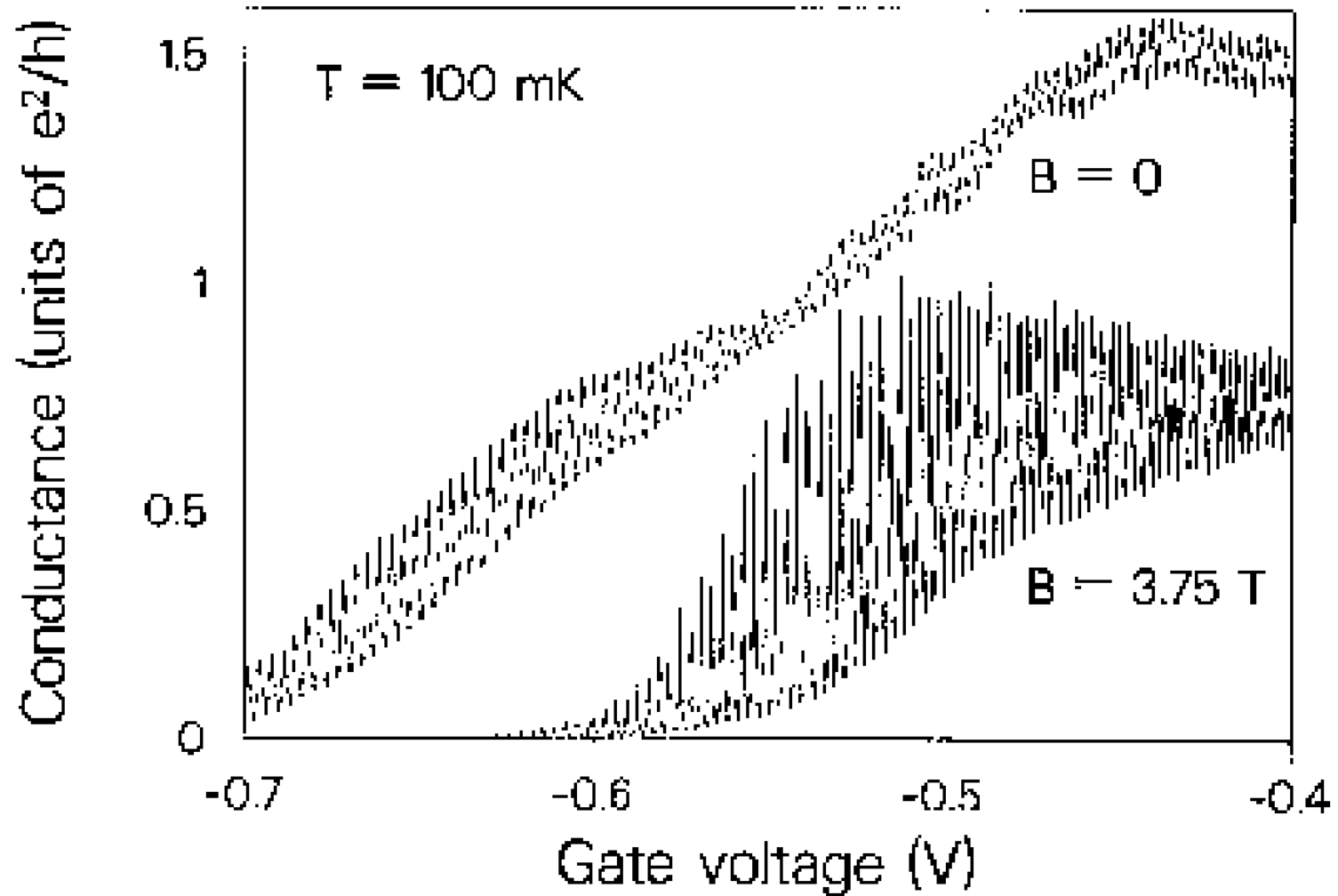


Experimental realization w/2DEGS



○ <http://marcuslab.harvard.edu/res.php>

Results

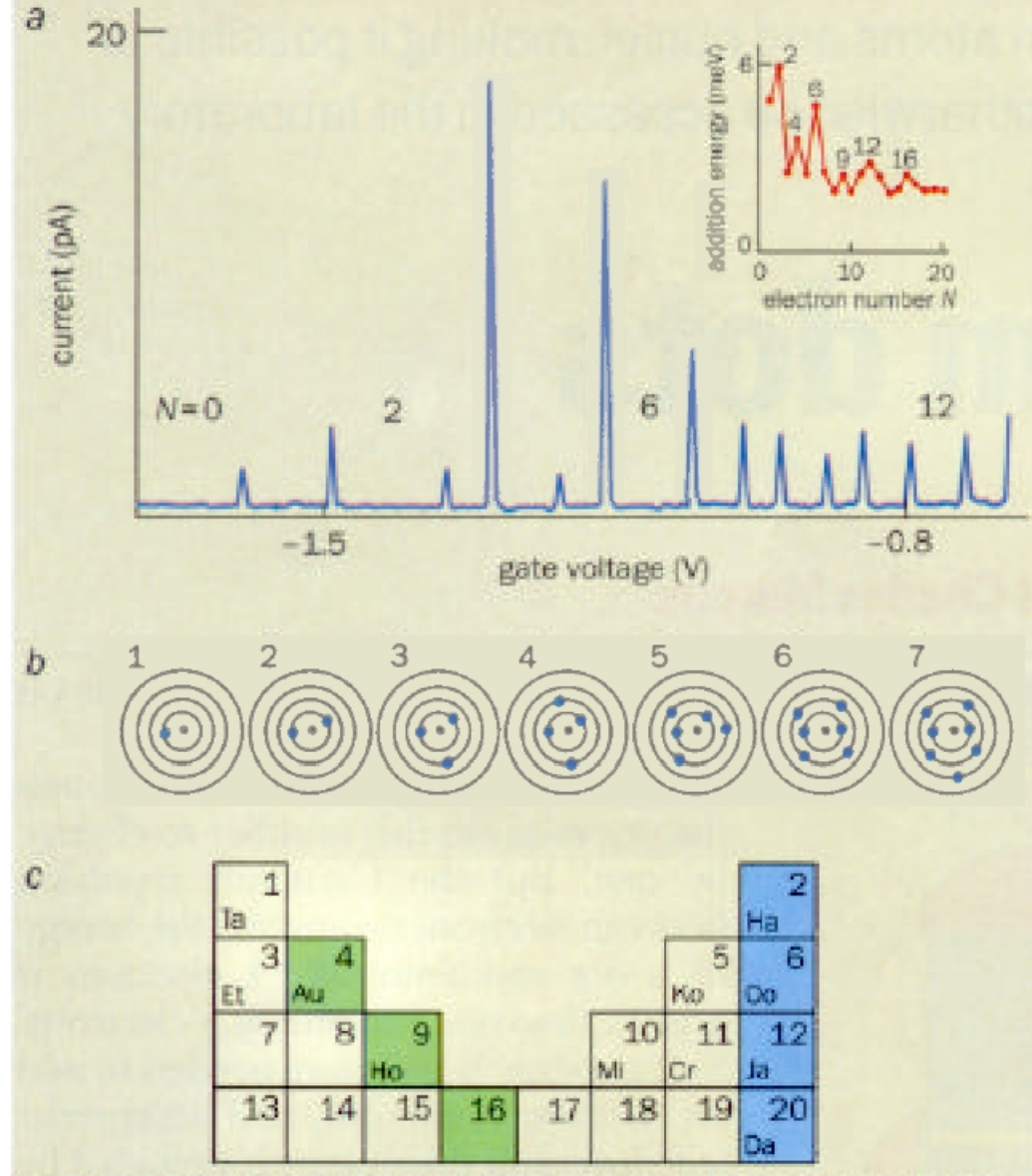


From .P. Kouwenhoven, C.M. Marcus, P.L. McEuen, S. Tarucha, R.M. Westervelt, and N.S. Wingreen
Electron Transport in Quantum Dots

Nato ASI conference proceedings, ed. By L. P. Kouwenhoven, G. Schön, L.L. Sohn (Kluwer, Dordrecht, 1997)

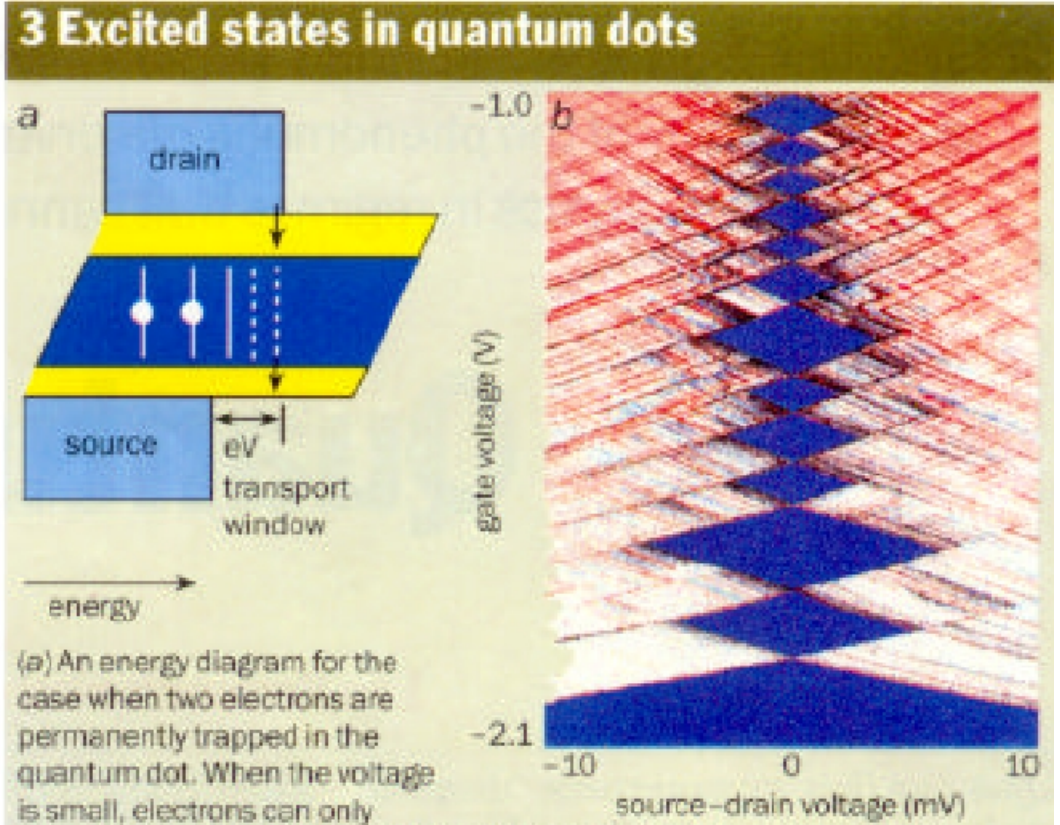
Artificial atoms

2 Artificial atoms



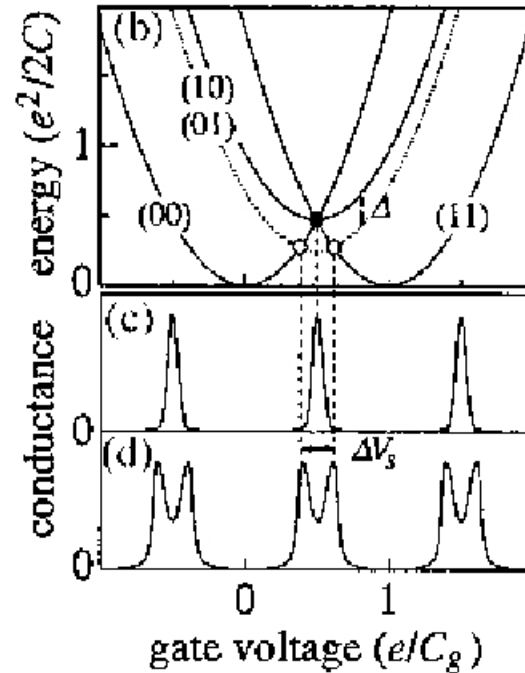
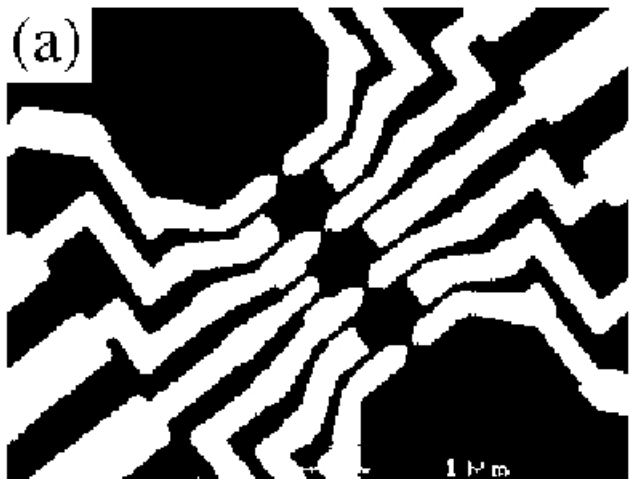
Leo Kouwenhoven and Charles Marcus
 Quantum Dots
 Physics World, June 1998

Coulomb diamonds



Leo Kouwenhoven and Charles Marcus
Quantum Dots
Physics World, June 1998

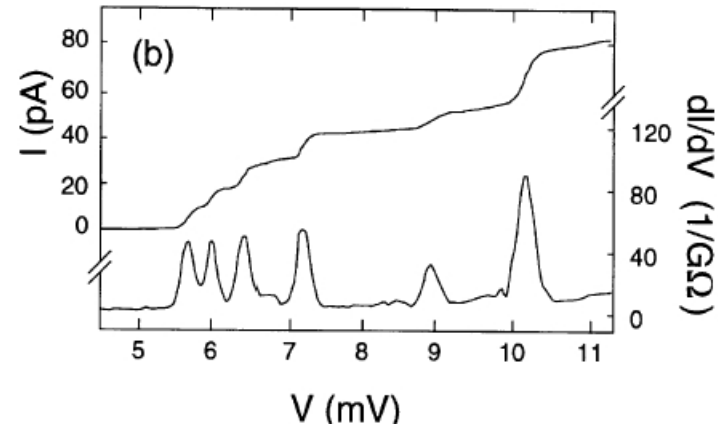
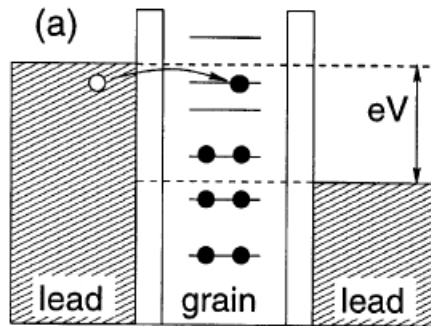
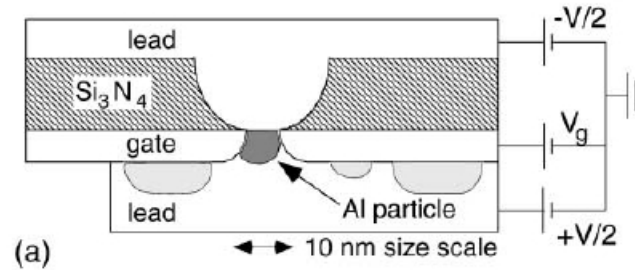
Artificial molecules



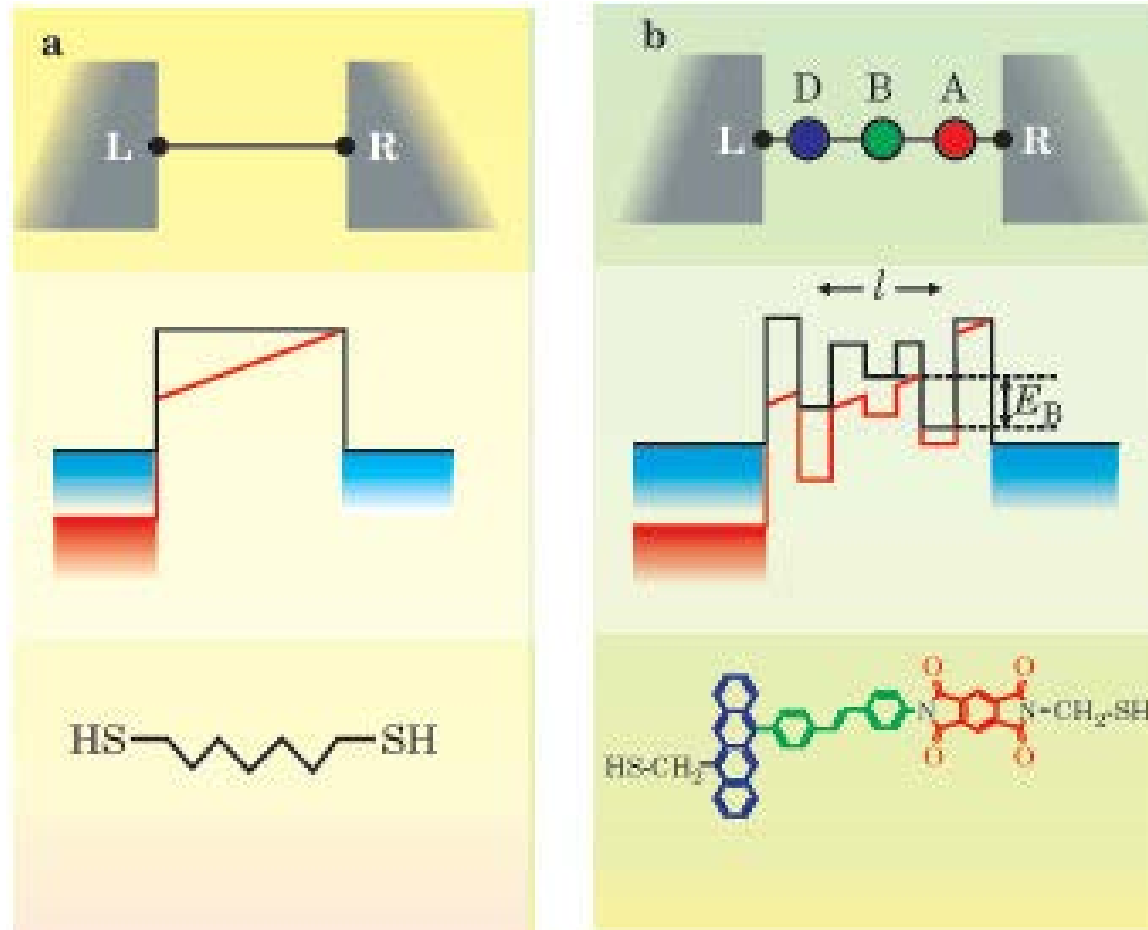
From .P. Kouwenhoven, C.M. Marcus, P.L. McEuen, S. Tarucha, R.M. Westervelt, and N.S. Wingreen
Electron Transport in Quantum Dots

Nato ASI conference proceedings, ed. By L. P. Kouwenhoven, G. Sch&ouml;n, L.L. Sohn (Kluwer, Dordrecht, 1997)

Metallic quantum dots



Molecular electronics



J. Heath, Physics Today, May 2003

Molecular electronics

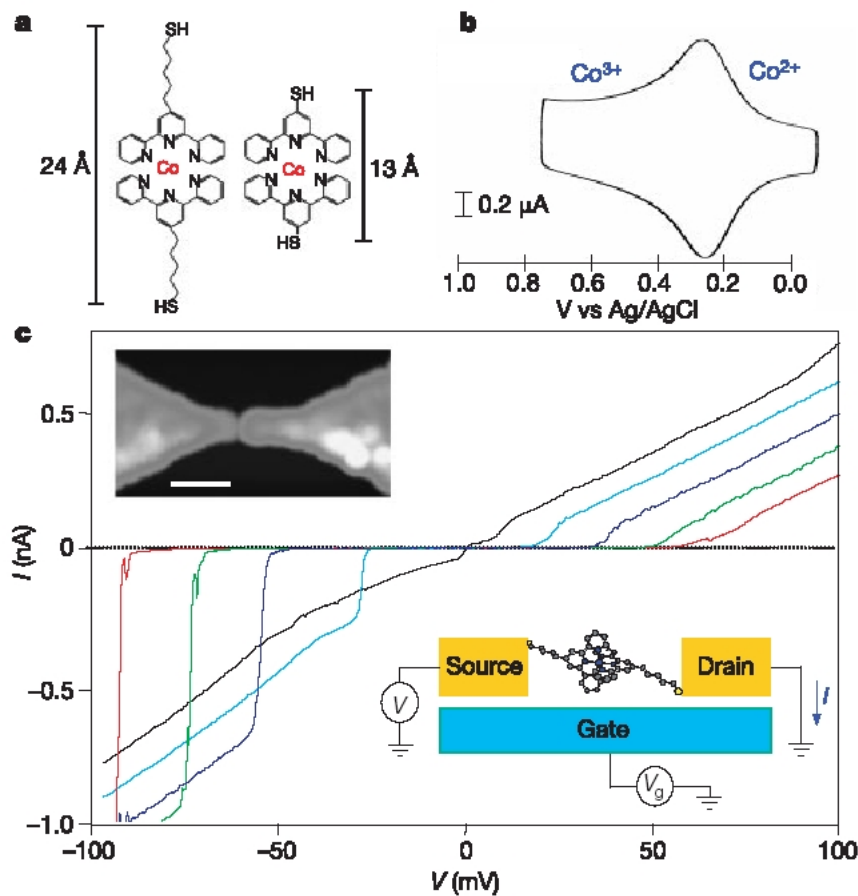
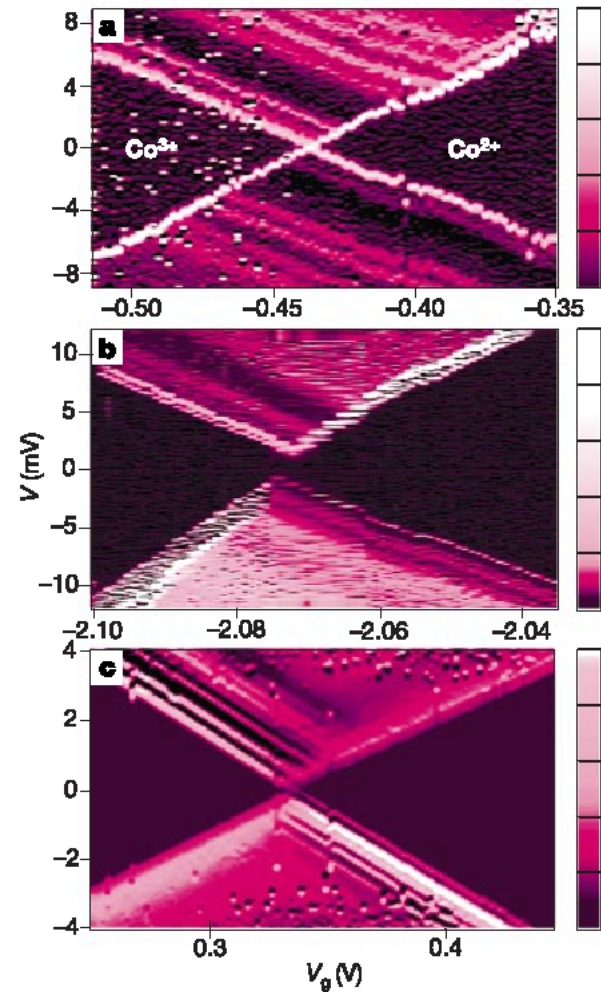


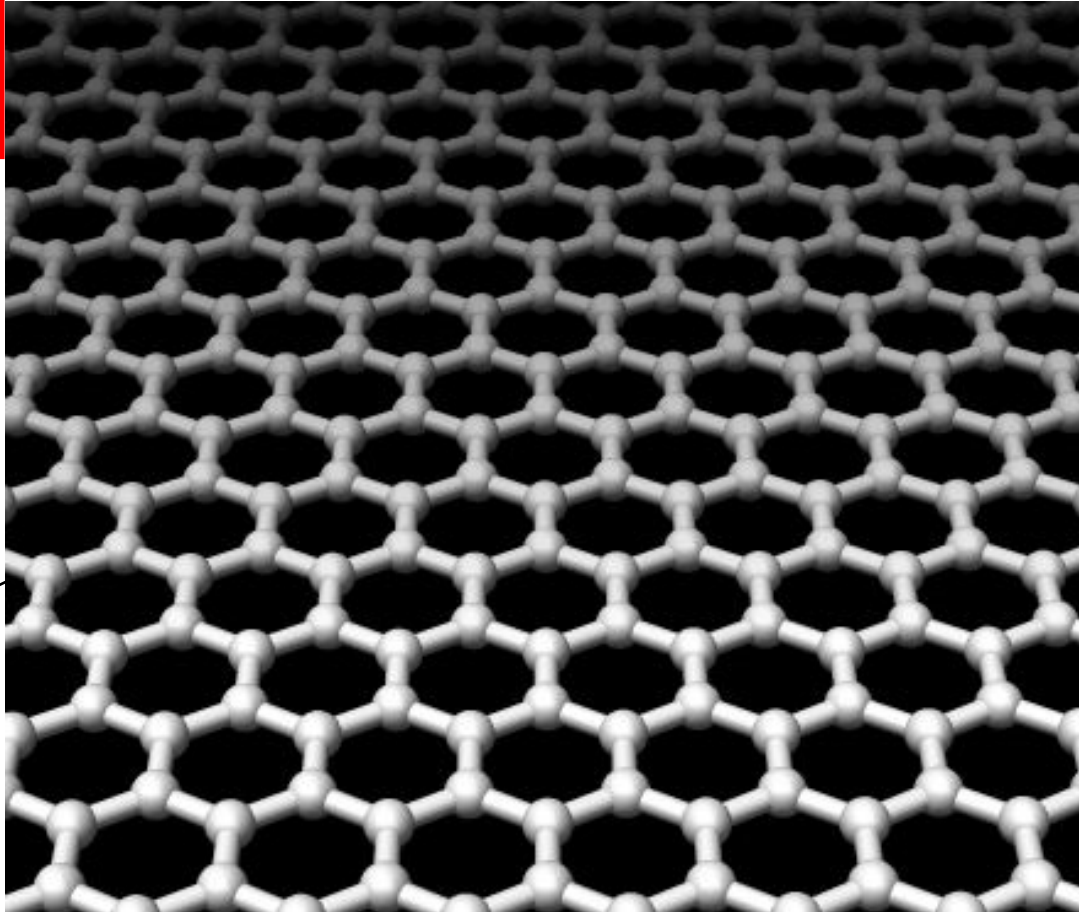
Figure 1 The molecules used in this study and their electronic properties. **a**, Structure of $[\text{Co}(\text{tpy}-(\text{CH}_2)_5\text{-SH})_2]^{2+}$ (where $\text{tpy}-(\text{CH}_2)_5\text{-SH}$ is 4'-(5-mercaptopentyl)-2,2':6',2''-terpyridinyl) and $[\text{Co}(\text{tpy-SH})_2]^{2+}$ (where tpy-SH is 4'-(mercapto)-2,2':6',2''-terpyridinyl). The scale bars show the lengths of the molecules as calculated by energy minimization.



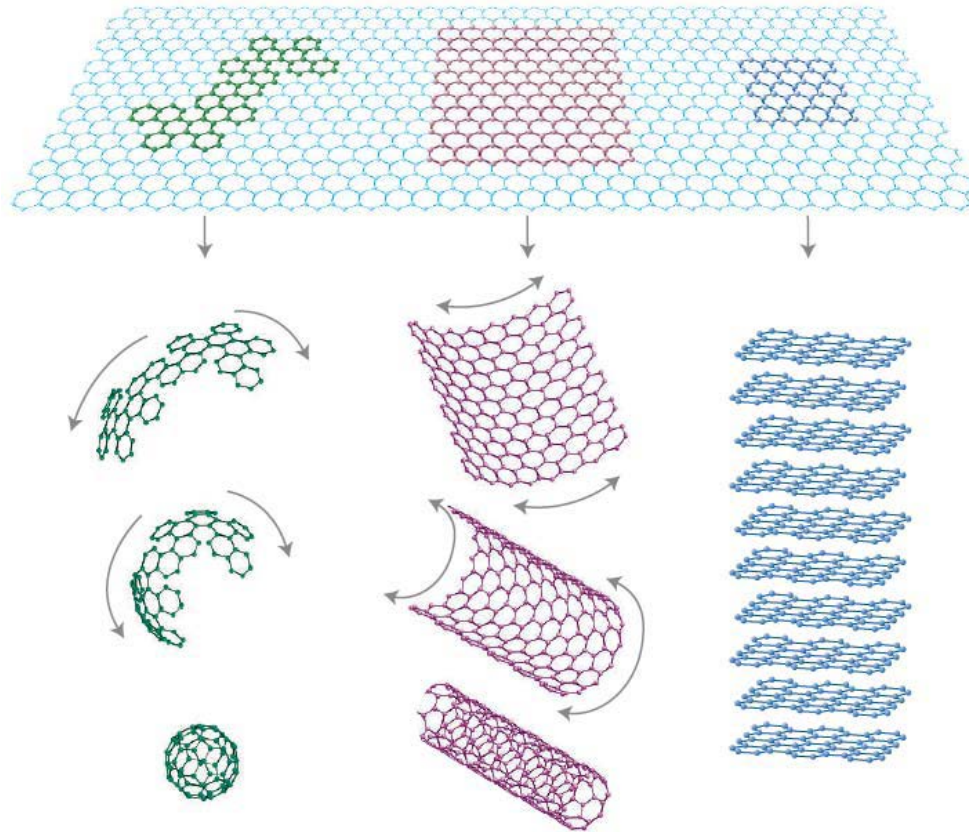
"Coulomb blockade and the Kondo effect in single-atom transistors," Jiwoong Park, Abhay N. Pasupathy, Jonas I. Goldsmith, Connie Chang, Yuval Yaish, Jason R. Petta, Marie Rinkoski, James P. Sethna, Hector D. Abruna, Paul L. McEuen & Daniel C. Ralph, Nature, 417, 722-725 (2002).

Carbon Electronics

$$R = ?$$

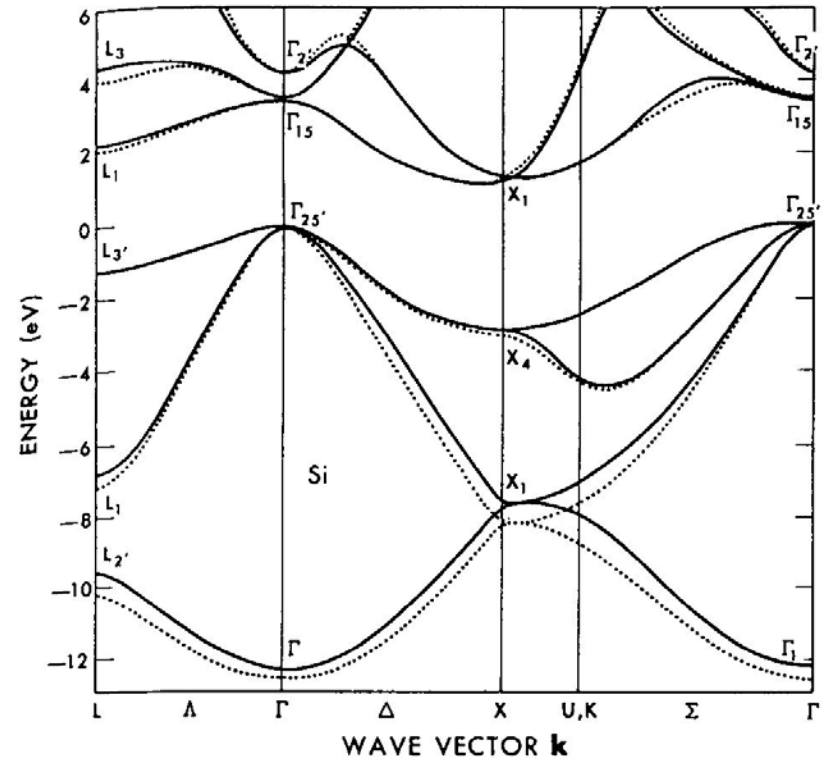
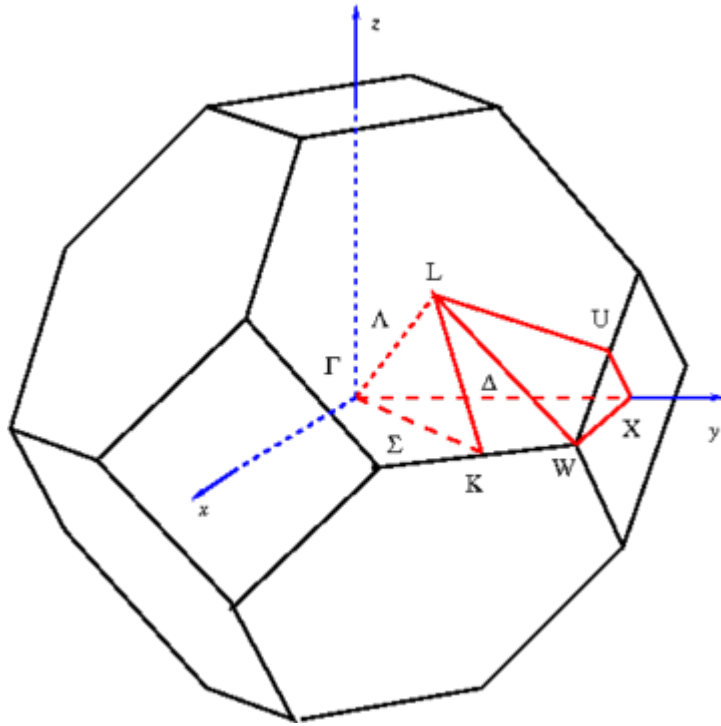


Allotropes of Carbon

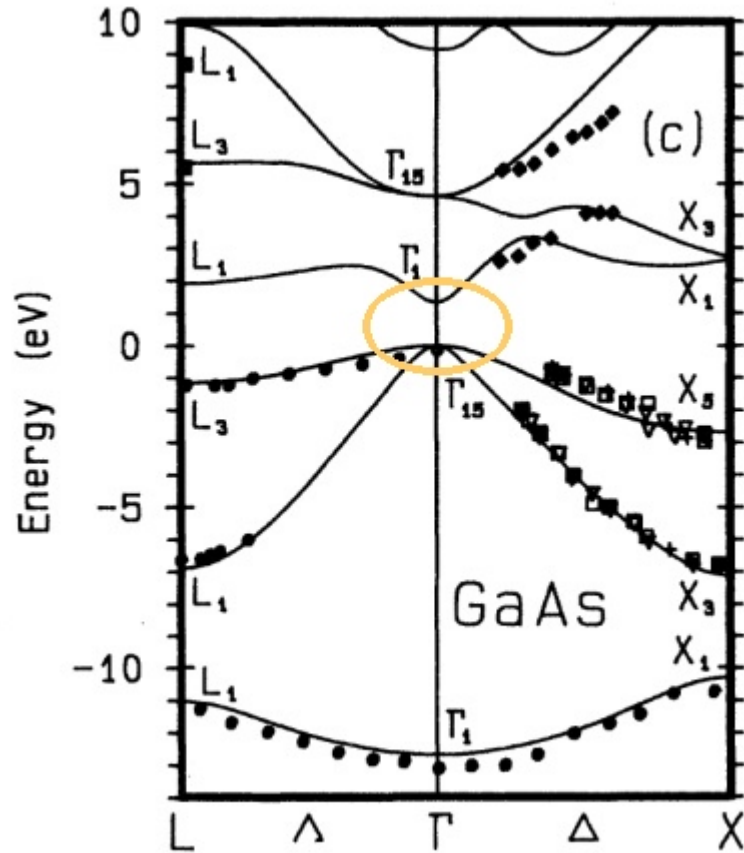


A. Geim and K. Novoselov, "The Rise of Graphene", *Nature Materials*, **6**, 183-191, (2007).

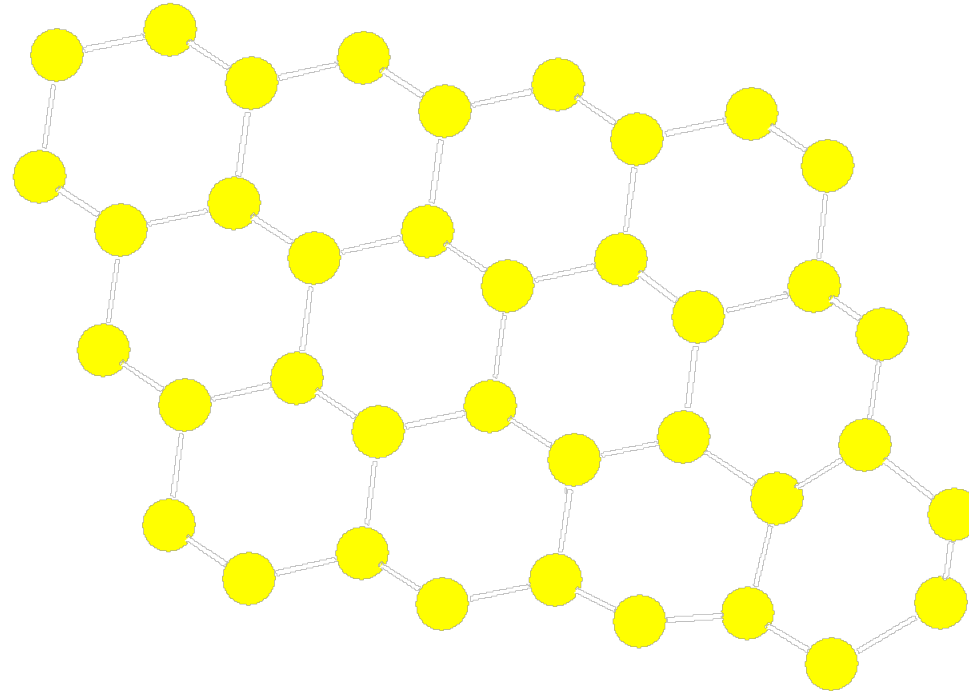
Silicon



GaAs

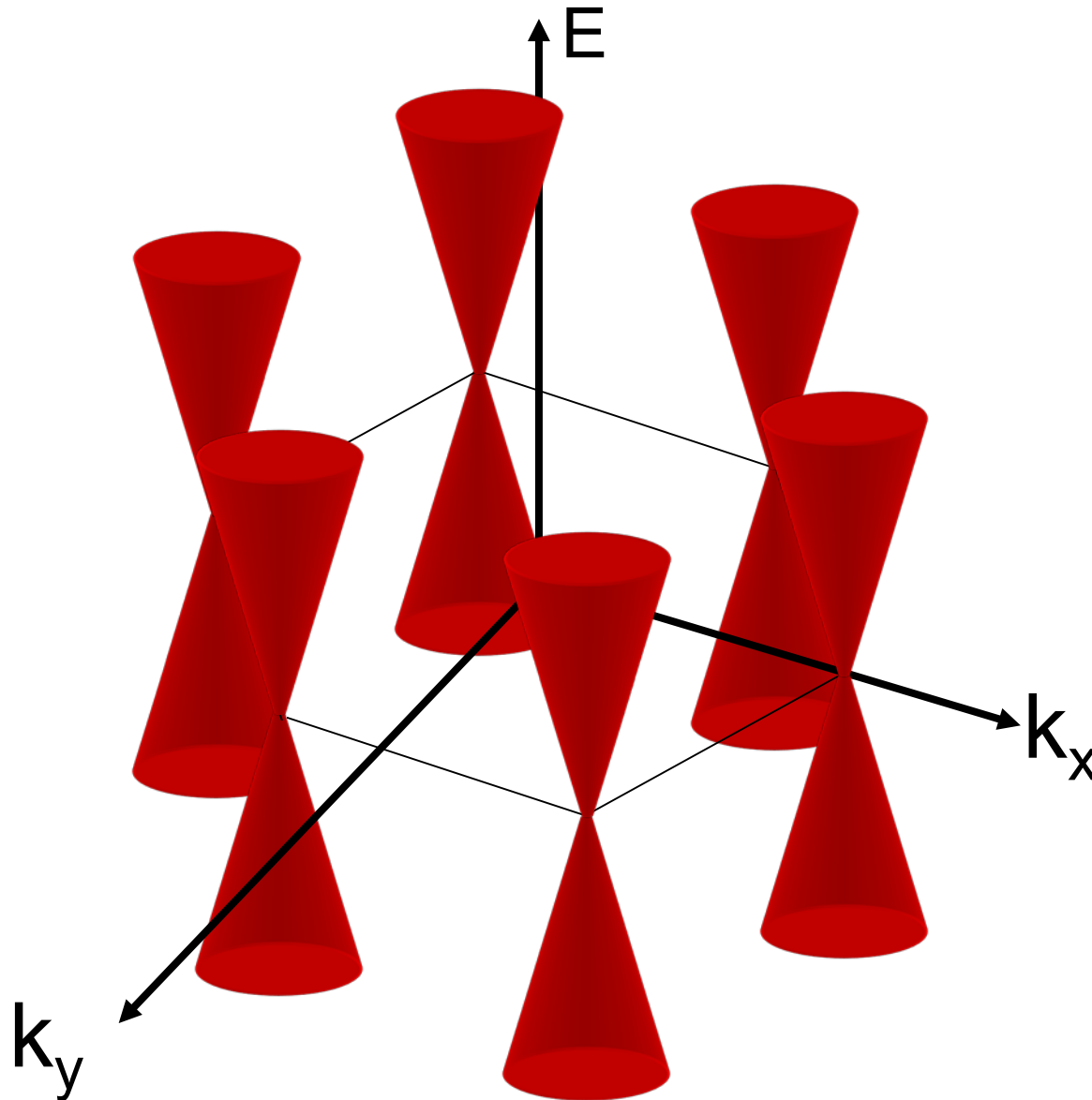


Graphene: 2d semiconductor



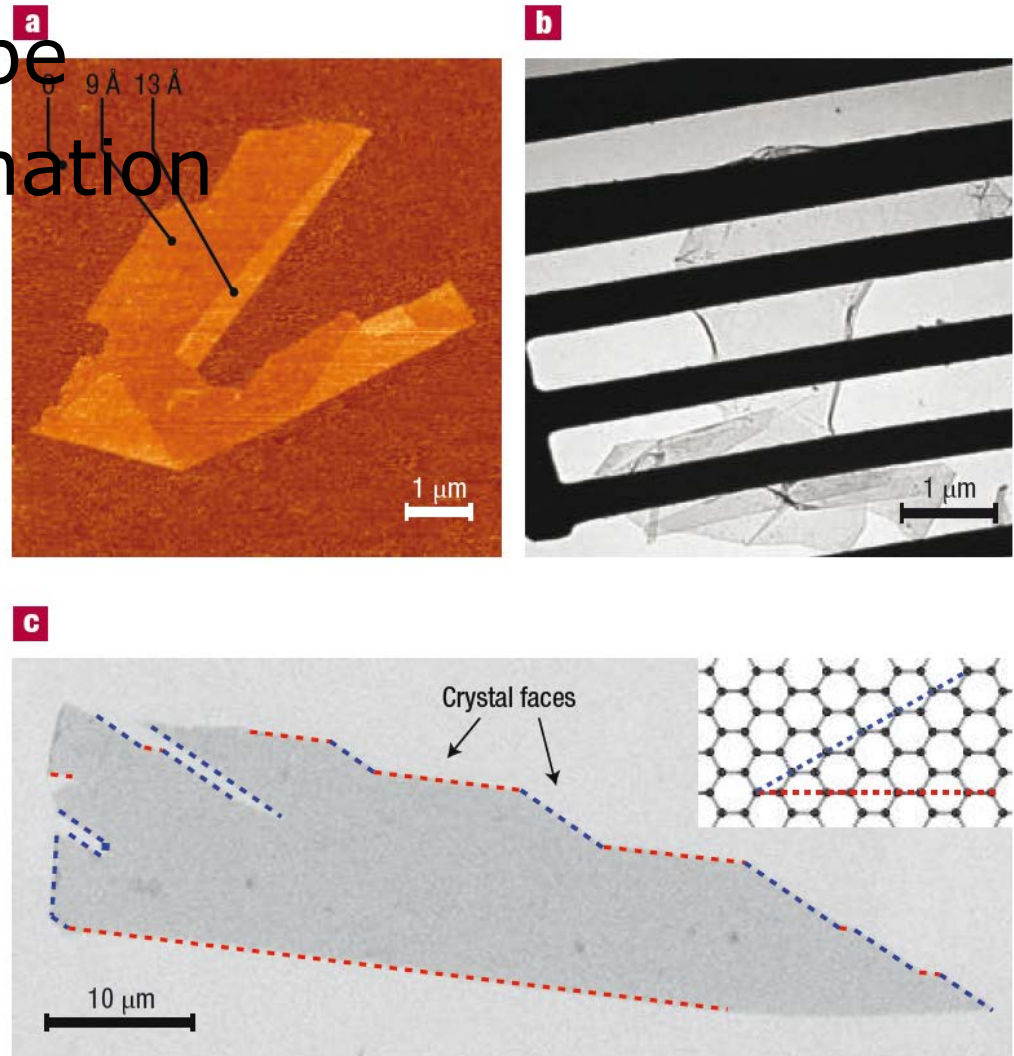
Bond length = 0.142 nm

Graphene band structure



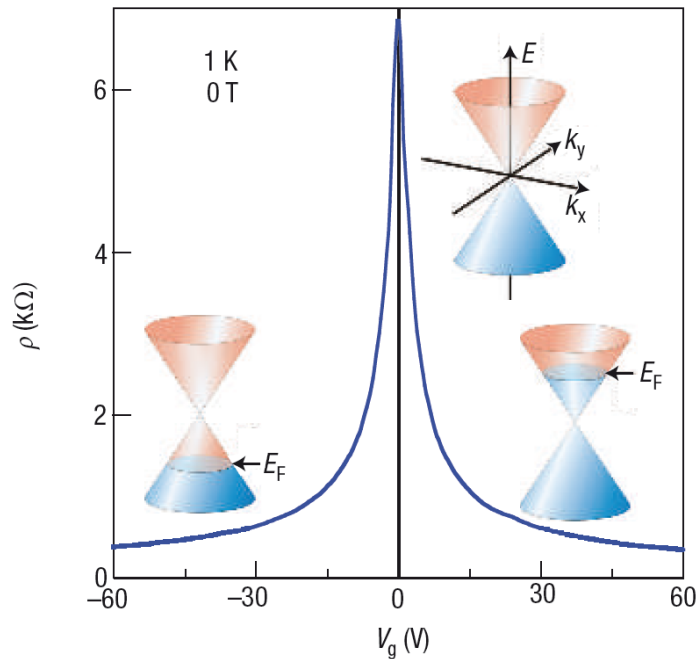
Synthesis

- Scotch tape
- SiC sublimation
- CVD

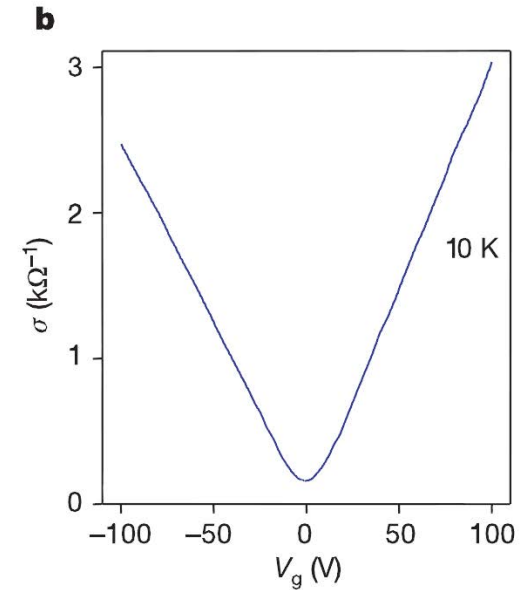


A. Geim and K. Novoselov, "The Rise of Graphene", *Nature Materials*, **6**, 183-191, (2007).

Transport (back gate)

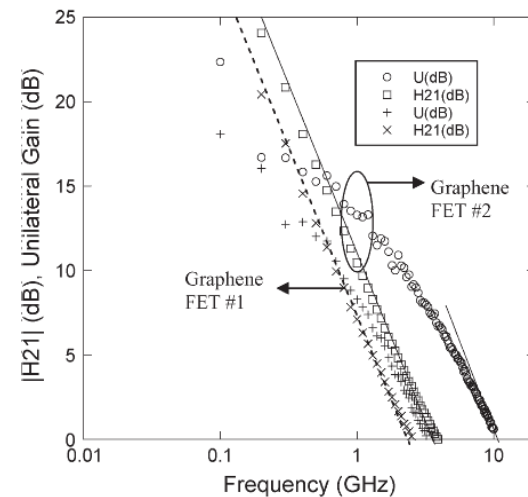
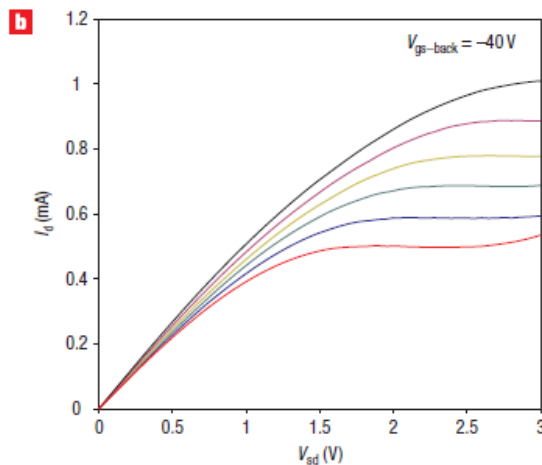
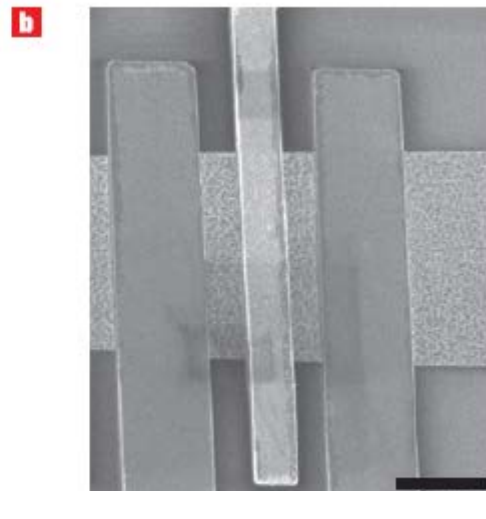
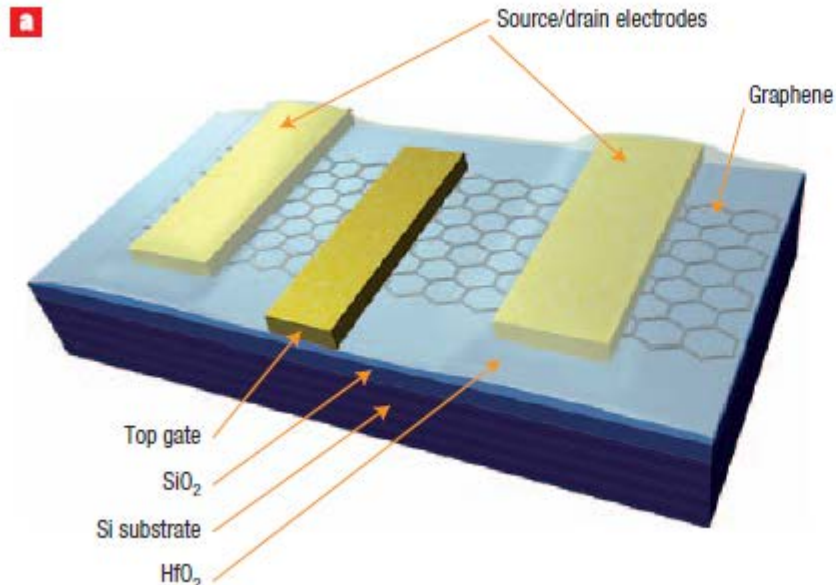


A. Geim and K. Novoselov, "The Rise of Graphene", *Nature Materials*, **6**, 183-191, (2007).



Novoselov, K., A. Geim, et al. (2005). "Two-dimensional gas of massless Dirac fermions in graphene." *Nature* **438**(7065): 197-200.

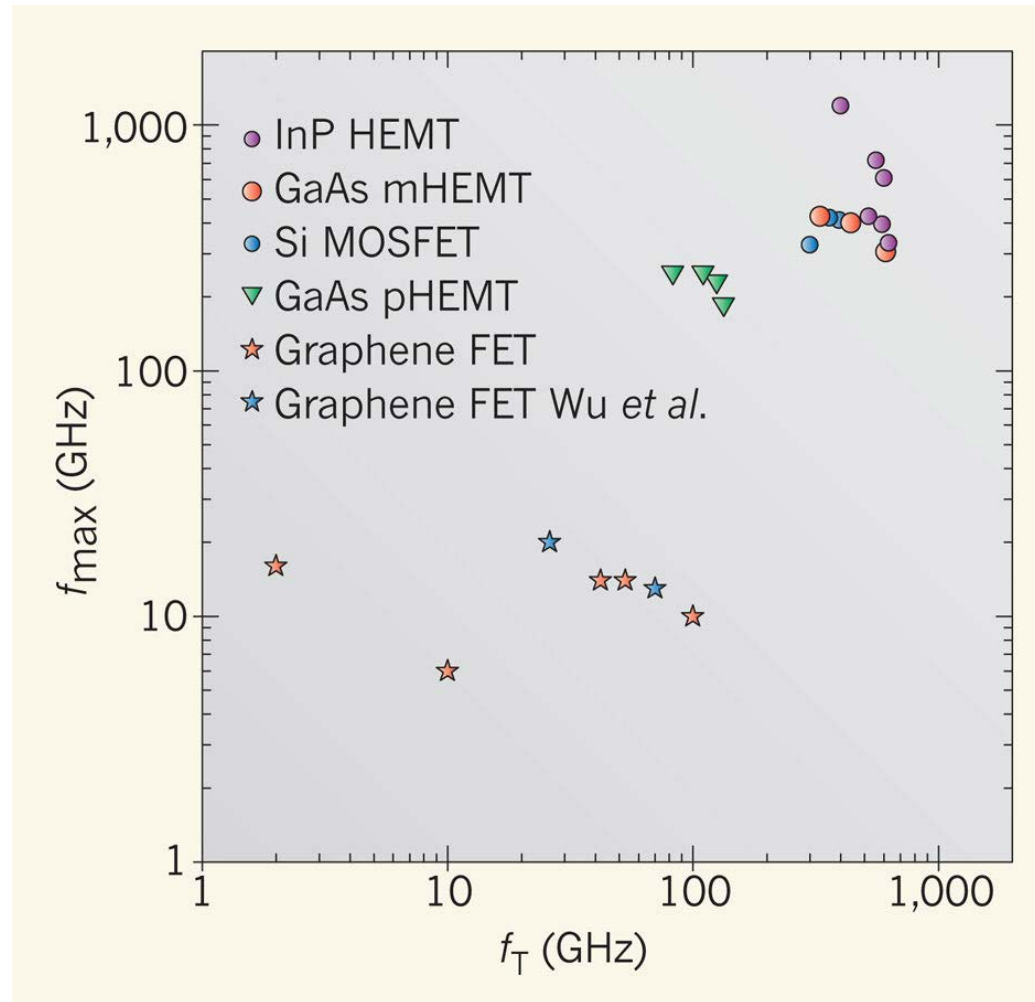
Graphene RF FET devices



I. Meric, M. Han, A. Young, B. Ozyilmaz, P. Kim and K. Shepard, "Current Saturation in Zero-Bandgap, Top-Gated Graphene Field-Effect Transistors", *Nature Nanotechnology*, **3**, 654-659, (2008)

J. S. Moon, D. Curtis, M. Hu, D. Wong, C. McGuire, P. M. Campbell, G. Jernigan, J. L. Tedesco, B. VanMil, R. Myers-Ward, C. Eddy and D. K. Gaskill, "Epitaxial-Graphene Rf Field-Effect Transistors on Si-Face 6h-Sic Substrates", *Electron Device Letters, IEEE*, **30**, 650-652, (2009).

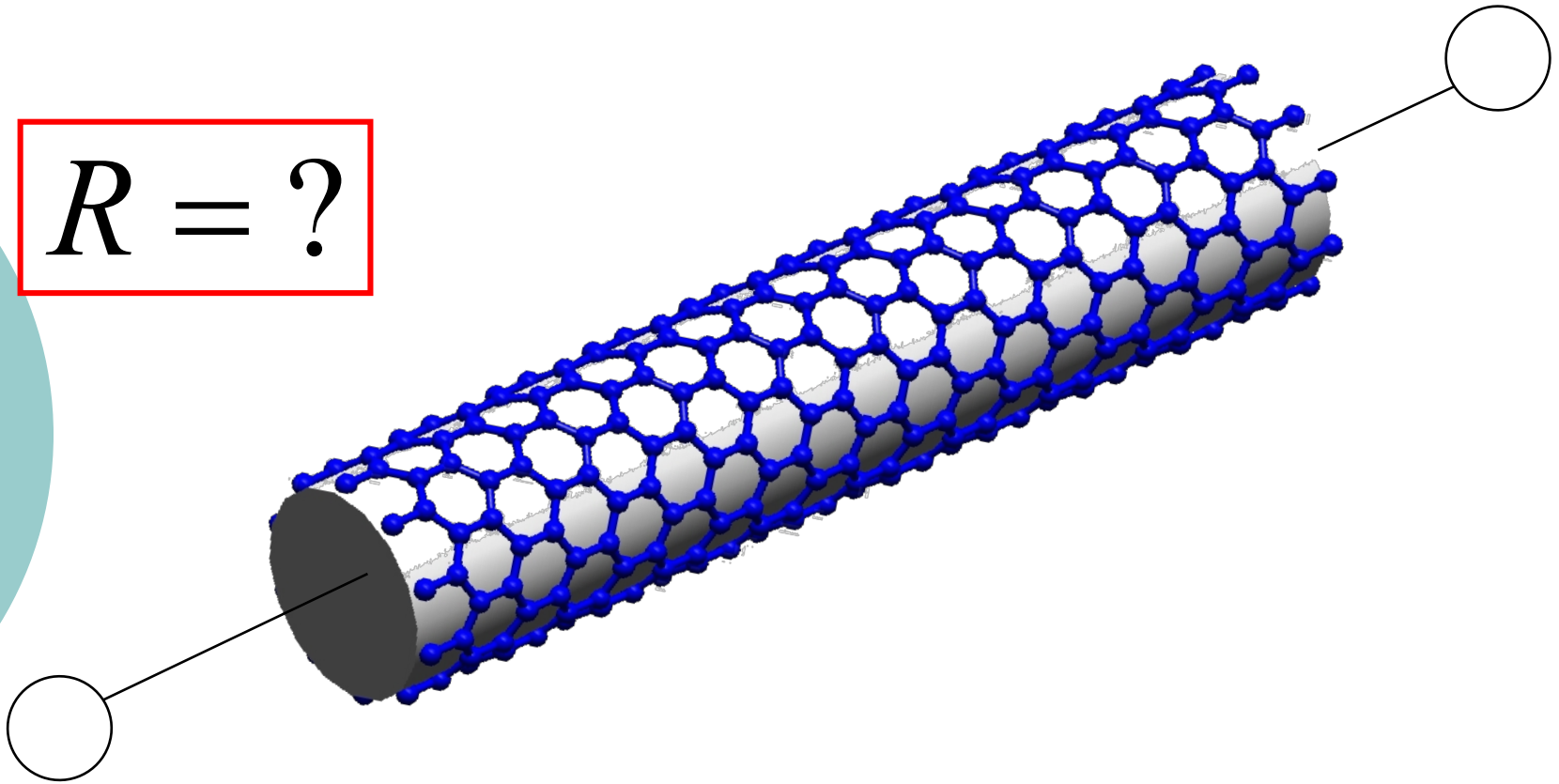
Cutoff frequency



Schwierz, F. (2011). "Electronics: Industry-compatible graphene transistors." *Nature* **472**(7341): 41-42.

Lectures 14: Carbon Nanotubes

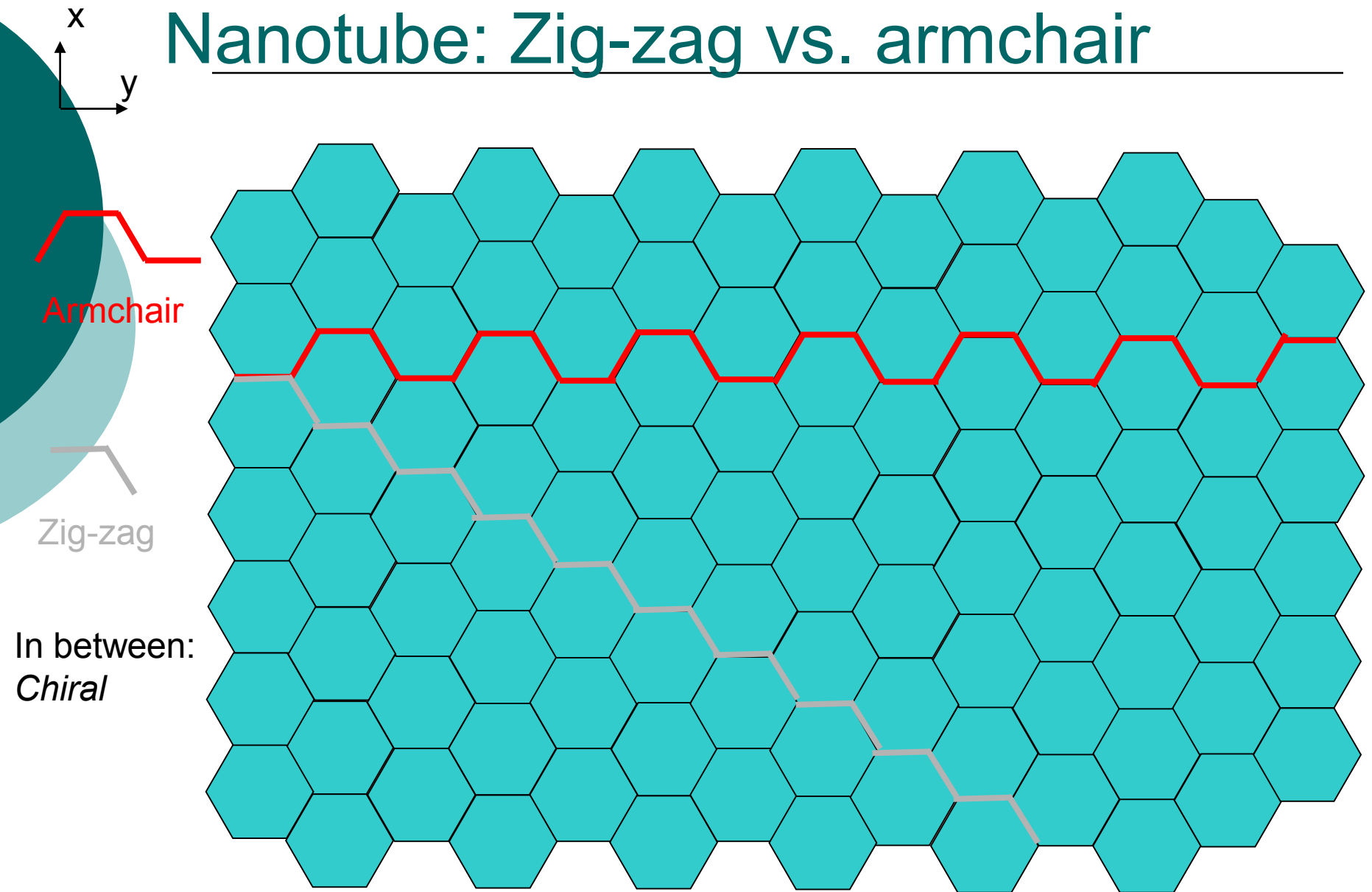
$$R = ?$$



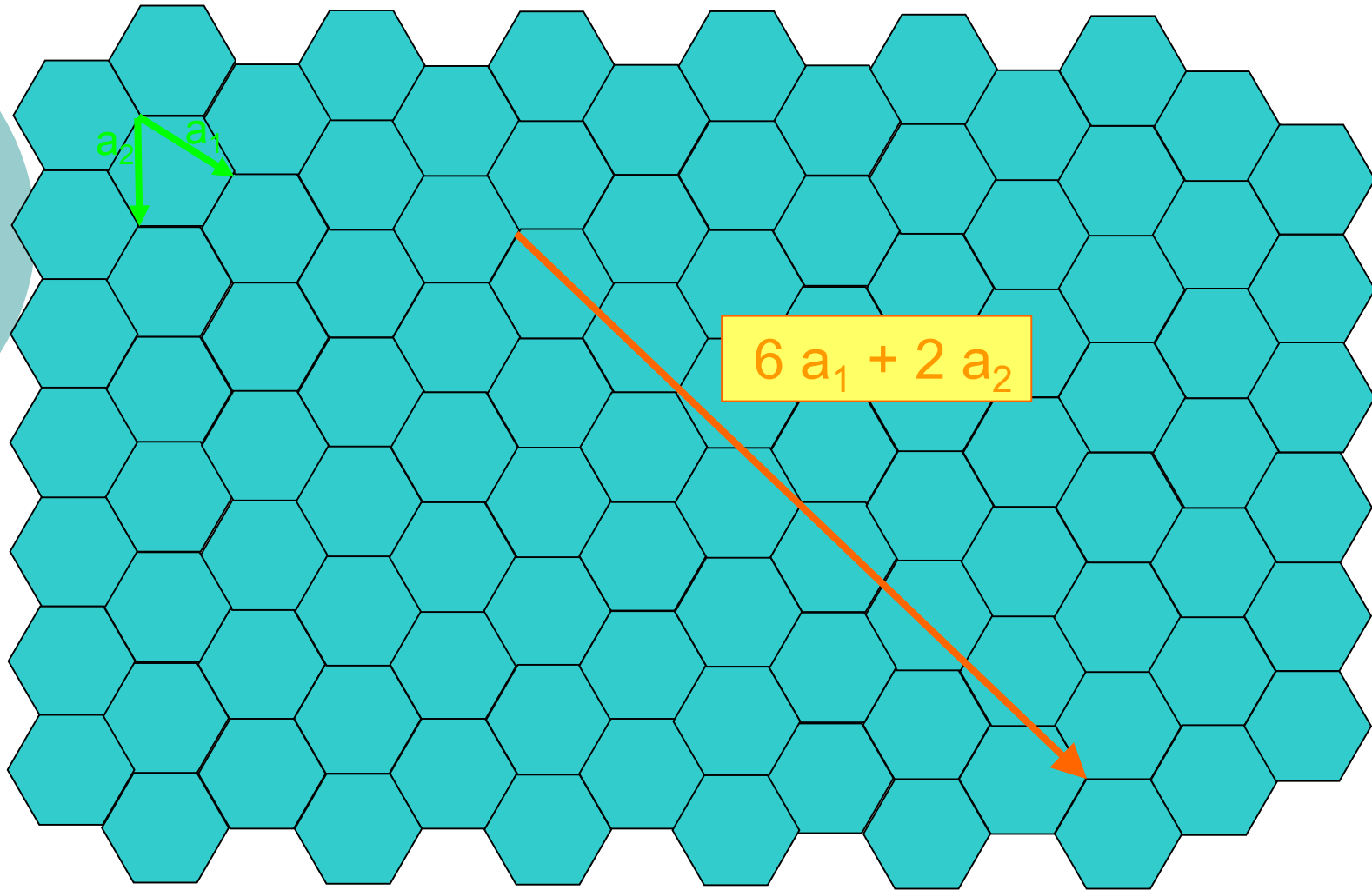
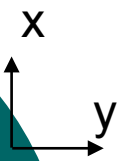
Readings this lecture covers

- Hanson, pp. 170-176
- McEuen review, *IEEE Transactions on Nanotechnology*, reading packet

Nanotube: Zig-zag vs. armchair



Nanotube: (n,m) description

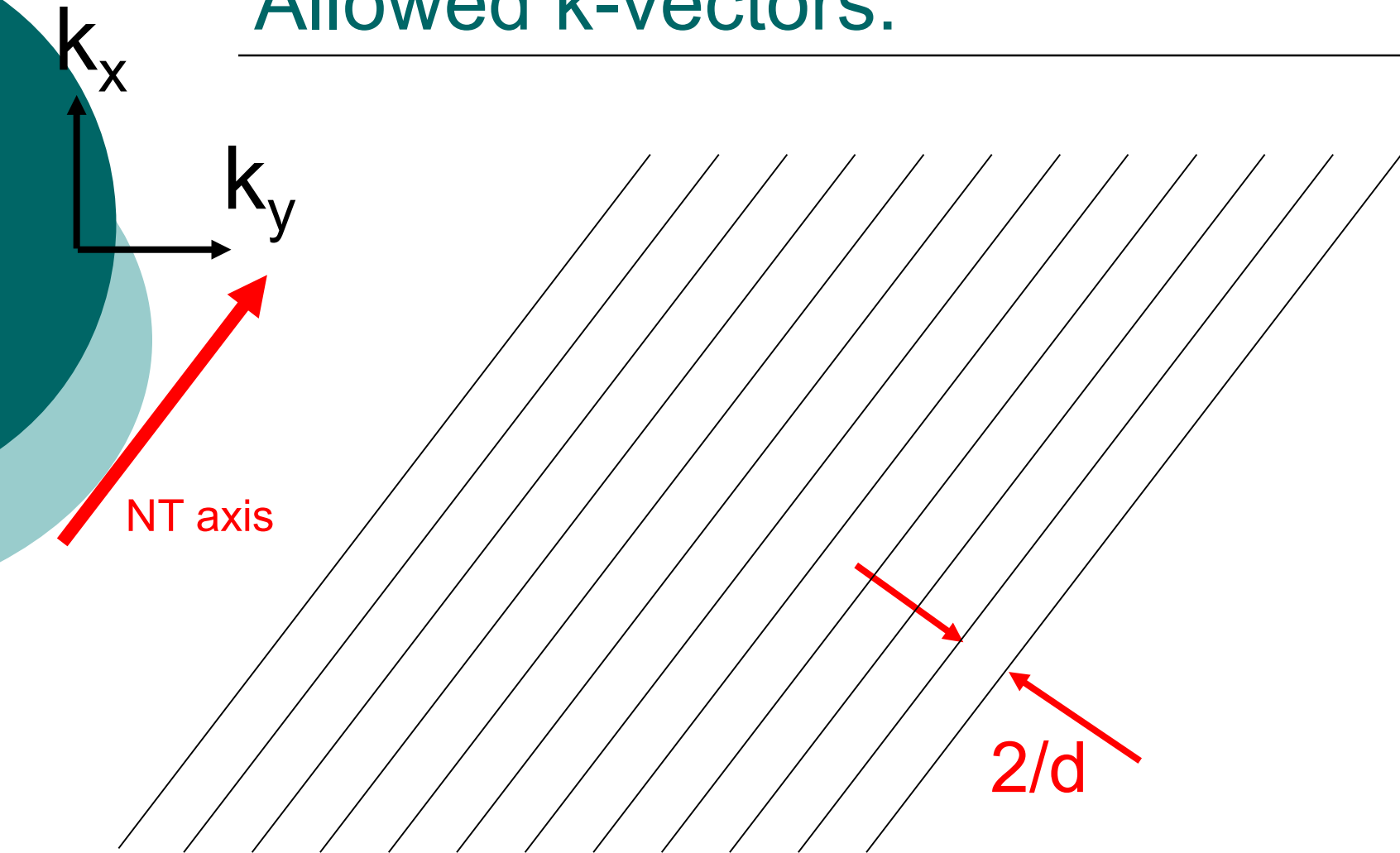


In this example: $(n,m) = (6,2)$

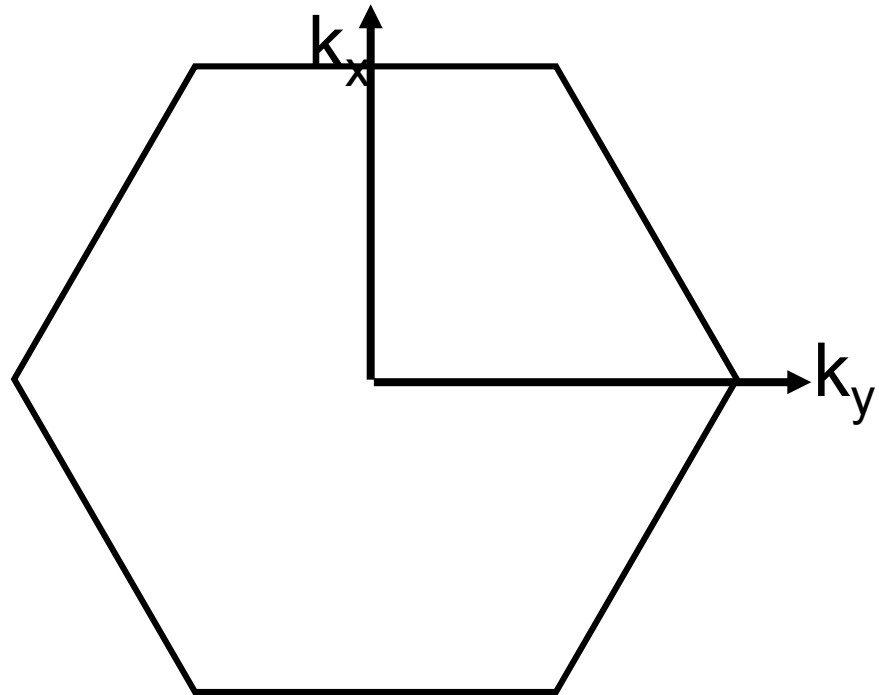
k-vector

- Graphite:
 - Arbitrary k_x, k_y allowed
- Nanotube:
 - $\psi(\phi) = \psi(\phi + 2\pi)$
 - k_{perp} spaced by $2/d$

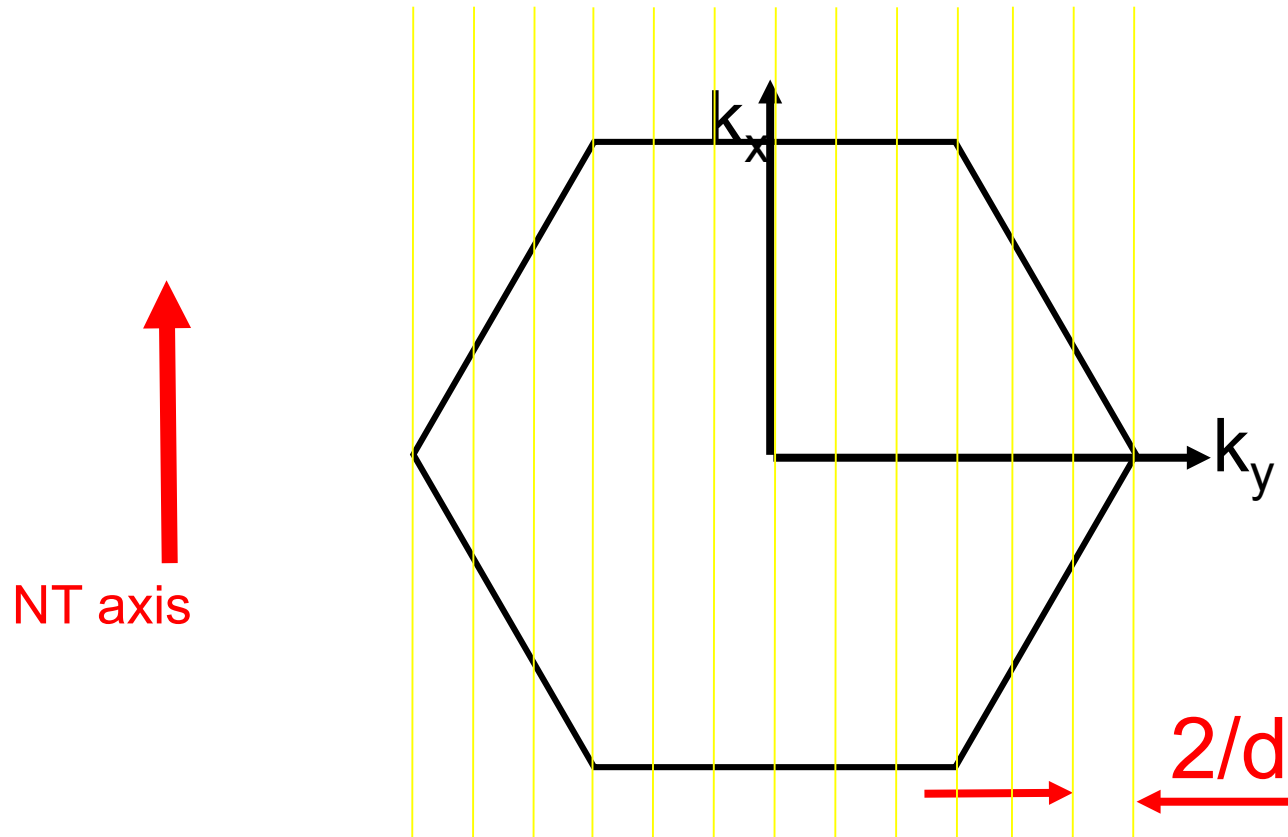
Allowed k-vectors:



k-space



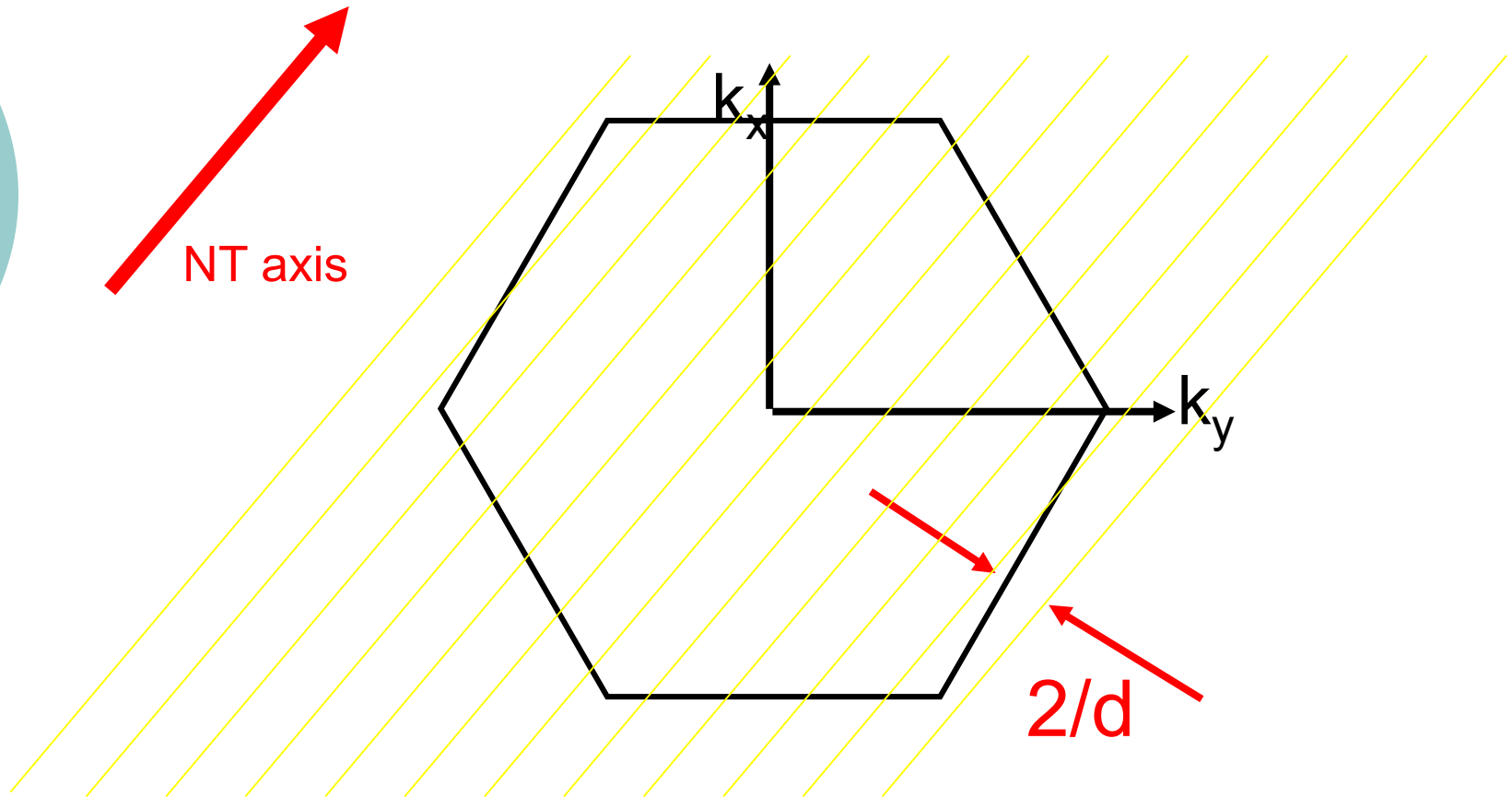
(9,0) armchair nanotube



All armchairs are metallic.

$$G = \frac{2e^2}{h} \sum T_n = \frac{4e^2}{h}$$

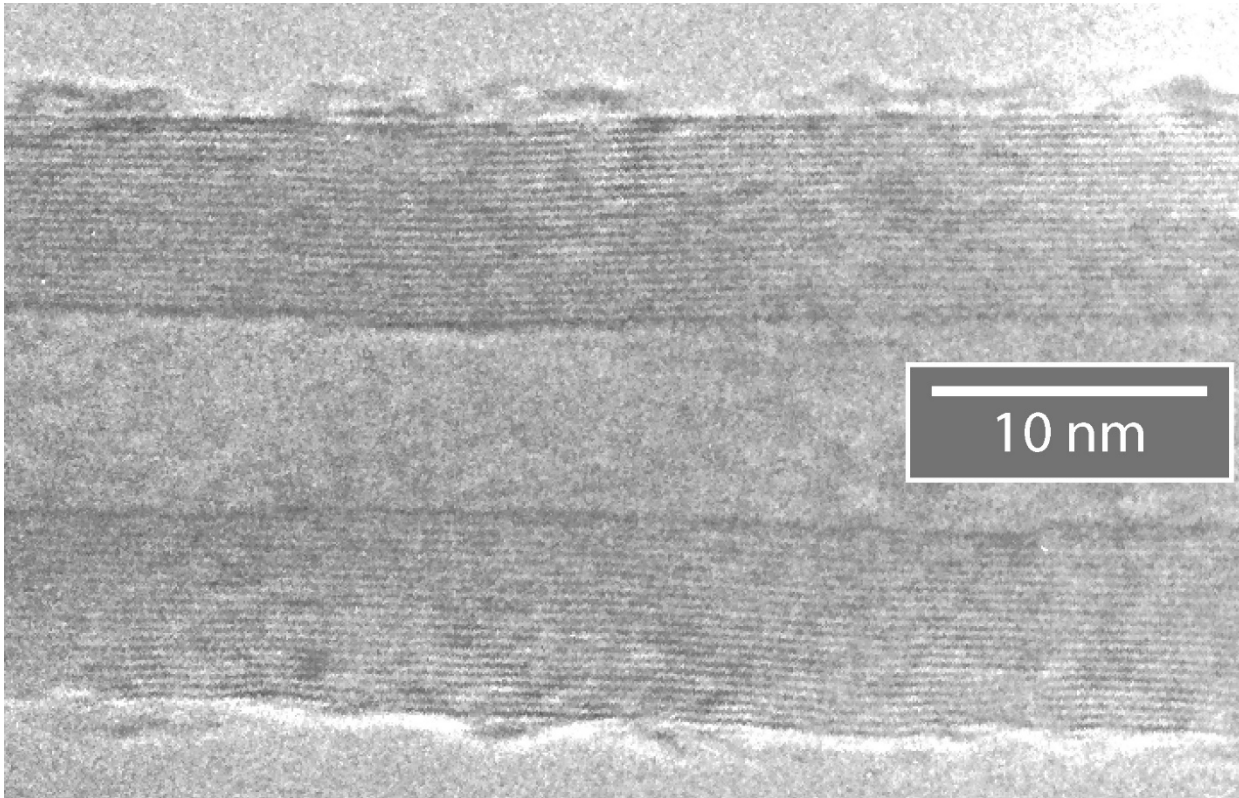
Semiconducting nanotube



Electrical properties

- All armchair metallic
- 33% of zig-zag metallic
- Semiconducting tubes:
 - Gap = $0.9 \text{ eV}/d[\text{nm}]$

Multi-walled nanotube (MWNT)

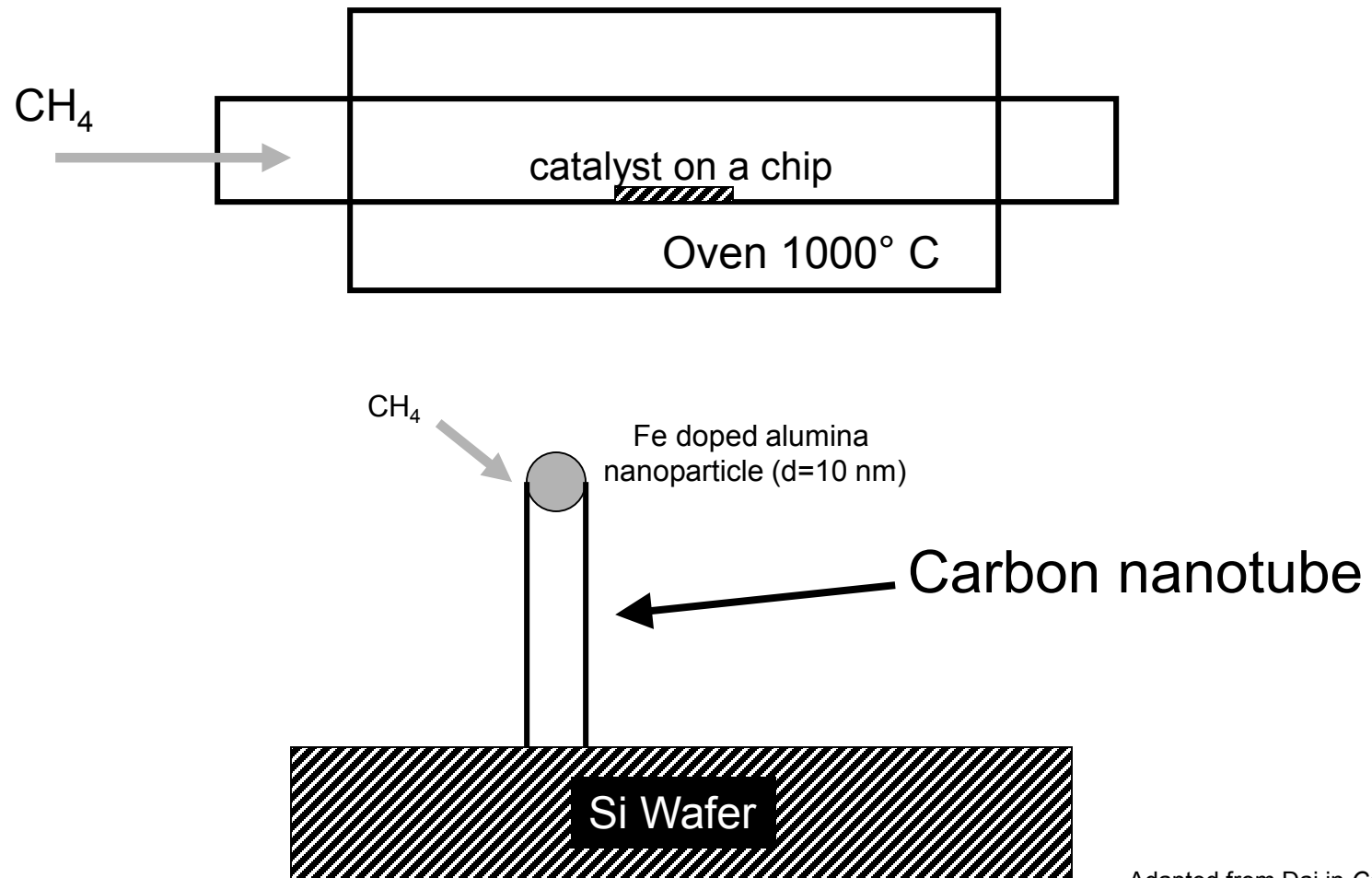


Shengdong Li, unpublished

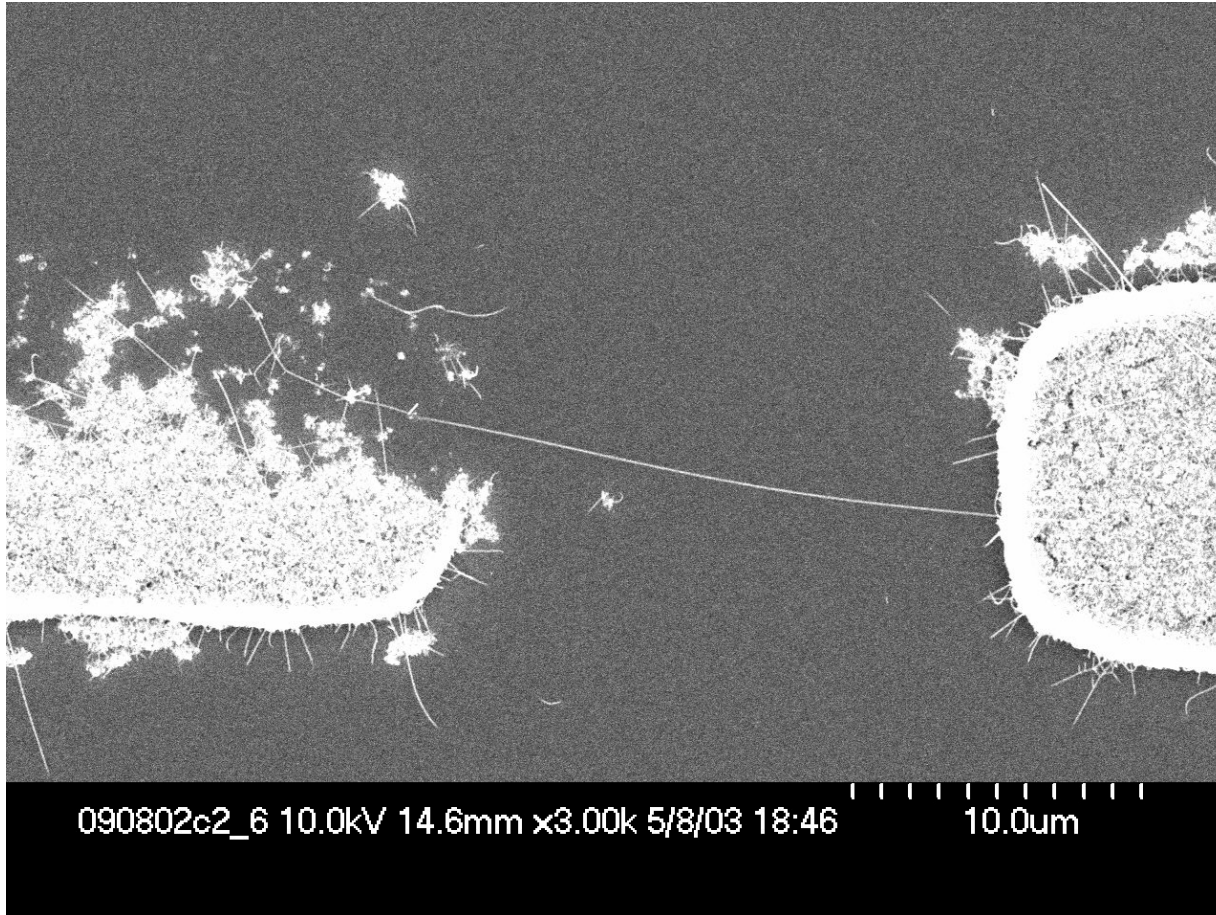
Growth technologies

- Arc discharge
- Laser ablation
- Chemical vapor deposition (CVD)

CVD



Lithographically defined catalysts



Shengdong Li, unpublished

Single Walled Carbon Nanotube

$L = 0.4 \text{ cm}$

$$d/L = \text{cm/nm} = 10^7$$

$d = 1.5 \text{ nm}$

Would Schelkunoff be excited?

SWNT

Au

Au

Conductivity larger than copper!

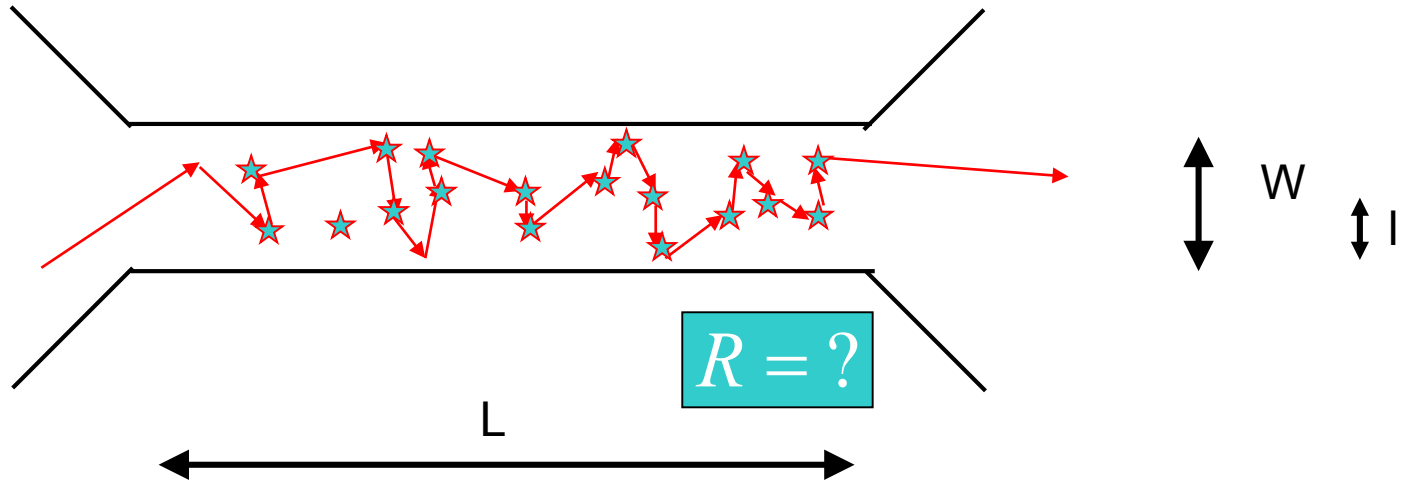
1 mm

S. D. Li, Z. Yu, C. Rutherglen and P. J. Burke, "Electrical Properties of 0.4 Cm Long Single-Walled Carbon Nanotubes", *Nano Letters*, **4**, 2003-2007, (2004).

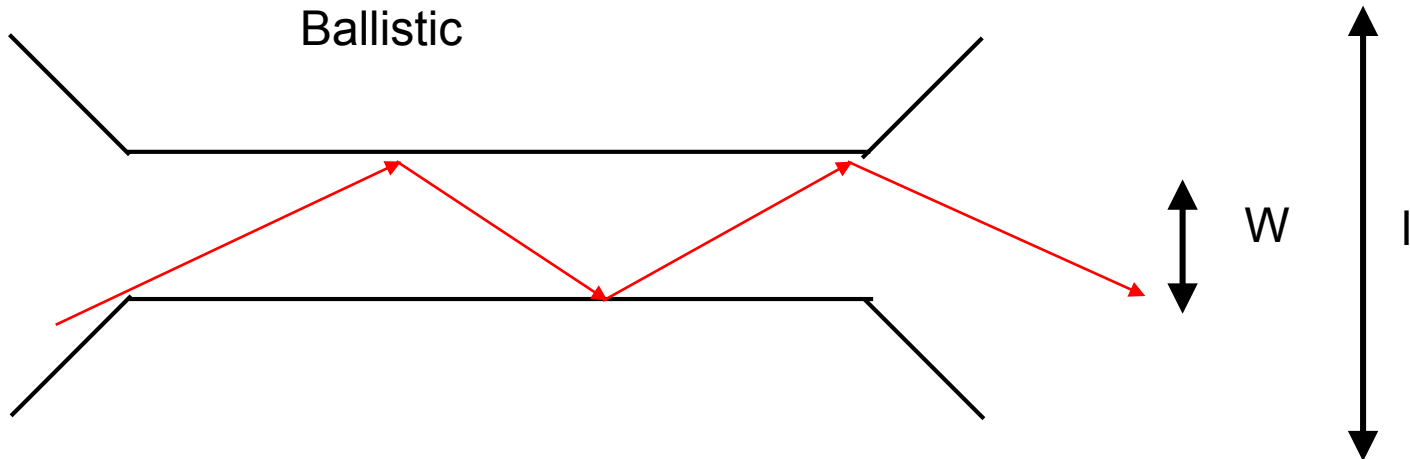
Ballistic vs. diffusive transport

Diffusive

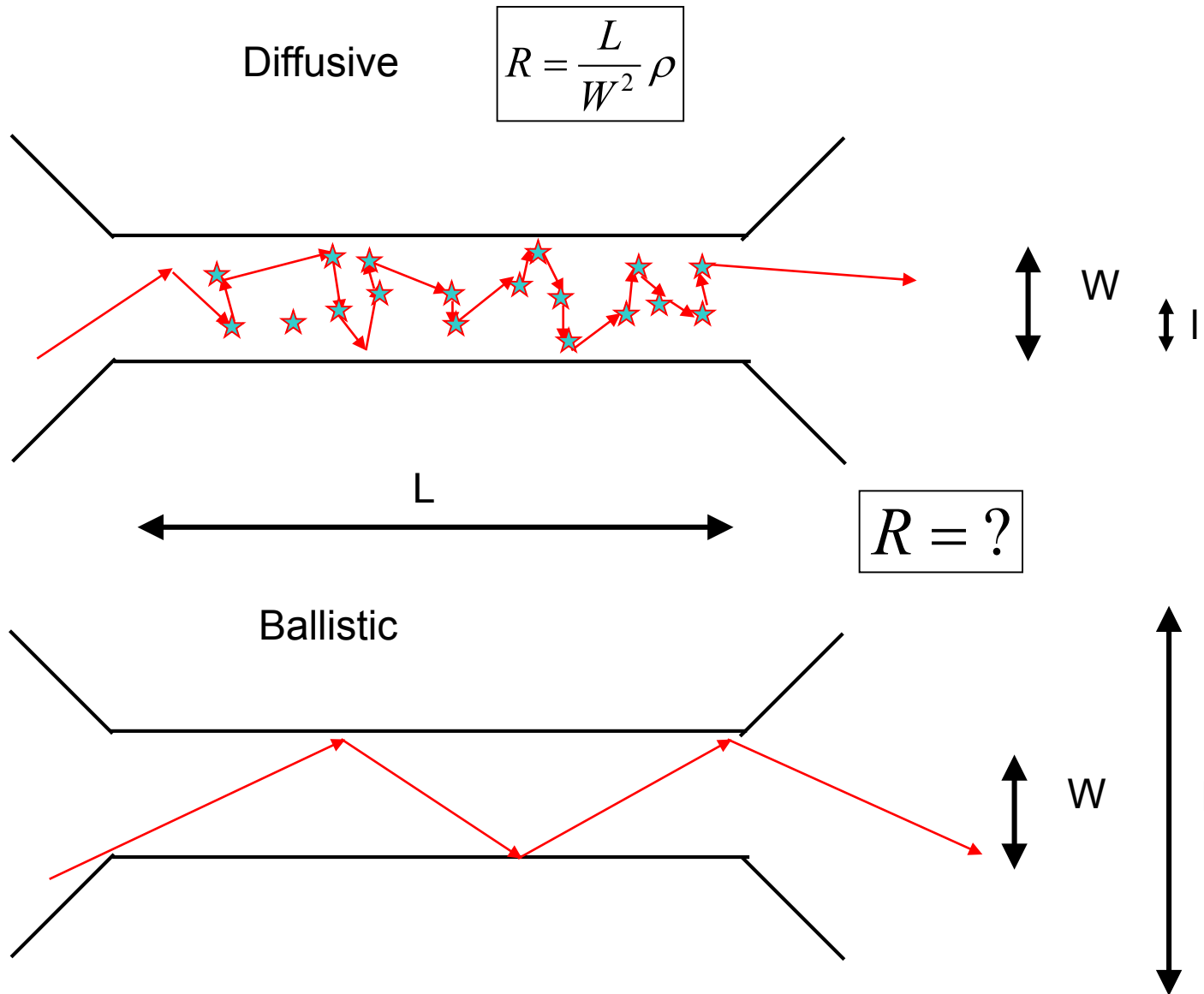
$$R = \frac{L}{W^2} \rho$$



Ballistic



Ballistic vs. diffusive transport



Landauer formula:

$$G = n \frac{2e^2}{h}$$

If the leads are not perfect injectors into each “channel” then:

$$G = \frac{2e^2}{h} \sum T_n$$

Resistance vs. length

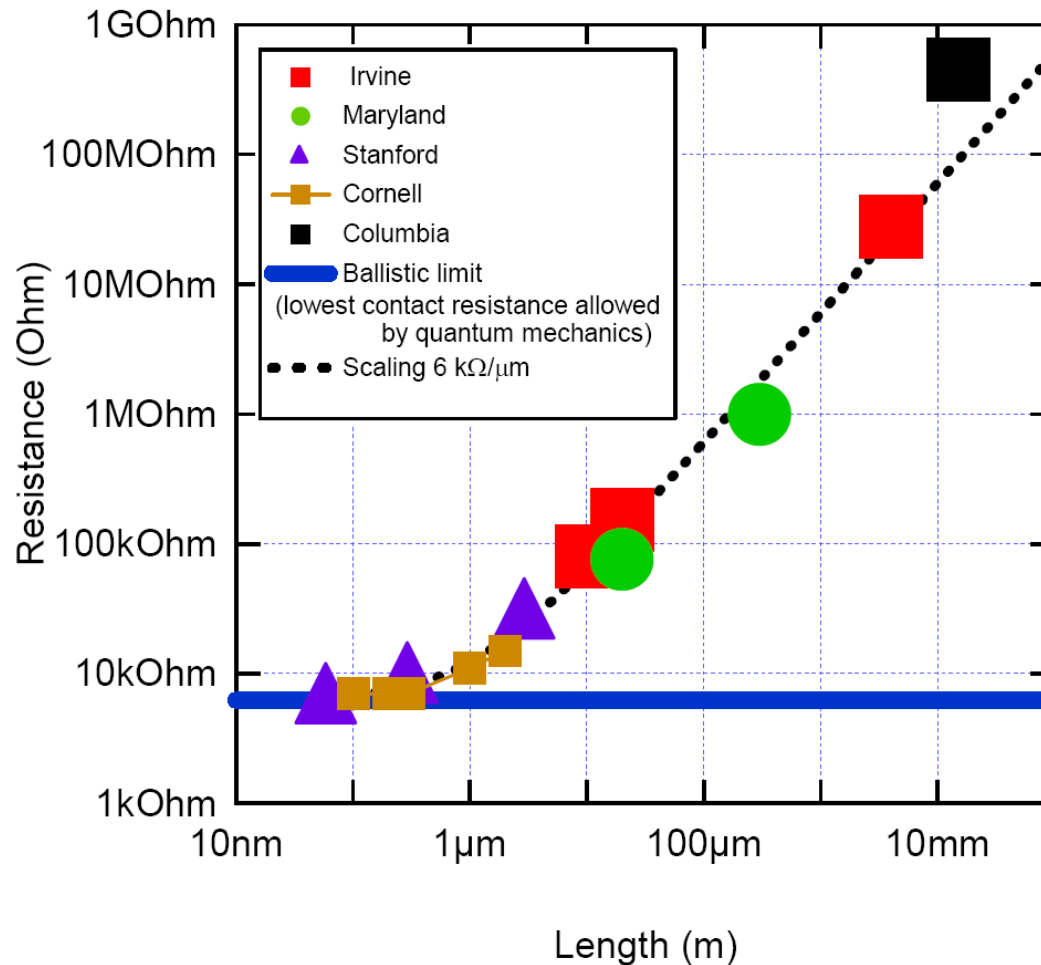
$$R(L) = R_{\text{contact}} + \frac{L}{L_{\text{mfp}}} \frac{h}{4e^2}$$

$$R_{\text{contact}} \geq h/4e^2 = 6 \text{ k}\Omega$$

Shengdong Li, Zhen Yu, C. Rutherglen, P. J. Burke "Electrical Properties of 0.4 cm Long Single-Walled Carbon Nanotubes", *Nano Letters*, 2004.

Resistance vs. length

$$R = R_{\text{contact}} + L \cdot 6 \text{ k}\Omega/\mu\text{m}$$



Shengdong Li, Zhen Yu, C. Rutherglen, P. J. Burke "Electrical Properties of 0.4 cm Long Single-Walled Carbon Nanotubes", *Nano Letters*, 2004.

R vs L single tube

PRL 98, 186808 (2007)

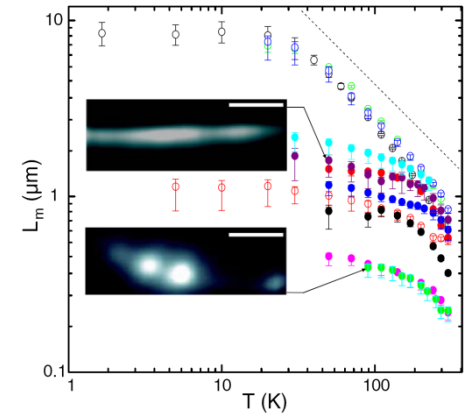
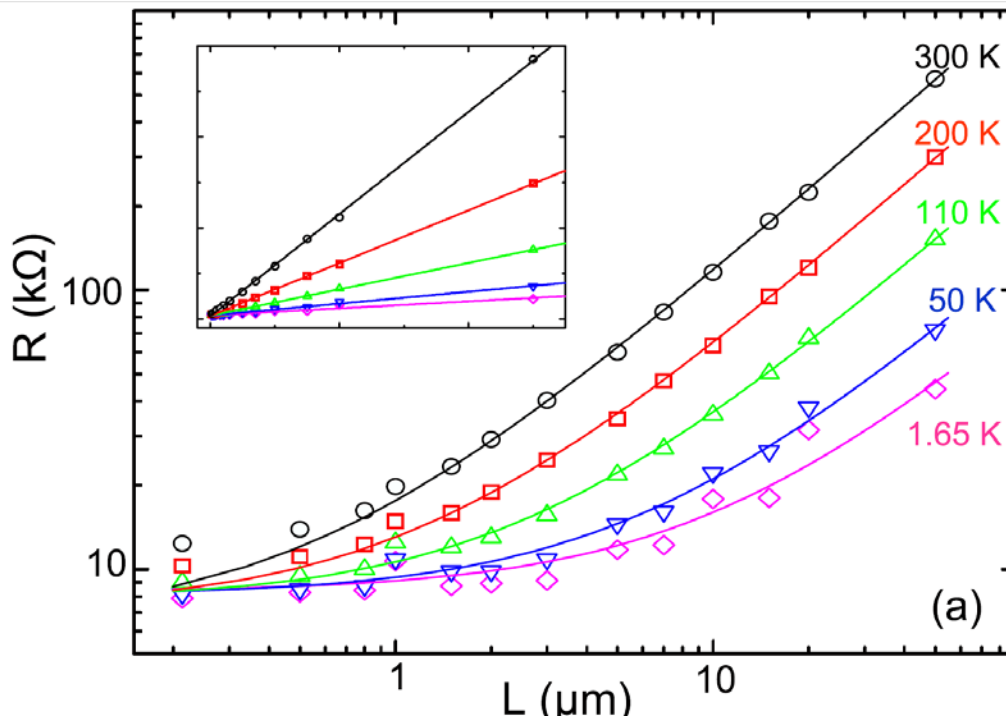
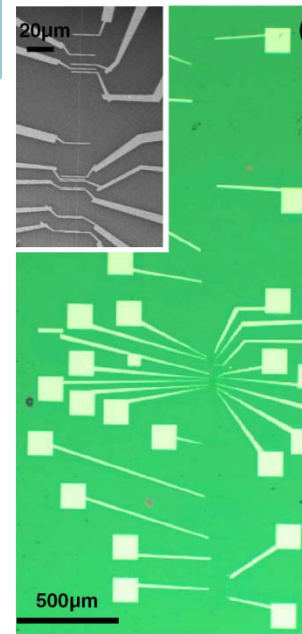
PHYSICAL REVIEW LETTERS

week ending
4 MAY 2007

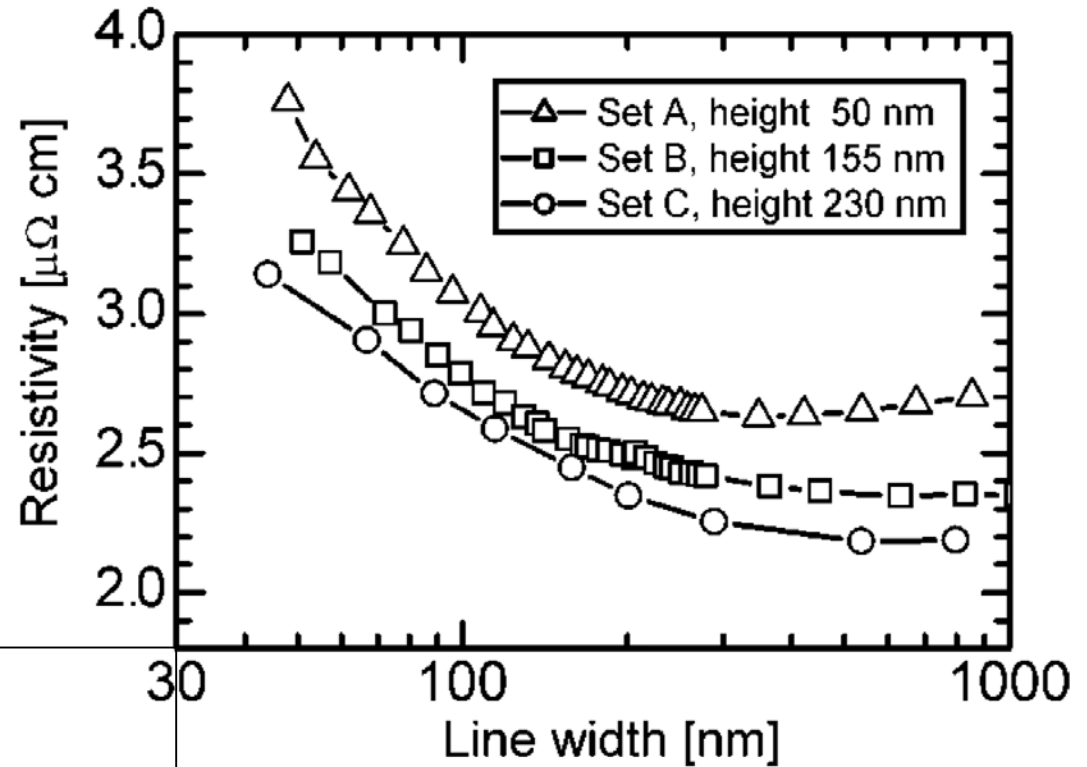


Scaling of Resistance and Electron Mean Free Path of Single-Walled Carbon Nanotubes

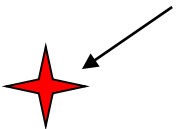
Meninder S. Purewal,¹ Byung Hee Hong,² Anirudhh Ravi,² Bhupesh Chandra,³ James Hone,³ and Philip Kim²



Comparison to Cu



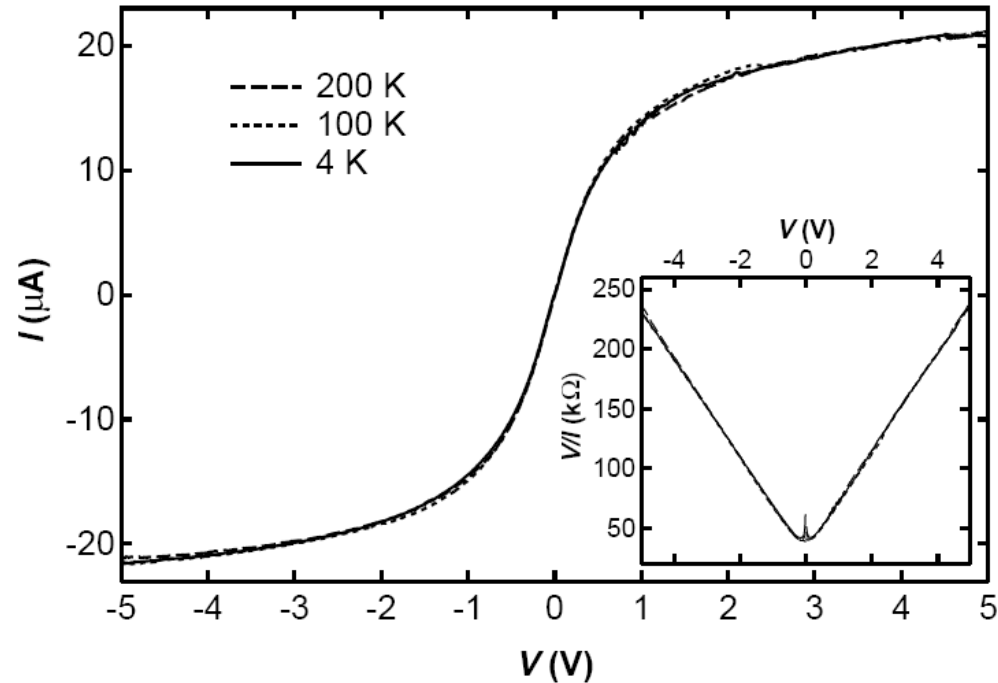
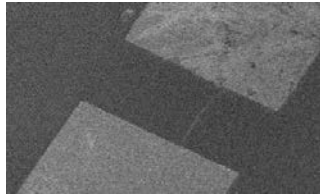
SWNT



$d=1.5\text{ nm}$, $6\text{ k}\Omega/\mu\text{m}$
 $\Rightarrow 1.1\ \mu\Omega\text{-cm}$

[1.] W. Steinhogel, G. Schindler, G. Steinlesberger, M. Traving and M. Engelhardt, "Comprehensive Study of the Resistivity of Copper Wires with Lateral Dimensions of 100 Nm and Smaller", *Journal of Applied Physics*, **97**, 023706, (2005).

High field transport: Diffusive regime



High-Field Electrical Transport in Single-Wall Carbon Nanotubes

[Zhen Yao](#)¹, [Charles L. Kane](#)², and [Cees Dekker](#)¹

Phys. Rev. Lett. 84, 2941 - 2944 (2000)

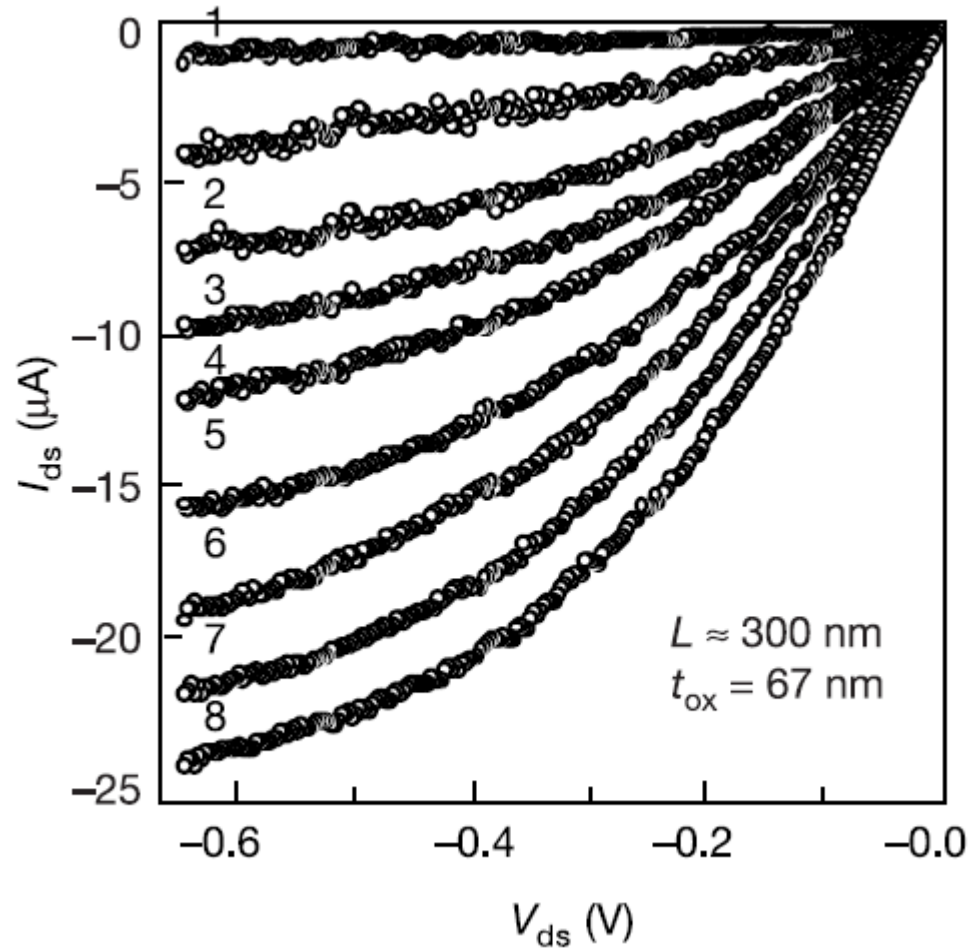
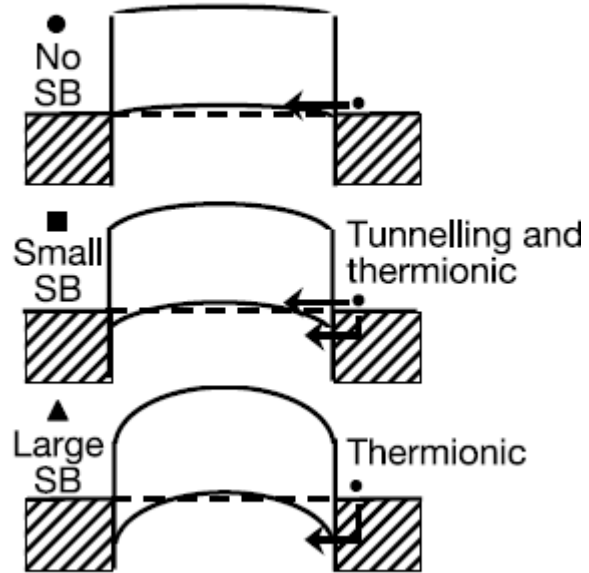
[Issue 13 – March 2000]

Prior dc work:

$$V/I = R_0 + |V|/I_0$$



Ohmic p-type contact

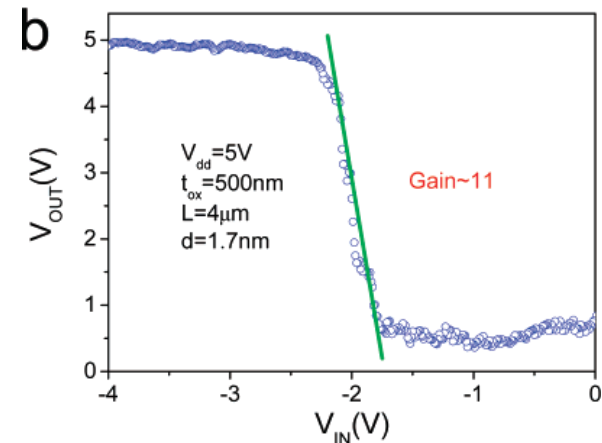
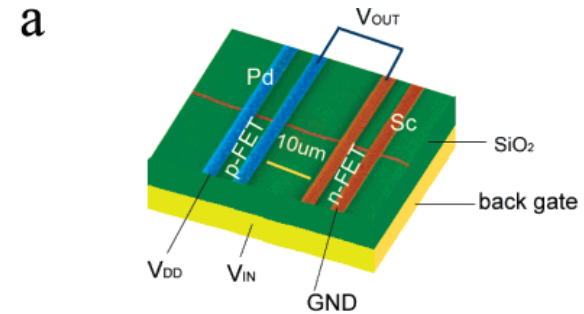
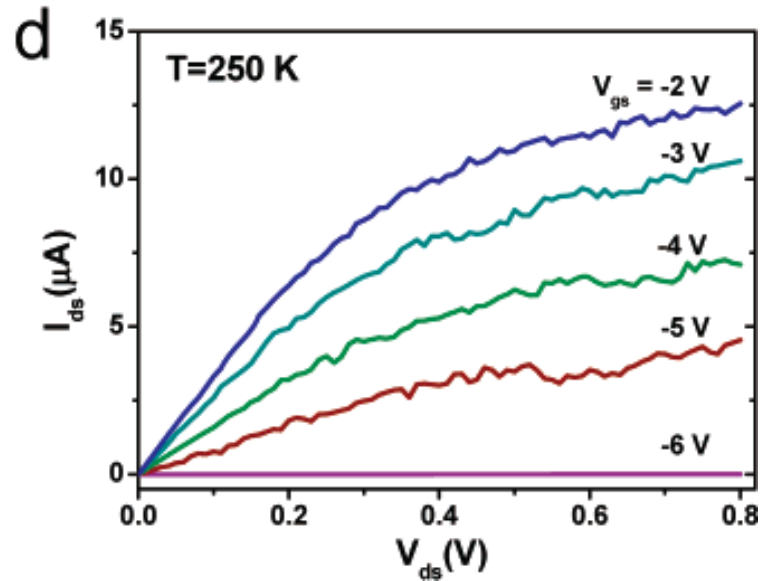
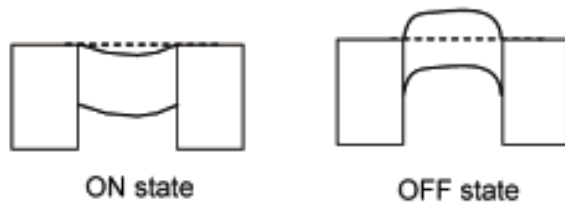


Ballistic carbon nanotube field-effect transistors

Ali Javey Jing Guo Qian Wang Mark Lundstrom & Hongjie Dai

Nature 424, 654 - 657 (2003).

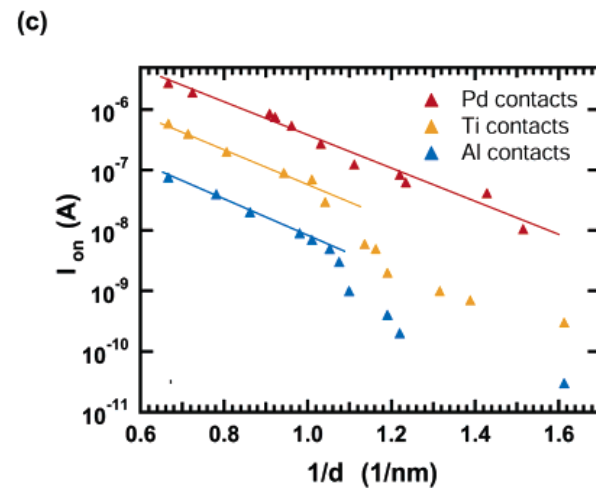
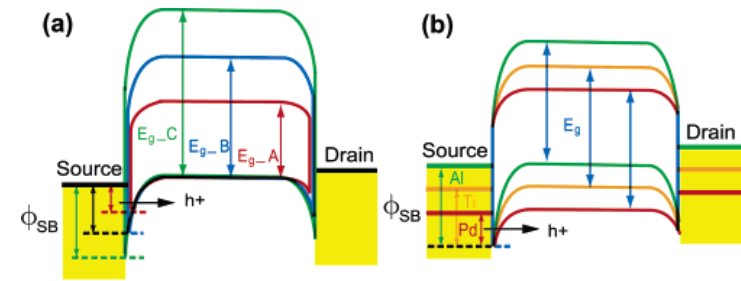
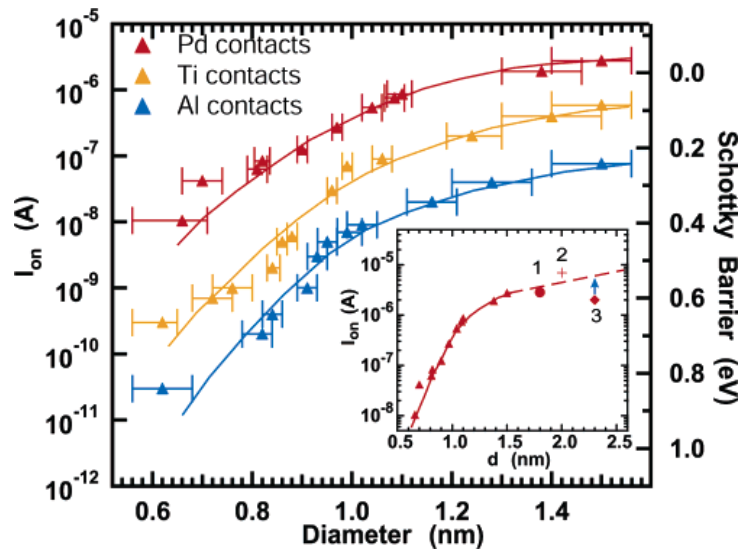
Ohmic n-type contact



Doping-Free Fabrication of Carbon Nanotube Based Ballistic CMOS Devices and Circuits

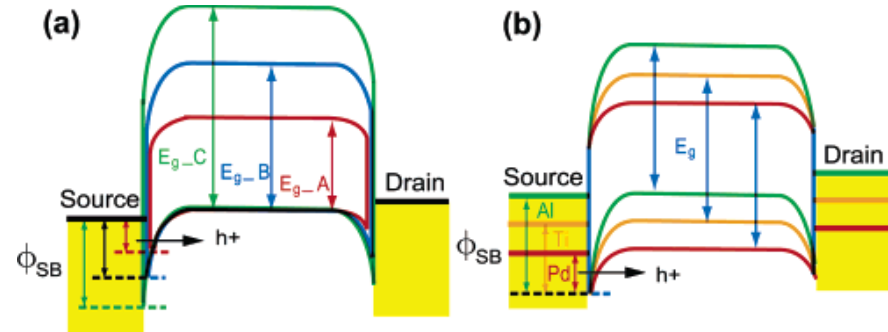
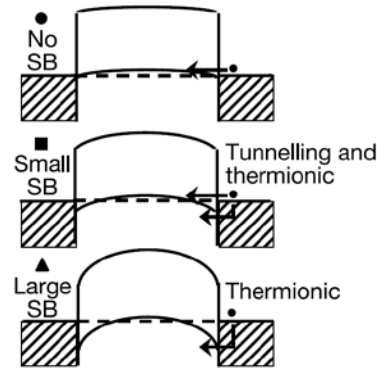
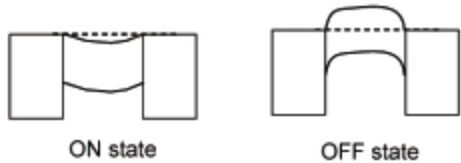
Zhang, Z.; Liang, X.; Wang, S.; Yao, K.; Hu, Y.; Zhu, Y.; Chen, Q.; Zhou, W.; Li, Y.; Yao, Y.; Zhang, J.; Peng, L.-M. Nano Lett.; (Letter); 2007; 7(12); 3603-3607

Electrical contact: Role of metals



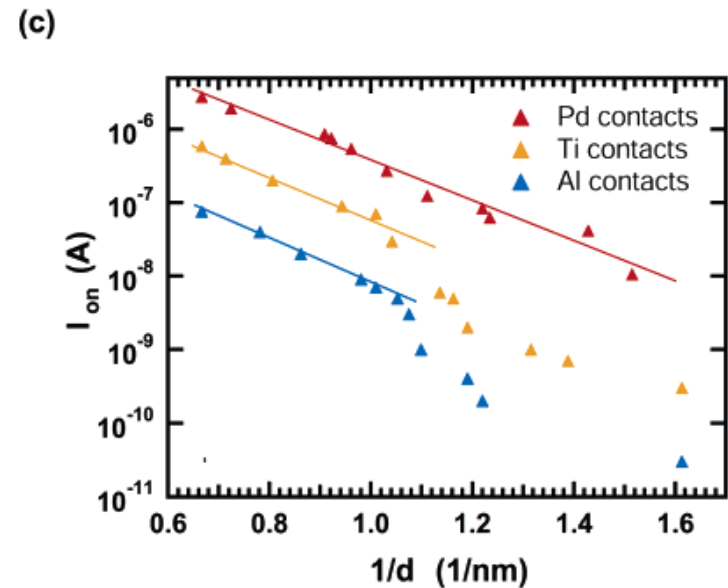
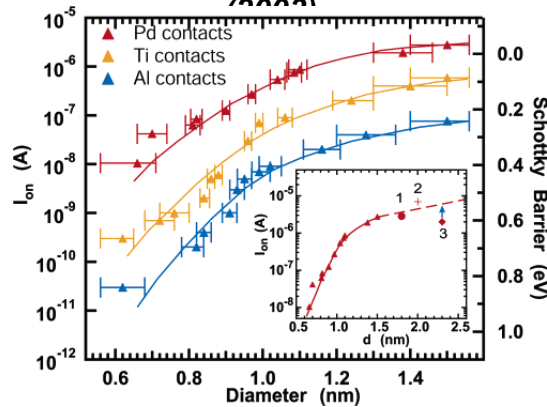
The Role of Metal-Nanotube Contact in the Performance of Carbon Nanotube Field-Effect Transistors
 Chen, Z.; Appenzeller, J.; Knoch, J.; Lin, Y.-M.; Avouris, Ph.
 Nano Lett.; (Letter); 2005; 5(7); 1497-1502.

N-type, p-type, SB FET



X. Peng, N. Komatsu, S. Bhattacharya, T. Shimawaki, S. Aonuma, T. Kimura and A. Osuka, "Optically Active Single-Walled Carbon Nanotubes", *Nature*, **2**, 361-365, (2007).

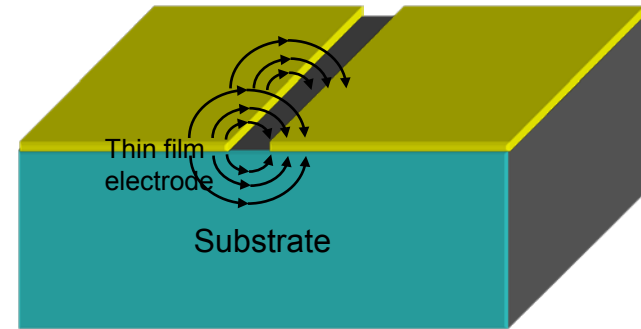
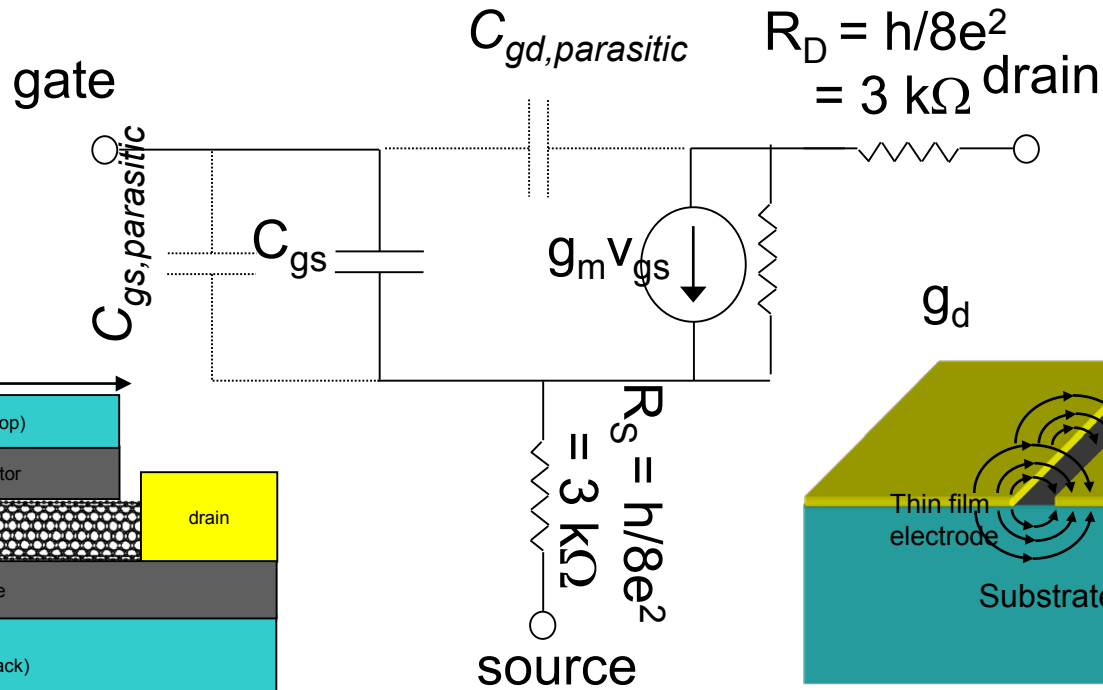
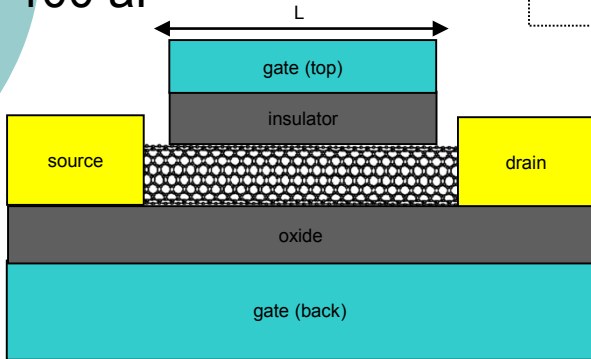
A. Javey, J. Guo, Q. Wang, M. Lundstrom and H. J. Dai, "Ballistic Carbon Nanotube Field-Effect Transistors", *Nature*, **424**, 654-657, (2002).



Z. Chen, J. Appenzeller, J. Knoch, Y.-M. Lin and P. Avouris, "The Role of Metal-Nanotube Contact in the Performance of Carbon Nanotube Field-Effect Transistors", *Nano Lett.*, **5**, 1497-1502, (2005).

Effect of parasitics

$C_{gs} \sim 1-10 \text{ aF}$
 $g_m \sim 10 \mu\text{S}$
 $C_p \sim 100 \text{ aF}$



If parasitics minimized:

$$\frac{1}{2\pi f_T} = (R_S + R_D)C_{gd,p} + \frac{1}{g_m}(C_{gs} + C_{gd,p} + C_{gd,p}) + \frac{g_d}{g_m}(R_S + R_D)(C_{gs} + C_{gd,p} + C_{gd,p})$$

~ 10 GHz

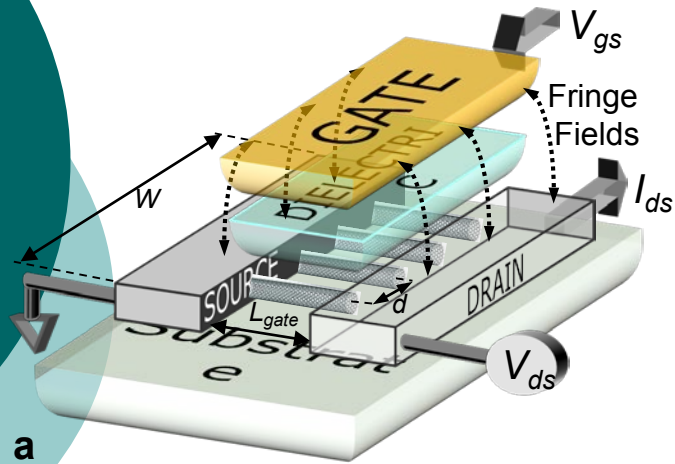
$$\frac{1}{2\pi f_T} = \frac{C_{gs}}{g_m}$$

~ 1 THz

P. J. Burke, "AC Performance of Nanoelectronics: Towards a Ballistic THz Nanotube Transistor", *Solid State Electronics*, **40**, 1981-1986

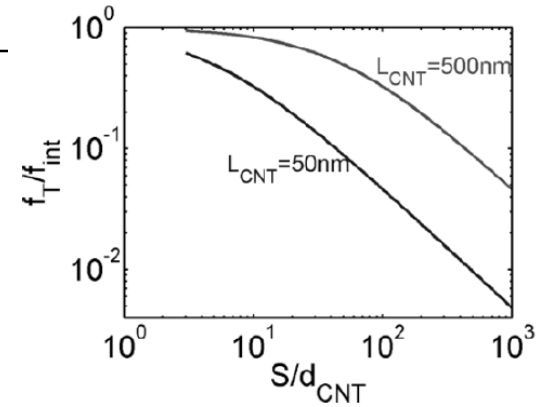


Nanotube density

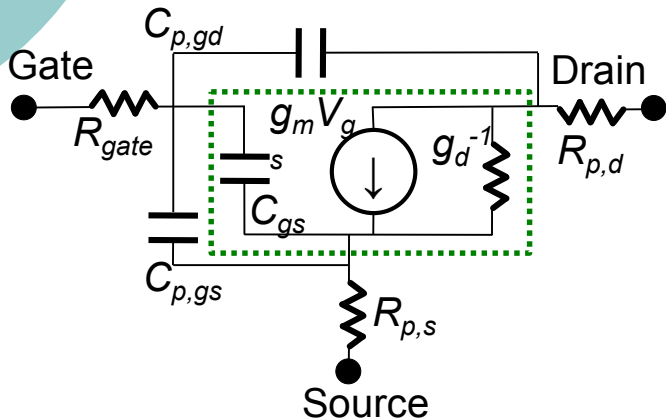


$$f_T = \frac{g_m}{2\pi C_{gs}}$$

$$f_T = \frac{g_m}{2\pi C_{gs}} \left(\frac{1}{1 + \frac{C_w}{C_{gs}} d} \right)$$



J. Guo, S. Hasan, A. Javey, G. Bosman and M. Lundstrom, "Assessment of High-Frequency Performance Potential of Carbon Nanotube Transistors", *IEEE Transactions on Nanotechnology*, **4**, 715-721, (2005).

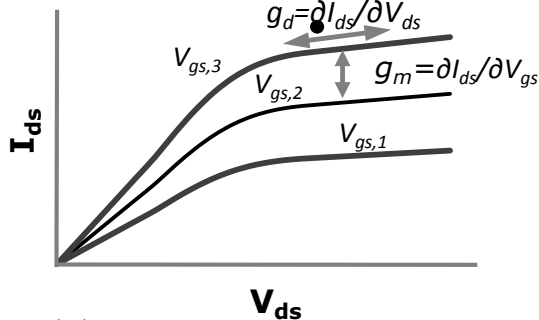


C. Rutherglen, D. Jain and P. Burke, "Nanotube Electronics for RF Applications", *Nature Nanotechnology*, in press, (2009).

$$v_{drift} = \begin{cases} \mu E & E = V_{ds}/L_{gate} \text{ small} \Leftrightarrow L_{gate} \text{ large} \\ v_{sat} & E = V_{ds}/L_{gate} \text{ large} \Leftrightarrow L_{gate} \text{ small} \end{cases}$$

$$f_T = \begin{cases} \mu(V_{gate} - V_T)/\pi L_{gate}^2 & L_{gate} \text{ "large"} \\ v_{sat}/2\pi L_{gate} & L_{gate} \text{ "small"} \end{cases}$$

$$f_{max} \approx \frac{f_T}{2[g_d(R_{parasitic,s} + R_{gate}) + 2\pi f_T C_{parasitic,gd} R_{gate}]^{1/2}}$$



Dense arrays on quartz

- What is length, diameter, chirality, impurity density of each tube on wafer scale?
- Raman?
- PL?
- Other techniques?

L. Ding, D. Yuan and J. Liu, "Growth of High-Density Parallel Arrays of Long Single-Walled Carbon Nanotubes on Quartz Substrates", *J. Am. Chem. Soc.*, **130**, 5428-5429, (2008).

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S. Han, X. Liu and C. Zhou, "Template-Free Directional Growth of Single-Walled Carbon Nanotubes on a- and R-Plane Sapphire", *J. Am. Chem. Soc.*, **127**, 5294-5295, (2005).

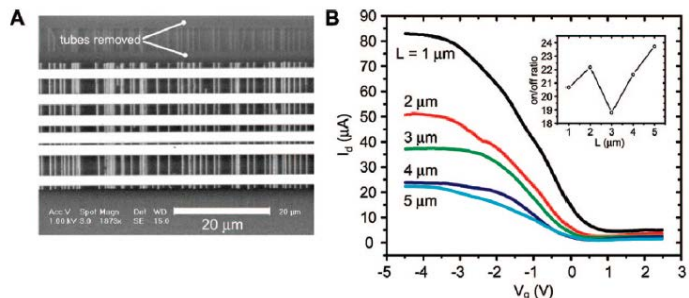
Z. Chongwu, L. Xiaolei, H. Song and I. Fumiaki, "A Nanotube-on-Insulator (Noi) Approach toward Scalable and Integratable Nanotube Devices on Sapphire", in *Solid-State and Integrated Circuit Technology, 2006. ICSICT '06. 8th International Conference on. 2006. p. 1065-1067.*

W. Zhou, C. Rutherglen and P. Burke, "Wafer Scale Synthesis of Dense Aligned Arrays of Swnts", *Nano Research*, **1**, 158-165, (2008).

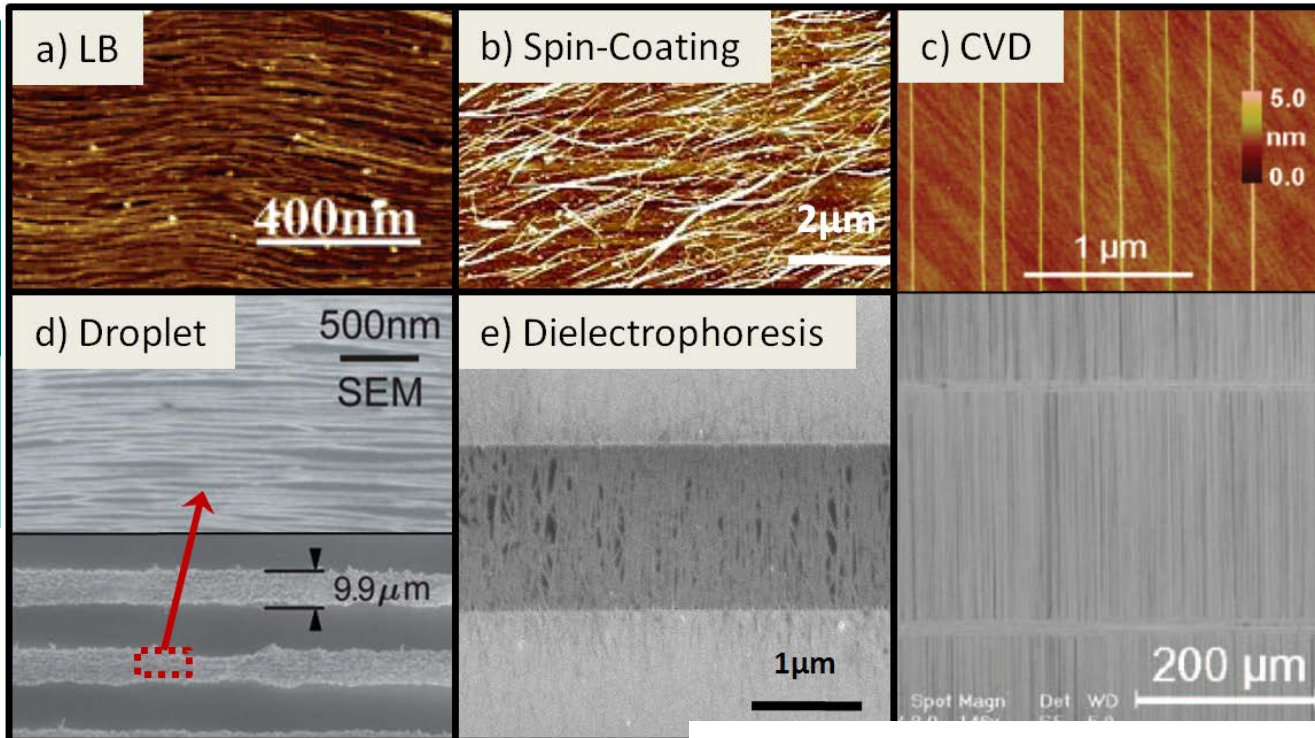
H. Ago, K. Imamoto, N. Ishigami, R. Ohdo, K. Ikeda and M. Tsuji, "Competition and Cooperation between Lattice-Oriented Growth and Step-Templated Growth of Aligned Carbon Nanotubes on Sapphire", *Applied Physics Letters*, **90**, -, (2007).

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L. Ding, A. Tselev, J. Wang, D. Yuan, H. Chu, T. P. McNicholas, Y. Li



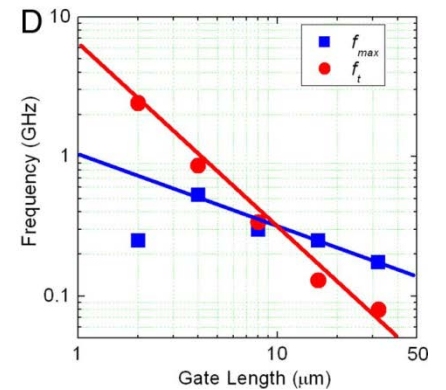
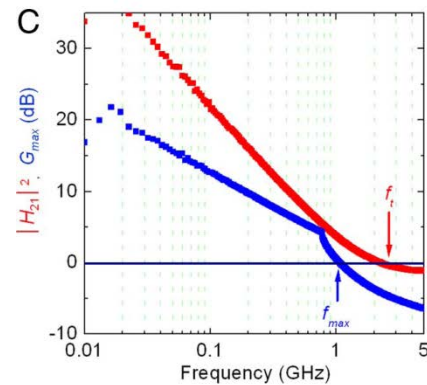
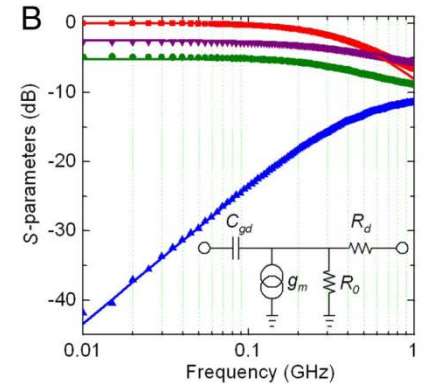
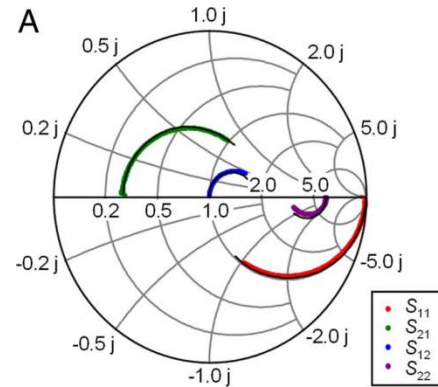
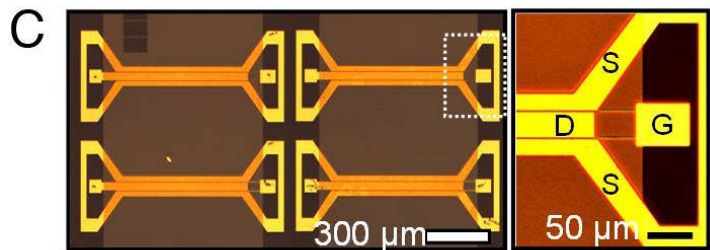
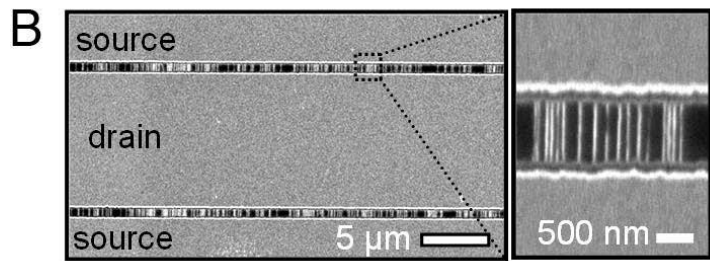
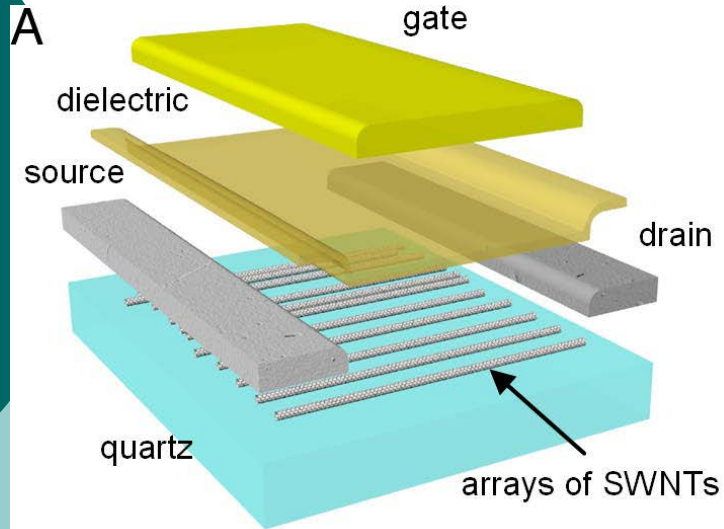
Alignment: Status & Goals



C. Rutherglen, D. Jain and P. Burke, "Nanotube Electronics for RF Applications", *Nature Nanotechnology*, in press, (2009).

Property/Parameter	Target Value or Range	Justification
Diameter	1.5 – 2.0 nm	•Current is largest in this range ^{107,108} .
Chirality	semiconducting & same (n,m)	•To obtain identical transport properties.
Purity	>99%	• No metalics for high gain and f_{Max}
Length	> 1 μm	•SWNT length must be longer than the intended electrode gap channel length.
Density	>10 SWNT/ μm	• Reduces parasitic capacitance, increases current carrying capacity, and improves impedance matching.
Alignment	All parallel	•Result in higher transconductance, and denser SWNT packing
Uniformity	Wafer scale	•Essential for large scale processing.

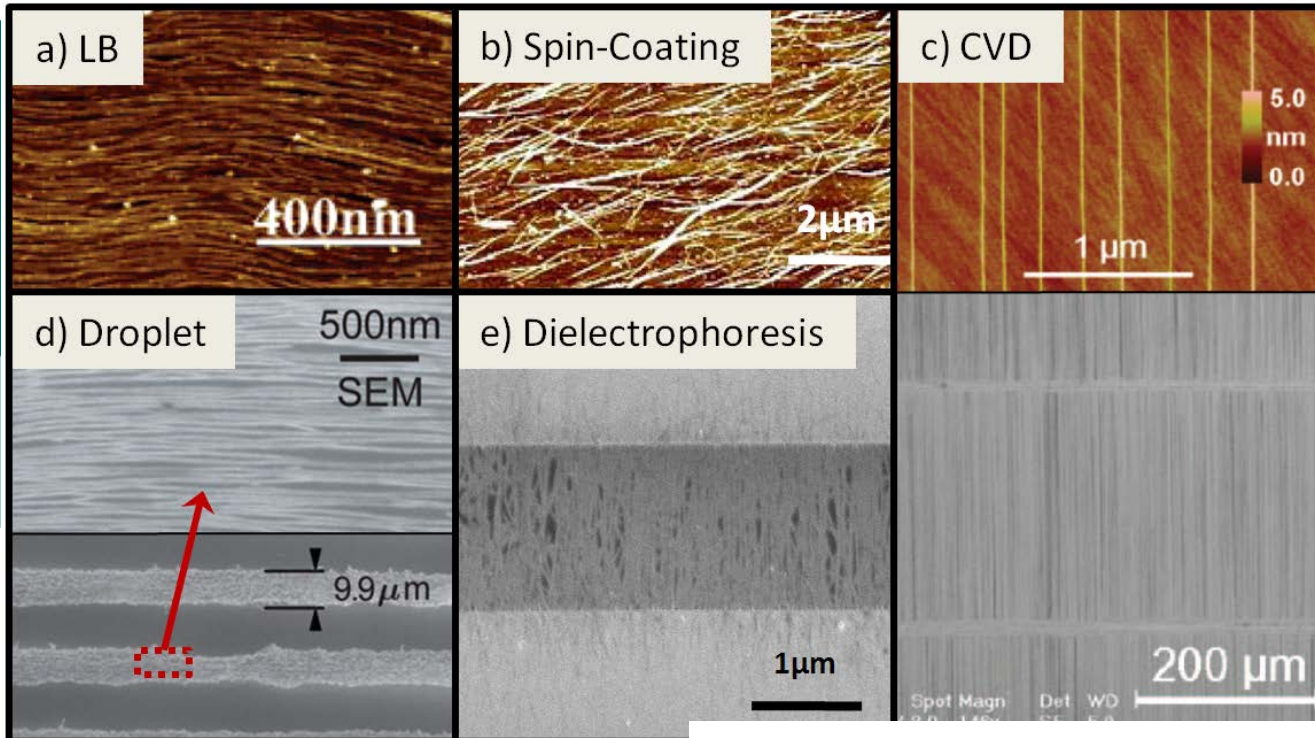
quartz



E. Cubukcu, F. Degirmenci, C. Kocabas, M. A. Zimmler, J. A. Rogers and F. Capasso, "Aligned Carbon Nanotubes as Polarization-Sensitive, Molecular near-Field Detectors", *Proceedings of the National Academy of Sciences of the United States of America*, **106**, 2495-2499, (2009).



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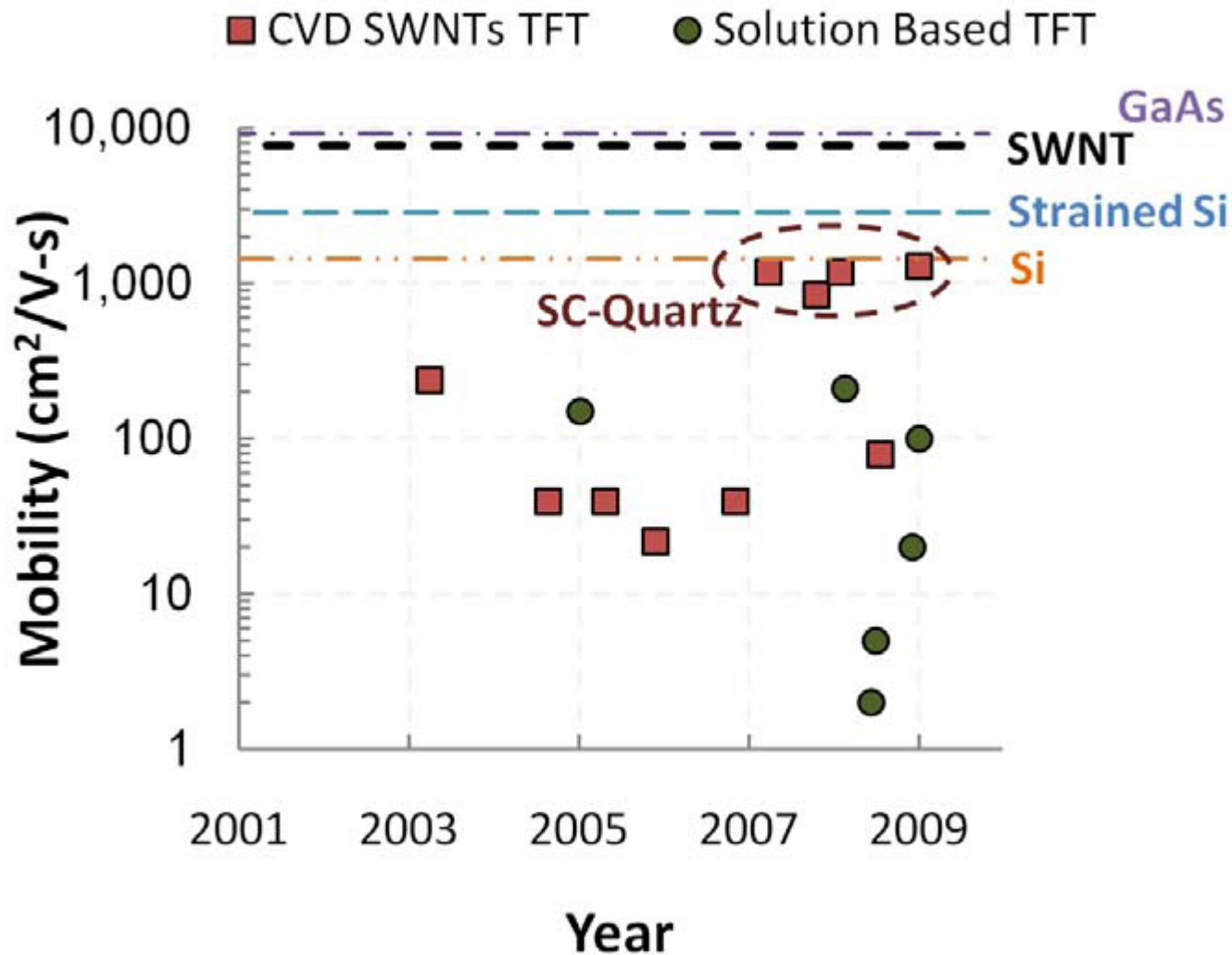


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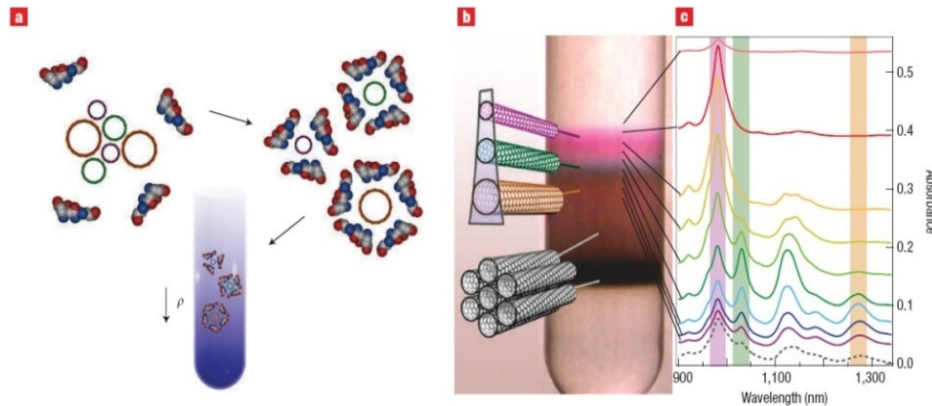
Mobilities



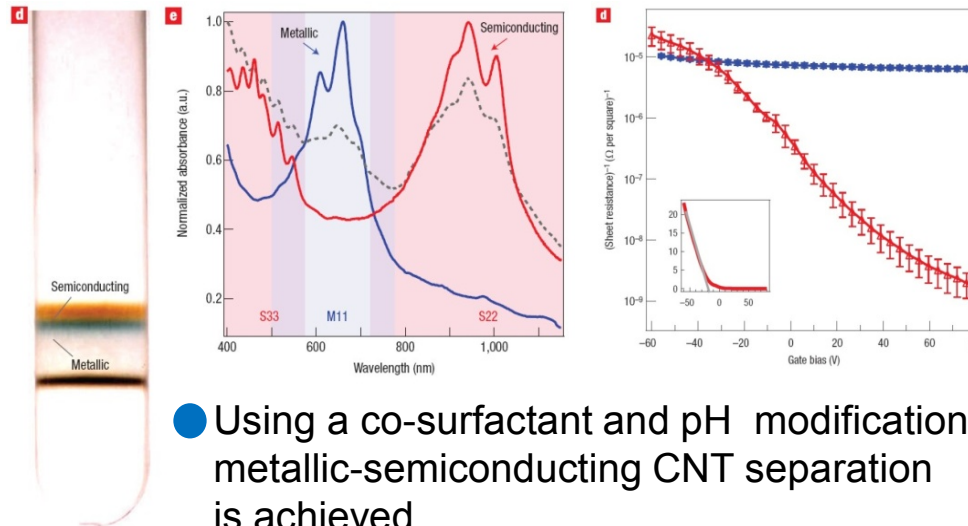
C. Rutherglen, D. Jain and P. Burke, "Nanotube Electronics for Radiofrequency Applications", *Nature Nanotechnology*, **4**, 811-819, (2009).



(n,m) enrichment



- CNTs are surfactant encapsulated and separate by density during centrifugation

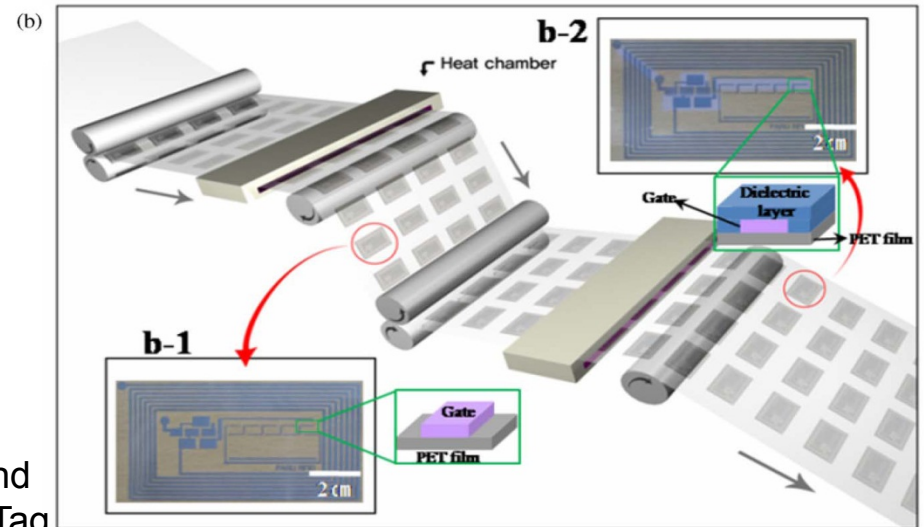
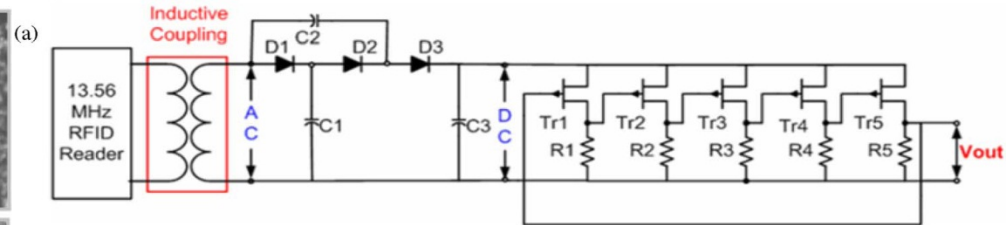
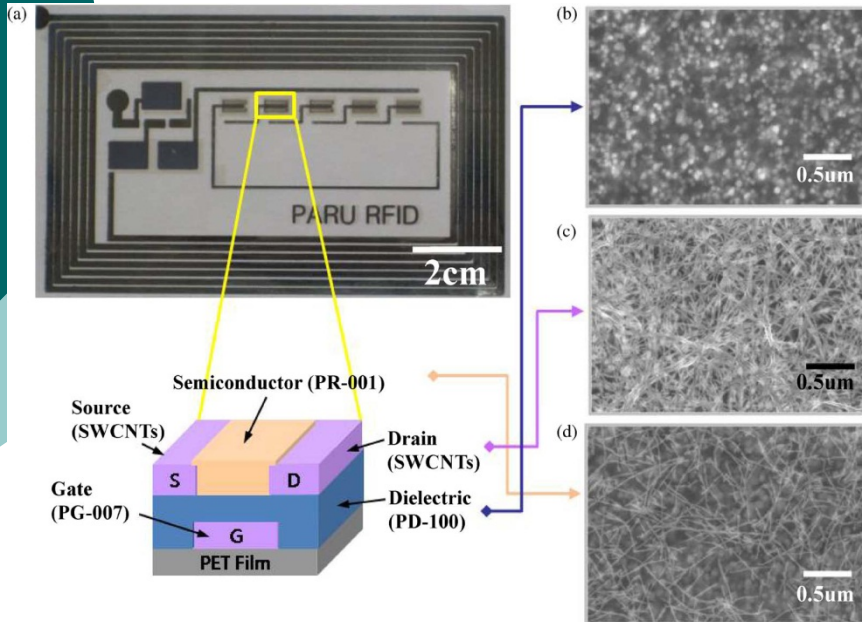


- Using a co-surfactant and pH modification, metallic-semiconducting CNT separation is achieved

M. Hersam, "Progress Towards Monodisperse Single-Walled Carbon Nanotubes", *Nature Nanotechnology*, **3**, 387-394, (2008).



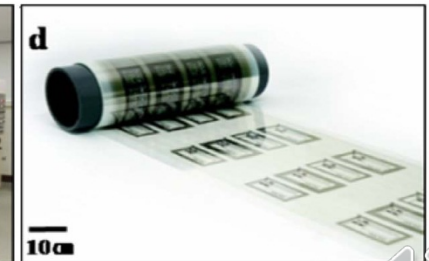
Applications: Low Cost- RFID



Mob ~ 5 & on/off ratio 100

Minhun, J., K. Jaeyoung, et al. (2010). "All-Printed and Roll-to-Roll-Printable 13.56-MHz-Operated 1-bit RF Tag on Plastic Foils." *Electron Devices, IEEE Transactions on* **57(3): 571-580.**

Our Goal:
Mob ~ 100 &
on/off ratio 100000



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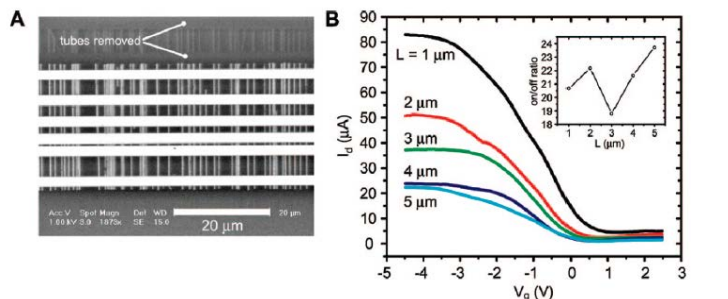
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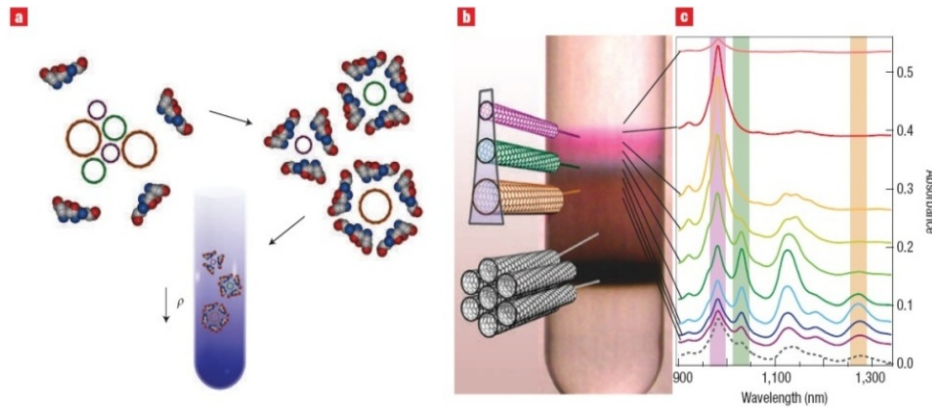
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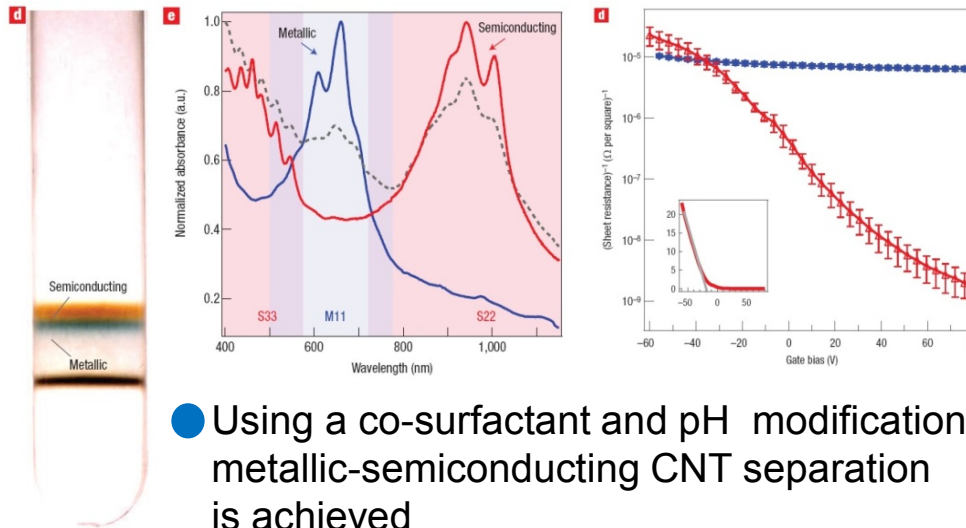
L. Ding, A. Tselev, J. Wang, D. Yuan, H. Chu, T. P. McNicholas, Y. Li



(n,m) enrichment



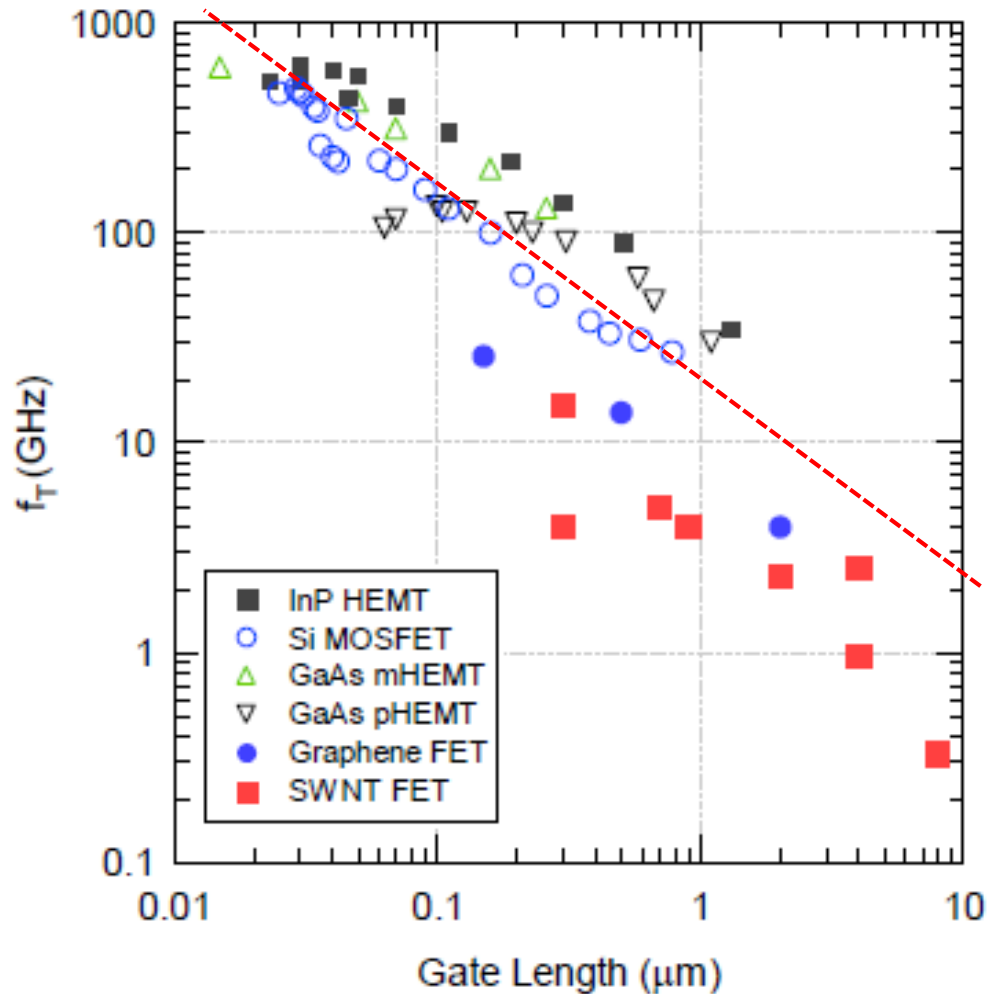
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M. Hersam, "Progress Towards Monodisperse Single-Walled Carbon Nanotubes", *Nature Nanotechnology*, **3**, 387-394, (2008).

Comparison to other semiconductors



Dashed line:
 1.2×10^7 cm/s v_{Sat}
(Rogers)

Graphene (Kim)
0.5 to 5x that value

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